



## N25Q032

32-Mbit 3 V, multiple I/O, 4-Kbyte subsector erase,  
XiP enabled, serial flash memory with 108 MHz SPI bus interface

### Features

- SPI-compatible serial bus interface
- 108 MHz (maximum) clock frequency
- 2.7 V to 3.6 V single supply voltage
- Supports legacy SPI protocol and new Quad I/O or Dual I/O SPI protocol
- Quad/Dual I/O instructions resulting in an equivalent clock frequency up to 432 MHz:
- XiP mode for all three protocols
  - Configurable via volatile or non-volatile registers (enabling the memory to work in XiP mode directly after power on)
- Program/Erase suspend instructions
- Continuous read of entire memory via single instruction:
  - Fast Read
  - Quad or Dual Output Fast Read
  - Quad or Dual I/O Fast Read
- Flexible to fit application:
  - Configurable number of dummy cycles
  - Output buffer configurable
  - Reset function available upon customer request
- 64-byte user-lockable, one-time programmable (OTP) area
- Erase capability
  - Subsector (4-Kbyte) granularity on the entire memory array.
  - Sector (64-Kbyte) granularity
- Write protections
  - Software write protection applicable to every 64-Kbyte sector (volatile lock bit)
  - Hardware write protection: protected area size defined by five non-volatile bits (BP0, BP1, BP2, and TB bit)
  - Additional smart protections available upon customer request
- Electronic signature
  - JEDEC standard two-byte signature (BA16h)
  - Additional 2 Extended Device ID (EDID) bytes to identify device factory options
  - Unique ID code (UID) with 14 bytes read-only, factory programmed
- More than 100,000 program/erase cycles per sector
- More than 20 years data retention
- Packages (All packages RoHS compliant):
  - F4 = UFDFPN8 4 x 3 mm (MLP8)
  - F6 = VDFPN8 6 x 5 mm (MLP8)
  - F8 = VDFPN8 8 x 6 mm (MLP8)
  - SC = SO8N (150 mils body width)
  - SE = SO8W (208 mils body width)
  - SF = SO16 (300 mils body width)
  - 12 = TBGA24 6 x 8 mm

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# 1 Description

The N25Q032 is a 32 Mbit (4Mb x 8) serial Flash memory, with advanced write protection mechanisms. It is accessed by a high speed SPI-compatible bus and features the possibility to work in XIP ("eXecution in Place") mode.

The N25Q032 supports innovative, high-performance quad/dual I/O instructions, these new instructions allow to double or quadruple the transfer bandwidth for read and program operations.

Furthermore the memory can be operated with 3 different protocols:

- Standard SPI (Extended SPI protocol)
- Dual I/O SPI
- Quad I/O SPI

The Standard SPI protocol is enriched by the new quad and dual instructions (Extended SPI protocol). For Dual I/O SPI (DIO-SPI) all the instructions codes, the addresses and the data are always transmitted across two data lines. For Quad I/O SPI (QIO-SPI) the instructions codes, the addresses and the data are always transmitted across four data lines thus enabling a tremendous improvement in both random access time and data throughput.

The memory can work in "XIP mode", that means the device only requires the addresses and not the instructions to output the data. This mode dramatically reduces random access time thus enabling many applications requiring fast code execution without shadowing the memory content on a RAM.

The XIP mode can be used with QIO-SPI, DIO-SPI, or Extended SPI protocol, and can be entered and exited using different dedicated instructions to allow maximum flexibility: for applications required to enter in XIP mode right after power up of the device, this can be set as default mode by using dedicated Non Volatile Register (NVR) bits.

Another feature is the ability to pause and resume program and erase cycles by using dedicated Program/Erase Suspend and Resume instructions.

The N25Q032 memory offers the following additional features to be configured by using the Non Volatile Configuration Register (NVCR) for default /Non-Volatile settings or by using the Volatile and Volatile Enhanced Configuration Registers for Volatile settings:

- the number of dummy cycles for fast read instructions (single, dual and, quad I/O) according to the operating frequency
- the output buffer impedance
- the type of SPI protocol (extended SPI, DIO-SPI or QIO-SPI)
- the required XIP mode
- the Hold (Reset) functionality enabling/disabling
- the Wrap mode enabling/disabling.

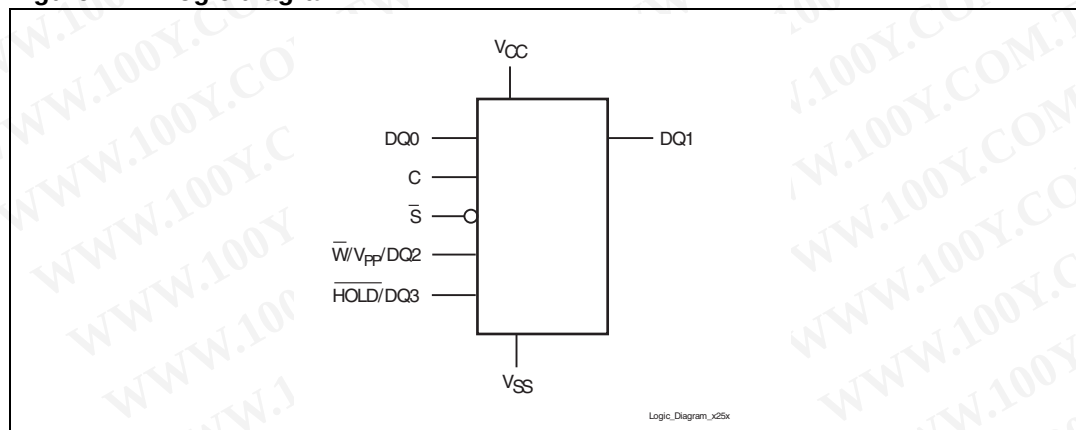
The memory is organized as 64 (64-Kbyte) main sectors that are further divided into 16 subsectors each (1024 subsectors in total). The memory can be erased a 4-KByte subsector at a time, a 64-KByte sector at a time, or as a whole.

The memory can be write protected by software using a mix of volatile and non-volatile protection features, depending on the application needs. The protection granularity is of 64-Kbyte (sector granularity) for volatile protections.

The N25Q032 has 64 one-time-programmable bytes (OTP bytes) that can be read and programmed using two dedicated instructions, Read OTP (ROTP) and Program OTP (POTP), respectively. These 64 bytes can be permanently locked by a particular Program OTP (POTP) sequence. Once they have been locked, they become read-only and this state cannot be reversed.

Many different N25Q032 configurations are available, please refer to the ordering scheme page for the possibilities. Additional features are available as security options (The Security features are described in a dedicated Application Note). Please contact your nearest Numonyx Sales office for more information.

**Figure 1. Logic diagram**



**Note:** Reset functionality is available in devices with a dedicated part number. See [Section 16: Ordering information](#).

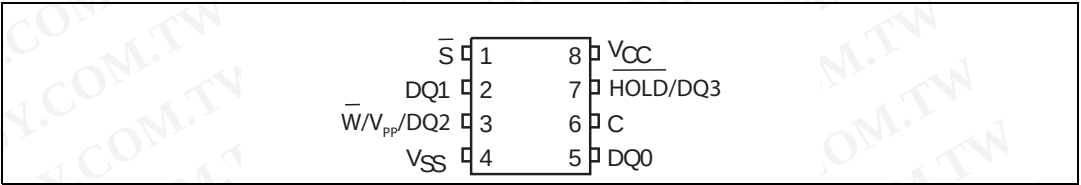
**Table 1. Signal names**

| Signal                  | Description                                                               | I/O                |
|-------------------------|---------------------------------------------------------------------------|--------------------|
| C                       | Serial Clock                                                              | Input              |
| DQ0                     | Serial Data input                                                         | I/O <sup>(1)</sup> |
| DQ1                     | Serial Data output                                                        | I/O <sup>(2)</sup> |
| $\bar{S}$               | Chip Select                                                               | Input              |
| $\bar{W}/VPP/DQ2$       | Write Protect/Enhanced Program supply voltage/additional data I/O         | I/O <sup>(3)</sup> |
| HOLD/DQ3 <sup>(4)</sup> | Hold (Reset function available upon customer request)/additional data I/O | I/O <sup>(3)</sup> |
| VCC                     | Supply voltage                                                            | —                  |
| VSS                     | Ground                                                                    | —                  |

1. Provides dual and quad I/O for Extended SPI protocol instructions, dual I/O for Dual I/O SPI protocol instructions, and quad I/O for Quad I/O SPI protocol instructions.
2. Provides dual and quad instruction input for Extended SPI protocol, dual instruction input for Dual I/O SPI protocol, and quad instruction input for Quad I/O SPI protocol.
3. Provides quad I/O for Extended SPI protocol instructions, and quad I/O for Quad I/O SPI protocol instructions.
4. Reset functionality available with a dedicated part number. See [Section 16: Ordering information](#).

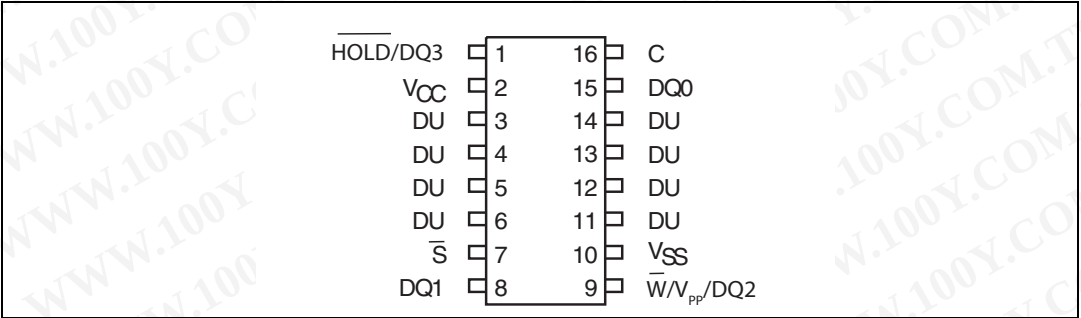
**Note:** There is an exposed central pad on the underside of the MLP8 package. This is pulled, internally, to VSS, and must not be allowed to be connected to any other voltage or signal line on the PCB.

Figure 2. SO8N, SO8W and MLP8 connections



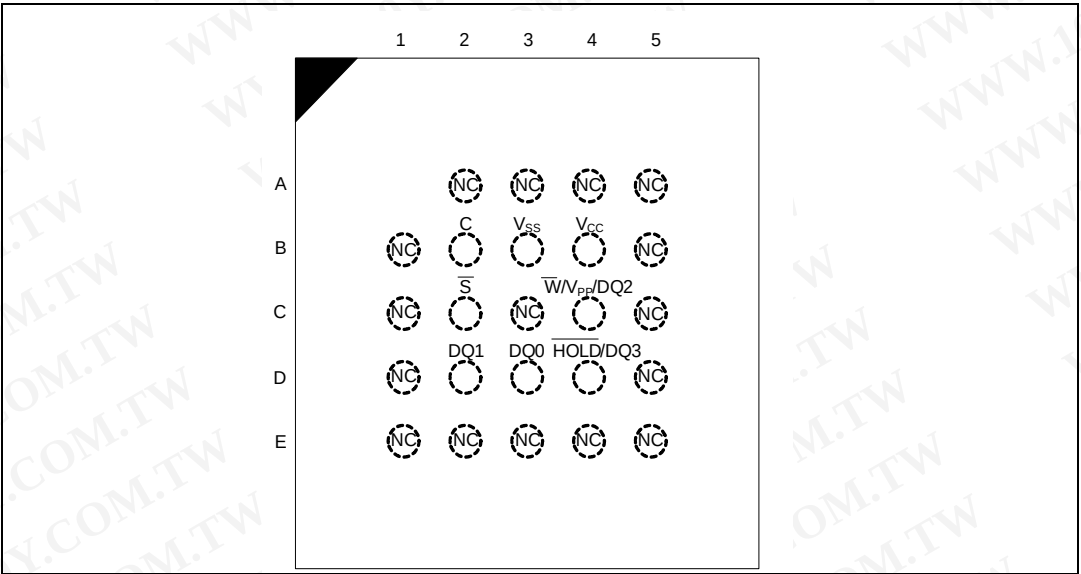
1. Reset functionality available in devices with a dedicated part number. See [Section 16: Ordering information](#).

Figure 3. SO16 connections



1. DU = don't use.
2. See [Package mechanical](#) section for package dimensions, and how to identify pin-1.
3. Reset functionality available in devices with a dedicated part number. See [Section 16: Ordering information](#).

Figure 4. BGA connections



1. NC = No Connect.
2. See [Figure 115: TBGA - 6 x 8 mm, 24-Ball, Drawing](#).

## 2 Signal descriptions

### 2.1 Serial data output (DQ1)

This output signal is used to transfer data serially out of the device. Data are shifted out on the falling edge of Serial Clock (C). When used as an Input, It is latched on the rising edge of the Serial Clock (C).

In the Extended SPI protocol, during the Quad and Dual Input Fast Program (QIFP, DIFP) instructions and during the Quad and Dual Input Extended Fast Program (QIEFP, DIEFP) instructions, pin DQ1 is used also as an input.

In the Dual I/O SPI protocol (DIO-SPI) the DQ1 pin always acts as an input/output.

In the Quad I/O SPI protocol (QIO-SPI) the DQ1 pin always acts as an input/output, with the exception of the Program or Erase cycle performed with the Enhanced Program Supply Voltage (VPP). In this case the device temporarily goes in Extended SPI protocol. The protocol then becomes QIO-SPI as soon as the VPP pin voltage goes low.

### 2.2 Serial data input (DQ0)

This input signal is used to transfer data serially into the device. It receives instructions, addresses, and the data to be programmed. Values are latched on the rising edge of Serial Clock (C). Data are shifted out on the falling edge of the Serial Clock (C).

In the Extended SPI protocol, during the Quad and Dual Output Fast Read (QOFR, DOFR) and the Quad and Dual Input/Output Fast Read (QIOFR, DIOFR) instructions, pin DQ0 is also used as an input/output.

In the DIO-SPI protocol the DQ0 pin always acts as an input/output.

In the QIO-SPI protocol, the DQ0 pin always acts as an input/output, with the exception of the Program or Erase cycle performed with the enhanced program supply voltage (VPP). In this case the device temporarily goes in Extended SPI protocol. Then, the protocol returns to QIO-SPI as soon as the VPP pin voltage goes low.

### 2.3 Serial Clock (C)

This input signal provides the timing for the serial interface. Instructions, addresses, or data present at serial data input (DQ0) are latched on the rising edge of Serial Clock (C). Data are shifted out on the falling edge of the Serial Clock (C).

### 2.4 Chip Select ( $\bar{S}$ )

When this input signal is high, the device is deselected and serial data output (DQ1) is at high impedance. Unless an internal program, erase or write status register cycle is in progress, the device will be in the standby power mode (this is not the deep power-down mode). Driving Chip Select ( $\bar{S}$ ) low enables the device, placing it in the active power mode.

After power-up, a falling edge on Chip Select ( $\bar{S}$ ) is required prior to the start of any instruction.

## 2.5 Hold ( $\overline{\text{HOLD}}$ ) or Reset ( $\overline{\text{Reset}}$ )

The Hold ( $\overline{\text{HOLD}}$ ) signal is used to pause any serial communications with the device without deselecting the device.

Reset functionality is present instead of Hold in devices with a dedicated part number. See [Section 16: Ordering information](#).

During Hold condition, the Serial Data output (DQ1) is in high impedance, and Serial Data input (DQ0) and Serial Clock (C) are Don't Care.

To start the Hold condition, the device must be selected, with Chip Select ( $\overline{\text{S}}$ ) driven Low.

For devices featuring Reset instead of Hold functionality, the Reset ( $\overline{\text{Reset}}$ ) input provides a hardware reset for the memory.

When  $\overline{\text{Reset}}$  ( $\overline{\text{Reset}}$ ) is driven High, the memory is in the normal operating mode. When Reset ( $\overline{\text{Reset}}$ ) is driven Low, the memory will enter the Reset mode. In this mode, the output is high impedance.

Driving Reset ( $\overline{\text{Reset}}$ ) Low while an internal operation is in progress will affect this operation (write, program or erase cycle) and data may be lost.

In the Extended SPI protocol, during the QOFR, QIOFR, QIFP and the Quad Extended Fast Program (QIEFP) instructions, the Hold (Reset) / DQ3 is used as an input/output (DQ3 functionality).

In QIO-SPI, the  $\overline{\text{Hold}}$  ( $\overline{\text{Reset}}$ ) / DQ3 pin acts as an I/O (DQ3 functionality), and the  $\overline{\text{HOLD}}$  ( $\overline{\text{Reset}}$ ) functionality disabled when the device is selected. When the device is deselected ( $\overline{\text{S}}$  signal is high), in parts with Reset functionality, it is possible to reset the device unless this functionality is not disabled by mean of dedicated registers bits.

The HOLD (Reset) functionality can be disabled using bit 3 of the NVCR or bit 4 of the VECR.

## 2.6 Write protect/enhanced program supply voltage ( $\overline{\text{W/VPP}}$ ), DQ2

$\overline{\text{W/VPP}}$ /DQ2 can be used as:

- A protection control input.
- A power supply pin.
- I/O in Extended SPI protocol quad instructions and in QIO-SPI protocol instructions.

When the device is operated in Extended SPI protocol with single or dual instructions, the two functions  $\overline{\text{W}}$  or VPP are selected by the voltage range applied to the pin. If the  $\overline{\text{W/VPP}}$  input is kept in a low voltage range (0 V to VCC) the pin is seen as a control input. This input signal is used to freeze the size of the area of memory that is protected against program or erase instructions (as specified by the values in the BP[0:3] bits of the Status Register. (See [Table 2.: Status register format](#)).

If VPP is in the range of VPPH, it acts as an additional power supply during the Program or Erase cycles (See [Table 27.: Operating conditions](#)). In this case VPP must be stable until the Program or Erase algorithm is completed.

During the Extended SPI protocol, the QOFR and QIOFR instructions, and the QIO-SPI protocol instructions, the pin  $\overline{\text{W/VPP}}$ /DQ2 is used as an input/output (DQ2 functionality).

Using the Extended SPI protocol the QIFP, QIEFP and the QIO-SPI Program/Erase instructions, it is still possible to use the VPP additional power supply to speed up internal operations. However, to enable this possibility it is necessary to set bit 3 of the Volatile Enhanced Configuration Register to 0.

In this case the  $\overline{W}/VPP/DQ2$  pin is used as an I/O pin until the end of the instruction sequence. After the last input data is shifted in, the application should apply VPP voltage to  $\overline{W}/VPP/DQ2$  within 200 ms to speed up the internal operations. If the VPP voltage is not applied within 200 ms the Program/Erase operations start with standard speed.

The default value of the VECR bit 3 is 1, and the VPP functionality for Quad I/O modify instruction is disabled.

## 2.7 $V_{CC}$ supply voltage

$V_{CC}$  is the supply voltage.

## 2.8 $V_{SS}$ ground

$V_{SS}$  is the reference for the  $V_{CC}$  supply voltage.

# 3

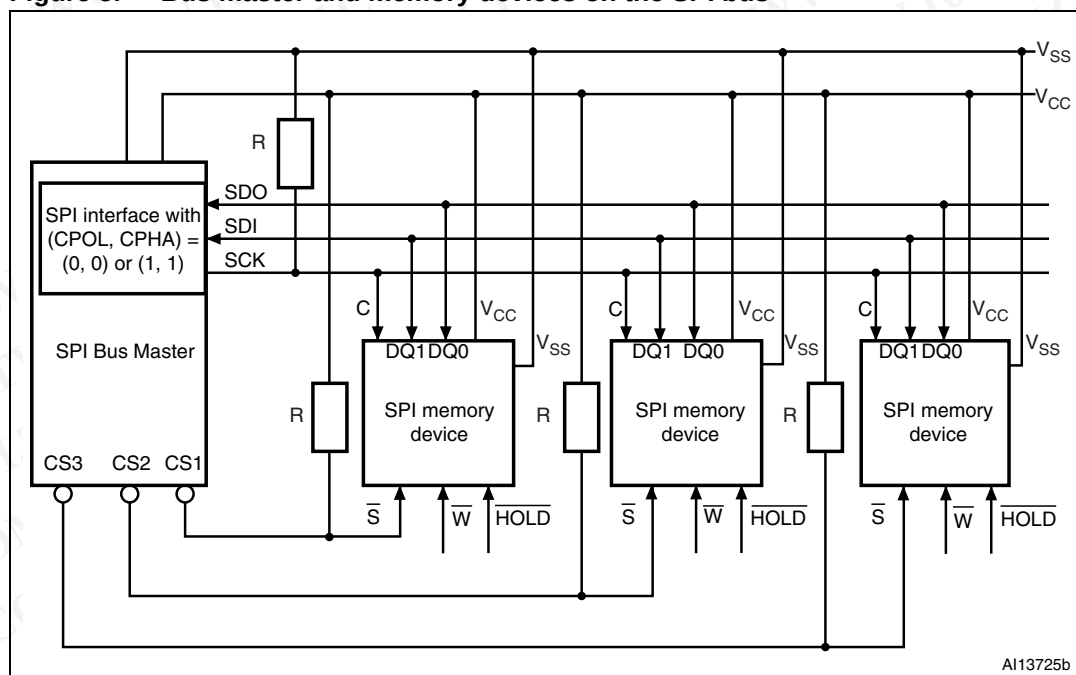
CPOL=0, CPHA=0

For these two modes, input data is latched in on the rising edge of Serial Clock (C), and output data is available from the falling edge of Serial Clock (C).

C remains at 0 for (CPOL=0, CPHA=0)

C remains at 1 for (CPOL=1, CPHA=1)

**Figure 5. Bus master and memory devices on the SPI bus**

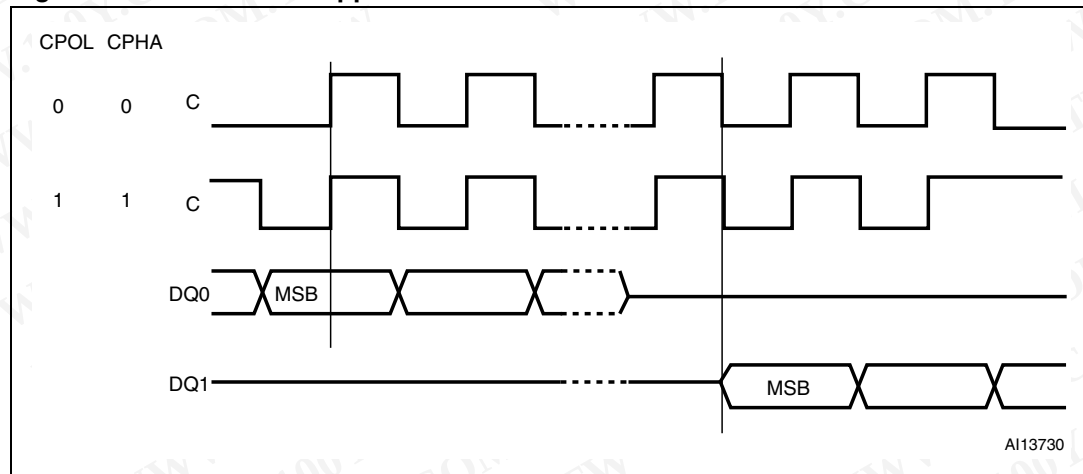


Shown here is an example of three devices working in Extended SPI protocol for simplicity connected to an MCU, on an SPI bus. Only one device is selected at a time, so only one device drives the serial data output (DQ1) line at a time; the other devices are high impedance. Resistors R ensures that the N25Q032 is not selected if the bus master leaves the  $\overline{S}$  line in the high impedance state. As the bus master may enter a state where all inputs/outputs are in high impedance at the same time (for example, when the bus master is reset), the clock line (C) must be connected to an external pull-down resistor so that, when all inputs/outputs become high impedance, the  $\overline{S}$  line is pulled High while the C line is pulled Low. This ensures that  $\overline{S}$  and C do not become High at the same time, and so that the  $t_{SHCH}$  requirement is met. The typical value of R is 100 k $\Omega$ , assuming that the time constant  $R \cdot C$ ,

( $C_p$  = parasitic capacitance of the bus line) is shorter than the time during which the bus master leaves the SPI bus in high impedance.

**Example:**  $C_p = 50$  pF, that is  $R \cdot C_p = 5 \mu s \Leftrightarrow$  the application must ensure that the bus master never leaves the SPI bus in the high impedance state for a time period shorter than  $5 \mu s$ . The Write Protect (W) and Hold (HOLD) signals should be driven, High or Low as appropriate.

**Figure 6. SPI modes supported**



## 4 SPI Protocols

The N25Q032 memory can work with 3 different Serial protocols:

- Extended SPI protocol.
- Dual I/O SPI (DIO-SPI) protocol.
- Quad I/O SPI (QIO-SPI) protocol.

It is possible to choose among the three protocols by means of user volatile or non-volatile configuration bits. It's not possible to mix Extended SPI, DIO-SPI, and QIO-SPI protocols. The device can operate in XIP mode in all 3 protocols.

### 4.1 Extended SPI protocol

This is an extension of the standard (legacy) SPI protocol. Instructions are transmitted on a single data line (DQ0), while addresses and data are transmitted by one, two or four data lines (DQ0, DQ1, W/VPP(DQ2) and HOLD / (DQ3) according to the instruction.

When used in the Extended SPI protocol, these devices can be driven by a micro controller in either of the two following modes:

- CPOL=0, CPHA=0
- CPOL=1, CPHA=1

Please refer to the SPI modes for a detailed description of these two modes

### 4.2 Dual I/O SPI (DIO-SPI) protocol

Dual I/O SPI (DIO-SPI) protocol: instructions, addresses and I/O data are always transmitted on two data lines (DQ0 and DQ1).

Also when in DIO-SPI mode, the device can be driven by a micro controller in either of the two following modes:

- CPOL= 0, CPHA= 0
- CPOL= 1, CPHA= 1

Please refer to the SPI modes for a detailed description of these two modes.

*Note:*

*Extended SPI protocol Dual I/O instructions allow only address and data to be transmitted over two data lines. However, DIO-SPI allows instructions, addresses, and data to be transmitted on two data lines.*

This mode can be set using two ways

- **Volatile:** by setting bit 6 of the VECR to 0. The device enters DIO-SPI protocol immediately after the Write Enhanced Volatile Configuration Register sequence completes. The device returns to the default working mode (defined by NVCR) on power on.
- **Default/ Non-Volatile:** This is default mode on power-up. By setting bit 2 of the NVCR to 0. The device enters DIO-SPI protocol on the subsequent power-on. After all subsequent power-on sequences, the device still starts in DIO-SPI protocol unless bit 2 of NVCR is set to 1 (default value, corresponding to Extended SPI protocol) or bit 3 of NVCR is set to 0 (corresponding to QIO-SPI protocol).

### 4.3 Quad SPI (QIO-SPI) protocol

Quad SPI (QIO-SPI) protocol: instructions, addresses, and I/O data are always transmitted on four data lines DQ0, DQ1, W/VPP(DQ2), and HOLD / (DQ3).

The exception is the Program/Erase cycle performed with the VPP, in which case the device temporarily goes to Extended SPI protocol. Going temporarily into Extended SPI protocol allows the application either to:

- check the polling bits: WIP bit in the Status Register or Program/Erase Controller bit in the Flag Status Register
- perform Program/Erase suspend functions.

*Note:* As soon as the VPP pin voltage goes low, the protocol returns to the QIO-SPI protocol.

In QIO-SPI protocol the  $\overline{W}$  and HOLD/ (RESET) functionality is disabled when the device is selected ( $\overline{S}$  signal low).

When used in the QIO-SPI mode, these devices can be driven by a micro controller in either of the two following modes:

- CPOL=0, CPHA=0
- CPOL=1, CPHA=1

Please refer to the SPI modes for a detailed description of the 2 modes.

*Note:* In the Extended SPI protocol only Address and data are allowed to be transmitted on 4 data lines, However in QIO-SPI protocol, the address, data and instructions are transmitted across 4 data lines.

This working mode is set in either bit 7 of the Volatile Enhanced Configuration Register (VECR) or in bit 3 of the Non Volatile Configuration Register (NVCR).

This mode can be set using two ways

- **Volatile:** by setting bit 7 of the VECR to 0, the device enters QIO-SPI protocol immediately after the Write Enhanced Volatile Configuration Register sequence completes. The device returns to the default working protocol (defined by the NVCR) on the next power on.
- **Default/ Non- Volatile:** This is default protocol on power up. By setting bit 3 of the NVCR to 0, the device enters QIO-SPI protocol on the subsequent power-on. After all subsequent power-on sequences, the device still starts in QIO-SPI protocol unless bit 3 of the NVCR is set to 1 (default value, corresponding to Extended SPI mode).

## 5 Operating features

### 5.1 Extended SPI Protocol Operating features

#### 5.1.1 Read Operations

To read the memory content in Extended SPI protocol different instructions are available: READ, Fast Read, Dual Output Fast Read, Dual Input Output Fast Read, Quad Output Fast Read and Quad Input Output Fast read, allowing the application to choose an instruction to send addresses and receive data by one, two or four data lines.

*Note:* In the Extended SPI protocol the instruction code is always sent on one data line (DQ0): to use two or four data lines the user must use either the DIO-SPI or the QIO-SPI protocol respectively.

For fast read instructions the number of dummy clock cycles is configurable by using VCR bits [7:4] or NVCR bits [15:12].

After a successful reading instruction a reduced tSHSL equal to 20 ns is allowed to further improve random access time (in all the other cases tSHSL should be at least 50 ns). See [Table 31.: AC Characteristics](#).

#### 5.1.2 Page programming

To program one data byte, two instructions are required: write enable (WREN), which is one byte, and a page program (PP) sequence, which consists of four bytes plus data. This is followed by the internal program cycle (of duration t<sub>pp</sub>).

To spread this overhead, the page program (PP) instruction allows up to 256 bytes to be programmed at a time (changing bits from '1' to '0'), provided that they lie in consecutive addresses on the same page of memory.

For optimized timings, it is recommended to use the page program (PP) instruction to program all consecutive targeted bytes in a single sequence versus using several page program (PP) sequences with each containing only a few bytes (see [Section 5.2.3: Page programming](#) and [Table 31: AC Characteristics](#)).

#### 5.1.3 Dual input fast program

The dual input fast program (DIFP) instruction makes it possible to program up to 256 bytes using two input pins at the same time (by changing bits from '1' to '0').

For optimized timings, it is recommended to use the DIFP instruction to program all consecutive targeted bytes in a single sequence rather using several DIFP sequences each containing only a few bytes (see [Section 9.1.13: Dual Input Fast Program \(DIFP\)](#)).

#### 5.1.4 Dual Input Extended Fast Program

The Dual Input Extended Fast Program (DIEFP) instruction is an enhanced version of the Dual Input Fast Program instruction, allowing to transmit address across two data lines.

For optimized timings, it is recommended to use the DIEFP instruction to program all consecutive targeted bytes in a single sequence rather than using several DIEFP sequences, each containing only a few bytes.

### 5.1.5 Quad Input Fast Program

The Quad Input Fast Program (QIFP) instruction makes it possible to program up to 256 bytes using 4 input pins at the same time (by changing bits from 1 to 0).

For optimized timings, it is recommended to use the QIFP instruction to program all consecutive targeted bytes in a single sequence rather than using several QIFP sequences each containing only a few bytes.

### 5.1.6 Quad Input Extended Fast Program

The Quad Input Extended Fast Program (QIEFP) instruction is an enhanced version of the Quad Input Fast Program instruction, allowing parallel input on the 4 input pins, including the address being sent to the device.

For optimized timings, it is recommended to use the QIEFP instruction to program all consecutive targeted bytes in a single sequence rather than using several QIEFP sequences each containing only a few bytes.

### 5.1.7 Subsector erase, sector erase and bulk erase

The page program (PP) instruction allows bits to be reset from '1' to '0'. In order to do this the bytes of memory need to be erased to all 1s (FFh).

This can be achieved as follows:

- a subsector at a time, using the subsector erase (SSE) instruction. See [Section 16: Ordering information](#);
- a sector at a time, using the sector erase (SE) instruction;
- throughout the entire memory, using the bulk erase (BE) instruction.

This starts an internal erase cycle (of duration  $t_{SSE}$ ,  $t_{SE}$  or  $t_{BE}$ ). The erase instruction must be preceded by a write enable (WREN) instruction.

### 5.1.8 Polling during a write, program or erase cycle

A further improvement in the time to Write Status Register (WRSR), POTP, PP, DIFP, DIEFP, QIFP, QIEFP or Erase (SSE, SE or BE) can be achieved by not waiting for the worst case delay ( $t_W$ ,  $t_{PP}$ ,  $t_{SSE}$ ,  $t_{SE}$ , or  $t_{BE}$ ). The application program can monitor if the required internal operation is completed, by polling the dedicated register bits to establish when the previous Write, Program or Erase cycle is complete.

The information on the memory being in progress for a Program, Erase, or Write instruction can be checked either on the Write In Progress (WIP) bit of the Status Register or in the Program/Erase Controller bit of the Flag Status Register.

**Note:** *The Program/Erase Controller bit is the opposite state of the WIP bit in the Status Register.*

In the Flag Status Register additional information can be checked, as eventual Program/Erase failures by mean of the Program or erase Error bits.

### 5.1.9 Active power and standby power modes

When Chip Select ( $\overline{S}$ ) is Low, the device is selected, and in the active power mode.

When Chip Select ( $\overline{S}$ ) is High, the device is deselected, but could remain in the active power mode until all internal cycles have completed (program, erase, write status register). The device then goes in to the standby power mode. The device consumption drops to  $I_{CC1}$ .

### 5.1.10 Hold (or Reset) condition

The Hold ( $\overline{HOLD}$ ) signal is used to pause serial communications with the device without resetting the clocking sequence. However, taking this signal Low does not terminate any write status register, program or erase cycle that is currently in progress.

To enter the hold condition, the device must be selected, with Chip Select ( $\overline{S}$ ) Low.

The hold condition starts on the falling edge of the Hold ( $\overline{HOLD}$ ) signal, provided that the Serial Clock (C) is Low (as shown in [Figure 7](#)).

The hold condition ends on the rising edge of the Hold ( $\overline{HOLD}$ ) signal, provided that the Serial Clock (C) is Low.

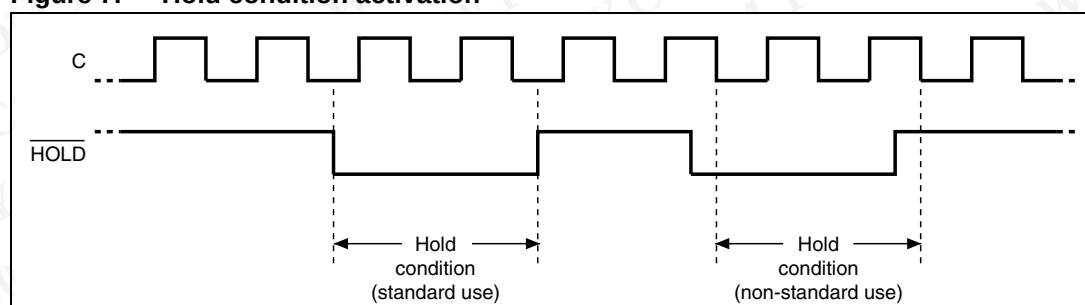
If the falling edge does not coincide with Serial Clock (C) being Low, the hold condition starts after Serial Clock (C) next goes Low. Similarly, if the rising edge does not coincide with Serial Clock (C) being Low, the hold condition ends after Serial Clock (C) next goes Low (this is shown in [Figure 7](#)).

During the hold condition, the serial data output (DQ1) is high impedance, and serial data input (DQ0) and Serial Clock (C) are don't care.

Normally, the device is kept selected, with Chip Select ( $\overline{S}$ ) driven Low for the whole duration of the hold condition. This is to ensure that the state of the internal logic remains unchanged from the moment of entering the hold condition.

If Chip Select ( $\overline{S}$ ) goes High while the device is in the Hold condition, this has the effect of resetting the internal logic of the device. To restart communication with the device, it is necessary to drive Hold ( $\overline{HOLD}$ ) High, and then to drive Chip Select ( $\overline{S}$ ) Low. This prevents the device from going back to the hold condition.

**Figure 7. Hold condition activation**



Reset functionality is available instead of Hold in parts with a dedicated part number. See [Section 16: Ordering information](#).

Driving Reset ( $\overline{Reset}$ ) Low while an internal operation is in progress will affect this operation (write, program or erase cycle) and data may be lost. On Reset going Low, the device enters the reset mode and a time of  $t_{RHSL}$  is then required before the device can be reselected by

driving Chip Select ( $\overline{S}$ ) Low. For the value of tRHS<sub>L</sub>, see [Table 31.: AC Characteristics](#). All the lock bits are reset to 0 after a Reset Low pulse.

The Hold/Reset feature is not available when the Hold (Reset) / DQ3 pin is used as I/O (DQ3 functionality) during Quad Instructions: QOFR, QIOFR, QIFP and QIEFP.

The Hold/Reset feature can be disabled by using of the bit 4 of the VECR.

## 5.2 Dual SPI (DIO-SPI) Protocol

In the Dual SPI (DIO-SPI) protocol all the instructions, addresses and I/O data are transmitted on two data lines. All the functionality available in the Extended SPI protocol is also available in the DIO-SPI protocol. The DIO-SPI instructions are comparable with the Extended SPI instructions; however, in DIO-SPI, the instructions are multiplexed on the two data lines, DQ0 and DQ1.

The only exceptions are the READ, Quad Read, and Program instructions, which are not available in DIO-SPI protocol, and the RDID instruction, which is replaced in the DIO-SPI protocol by the Multiple I/O Read Identification (MIORDID) instruction.

The Multiple I/O Read Identification Instruction reads just the standard SPI electronic ID (3 bytes), while the Extended SPI protocol RDID instruction allows access to the UID bytes.

To help the application code port from Extended SPI to DIO-SPI protocol, the instructions available in the DIO-SPI protocol have the same operation code as the Extended SPI protocol, the only exception being the MIORDID instruction.

### 5.2.1 Multiple I/O Read Identification

The Multiple I/O Read Identification (MIORDID) instruction is available to read the device electronic ID. With respect to the RDID instruction of the Extended SPI protocol, the output data, shifted out on the 2 data lines DQ0 and DQ1.

Since the read ID instruction in the DIO-SPI protocol is limited to 3 bytes of the standard electronic ID, the UID bytes are not read with the MIORDID instruction

### 5.2.2 Dual Command Fast reading

Reading the memory data multiplexing the instruction, the addresses and the output data on 2 data lines can be achieved in DIO-SPI protocol by mean of the Dual Command Fast Read instruction, that has 3 instruction codes (BBh, 3Bh and 0Bh) to help the application code porting from Extended SPI protocol to DIO-SPI protocol. Of course quad and single I/O Read instructions are not available in DIO-SPI mode.

For Dual Command fast read instructions the number of dummy clock cycles is configurable by using VCR bits [7:4] or NVCR bits [15:12].

After a successful reading instruction, a reduced tSHSL equal to 20ns is allowed to further improve random access time (in all the other cases tSHSL should be at least 50 ns). See [Table 31.: AC Characteristics](#).

### 5.2.3 Page programming

Programming the memory by transmitting the instruction, addresses and the output data on 2 data lines can be achieved in DIO-SPI protocol by using the Dual Command Page Program instruction, that has 3 instruction codes (D2h, A2h and 02h) to help port from Extended SPI protocol to DIO-SPI protocol

Quad and single input Program instructions are not available in DIO-SPI mode.

The DIO-SPI protocol is similar to the Extended SPI protocol i.e., to program one data byte two instructions are required:

- Write Enable (WREN), which is one byte, and a
- Dual Command Page Program (DCPP) sequence, which consists of four bytes plus data.

This is followed by the internal Program cycle (of duration tPP).

To spread this overhead, the Dual Command Page Program (DCPP) instruction allows up to 256 bytes to be programmed at a time (changing bits from 1 to 0), provided that they are consecutive addresses on the same page of memory.

For optimized timings, it is recommended to use the DCPP instruction to program all consecutive targeted bytes in a single sequence versus using several DCPP sequences with each containing only a few bytes. See [Table 31.: AC Characteristics](#).

## 5.2.4 Subsector Erase, Sector Erase and Bulk Erase

Similar to the Extended SPI protocol, in the DIO-SPI protocol to erase the memory bytes to all 1s (FFh) the Subsector Erase (SSE), the Sector Erase (SE) and the Bulk Erase (BE) instructions are available. These instructions start an internal Erase cycle (of duration tSSE, tSE or tBE).

The Erase instruction must be preceded by a Write Enable (WREN) instruction.

## 5.2.5 Polling during a Write, Program or Erase cycle

Similar to the Extended SPI protocol, in the DIO-SPI protocol it is possible to monitor if the internal write, program or erase operation is completed, by polling the dedicated register bits by using the Read Status Register (RDSR) or Read Flag Status Register (RFSR) instructions, the only obvious difference is that instruction codes, addresses and output data are transmitted across two data lines.

## 5.2.6 Read and Modify registers

Similar to the Extended SPI protocol, the only obvious difference is that instruction codes, addresses and output data are transmitted across two data lines

## 5.2.7 Active Power and Standby Power modes

Similar to the Extended SPI protocol, when Chip Select ( $\overline{S}$ ) is Low, the device is selected, and in the Active Power mode. When Chip Select ( $\overline{S}$ ) is High, the device is deselected, but could remain in the Active Power mode until all internal cycles have completed (Program, Erase, Write Cycles). The device then goes in to the Standby Power mode. The device consumption drops to ICC1.

## 5.2.8 HOLD (or Reset) condition

The  $\overline{HOLD}$  (or  $\overline{Reset}$  i.e. for parts having the reset functionality instead of hold pin) signal has exactly the same behavior in DIO-SPI protocol as do in Extended SPI protocol, so please refer to section 5.1.10, "Hold (or Reset) condition" in the Extend SPI protocol section for further details.

### 5.3 Quad SPI (QIO-SPI) Protocol

In the Quad SPI (QIO-SPI) protocol all the Instructions, addresses and I/O data are transmitted on four data lines, with the exception of the polling instructions performed during a Program or Erase cycle performed with VPP, in this case the device temporarily goes in Extended SPI protocol. The protocol again becomes QIO-SPI as soon as the VPP voltage goes low.

All the functionality available in the Extended SPI protocol are also available in the QIO-SPI mode, with equivalent instruction transmitted on the 4 data lines DQ0, DQ1, DQ2 and DQ3. The exceptions are the READ, Dual Read and Dual Program instructions, that are not available in QIO-SPI protocol, and the RDID instruction, that is replaced in the QIO-SPI protocol by the Multiple I/O Read Identification (MIORDID) instruction. The Multiple I/O Read Instruction reads just the standard SPI electronic ID (3 bytes), while with the Extended SPI protocol RDID instruction is possible to access also the UID bytes.

To help the application code port from Extended SPI to QIO-SPI protocol, the instructions available in the QIO-SPI protocol have the same operation code as in the Extended SPI protocol, the only exception is the MIORDID instruction.

#### 5.3.1 Multiple I/O Read Identification

The Multiple I/O Read Identification (MIORDID) instruction is available to read the device electronic ID. With respect to the RDID instruction of the Extended SPI protocol, the output data, shifted out on the 4 data lines DQ0, DQ1, DQ2 and DQ3.

Since in the QIO-SPI protocol the Read ID instruction is limited to 3 bytes of the standard electronic ID, the UID bytes are not read with the MIORDID instruction.

#### 5.3.2 Quad Command Fast reading

The Array Data can be read by the Quad Command Fast Read instruction using 3 instructions (EBh, 6Bh and 0Bh) to help the application code port from Extended SPI protocol to QIO-SPI protocol. The instruction, address and output data are transmitted across 4 data lines.

The Dual and Single I/O Read instructions are not available in QIO-SPI protocol.

#### 5.3.3 QUAD Command Page programming

The memory can be programmed in QIO-SPI protocol by the Quad Command Page Program instruction using (02h, 12h and 32h). The instruction, address and input data are transmitted across 4 data lines

The Dual and Single I/O Program instructions are not available in QIO-SPI protocol

Programming the memory by multiplexing the instruction, the addresses and the output data on 4 wires can be achieved in QIO-SPI protocol by mean of the Quad Command Page Program instruction, that has 3 instruction codes (02h, 12h and 32h) to help the application code porting from Extended SPI protocol to QIO-SPI protocol.

Similar to the Extended SPI protocol in the QIO-SPI protocol, to program one data byte two instructions are required:

- Write Enable (WREN), which is one byte, and
- Quad Command Page Program (QCPP) sequence, which consists of instruction (one byte), address (3 bytes) and input data.

This is followed by the internal Program cycle (of duration  $t_{PP}$ ).

To spread this overhead, the Quad Command Page Program (QCPP) instruction allows up to 256 bytes to be programmed at a time (changing bits from 1 to 0), provided that they are in consecutive addresses on the same page of memory.

For optimized timings, it is recommended to use the QCPP instruction to program all consecutive targeted bytes in a single sequence versus using several QCPP sequences with each containing only a few bytes. See [Table 31.: AC Characteristics](#).

The QCPP instruction is transmitted across 4 data lines except when VPP is raised to VPPH.

The VPP can be raised to VPPH to decrease programming time (provided that the bit 3 of the VECR has been set to 0 in advance). When bit 3 of VECR is set to 0 after the Quad Command Page Program instruction sequence has been received, the memory temporarily goes in Extended SPI protocol, and is possible to perform polling instructions (checking the WIP bit of the Status Register or the Program/Erase Controller bit of the Flag Status Register) or Program/Erase Suspend instruction even if DQ2 is temporarily used in this VPP functionality. The memory automatically comes back in QIO-SPI protocol as soon as the VPP pin goes Low.

### 5.3.4 Subsector Erase, Sector Erase and Bulk Erase

Similar to the Extended SPI protocol, Subsector Erase (SSE), the Sector Erase (SE) and the Bulk Erase (BE) instructions are used to erase the memory in the QIO-SPI protocol. These instructions start an internal Erase cycle (of duration  $t_{SSE}$ ,  $t_{SE}$  or  $t_{BE}$ ).

The Erase instruction must be preceded by a Write Enable (WREN) instruction.

The erase instructions are transmitted across 4 data lines unless the VPP is raised to VPPH.

The VPP can be raised to VPPH to decrease erasing time, provided that the bit 3 of the VECR has been set to 0 in advance. In this case, after the erase instruction sequence has been received, the memory temporarily goes in extended SPI protocol, and it is possible to perform polling instructions (checking the WIP bit of the Status Register or the Program/Erase Controller bit of the Flag Status Register) or Program/Erase Suspend instruction even if DQ2 is temporarily used in this VPP functionality. The memory automatically comes back in QIO-SPI protocol as soon as the VPP pin goes Low.

### 5.3.5 Polling during a Write, Program or Erase cycle

It is possible to check if the internal write, program or erase operation is completed, by polling the dedicated register bits of the Read Status Register (RDSR) or Read Flag Status Register (RFSR).

When the Program or Erase cycle is performed with the VPP, the device temporarily goes in single I/O SPI mode. The protocol became again QIO-SPI as soon as the VPP pin voltage goes low.

### 5.3.6 Read and Modify registers

The read and modify register instructions are available and behave in QIO-SPI protocol exactly as they do in Extended SPI protocol, the only difference is that instruction codes, addresses and output data are transmitted across 4 data lines.

### 5.3.7 Active Power and Standby Power modes

Exactly as in Extended SPI protocol, when Chip Select ( $\overline{S}$ ) is Low, the device is selected, and in the Active Power mode. When Chip Select ( $\overline{S}$ ) is High, the device is deselected, but could remain in the Active Power mode until all internal (Program, Erase, Write) Cycles have completed. The device then goes in to the Standby Power mode. The device consumption drops to ICC1.

### 5.3.8 HOLD (or Reset) condition

The HOLD ( $\overline{Hold}$ ) feature (or Reset feature, for parts having the reset functionality instead of hold) is disabled in QIO-SPI protocol when the device is selected: the  $\overline{Hold}$  (or Reset)/ DQ3 pin always behaves as an I/O pin (DQ3 function) when the device is deselected. For parts with reset functionality, it is still possible to reset the memory when it is deselected (C signal high).

### 5.3.9 VPP pin Enhanced Supply Voltage feature

It is possible in the QIO-SPI protocol to use the VPP pin as an enhanced supply voltage, but the intention to use VPP as accelerated supply voltage must be declared by setting bit 3 of the VECR to 0.

In this case, to accelerate the Program cycle the VPP pin must be raised to VPPH after the device has received the last data to be programmed within 200ms. If the VPP is not raised within 200ms, the program operation starts with the standard internal cycle speed as if the Vpp high voltage were not used, and a flag error appears on Flag Status Register bit 3".

## 6 Volatile and Non Volatile Registers

The device features many different registers to store, in volatile or non volatile mode, many parameters and operating configurations:

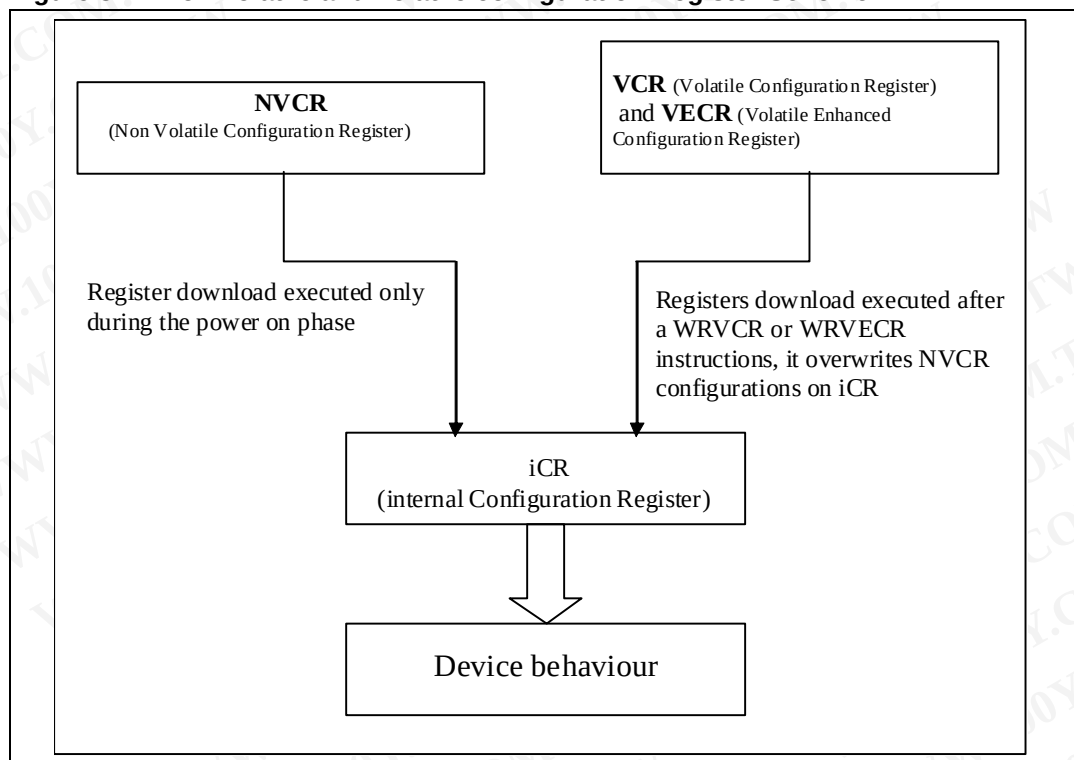
- Legacy SPI Status Register
- 3 configuration registers:
  - Non Volatile Configuration Register (NVCR), 16 bits
  - Volatile Configuration Register (VCR), 8 bits
  - Volatile Enhanced Configuration Register (VECR), 8 bits

The Non Volatile Configuration Register (NVCR) affects the memory configuration starting from the successive power-on. It can be used to make the memory start in a determined condition.

The VCR and VECR affect the memory configuration after every execution of the related Write Volatile configuration Register (WRVCR) and Write Enhanced Volatile Configuration register (WRVECR) instructions. These instructions overwrite the memory configuration set at POR by NVCR.

As described in [Figure 8.: Non Volatile and Volatile configuration Register Scheme](#), the working condition of the memory is set by an internal configuration register, which is not accessible by the user. The working parameters of the internal configuration register are loaded from the NVCR during the boot phase of the device. In this sense the NVCR can be seen as having the default settings of the memory.

During the normal life of the application, every time a write volatile or enhanced volatile configuration register instruction is performed, the new configuration parameters set in the volatile registers are also copied in the internal configuration register, thus instantly affecting the memory behavior. Please note that on the next power on the memory will start again in the working protocol set by the Non Volatile Register parameters.

**Figure 8. Non Volatile and Volatile configuration Register Scheme**

A Flag Status Register (FSR), 8 bits, is also available to check the status of the device, detecting possible errors or a Program/Erase internal cycle in progress.

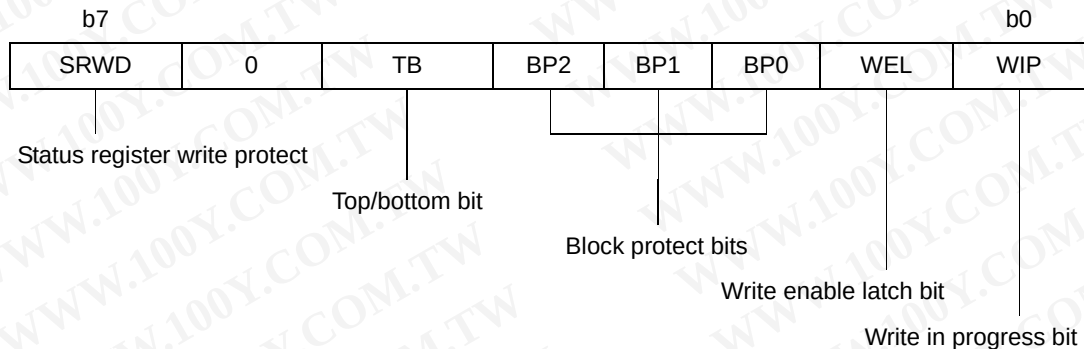
Each register can be read and modified by means of dedicated instructions in all the 3 protocols (Extended SPI, DIO-SPI, and QIO-SPI).

Reading time for all registers is comparable; writing time instead is very different: NVCR bits are set as Flash Cell memory content requiring a longer time to perform internal writing cycles. See [Table 31.: AC Characteristics](#).

## 6.1 Legacy SPI Status Register

The Status Register contains a number of status and control bits that can be read or set by specific instructions: Read Status Register (RDSR) and Write Status Register (WRSR). This is available in all the 3 protocols (Extended SPI, DIO-SPI, and QIO-SPI).

**Table 2. Status register format**



### 6.1.1 WIP bit

The Write In Progress (WIP) bit set to 1 indicates that the memory is busy with a Write Status Register, Program or Erase cycle. 0 indicates no cycle is in progress.

### 6.1.2 WEL bit

The Write Enable Latch (WEL) bit set to 1 indicates that the internal Write Enable Latch is set. When set to 0 the internal Write Enable Latch is reset and no Write Status Register, Program or Erase instruction is accepted.

### 6.1.3 Block Protect bits (BP2, BP1, BP0)

The Block Protect (BP2, BP1, BP0) bits are non-volatile. They define the size of the area to be software protected against Program and Erase instructions. These bits are written with the Write Status Register (WRSR) instruction. When one or more of the Block Protect (BP2, BP1, BP0) bits is set to 1, the relevant memory area, as defined in [Table 10.: Protected area sizes, Upper \(TB bit = 0\)](#) becomes protected against all program and erase instructions. The Block Protect (BP2, BP1, BP0) bits can be written provided that the Hardware Protected mode has not been set. The Bulk Erase (BE) instruction is executed if, and only if, all Block Protect (BP2, BP1, BP0) bits are 0.

### 6.1.4 TB bit

The Top/Bottom (TB) bit is non-volatile. It can be set and reset with the Write Status Register (WRSR) instruction provided that the Write Enable (WREN) instruction has been issued.

The Top/Bottom (TB) bit is used in conjunction with the Block Protect (BP2, BP1, BP0) bits to determine if the protected area defined by the Block Protect bits starts from the top or the bottom of the memory array:

- When TB is reset to '0' (default value), the area protected by the Block Protect bits starts from the top of the memory array.
- When TB is set to '1', the area protected by the Block Protect bits starts from the bottom of the memory array.

The TB bit cannot be written when the SRWD bit is set to '1' and the  $\overline{W}$  pin is driven Low.

### 6.1.5 SRWD bit

The Status Register Write Disable (SRWD) bit is operated in conjunction with the Write Protect ( $\overline{W}/VPP$ ) signal. The Status Register Write Disable (SRWD) bit and the Write Protect ( $\overline{W}/VPP$ ) signal allow the device to be put in the hardware protected mode (when the Status Register Write Disable (SRWD) bit is set to '1', and Write Protect ( $\overline{W}/VPP$ ) is driven Low). In this mode, the non-volatile bits of the Status Register (TB, BP2, BP1, BP0) become read-only bits and the Write Status Register (WRSR) instruction is no longer accepted for execution.

## 6.2 Non Volatile Configuration Register

The Non Volatile Configuration Register (NVCR) bits affects the default memory configuration after power-on. It can be used to make the memory start in the configuration to fit the application requirements.

The device is delivered with Non Volatile Configuration Register (NVCR) bits all erased to 1 (FFFFh).

The purpose of the NVCR is to define the default memory settings after the power-on sequence related to many features:

- The number of dummy clock cycle for fast read instructions,
- XIP mode configurations,
- output driver strengths,
- Reset (or Hold) disabling
- Multiple I/O protocol enabling.

The NVCR can be read by the Read Non Volatile Configuration Register (RDNVCR) instruction and written by the Write Non Volatile Configuration Register (WRNVCR) in all the 3 available SPI protocols. See the sections that follow as well as [Table 3.: Non-Volatile Configuration Register](#).

**Table 3. Non-Volatile Configuration Register**

| Bit         | Parameter              | Value | Description            | Note                                                                                                            |
|-------------|------------------------|-------|------------------------|-----------------------------------------------------------------------------------------------------------------|
| NVCR<15:12> | Dummy clock cycles     | 0000  | As '1111'              | To optimize instruction execution (FASTREAD, DOFR, DIOFR, QOFR, QIOFR, ROTP, RDSFDP) according to the frequency |
|             |                        | 0001  | 1                      |                                                                                                                 |
|             |                        | 0010  | 2                      |                                                                                                                 |
|             |                        | 0011  | 3                      |                                                                                                                 |
|             |                        | 0100  | 4                      |                                                                                                                 |
|             |                        | 0101  | 5                      |                                                                                                                 |
|             |                        | 0110  | 6                      |                                                                                                                 |
|             |                        | 0111  | 7                      |                                                                                                                 |
|             |                        | 1000  | 8                      |                                                                                                                 |
|             |                        | 1001  | 9                      |                                                                                                                 |
|             |                        | 1010  | 10                     |                                                                                                                 |
|             |                        | 1011  | 11                     |                                                                                                                 |
|             |                        | 1100  | 12                     |                                                                                                                 |
|             |                        | 1101  | 13                     |                                                                                                                 |
|             |                        | 1110  | 14                     |                                                                                                                 |
| NVCR<11:9>  | XIP enabling at POR    | 000   | XIP for SIO Read       |                                                                                                                 |
|             |                        | 001   | XIP for DOFR           |                                                                                                                 |
|             |                        | 010   | XIP for DIOFR          |                                                                                                                 |
|             |                        | 011   | XIP for QOFR           |                                                                                                                 |
|             |                        | 100   | XIP for QIOFR          |                                                                                                                 |
|             |                        | 101   | reserved               |                                                                                                                 |
|             |                        | 110   | reserved               |                                                                                                                 |
|             |                        | 111   | XIP disabled (default) |                                                                                                                 |
| NVCR<8:6>   | Output Driver Strength | 000   | reserved               | Impedance at Vcc/2                                                                                              |
|             |                        | 001   | 90                     |                                                                                                                 |
|             |                        | 010   | 60                     |                                                                                                                 |
|             |                        | 011   | 45                     |                                                                                                                 |
|             |                        | 100   | reserved               |                                                                                                                 |
|             |                        | 101   | 20                     |                                                                                                                 |
|             |                        | 110   | 15                     |                                                                                                                 |
|             |                        | 111   | 30 (default)           |                                                                                                                 |

**Table 3. Non-Volatile Configuration Register**

| Bit       | Parameter          | Value | Description        | Note                                 |
|-----------|--------------------|-------|--------------------|--------------------------------------|
| NVCR<5>   | Reserved           | x     | Don't Care         | Default value = 1                    |
| NVCR<4>   | Reset/Hold disable | 0     | disabled           | Disable Pad Hold/Reset functionality |
|           |                    | 1     | enabled (default)  |                                      |
| NVCR<3>   | Quad Input Command | 0     | enabled            | Enable command on four input lines   |
|           |                    | 1     | disabled (default) |                                      |
| NVCR<2>   | Dual Input Command | 0     | enabled            | Enable command on two input lines    |
|           |                    | 1     | disabled (default) |                                      |
| NVCR<1:0> | Reserved           | xx    | Don't care         | Default value = "11"                 |

### 6.2.1 Dummy clock cycles NV configuration bits (NVCR bits from 15 to 12)

The bits from 15 to 12 of the Non Volatile Configuration register store the default settings for the dummy clock cycles number after the fast read instructions (in all the 3 available protocols). The dummy clock cycles number can be set from 1 up to 15 as described here, according to operating frequency (the higher is the operating frequency, the bigger must be the dummy clock cycle number) to optimize the fast read instructions performance.

The default values of these bits allow the memory to be safely used with fast read instructions at the maximum frequency (108 MHz). Please note that if the dummy clock number is not sufficient for the operating frequency, the memory reads wrong data.

**Table 4. Maximum operative frequency by dummy clock cycles**

| Maximum allowed frequency (MHz) <sup>(1)</sup>                                         |          |      |       |      |       |
|----------------------------------------------------------------------------------------|----------|------|-------|------|-------|
| Dummy Clock                                                                            | FASTREAD | DOFR | DIOFR | QOFR | QIOFR |
| 1                                                                                      | 54       | 50   | 39    | 43   | 20    |
| 2                                                                                      | 95       | 85   | 59    | 56   | 39    |
| 3                                                                                      | 105      | 95   | 75    | 70   | 49    |
| 4                                                                                      | 108      | 105  | 88    | 83   | 59    |
| 5                                                                                      | 108      | 108  | 94    | 94   | 69    |
| 6                                                                                      | 108      | 108  | 105   | 105  | 78    |
| 7                                                                                      | 108      | 108  | 108   | 108  | 86    |
| 8                                                                                      | 108      | 108  | 108   | 108  | 95    |
| 9                                                                                      | 108      | 108  | 108   | 108  | 105   |
| 10                                                                                     | 108      | 108  | 108   | 108  | 108   |
| 1. All the values are guaranteed by characterization and not 100% tested in production |          |      |       |      |       |

### 6.2.2 XIP NV configuration bits (NVCR bits from 11 to 9)

The bits from 11 to 9 of the Non Volatile Configuration register store the default settings for the XIP operation, allowing the memory to start working directly on the required XIP mode after successive POR sequence: the device then accepts only address on one, two, or four wires (skipping the instruction) depending on the NVCR XIP bits settings.

The default settings for the XIP bits of the NVCR enable the memory to start working in Extended SPI mode after the POR sequence (XIP directly after POR is disabled).

### 6.2.3 Output Driver Strength NV configuration bits (NVCR bits from 8 to 6)

The bits from 8 to 6 of the Non Volatile Configuration register store the default settings for the output driver strength, enabling to optimize the impedance at  $V_{cc}/2$  output voltage for the specific application.

The default values of Output Driver Strength bits of the NVCR set the output impedance at  $V_{cc}/2$  equal to 30 Ohms.

### 6.2.4 Hold (Reset) disable NV configuration bit (NVCR bit 4)

The Hold (RESET) disable bit can be used to disable the Hold (Reset) functionality of the Hold (Reset) / DQ3 pin as described in [Table 3.: Non-Volatile Configuration Register](#). This feature can be useful to avoid accidental Hold or Reset condition entries in applications that never require the Hold (Reset) functionality.

The default values of Hold (Reset) bit of the NVCR is set to enable the Hold (Reset) functionality.

*Note:* Reset functionality is available instead of Hold in devices with a dedicated part number. See [Section 16: Ordering information](#).

### 6.2.5 Quad Input NV configuration bit (NVCR bit 3)

The Quad Input NV configuration bit can be used to make the memory start working in QIO-SPI protocol directly after the power on sequence. The products are delivered with this set to 1, making the memory default in Extended SPI protocol. If the application sets this bit to 0, the device will enter in DIO-SPI protocol right after the next power on.

Please note that in case both QIO-SPI and DIO-SPI are enabled (both bit 3 and bit 2 of the Non Volatile Configuration Register set to 0), the memory will work in QIO-SPI.

### 6.2.6 Dual Input NV configuration bit (NVCR bit 2)

The Dual Input NV configuration bit can be used to make the memory start working in DIO-SPI protocol directly after the power on sequence. The products are delivered with this set to 1, making the memory default in Extended SPI protocol, if the application sets this bit to 0 the device will enter in QIO-SPI protocol right after the next power on.

Please note that in case both QIO-SPI and DIO-SPI are enabled (both bit 3 and bit 2 of the Non Volatile Configuration Register set to 0), the memory will work in QIO-SPI.

## 6.3 Volatile Configuration Register

The Volatile Configuration Register (VCR) affects the memory configuration after every execution of Write Volatile Configuration Register (WRVCR) instruction: this instruction overwrite the memory configuration set at POR by the Non Volatile Configuration Register (NVCR). Its purpose is to define the dummy clock cycles number and to make the device ready to enter in the required XIP mode.

**Table 5. Volatile Configuration Register**

| Bit      | Parameter                         | Binary Value | Decimal Value | Description                                                                                                                 |
|----------|-----------------------------------|--------------|---------------|-----------------------------------------------------------------------------------------------------------------------------|
| VCR<7:4> | Dummy clock cycles <sup>(1)</sup> | 0000         | As '1111'     | To optimize instruction execution (FASTREAD, DOFR, DIOFR, QOFR, QIOFR, ROTP, RDSFDP) according to the frequency             |
|          |                                   | 0001         | 1             |                                                                                                                             |
|          |                                   | 0010         | 2             |                                                                                                                             |
|          |                                   | 0011         | 3             |                                                                                                                             |
|          |                                   | 0100         | 4             |                                                                                                                             |
|          |                                   | 0101         | 5             |                                                                                                                             |
|          |                                   | 0110         | 6             |                                                                                                                             |
|          |                                   | 0111         | 7             |                                                                                                                             |
|          |                                   | 1000         | 8             |                                                                                                                             |
|          |                                   | 1001         | 9             |                                                                                                                             |
|          |                                   | 1010         | 10            |                                                                                                                             |
|          |                                   | 1011         | 11            |                                                                                                                             |
|          |                                   | 1100         | 12            |                                                                                                                             |
|          |                                   | 1101         | 13            |                                                                                                                             |
|          |                                   | 1110         | 14            |                                                                                                                             |
|          |                                   | 1111         | 15            | Targets maximum allowed frequency $f_c$ (108MHz) and guarantees backward compatibility (default)                            |
| VCR<3>   | XIP <sup>(2)</sup>                | 0            | 0             | Ready to enter XIP mode                                                                                                     |
|          |                                   | 1            | 1             | XIP disabled (default)                                                                                                      |
| VCR<2>   | Reserved                          | x            | reserved      | Fixed value = 0b                                                                                                            |
| VCR<1:0> | Wrap                              | 00           | 0             | 16-byte wrap: Output data wraps within an aligned 16-byte boundary starting from the address issued after the command code. |
|          |                                   | 01           | 1             | 32-byte wrap: Output data wraps within an aligned 32-byte boundary starting from the address issued after the command code. |
|          |                                   | 10           | 2             | 64-byte wrap: Output data wraps within an aligned 64-byte boundary starting from the address issued after the command code. |
|          |                                   | 11           | 3             | Continous reading (Default): All bytes are read sequentially                                                                |

1. To optimize instruction execution (FASTREAD, DOFR, DIOFR, QOFR, QIOFR, ROTP) according to the frequency.
2. To make the data on DQ0 during the first dummy clock NOT "Don't Care." For devices with feature set digit equal to 2 or 4 in the part number (Basic XiP), this bit is always Don't Care."

### 6.3.1 Dummy clock cycle: VCR bits 7:4

The bits from 7 to 4 of the Volatile Configuration Register, as the bits from 15 to 12 of the Non-Volatile Configuration register, set the dummy clock cycles number after the fast read instructions (in all the 3 available protocols). The dummy clock cycles number can be set from 1 up to 15 as described in [Table 5.: Volatile Configuration Register](#), according to operating frequency (the higher is the operating frequency, the bigger must be the dummy clock cycle number, according to [Table 4.: Maximum operative frequency by dummy clock cycles](#)) to optimize the fast read instructions performance.

**Note:** *If the dummy clock number is not sufficient for the operating frequency, the memory reads wrong data.*

### 6.3.2 XIP Volatile Configuration bits (VCR bit 3)

The bit 3 of the Volatile Configuration Register is the XIP enabling bit, this bit must be set to 0 to enable the memory working on XIP mode. For devices with a feature set digit equal to 2 or 4 in the part number (Basic XiP), this bit is always Don't Care, and it is possible to operate the memory in XIP mode without setting it to 0. See [Section 16: Ordering information](#).

### 6.3.3 Wrap: VCR bits 1:0

The bits from 1 to 0 allow the Wrap mode to be available for each kind of read instruction and protocol. A specific setting provides the ability to read the memory from sequentially (standard) mode to a wrap mode, where the reads can be confined inside the 16, 32, or 64 byte boundary. For Wrap setting options, see [Table 5.: Volatile Configuration Register](#). The following table shows an example of the sequence of bytes in the 16-byte, 32-byte, and 64-byte options, according to the starting address.

**Table 6. Sequence of Bytes Read during Wrap Mode**

| Starting Address | 16-Byte Wrap                 | 32-Byte Wrap                 | 64-Byte Wrap               |
|------------------|------------------------------|------------------------------|----------------------------|
| 0                | 0-1-2- ... -15-0-1- ...      | 0-1-2- ... -31-0-1- ...      | 0-1-2- ... -63-0-1- ...    |
| 1                | 1-2- ... -15-0-1-2- ...      | 1-2- ... -31-0-1-2- ...      | 1-2- ... -63-0-1-2- ...    |
| 15               | 15-0-1-2-3- ... -15-0-1- ... | 15-16-17- ... -31-0-1- ...   | 15-16-17- ... -63-0-1- ... |
| 31               | 31-16-17- ... -31-16-17- ... | 31-0-1-2-3- ... -31-0-1- ... | 31-32-33- ... -63-0-1- ... |
| 63               | 63-48-49- ... -63-48-49- ... | 63-32-33- ... -63-32-33- ... | 63-0-1- ... -63-0-1- ...   |

## 6.4 Volatile Enhanced Configuration Register

The Volatile Enhanced Configuration Register (VECR) affects the memory configuration after every execution of Write Volatile Enhanced Configuration Register (WRVECR) instruction: this instruction overwrite the memory configuration set during the POR sequence by the Non Volatile Configuration Register (NVCR). Its purpose is:

- enabling of QIO-SPI protocol and DIO-SPI protocol

**Warning:** **WARNING: in case of both QIO-SPI and DIO-SPI enabled, the memory works in QIO-SPI**

- HOLD (Reset) functionality disabling
- To enable the VPP functionality in Quad I/O modify operations
- To define output driver strength (3 bit)

**Table 7. Volatile Enhanced Configuration Register**

| Bit       | Parameter                                                   | Value | Description        | Note                                                                                                  |
|-----------|-------------------------------------------------------------|-------|--------------------|-------------------------------------------------------------------------------------------------------|
| VECR<7>   | Quad Input Command                                          | 0     | Enabled            | Enable command on four input lines                                                                    |
|           |                                                             | 1     | Disabled (default) |                                                                                                       |
| VECR<6>   | Dual Input Command                                          | 0     | Enabled            | Enable command on two input lines                                                                     |
|           |                                                             | 1     | Disabled (default) |                                                                                                       |
| VECR<5>   | Reserved                                                    | x     | Reserved           | Fixed value = 0b                                                                                      |
| VECR<4>   | Reset/Hold disable                                          | 0     | Disabled           | Disable Pad Hold/Reset functionality                                                                  |
|           |                                                             | 1     | Enabled (default)  |                                                                                                       |
| VECR<3>   | Accelerator pin enable in QIO-SPI protocol or in QIFP/QIEFP | 0     | Enabled            | The bit must be considered in case of QIFP, QIEFP, or QIO-SPI protocol. It is "Don't Care" otherwise. |
|           |                                                             | 1     | Disabled (default) |                                                                                                       |
| VECR<2:0> | Output Driver Strength                                      | 000   | reserved           | Impedance at $V_{CC}/2$                                                                               |
|           |                                                             | 001   | 90                 |                                                                                                       |
|           |                                                             | 010   | 60                 |                                                                                                       |
|           |                                                             | 011   | 45                 |                                                                                                       |
|           |                                                             | 100   | reserved           |                                                                                                       |
|           |                                                             | 101   | 20                 |                                                                                                       |
|           |                                                             | 110   | 15                 |                                                                                                       |
|           |                                                             | 111   | 30 (default)       |                                                                                                       |

#### 6.4.1 Quad Input Command VECR<7>

The Quad Input Command configuration bit can be used to make the memory start working in QIO-SPI protocol directly after the Write Volatile Enhanced Configuration Register (WRVECR) instruction. The default value of this bit is 1, corresponding to Extended SPI protocol. If this bit is set to 0 the memory works in QIO-SPI protocol. If VECR bit 7 is set back to 1 the memory start working again in Extended SPI protocol, unless the bit 6 is set to 0 (in this case the memory start working in DIO-SPI mode).

Please note that in case both QIO-SPI and DIO-SPI are enabled (both bit 7 and bit 6 of the VECR set to 0), the memory will work in QIO-SPI.

### 6.4.2 Dual Input Command VECR<6>

The Dual Input Command configuration bit can be used to make the memory start working in DIO-SPI protocol directly after the Write Volatile Enhanced Configuration Register (WRVECR) instruction. The default value of this bit is 1, corresponding to Extended SPI protocol, if this bit is set to 0 the memory works in DIO-SPI protocol (unless the Volatile Enhanced Configuration Register bit 7 is also set to 0). If the Volatile Enhanced Configuration Register bit 6 is set back to 1 the memory start working again in Extended SPI protocol.

Please note that in case both QIO-SPI and DIO-SPI are enabled (both bit 7 and bit 6 of the VECR are set to 0), the memory will work in QIO-SPI.

### 6.4.3 Reset/Hold disable VECR<4>

The Hold (RESET) disable bit can be used to disable the Hold (Reset) functionality of the Hold (Reset) / DQ3 pin right after the Write Volatile Enhanced Configuration Register (WRVECR) instruction. This feature can be useful to avoid accidental Hold or Reset condition entries in applications that never require the Hold (Reset) functionality. If this bit is set to 0 the Hold (Reset) functionality is disabled, it is possible to enable it back by setting this bit to 1.

Please note that after the next power on the Hold (Reset) functionality will be enabled again unless the bit 4 of the Non Volatile Configuration Register is set to 0.

*Note:* Reset functionality is available instead of Hold in devices with a dedicated part number. See [Section 16: Ordering information](#).

### 6.4.4 Accelerator pin enable: QIO-SPI protocol / QIFP/QIEFP VECR<3>

The bit 3 of the Volatile Enhanced Configuration Register determines whether it is possible to use the Vpp accelerating voltage to speed up internal modify operation with Quad program and erase instructions (both in Extended or QIO-SPI protocols).

If we want to use the Vpp voltage with Quad I/O modify instructions, we must set previously this bit to 0 (his default value is 1, in this case the Vpp pin functionality is disabled in all Quad I/O operations: both in Extended SPI and QIO-SPI protocols).

If the Volatile Enhanced Configuration Register bit 3 is set to 0, using the QIO-SPI protocol, after a Quad Command Page Program instruction or an Erase instruction is received (with all input data in the Program case) and the memory is de-selected, the protocol temporarily switches to Extended SPI protocol until Vpp passes from Vpph to normal I/O value (this transition is mandatory to come back to QIO-SPI protocol), to enable the possibility to perform polling instructions (to check if the internal modify cycle is finished by means of the WIP bit of the Status Register or of the Program/Erase controller bit of the Flag Status register) or Program/Erase Suspend instruction even if the DQ2 pin is temporarily used in his Vpp functionality.

If the Volatile Enhanced Configuration Register bit 3 is set to 0, after any quad modify instruction (both in Extended SPI protocol and QIO-SPI protocol) there is a maximum allowed time-out of 200ms after the last instruction input is received and the memory is de-selected to raise the Vpp signal to Vpph, otherwise the modify instruction start at normal speed, without the Vpph enhancement, and a flag error appears on Flag Status Register bit 3.

### 6.4.5 Output Driver Strength VECR<2:0>

The bits from 2 to 0 of the VECR set the value of the output driver strength, enabling to optimize the impedance at Vcc/2 output voltage for the specific application as described in [Table 7.: Volatile Enhanced Configuration Register](#).

The default values of Output Driver Strength is set by the dedicated bits of the Non Volatile Configuration Register (NVCR), the parts are delivered with the output impedance at Vcc/2 equal to 30 Ohms.

## 6.5 Flag Status Register

The Flag Status Register is a powerful tool to investigate the status of the device, checking information regarding what is actually doing the memory and detecting possible error conditions.

The Flag status register is composed by 8 bit. Three bits (Program/Erase Controller bit, Erase Suspend bit and Program Suspend bit) are a "Status Indicator bit", they are set and reset automatically by the memory. Four bits (Erase error bit, Program error bit, VPP 1 to 0 error bit and Protection error bit) are "Error Indicators bits", they are set by the memory when some program or erase operation fails or the user tries to perform a forbidden operation. The user can clear the Error Indicators bits by mean of the Clear Flag Status Register (CLFSR) instruction.

All the Flag Status Register bits can be read by mean of the Read Status Register (RFSR) instruction.

**Table 8. Flag Status Register**

| BIT | Description              | Note   |
|-----|--------------------------|--------|
| 7   | P/E Controller (not WIP) | Status |
| 6   | Erase Suspend            | Status |
| 5   | Erase                    | Error  |
| 4   | Program                  | Error  |
| 3   | VPP                      | Error  |
| 2   | Program Suspend          | Status |
| 1   | Protection               | Error  |
| 0   | RESERVED                 |        |

### 6.5.1 P/E Controller Status bit

The bit 7 of the Flag Status register represents the Program/Erase Controller Status bit, It indicates whether there is a Program/Erase internal cycle active. When P/E Controller Status bit is Low (FSR<7>=0) the device is busy; when the bit is High (FSR<7>=1) the device is ready to process a new command.

This bit has the same meaning of Write In Progress (WIP) bit of the standard SPI Status Register, but with opposite logic: FSR<7> = not WIP

It's possible to make the polling instructions, to check if the internal modify operations are finished, both on the Flag Status register bit 7 or on WIP bit of the Status Register.

### 6.5.2 Erase Suspend Status bit

The bit 6 of the Flag Status register represents the Erase Suspend Status bit, It indicates that an Erase operation has been suspended or is going to be suspended.

The bit is set (FSR<6>=1) within the Erase Suspend Latency time, that is as soon as the Program/Erase Suspend command (PES) has been issued, therefore the device may still complete the operation before entering the Suspend Mode.

The Erase Suspend Status should be considered valid when the P/E Controller bit is high (FSR<7>=1).

When a Program/Erase Resume command (PER) is issued the Erase Suspend Status bit returns Low (FSR<6>=0)

### 6.5.3 Erase Status bit

The bit 5 of the Flag Status Register represents the Erase Status bit. It indicates an erase failure or a protection error when an erase operation is issued.

When the Erase Status bit is High (FSR<5>=1) after an Erase failure that means that the P/E Controller has applied the maximum pulses number to the portion to be erased and still failed to verify that it has correctly erased.

The Erase Status bit should be read once the P/E Controller Status bit is High.

The Erase Status bit is related to all possible erase operations: Sector Erase, Sub Sector Erase, and Bulk Erase in all the three available protocols (SPI, DIO-SPI and QIO-SPI).

Once the bit 5 is set High, it can only be reset Low (FSR<5>=0) by a Clear Flag Status Register command (CLFSR).

If set High it should be reset before a new Erase command is issued; otherwise the new command will appear to fail.

### 6.5.4 Program Status bit

The bit 4 of the Flag Status Register represents the Program Status bit. It indicates:

- a Program failure
- an attempt to program a '1' on '0' when VPP=VPPH (only when the pattern is a multiple of 64 bits, otherwise this bit is "Don't care").
- a protection error when a program is issued

When the Program Status bit is High (FSR<4>=1) after a Program failure that means that the P/E Controller has applied the maximum pulses number to the bytes and it still failed to verify that the required data have been correctly programmed.

After an attempt to program '1' on '0', the FSR<4> only goes High (FSR<4>=1) if VPP=VPPH and the data pattern is a multiple of 64 bits: if VPP is not VPPH, FSR<4> remains Low and the attempt is not shown while if VPP is equal to VPPH but the pattern is not a 64 bits multiple the bit 4 is Don't Care. The Program Status bit should be read once the P/E Controller Status bit is High.

The Program Status bit is related to all possible program operations in the Extended SPI protocol: Page Program, Dual and Quad Input Fast Program, Dual and Quad Input Extended Fast Program, and OTP Program.

The Program Status bit is related to the following program operations in the DIO-SPI and QIO-SPI protocols: Dual and Quad Command Page program and OTP program.

Once the bit is set High, it can only be reset Low ( $FSR<4>=0$ ) by a Clear Flag Status Register command (CLFSR). If set High it should be reset before a new Program command is issued, otherwise the new command will appear to fail.

### 6.5.5 VPP Status bit

The bit 3 of the Flag Status Register represents the VPP Status bit. It indicates an invalid voltage on the VPP pin during Program and Erase operations. The VPP pin is sampled at the beginning of a Program or Erase operation.

If VPP becomes invalid during an operation, that is the voltage on VPP pin is below the VPPH Voltage (9V), the VPP Status bit goes High ( $FSR<3>=1$ ) and indeterminate results can occur.

Once set High, the VPP Status bit can only be reset Low ( $FSR<3>=0$ ) by a Clear Flag Status Register command (CLFSR). If set High it should be reset before a new Program or Erase command is issued; otherwise, the new command will appear to fail.

### 6.5.6 Program Suspend Status bit

The bit 2 of the Flag Status register represents the Program Suspend Status bit. It indicates that a Program operation has been suspended or is going to be suspended.

The bit is set ( $FSR<2>=1$ ) within the Program Suspend Latency time; that is, as soon as the Program/Erase Suspend command (PES) has been issued. Therefore the device may still complete the operation before entering the Suspend Mode.

The Program Suspend Status should be considered valid when the P/E Controller bit is high ( $FSR<7>=1$ ).

When a Program/Erase Resume command (PER) is issued the Program Suspend Status bit returns Low ( $FSR<2>=0$ ).

### 6.5.7 Protection Status bit

The bit 1 of the Flag Status Register represents the Protection Status bit. It indicates that an Erase or Program operation has tried to modify the contents of a protected array sector, or that a modify operation has tried to access to a locked OTP space. The Protection Status bit is related to all possible protection violations as follows:

- n The sector is protected by Software Protection Mode 1 (SPM1) Lock registers,
- n The sector is protected by Software Protection Mode 2 (SPM2) Block Protect Bits (standard SPI Status Register),
- n An attempt to program OTP when locked,
- n A Write Status Register command (WRSR) on STD SPI Status Register when locked by the SRWD bit in conjunction with the Write Protect (W/VPP) signal (Hardware Protection Mode).

Once set High, the Protection Status bit can only be reset Low ( $FSR<1>=0$ ) by a Clear Flag Status Register command (CLFSR). If set High it should be reset before a new command is issued, otherwise the new command will appear to fail.

## 7 Protection modes

There are protocol-related and specific hardware and software protection modes. They are described below.

### 7.1 SPI Protocol-related protections

This applies to all three protocols. The environments where non-volatile memory devices are used can be very noisy. No SPI device can operate correctly in the presence of excessive noise. To help combat this, the N25Q032 features the following data protection mechanisms:

- Power On Reset and an internal timer (tVTW) can provide protection against inadvertent changes while the power supply is outside the operating specification.
- Program, Erase, and Write Status Register instructions are checked to ensure the instruction includes a number of clock pulses that is a multiple of a byte before they are accepted for execution.
- All instructions that modify data must be preceded by a Write Enable (WREN) instruction to set the Write Enable Latch (WEL) bit. This bit is returned to its reset state by the following events (in Extended SPI protocol mode):
  - Power-up
  - Write Disable (WRDI) instruction completion
  - Write Status Register (WRSR) instruction completion
  - Write to Lock Register (WRLR) instruction completion
  - Program OTP (POTP) instruction completion
  - Page Program (PP) instruction completion
  - Dual Input Fast Program (DIFP) instruction completion
  - Dual Input Extended Fast Program (DIEFP) instruction completion
  - Quad Input Fast Program (QIFP) instruction completion
  - Quad Input Extended Fast Program (QIEFP) instruction completion
  - Subsector Erase (SSE) instruction completion
  - Sector Erase (SE) instruction completion
  - Bulk Erase (BE) instruction completion
  - Write Non-Volatile Configuration Register (WRNVCr) instruction completion

This bit is also returned to its reset state after all the analogous events in DIO-SPI and QIO-SPI protocol modes.

## 7.2 Specific hardware and software protection

There are two software protected modes, SPM1 and SPM2, that can be combined to protect the memory array as required. The SPM2 can be locked by hardware with the help of the  $\overline{W}$  input pin.

### SPM1

The first software protected mode (SPM1) is managed by specific Lock Registers assigned to each 64 Kbyte sector.

The Lock Registers can be read and written using the Read Lock Register (RDLR) and Write to Lock Register (WRLR) instructions.

In each Lock Register two bits control the protection of each sector: the Write Lock bit and the Lock Down bit.

- **Write Lock bit:** The Write Lock bit determines whether the contents of the sector can be modified (using the Program or Erase instructions). When the Write Lock bit is set to '1', the sector is write protected - any operations that attempt to change the data in the sector will fail. When the Write Lock bit is reset to '0', the sector is not write protected by the Lock Register, and may be modified.
- **Lock Down bit:** The Lock Down bit provides a mechanism for protecting software data from simple hacking and malicious attack. When the Lock Down bit is set to '1', further modification to the Write Lock and Lock Down bits cannot be performed. A powerup is required before changes to these bits can be made. When the Lock Down bit is reset to '0', the Write Lock and Lock Down bits can be changed.

The definition of the Lock Register bits is given in [Table 19: Lock Register out](#).

### SPM2

The second software protected mode (SPM2) uses the Block Protect bits (BP2, BP1, BP0) and the Top/Bottom bit (TB bit) to allow part of the memory to be configured as read-only. See [Section 16: Ordering information](#).

**Table 9. Software protection truth table (Sectors 0 to 63, 64 Kbyte granularity)**

| Sector Lock Register |                | Protection Status                                                                                                     |
|----------------------|----------------|-----------------------------------------------------------------------------------------------------------------------|
| Lock Down bit        | Write Lock bit |                                                                                                                       |
| 0                    | 0              | Sector unprotected from Program/Erase operations, protection status reversible.                                       |
| 0                    | 1              | Sector protected from Program/Erase operations, protection status reversible.                                         |
| 1                    | 0              | Sector unprotected from Program/Erase operations.<br>Sector protection status cannot be changed except by a power-up. |
| 1                    | 1              | Sector protected from Program/Erase operations.<br>Sector protection status cannot be changed except by a power-up.   |

As a second level of protection, the Write Protect signal (applied on the  $\overline{W}/VPP$  pin) can freeze the Status Register in a read-only mode. In this mode, the Block Protect bits (BP2, BP1, BP0), the Top/Bottom (TB) bit, and the Status Register Write Disable bit (SRWD) are protected.

Table 10. Protected area sizes, Upper (TB bit = 0)

| Status Register Content |         |         |         | Memory Content |                  |
|-------------------------|---------|---------|---------|----------------|------------------|
| TB bit                  | BP2 Bit | BP1 Bit | BP0 Bit | Protected Area | Unprotected Area |
| 0                       | 0       | 0       | 0       | None           | All sectors      |
| 0                       | 0       | 0       | 1       | Upper 64th     | Sectors 0 to 62  |
| 0                       | 0       | 1       | 0       | Upper 32th     | Sectors 0 to 61  |
| 0                       | 0       | 1       | 1       | Upper 16th     | Sectors 0 to 59  |
| 0                       | 1       | 0       | 0       | Upper eighth   | Sectors 0 to 55  |
| 0                       | 1       | 0       | 1       | Upper quarter  | Sectors 0 to 47  |
| 0                       | 1       | 1       | 0       | Upper half     | Sectors 0 to 31  |
| 0                       | 1       | 1       | 1       | All sectors    | None             |

Table 11. Protected area sizes, Lower (TB bit = 1)

| Status Register Content |         |         |         | Memory Content |                  |
|-------------------------|---------|---------|---------|----------------|------------------|
| TB bit                  | BP2 Bit | BP1 Bit | BP0 Bit | Protected Area | Unprotected Area |
| 1                       | 0       | 0       | 0       | None           | All sectors      |
| 1                       | 0       | 0       | 1       | Lower 64th     | Sectors 1 to 63  |
| 1                       | 0       | 1       | 0       | Lower 32nd     | Sectors 2 to 63  |
| 1                       | 0       | 1       | 1       | Lower 16th     | Sectors 4 to 63  |
| 1                       | 1       | 0       | 0       | Lower eighth   | Sectors 8 to 63  |
| 1                       | 1       | 0       | 1       | Lower quarter  | Sectors 16 to 63 |
| 1                       | 1       | 1       | 0       | Lower half     | Sectors 32 to 63 |
| 1                       | 1       | 1       | 1       | All sectors    | None             |

## 8 Memory organization

The memory is organized as:

- 4,194,304 bytes (8 bits each)
- 64 sectors (64 Kbytes each)
- 1,024 subsectors (4 Kbytes each)
- 16,384 pages (256 bytes each)
- 64 OTP bytes located outside the main memory array

Each page can be individually programmed: bits are programmed from 1 to 0. The device is Subsector erasable, Sector erasable or Bulk Erasable but not Page Erasable: bits are erased from 0 to 1.

**Figure 9. Block diagram**

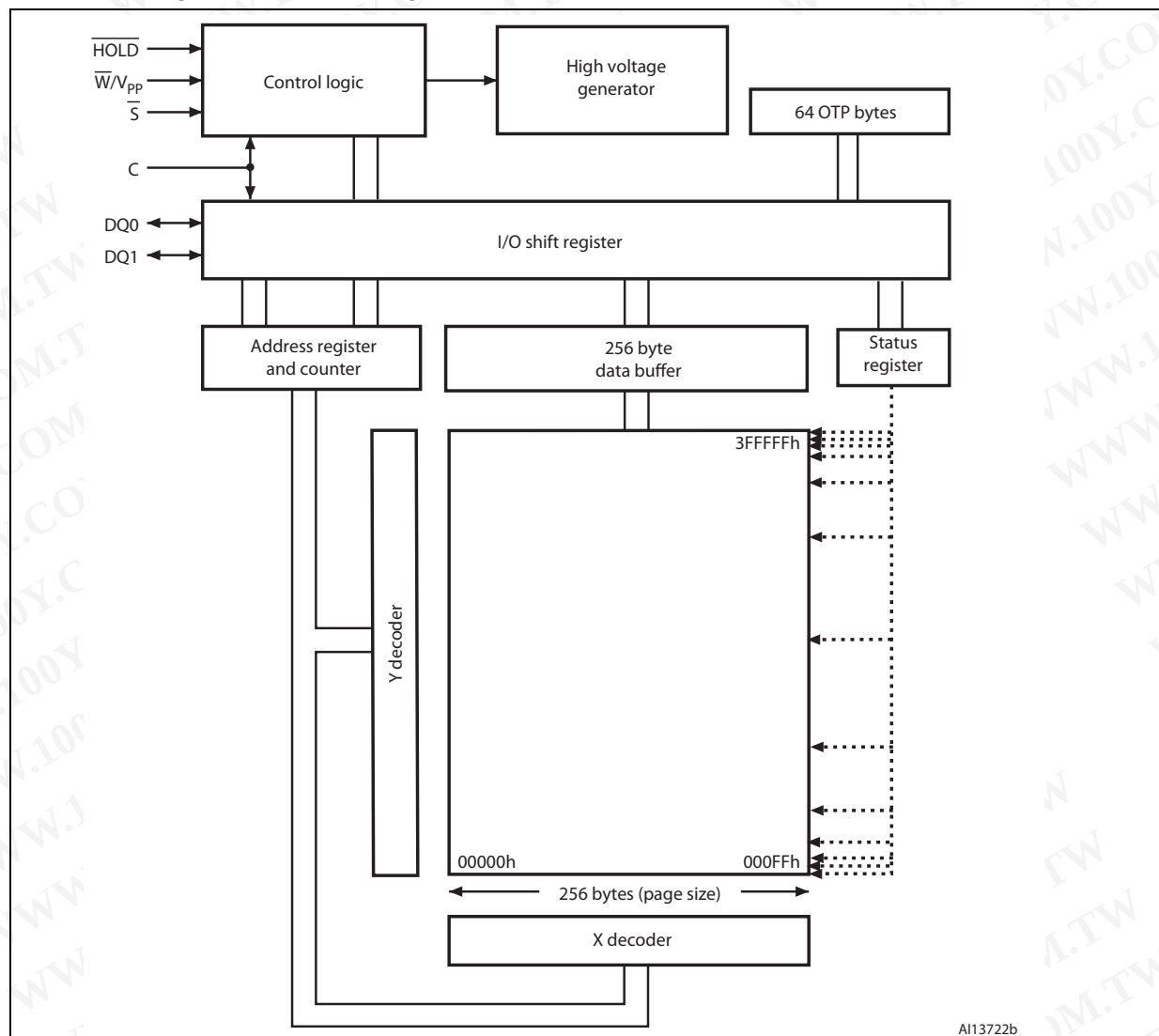


Table 12. Memory organization

| Sector | Subsector | Address range |           | Sector | Subsector | Address range |           |
|--------|-----------|---------------|-----------|--------|-----------|---------------|-----------|
| 63     | 1023      | 3FF000h       | 3FFFFFFh  | 52     | 847       | 34F000h       | 34FFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 1008      | 3F0000h       | 3F0FFFFh  |        | 832       | 340000h       | 340FFFFh  |
| 62     | 1007      | 3EF000h       | 3EFFFFFFh | 51     | 831       | 33F000h       | 33FFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 992       | 3E0000h       | 3E0FFFFh  |        | 816       | 330000h       | 330FFFFh  |
| 61     | 991       | 3DF000h       | 3DFFFFFFh | 50     | 815       | 32F000h       | 32FFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 976       | 3D0000h       | 3D0FFFFh  |        | 800       | 320000h       | 320FFFFh  |
| 60     | 975       | 3CF000h       | 3CFFFFFFh | 49     | 799       | 31F000h       | 31FFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 960       | 3C0000h       | 3C0FFFFh  |        | 784       | 310000h       | 310FFFFh  |
| 59     | 959       | 3BF000h       | 3BFFFFFFh | 48     | 783       | 30F000h       | 30FFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 944       | 3B0000h       | 3B0FFFFh  |        | 768       | 300000h       | 300FFFFh  |
| 58     | 943       | 3AF000g       | 3AFFFFFFh | 47     | 767       | 2FF000h       | 2FFFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 928       | 3A0000h       | 3A0FFFFh  |        | 752       | 2F0000h       | 2F0FFFFh  |
| 57     | 927       | 39F000h       | 39FFFFFFh | 46     | 751       | 2EF000h       | 2EFFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 912       | 390000h       | 390FFFFh  |        | 736       | 2E0000h       | 2E0FFFFh  |
| 56     | 911       | 38F000h       | 38FFFFFFh | 45     | 735       | 2DF000h       | 2DFFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 896       | 380000h       | 380FFFFh  |        | 720       | 2D0000h       | 2D0FFFFh  |
| 55     | 895       | 37F000h       | 37FFFFFFh | 44     | 719       | 2CF000h       | 2CFFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 880       | 370000h       | 370FFFFh  |        | 704       | 2C0000h       | 2C0FFFFh  |
| 54     | 879       | 36F000h       | 36FFFFFFh | 43     | 703       | 2BF000h       | 2BFFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 864       | 360000h       | 360FFFFh  |        | 688       | 2B0000h       | 2B0FFFFh  |
| 53     | 863       | 35F000h       | 35FFFFFFh | 42     | 687       | 2AF000h       | 2AFFFFFFh |
|        | :         | :             | :         |        | :         | :             | :         |
|        | 848       | 350000h       | 350FFFFh  |        | 672       | 2A0000h       | 2A0FFFFh  |

Table 12. Memory organization (continued)

| Sector | Subsector | Address range |         | Sector | Subsector | Address range |         |
|--------|-----------|---------------|---------|--------|-----------|---------------|---------|
| 41     | 671       | 29F000h       | 29FFFFh | 30     | 495       | 1EF000h       | 1EFFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 656       | 290000h       | 290FFFh |        | 480       | 1E0000h       | 1E0FFFh |
| 40     | 655       | 28F000h       | 28FFFFh | 29     | 479       | 1DF000h       | 1DFFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 640       | 280000h       | 280FFFh |        | 464       | 1D0000h       | 1D0FFFh |
| 39     | 639       | 27F000h       | 27FFFFh | 28     | 463       | 1CF000h       | 1CFFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 624       | 270000h       | 270FFFh |        | 448       | 1C0000h       | 1C0FFFh |
| 38     | 623       | 26F000h       | 26FFFFh | 27     | 447       | 1BF000h       | 1BFFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 608       | 260000h       | 260FFFh |        | 432       | 1B0000h       | 1B0FFFh |
| 37     | 607       | 25F000h       | 25FFFFh | 26     | 431       | 1AF000h       | 1AFFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 592       | 250000h       | 250FFFh |        | 416       | 1A0000h       | 1A0FFFh |
| 36     | 591       | 24F000h       | 24FFFFh | 25     | 415       | 19F000h       | 19FFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 576       | 240000h       | 240FFFh |        | 400       | 190000h       | 190FFFh |
| 35     | 575       | 23F000h       | 23FFFFh | 24     | 399       | 18F000h       | 18FFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 560       | 230000h       | 230FFFh |        | 384       | 180000h       | 180FFFh |
| 34     | 559       | 22F000h       | 22FFFFh | 23     | 383       | 17F000h       | 17FFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 544       | 220000h       | 220FFFh |        | 368       | 170000h       | 170FFFh |
| 33     | 543       | 21F000h       | 21FFFFh | 22     | 367       | 16F000h       | 16FFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 528       | 210000h       | 210FFFh |        | 352       | 160000h       | 160FFFh |
| 32     | 527       | 20F000h       | 20FFFFh | 21     | 351       | 15F000h       | 15FFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 512       | 200000h       | 200FFFh |        | 336       | 150000h       | 150FFFh |
| 31     | 511       | 1FF000h       | 1FFFFFh | 20     | 335       | 14F000h       | 14FFFFh |
|        | :         | :             | :       |        | :         | :             | :       |
|        | 496       | 1F0000h       | 1F0FFFh |        | 320       | 140000h       | 140FFFh |

Table 12. Memory organization (continued)

| Sector | Subsector | Address range |         | Sector | Subsector | Address range |        |
|--------|-----------|---------------|---------|--------|-----------|---------------|--------|
| 19     | 319       | 13F000h       | 13FFFFh | 8      | 143       | 8F000h        | 8FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 304       | 130000h       | 130FFFh |        | 128       | 80000h        | 80FFFh |
| 18     | 303       | 12F000h       | 12FFFFh | 7      | 127       | 7F000h        | 7FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 288       | 120000h       | 120FFFh |        | 112       | 70000h        | 70FFFh |
| 17     | 287       | 11F000h       | 11FFFFh | 6      | 111       | 6F000h        | 6FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 272       | 110000h       | 110FFFh |        | 96        | 60000h        | 60FFFh |
| 16     | 271       | 10F000h       | 10FFFFh | 5      | 95        | 5F000h        | 5FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 256       | 100000h       | 100FFFh |        | 80        | 50000h        | 50FFFh |
| 15     | 255       | FF000h        | FFFFFFh | 4      | 79        | 4F000h        | 4FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 240       | F0000h        | F0FFFh  |        | 64        | 40000h        | 40FFFh |
| 14     | 239       | EF000h        | EFFFFh  | 3      | 63        | 3F000h        | 3FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 224       | E0000h        | E0FFFh  |        | 48        | 30000h        | 30FFFh |
| 13     | 223       | DF000h        | DFFFFh  | 2      | 47        | 2F000h        | 2FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 208       | D0000h        | D0FFFh  |        | 32        | 20000h        | 20FFFh |
| 12     | 207       | CF000h        | CFFFFh  | 1      | 31        | 1F000h        | 1FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 192       | C0000h        | C0FFFh  |        | 16        | 10000h        | 10FFFh |
| 11     | 191       | BF000h        | BFFFFh  | 0      | 15        | 0F000h        | 0FFFFh |
|        | :         | :             | :       |        | :         | :             | :      |
|        | 176       | B0000h        | B0FFFh  |        | 4         | 04000h        | 04FFFh |
| 10     | 175       | AF000h        | AFFFFh  |        | 3         | 03000h        | 03FFFh |
|        | :         | :             | :       |        | 2         | 02000h        | 02FFFh |
|        | 160       | A0000h        | A0FFFh  |        | 1         | 01000h        | 01FFFh |
| 9      | 159       | 9F000h        | 9FFFFh  |        | 0         | 00000h        | 00FFFh |
|        | :         | :             | :       |        |           |               |        |
|        | 144       | 90000h        | 90FFFh  |        |           |               |        |

## 9 Instructions

The device can work in three different protocols: Extended SPI, DIO-SPI and QIO-SPI. Each protocol has a dedicated instruction set, and each instruction set features the same functionality:

- Read, program and erase the memory and the 64 byte OTP area,
- Suspend and resume the program or erase operations,
- Read and modify all the registers, read the Serial Flash Discovery Parameter area (SFDP), and read the device ID: please note that in this case there is a small functionality difference among the single and the multiple I/O read ID instructions. See [Section 9.2.1: Multiple I/O Read Identification protocol](#) and [Section 9.3.1: Multiple I/O Read Identification \(MIORDID\)](#).

The application can choose in every time of the device life which protocol to use by setting the dedicated bits either in the Non Volatile Configuration Register or the Volatile Enhanced Configuration Register.

**Note:** *In multiple SPI protocols, all instructions, addresses, and data are parallel on two lines (DIO-SPI protocol) or four lines (QIO-SPI protocol).*

All instructions, addresses and data are shifted in and out of the device, most significant bit first.

Serial Data input(s) is (are) sampled on the first rising edge of Serial Clock (C) after Chip Select ( $\bar{S}$ ) is driven Low. Then, the one-byte instruction code must be shifted in to the device, most significant bit first, on Serial Data input(s), each bit being latched on the rising edges of Serial Clock (C). Instruction code is shifted into the device just on DQ0 in Extended SPI protocol, on DQ0 and DQ1 in DIO-SPI protocol and on DQ0, DQ1, DQ2, and DQ3 in QIO-SPI protocol.

In standard mode every instruction sequence starts with a one-byte instruction code. Depending on the instruction, this might be followed by address bytes, or by data bytes, or by both or none.

In XIP modes only read operation and exit XIP mode can be performed, and to read the memory content no instructions code are needed: the device directly receives addresses and after a configurable number of dummy clock cycles, it outputs the required data.

### 9.1 Extended SPI Instructions

In Extended SPI protocol instruction set the instruction code is always shifted into the device just on DQ0 pin, while depending on the instruction addresses and input/output data can run on single, two or four wires.

In the case of a Read Instructions Data Bytes (READ), Read Data Bytes at Higher Speed (FAST\_READ), Dual Output Fast Read (DOFR), Dual Input/Output Fast Read (DIOFR), Quad Output Fast Read (QOFR), Quad Input/Output Fast Read (QIOFR), Read OTP (ROTP), Read Lock Registers (RDLR), Read Status Register (RDSR), Read Flag Status Register (RFSR), Read NV Configuration Register (RDNVCR), Read Volatile Configuration Register (RDVCR), Read Volatile Enhanced Configuration Register (RDVECR), Read Serial Flash Discovery Parameter (RDSFDP), and Read Identification (RDID) instruction, the shifted-in instruction sequence is followed by a data-out sequence. Chip Select ( $\bar{S}$ ) can be driven High after any bit of the data-out sequence is being shifted out.

In the case of a Page Program (PP), Program OTP (POTP), Dual Input Fast Program (DIFP), Dual Input Extended Fast Program (DIEFP), Quad Input Fast Program (QIFP), Quad Input Extended Fast Program (QIEFP), Subsector Erase (SSE), Sector Erase (SE), Bulk Erase (BE), Write Status Register (WRSR), Clear Flag Status Register (CLFSR), Write to Lock Register (WRLR), Write Configuration Register (WRVCR), Write Enhanced Configuration Register (WRVECR), Write NV Configuration Register (WRNVCR), Write Enable (WREN) or Write Disable (WRDI) instruction, Chip Select (S) must be driven High exactly at a byte boundary, otherwise the instruction is rejected, and is not executed. That is, Chip Select (S) must be driven High when the number of clock pulses after Chip Select (S) being driven Low is an exact multiple of eight.

All attempts to access the memory array are ignored during:

- Write Status Register cycle
- Write Non Volatile Configuration Register
- Program cycle
- Erase cycle

The following continue unaffected, with one exception:

- Internal Write Status Register cycle,
- Write Non Volatile Configuration Register,
- Program cycle,
- Erase cycle

The only exception is the Program/Erase Suspend instruction (PES), that can be used to pause all the program and the erase cycles except for:

- Program OTP (POTP),
- Bulk Erase,
- Write Status Register,
- Write Non Volatile Configuration Register.

The suspended program or erase cycle can be resumed by the Program/Erase Resume instruction (PER). During the program/erase cycles, the polling instructions (both on the Status register and on the Flag Status register) are also accepted to allow the application to check the end of the internal modify cycles.

*Note: These polling instructions don't affect the internal cycles performing.*

Table 13. Instruction set: extended SPI protocol (page 1 of 2)

| Instruction | Description                           | One-byte Instruction Code (BIN) | One-byte Instruction Code (HEX) | Address bytes | Dummy clock cycle | Data bytes |
|-------------|---------------------------------------|---------------------------------|---------------------------------|---------------|-------------------|------------|
| RDID        | Read Identification                   | 1001 111x                       | 9Eh / 9Fh                       | 0             | 0                 | 1 to 20    |
| READ        | Read Data Bytes                       | 0000 0011                       | 03h                             | 3             | 0                 | 1 to ∞     |
| FAST_READ   | Read Data Bytes at Higher Speed       | 0000 1011                       | 0Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| RDSFDP      | Read Serial Flash Discovery Parameter | 01011010                        | 5Ah                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| DOFR        | Dual Output Fast Read                 | 0011 1011                       | 3Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| DIOFR       | Dual Input/Output Fast Read           | 1011 1011                       | BB                              | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| QOFR        | Quad Output Fast Read                 | 0110 1011                       | 6Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| QIOFR       | Quad Input/Output Fast Read           | 1110 1011                       | EBh                             | 3             | 10 <sup>(1)</sup> | 1 to ∞     |
| ROTP        | Read OTP (Read of OTP area)           | 0100 1011                       | 4Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to 65    |
| WREN        | Write Enable                          | 0000 0110                       | 06h                             | 0             | 0                 | 0          |
| WRDI        | Write Disable                         | 0000 0100                       | 04h                             | 0             | 0                 | 0          |
| PP          | Page Program                          | 0000 0010                       | 02h                             | 3             | 0                 | 1 to 256   |
| DIFP        | Dual Input Fast Program               | 1010 0010                       | A2h                             | 3             | 0                 | 1 to 256   |
| DIEFP       | Dual Input Extended Fast Program      | 1101 0010                       | D2h                             | 3             | 0                 | 1 to 256   |
| QIFP        | Quad Input Fast Program               | 0011 0010                       | 32h                             | 3             | 0                 | 1 to 256   |
| QIEFP       | Quad Input Extended Fast Program      | 0001 0010                       | 12h                             | 3             | 0                 | 1 to 256   |
| POTP        | Program OTP (Program of OTP area)     | 0100 0010                       | 42h                             | 3             | 0                 | 1 to 65    |
| SSE         | SubSector Erase                       | 0010 0000                       | 20h                             | 3             | 0                 | 0          |
| SE          | Sector Erase                          | 1101 1000                       | D8h                             | 3             | 0                 | 0          |
| BE          | Bulk Erase                            | 1100 0111                       | C7h                             | 0             | 0                 | 0          |
| PER         | Program/Erase Resume                  | 0111 1010                       | 7Ah                             | 0             | 0                 | 0          |
| PES         | Program/Erase Suspend                 | 0111 0101                       | 75h                             | 0             | 0                 | 0          |
| RDSR        | Read Status Register                  | 0000 0101                       | 05h                             | 0             | 0                 | 1 to ∞     |
| WRSR        | Write Status Register                 | 0000 0001                       | 01h                             | 0             | 0                 | 1          |
| RDLR        | Read Lock Register                    | 1110 1000                       | E8h                             | 3             | 0                 | 1 to ∞     |
| WRLR        | Write to Lock Register                | 1110 0101                       | E5h                             | 3             | 0                 | 1          |
| RFSR        | Read Flag Status Register             | 0111 0000                       | 70h                             | 0             | 0                 | 1 to ∞     |
| CLFSR       | Clear Flag Status Register            | 0101 0000                       | 50h                             | 0             | 0                 | 0          |
| RDNVCR      | Read NV Configuration Register        | 1011 0101                       | B5h                             | 0             | 0                 | 2          |
| WRNVCR      | Write NV Configuration Register       | 1011 0001                       | B1h                             | 0             | 0                 | 2          |
| RDVCR       | Read Volatile Configuration Register  | 1000 0101                       | 85h                             | 0             | 0                 | 1 to ∞     |
| WRVCR       | Write Volatile Configuration Register | 1000 0001                       | 81h                             | 0             | 0                 | 1          |

**Table 13. Instruction set: extended SPI protocol (page 2 of 2)**

| Instruction | Description                                    | One-byte Instruction Code (BIN) | One-byte Instruction Code (HEX) | Address bytes | Dummy clock cycle | Data bytes |
|-------------|------------------------------------------------|---------------------------------|---------------------------------|---------------|-------------------|------------|
| RDVECR      | Read Volatile Enhanced Configuration Register  | 0110 0101                       | 65h                             | 0             | 0                 | 1 to ∞     |
| WRVECR      | Write Volatile Enhanced Configuration Register | 0110 0001                       | 61h                             | 0             | 0                 | 1          |

1. The Number of dummy clock cycles is configurable by user

### 9.1.1 Read Identification (RDID)

The Read Identification (RDID) instruction allows to read the device identification data:

- Manufacturer identification (1 byte)
- Device identification (2 bytes)
- A Unique ID code (UID) (17 bytes, of which 14 are factory programmed)

The manufacturer identification is assigned by JEDEC, and has the value 20h. The device identification is assigned by the device manufacturer, and indicates the memory type in the first byte (BAh), and the memory capacity of the device in the second byte (16h). The UID is composed by 17 read only bytes, containing the length of the following data in the first byte (set to 10h), 2 bytes of Extended Device ID (EDID) to identify the specific device configuration (Top, Bottom or uniform architecture, Hold or Reset functionality), and 14 bytes of the optional Customized Factory Data (CFD) content. The CFD bytes are factory programmed with specific data for each device.

Any Read Identification (RDID) instruction while an Erase or Program cycle is in progress, is not decoded, and has no effect on the cycle that is in progress.

The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. Then, the 8-bit instruction code for the instruction is shifted in. After this, the 24-bit device identification, stored in the memory, the 17 bytes of UID content will be shifted out on Serial Data output (DQ1). Each bit is shifted out during the falling edge of Serial Clock (C).

The instruction sequence is shown in Figure 10.

The Read Identification (RDID) instruction is terminated by driving Chip Select ( $\overline{S}$ ) High at any time during data output.

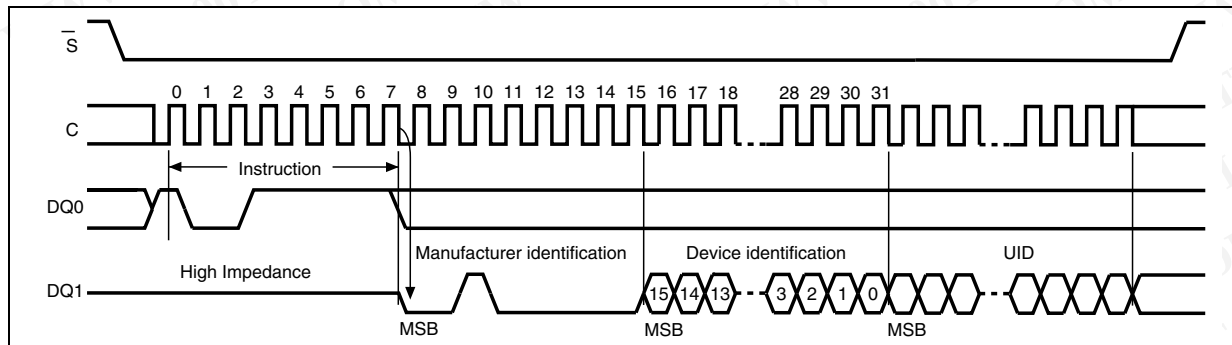
When Chip Select ( $\overline{S}$ ) is driven High, the device is put in the Standby Power mode. Once in the Standby Power mode, the device waits to be selected, so that it can receive, decode and execute instructions.

**Table 14. Read Identification data-out sequence**

| Manufacturer Identification | Device identification |                 | UID             |         |          |
|-----------------------------|-----------------------|-----------------|-----------------|---------|----------|
|                             | Memory type           | Memory capacity | EDID+CFD length | EDID    | CFD      |
| 20h                         | BAh                   | 16h             | 10h             | 2 bytes | 14 bytes |

**Table 15. Extended Device ID table (first byte)**

| Bit 7    | Bit 6    | Bit 5    | Bit 4                                                     | Bit 3                                          | Bit 2                       | Bit 1                          | Bit 0 |
|----------|----------|----------|-----------------------------------------------------------|------------------------------------------------|-----------------------------|--------------------------------|-------|
| Reserved | Reserved | Reserved | VCR XIP bit setting:<br>0 = required,<br>1 = not required | Hold/Reset function:<br>0 = HOLD,<br>1 = Reset | Addressing:<br>0 = by Byte, | Architecture:<br>00 = Uniform, |       |

**Figure 10. Read identification instruction and data-out sequence**

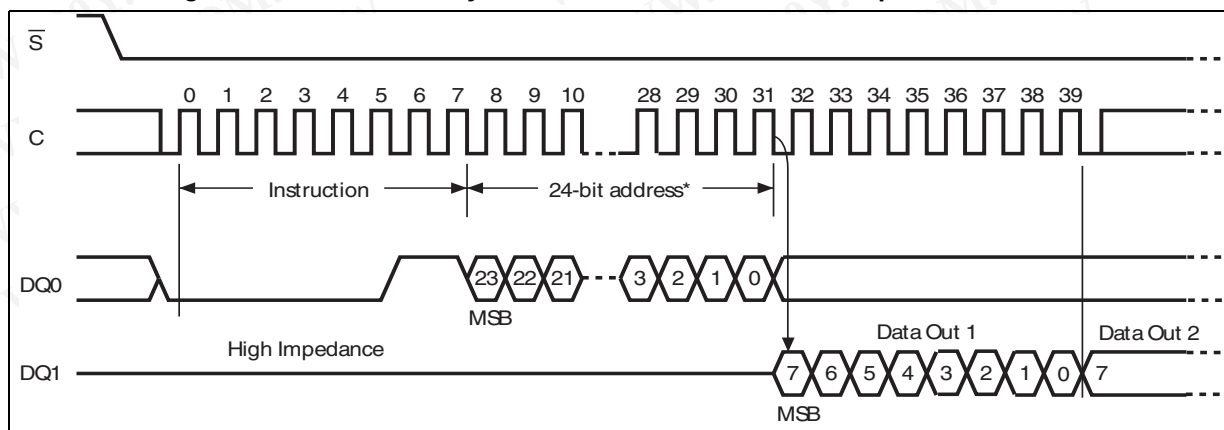
### 9.1.2 Read Data Bytes (READ)

The device is first selected by driving Chip Select ( $\bar{S}$ ) Low. The instruction code for the Read Data Bytes (READ) instruction is followed by a 3-byte address (A23-A0), each bit being latched-in during the rising edge of Serial Clock (C). Then the memory contents at that address are shifted out on Serial Data output (DQ1), each bit being shifted out at a maximum frequency  $f_R$  during the falling edge of Serial Clock (C).

The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. The whole memory can, therefore, be read with a single Read Data Bytes (READ) instruction. When the highest address is reached, the address counter rolls over to 000000h, allowing the read sequence to be continued indefinitely.

The Read Data Bytes (READ) instruction is terminated by driving Chip Select ( $\bar{S}$ ) High. Chip Select ( $\bar{S}$ ) can be driven High at any time during data output. Any Read Data Bytes (READ) instruction, while an Erase or Program cycle is in progress, is rejected without having any effects on the cycle that is in progress.

Figure 11. Read Data Bytes instruction and data-out sequence



Address bits A23 and A22 are "Don't Care."

### 9.1.3 Read Data Bytes at Higher Speed (FAST\_READ)

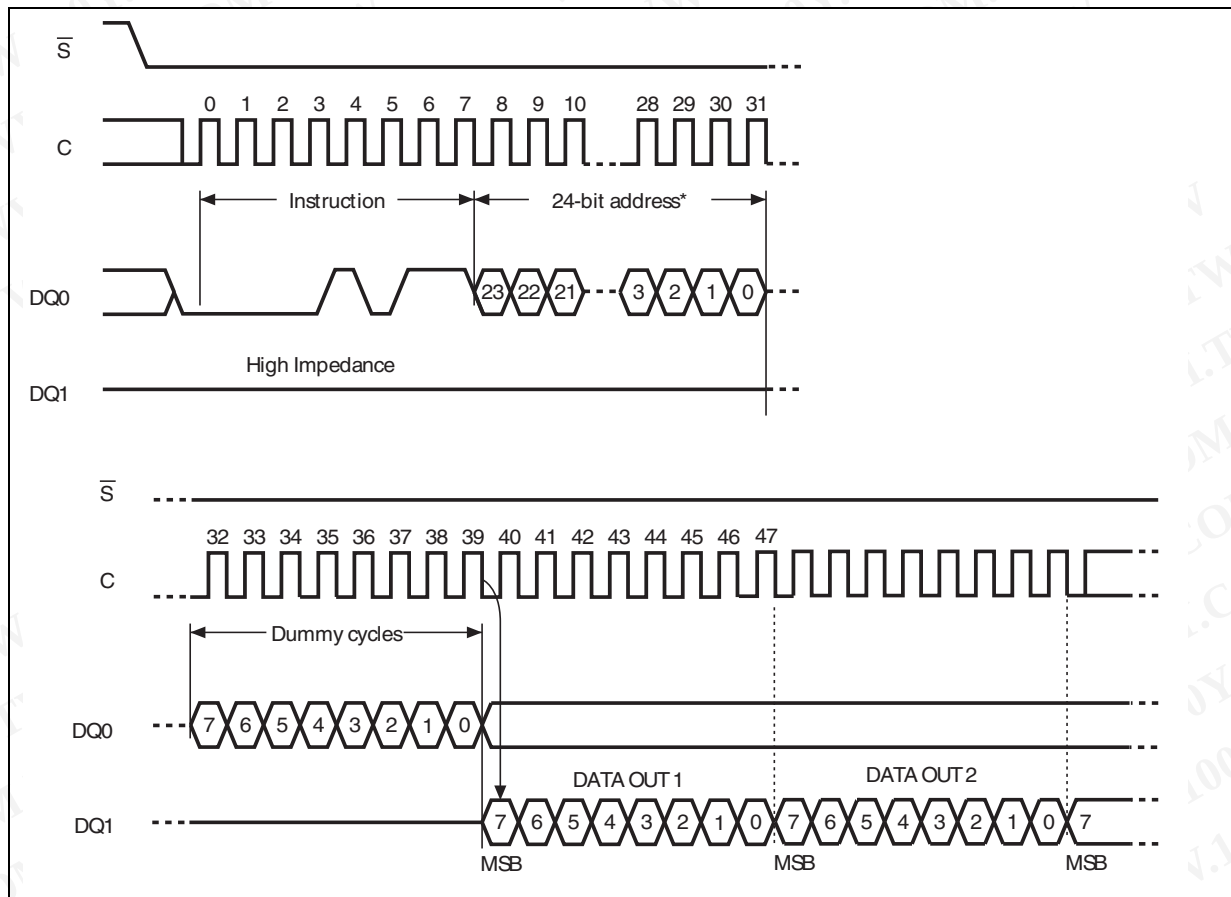
The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. The instruction code for the Read Data Bytes at Higher Speed (FAST\_READ) instruction is followed by a 3-byte address (A23-A0) and a configurable number of dummy clock cycles, each bit being latched-in during the rising edge of Serial Clock (C).

Then the memory contents, at that address, are shifted out on Serial Data output (DQ1) at a maximum frequency  $f_C$ , during the falling edge of Serial Clock (C).

The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. The whole memory can, therefore, be read with a single Read Data Bytes at Higher Speed (FAST\_READ) instruction. When the highest address is reached, the address counter rolls over to 000000h, allowing the read sequence to be continued indefinitely.

The Read Data Bytes at Higher Speed (FAST\_READ) instruction is terminated by driving Chip Select ( $\overline{S}$ ) High. Chip Select ( $\overline{S}$ ) can be driven High at any time during data output. Any Read Data Bytes at Higher Speed (FAST\_READ) instruction, while an Erase or Program cycle is in progress, is rejected without having any effects on the cycle that is in progress.

Figure 12. Read Data Bytes at Higher Speed instruction and data-out sequence



\*Address bits A23 and A22 are "Don't Care."

### 9.1.4 Read Serial Flash Discovery Parameter

The Read Serial Flash Discovery Parameter (RDSFDP) instruction allows reading the Serial Flash Discovery Parameter area (SFDP). This SFDP area is composed of 2048 read-only bytes containing operating characteristics and vendor specific information. The SFDP area is factory programmed.

**Note:** Data to be written to the SFDP area is in definition phase.

If the SFDP area is blank, the device is shipped with all the SFDP bytes at FFh. If only a portion of the SFDP area is written to, the portion not used is shipped with bytes in erased state (FFh).

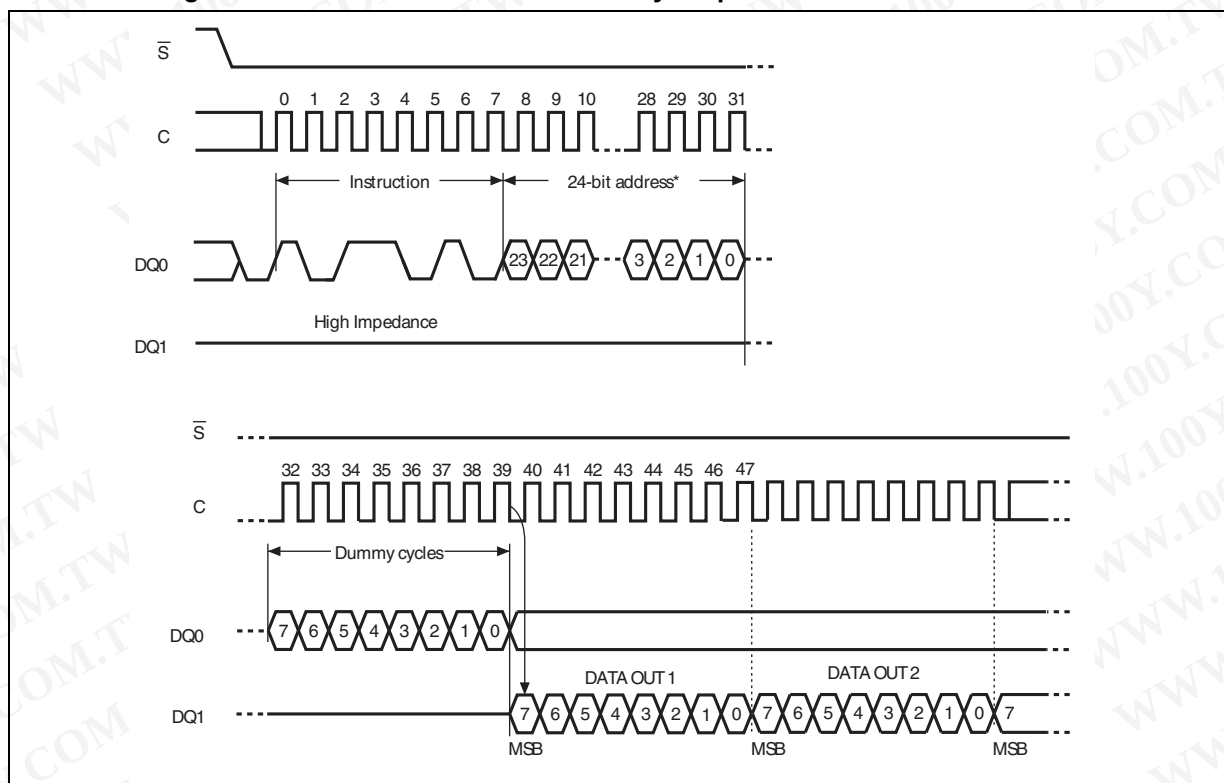
The instruction sequence for RDSFDP has the same structure as that of a Fast Read instruction. First, the device is selected by driving Chip Select (S) Low. Next, the 8-bit instruction code (5Ah) and the 24-bit address are shifted in, followed by a configurable number of dummy clock cycles.

Therefore, the entire SFDP area can be read with a single RDSFDP instruction. When the highest address (7FFh) is reached, the address counter rolls over to 000h, allowing the read sequence to be continued indefinitely.

The bytes of SFDP content are shifted out on the Serial Data Output (DQ1) starting from the specified address. Each bit is shifted out during the falling edge of Serial Clock (C). The Read SFDP instruction is terminated by driving Chip Select ( $\overline{S}$ ) High at any time during data output.

Any Read Serial Flash Discovery Parameter (RDSFDP) instruction issued while an Erase or Program cycle is in progress, is rejected without having any effect on the cycle that is in progress.

**Figure 13. Read Serial Flash Discovery Sequence**



\*Address bits A[23:11] are "Don't Care."

### 9.1.5 Dual Output Fast Read (DOFR)

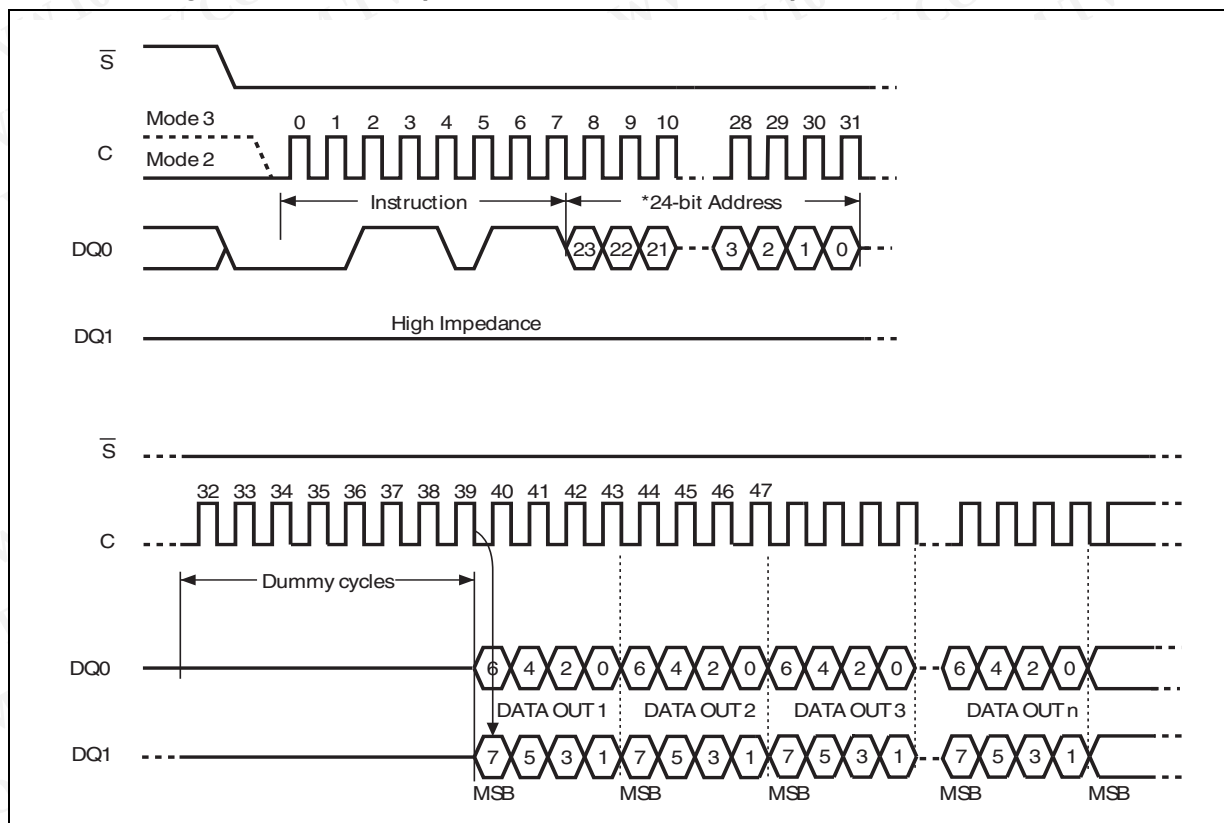
The Dual Output Fast Read (DOFR) instruction is very similar to the Read Data Bytes at Higher Speed (FAST\_READ) instruction, except that the data are shifted out on two pins (pin DQ0 and pin DQ1) instead of only one. Outputting the data on two pins instead of one doubles the data transfer bandwidth compared to the Read Data Bytes at Higher Speed (FAST\_READ) instruction.

The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. The instruction code for the Dual Output Fast Read instruction is followed by a 3-byte address (A23-A0) and a configurable number of dummy clock cycles, each bit being latched-in during the rising edge of Serial Clock (C). Then the memory contents, at that address, are shifted out on DQ0 and DQ1 at a maximum frequency  $F_c$ , during the falling edge of Serial Clock (C).

The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out on DQ0 and DQ1. The whole memory can, therefore, be read with a single Dual Output Fast Read (DOFR) instruction.

When the highest address is reached, the address counter rolls over to 00 0000h, so that the read sequence can be continued indefinitely.

**Figure 14. Dual Output Fast Read instruction sequence**

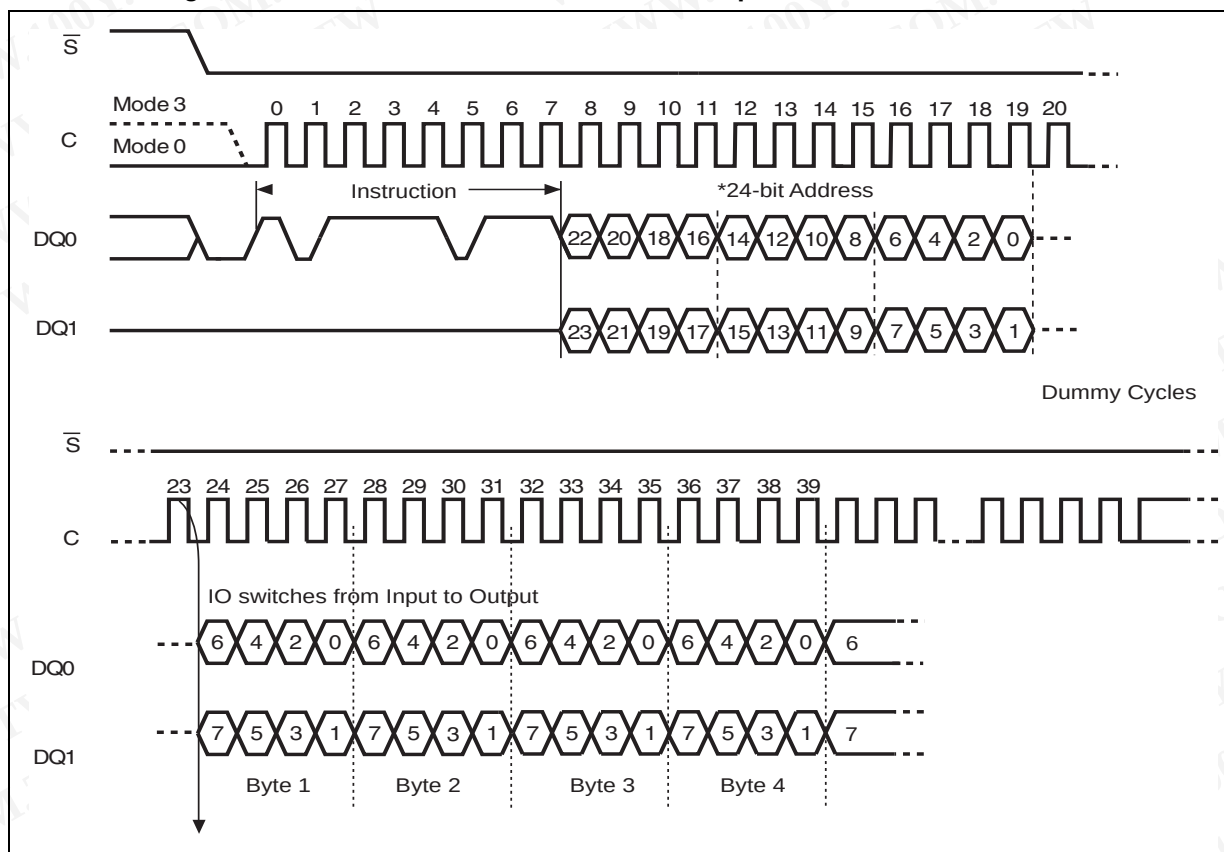


\*Address bits A23 and A22 are "Don't Care."

### 9.1.6 Dual I/O Fast Read

The Dual I/O Fast Read (DIOFR) instruction is very similar to the Dual Output Fast Read (DOFR), except that the address bits are shifted in on two pins (pin  $DQ0$  and pin  $DQ1$ ) instead of only one.

Figure 15. Dual I/O Fast Read instruction sequence



\*Address bits A23 and A22 are "Don't Care."

### 9.1.7 Quad Output Fast Read

The Quad Output Fast Read (QOFR) instruction is very similar to the Dual Output Fast Read (DOFR) instruction, except that the data are shifted out on four pins (pin DQ0, pin DQ1, pin W/VPP/DQ2 and pin HOLD/DQ3 (1) instead of only two. Outputting the data on four pins instead of one doubles the data transfer bandwidth compared to the Dual Output Fast Read (DOFR) instruction.

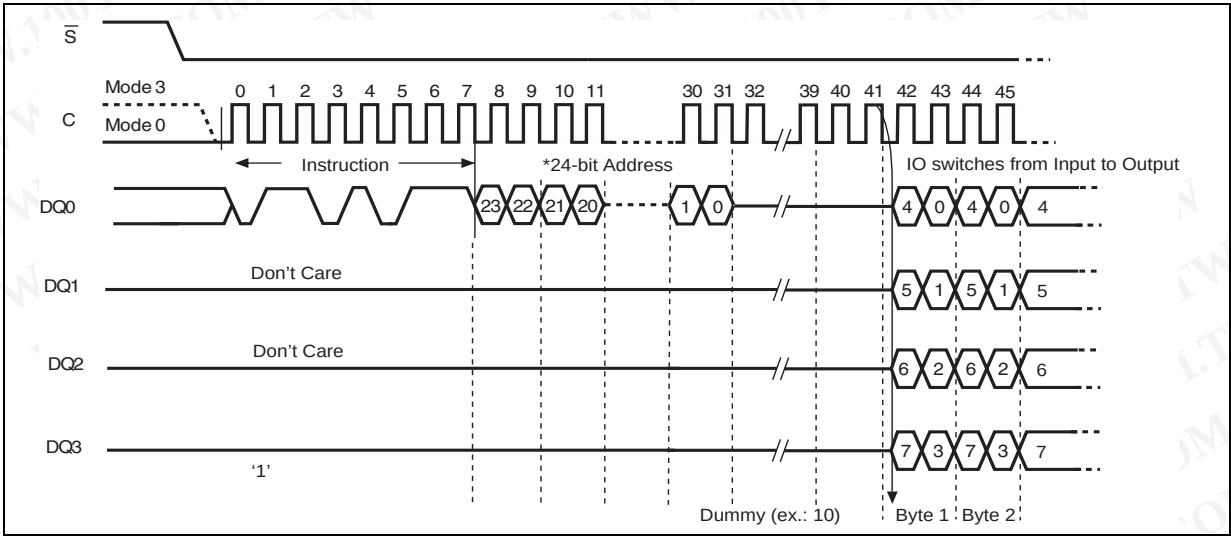
The device is first selected by driving Chip Select ( $\bar{S}$ ) Low. The instruction code for the Quad Output Fast Read instruction is followed by a 3-byte address (A23-A0) and a configurable number of dummy clock cycles, each bit being latched-in during the rising edge of Serial Clock (C). Then the memory contents, at that address, are shifted out on pin DQ0, pin DQ1, pin W/VPP/DQ2 and pin HOLD/DQ3 (1) at a maximum frequency  $f_C$ , during the falling edge of Serial Clock (C).

The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out on pin DQ0, pin DQ1, pin W/VPP/DQ2 and pin HOLD/DQ3 (1). The whole memory can, therefore, be read with a single Quad Output Fast Read (QOFR) instruction.

When the highest address is reached, the address counter rolls over to 00 0000h, so that the read sequence can be continued indefinitely.

**Note:** Reset functionality is available instead of Hold in devices with a dedicated part number. See [Section 16: Ordering information](#).

Figure 16. Quad Output Fast Read instruction sequence



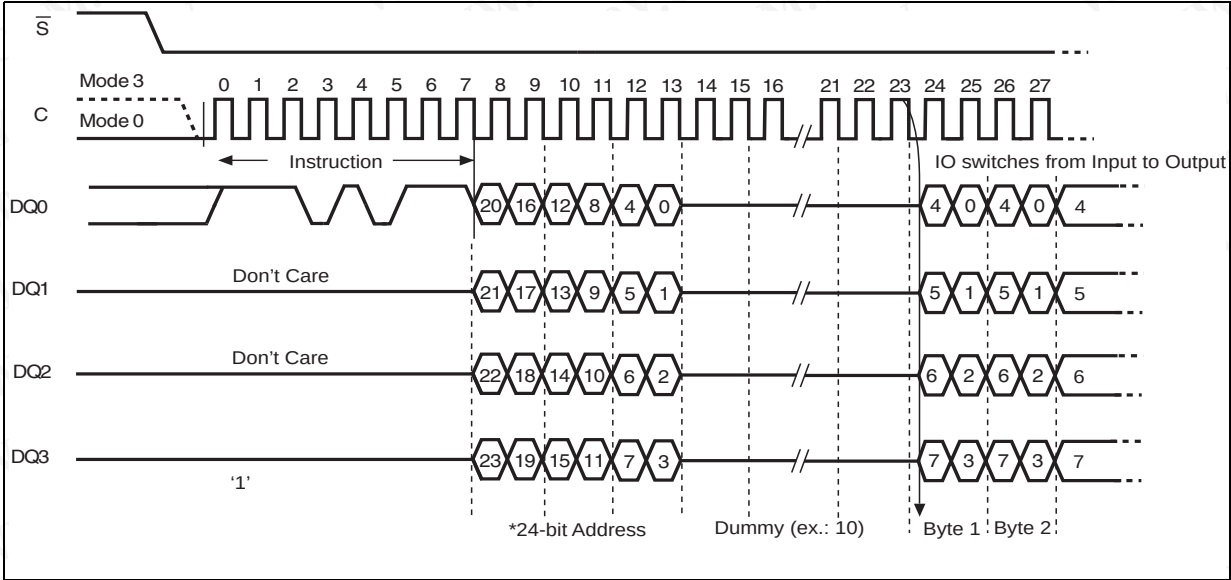
\*Address bits A23 and A22 are "Don't Care."

### 9.1.8 Quad I/O Fast Read

The Quad I/O Fast Read (QIOFR) instruction is very similar to the Quad Output Fast Read (QOFR), except that the address bits are shifted in on four pins (pin  $DQ0$ , pin  $DQ1$ , pin  $W/VPP/DQ2$  and pin  $HOLD/DQ3$  (1)) instead of only one.

**Note:** Reset functionality is available instead of Hold in devices with a dedicated part number. See [Section 16: Ordering information](#).

Figure 17. Quad Input/ Output Fast Read instruction sequence



\*Address bits A23 and A22 are "Don't Care."

### 9.1.9 Read OTP (ROTP)

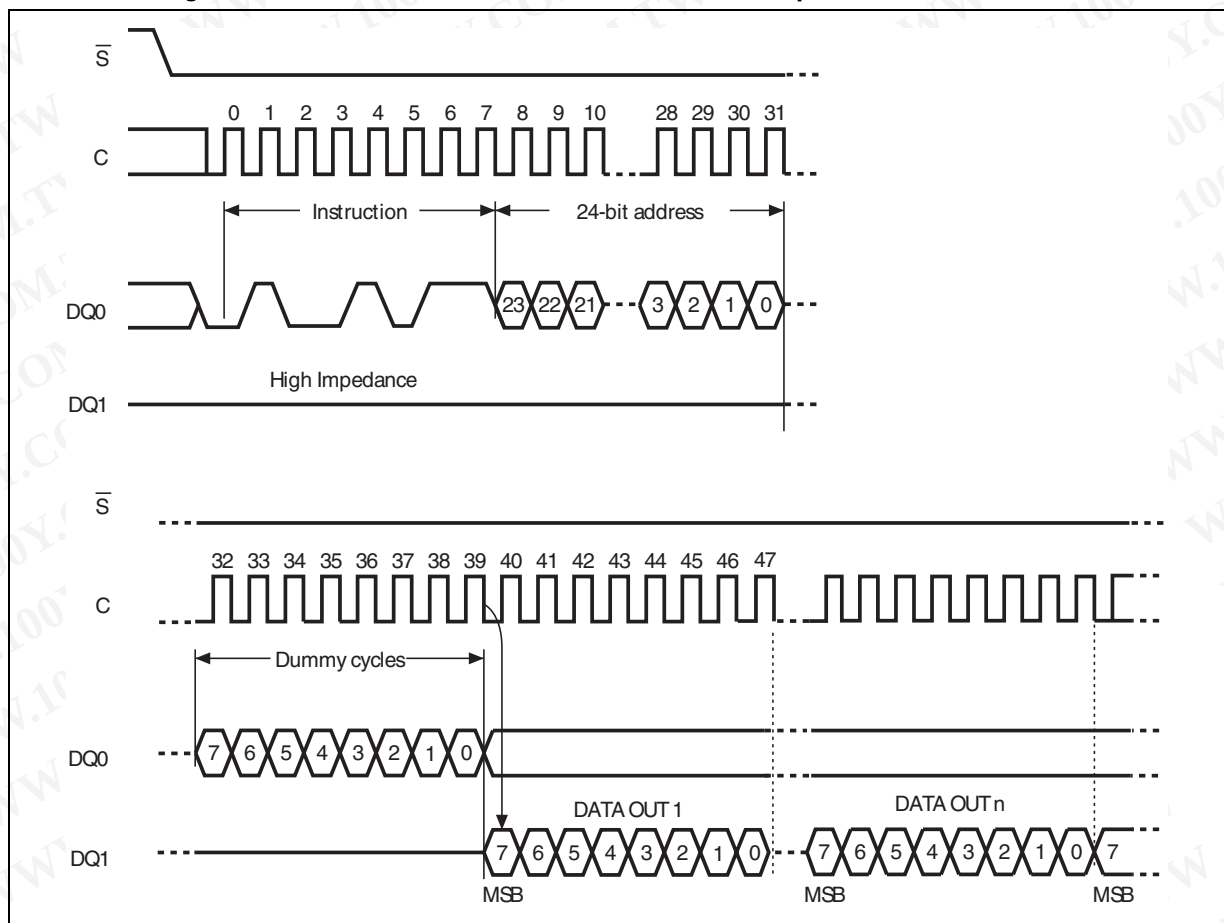
The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. The instruction code for the Read OTP (ROTP) instruction is followed by a 3-byte address (A23- A0) and a configurable number of dummy clock cycles. Each bit is latched in on the rising edge of Serial Clock (C). Then the memory contents at that address are shifted out on Serial Data output (DQ1).

Each bit is shifted out at the maximum frequency,  $f_{Cmax}$ , on the falling edge of Serial Clock (C). The address is automatically incremented to the next higher address after each byte of data is shifted out.

There is no rollover mechanism with the Read OTP (ROTP) instruction. This means that the Read OTP (ROTP) instruction must be sent with a maximum of 65 bytes to read. All other bytes outside the OTP area are "Don't Care."

The Read OTP (ROTP) instruction is terminated by driving Chip Select ( $\overline{S}$ ) High. Chip Select ( $\overline{S}$ ) can be driven High at any time during data output. Any Read OTP (ROTP) instruction issued while an Erase or Program cycle is in progress, is rejected without having any effect on the cycle that is in progress.

**Figure 18. Read OTP instruction and data-out sequence**



### 9.1.10 Write Enable (WREN)

The Write Enable (WREN) instruction sets the Write Enable Latch (WEL) bit.

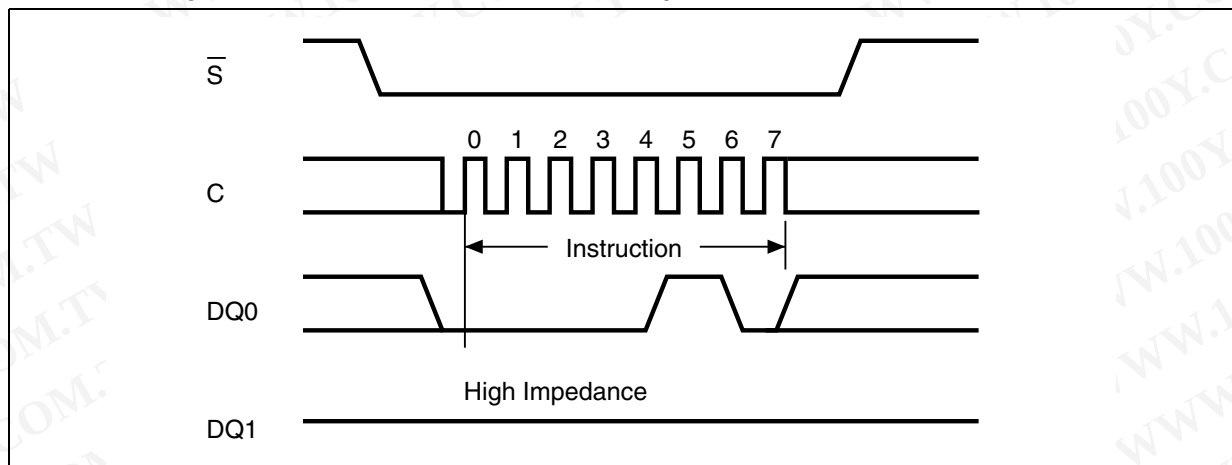
The Write Enable Latch (WEL) bit must be set prior to every Program or Erase instruction:

Page Program (PP), Dual Input Fast Program (DIFP), Dual Input Extended Fast Program (DIEFP), Quad Input Fast Program (QIFP), Quad Input Extended Fast Program (QIEFP), Program OTP (POTP), Write to Lock Register (WRLR), Subsector Erase (SSE), Sector Erase (SE), Bulk Erase (BE), Write Status Register (WRSR), Write Volatile Configuration Register (WRVCR), Write Volatile Enhanced Configuration Register (WRVECR) and Write NV Configuration Register (WRNVCR) instruction.

The Write Enable (WREN) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, sending the instruction code, and then driving Chip Select ( $\overline{S}$ ) High.

At the end of the POR sequence the WEL bit is low, so the next modify instruction can be accepted.

**Figure 19. Write Enable instruction sequence**



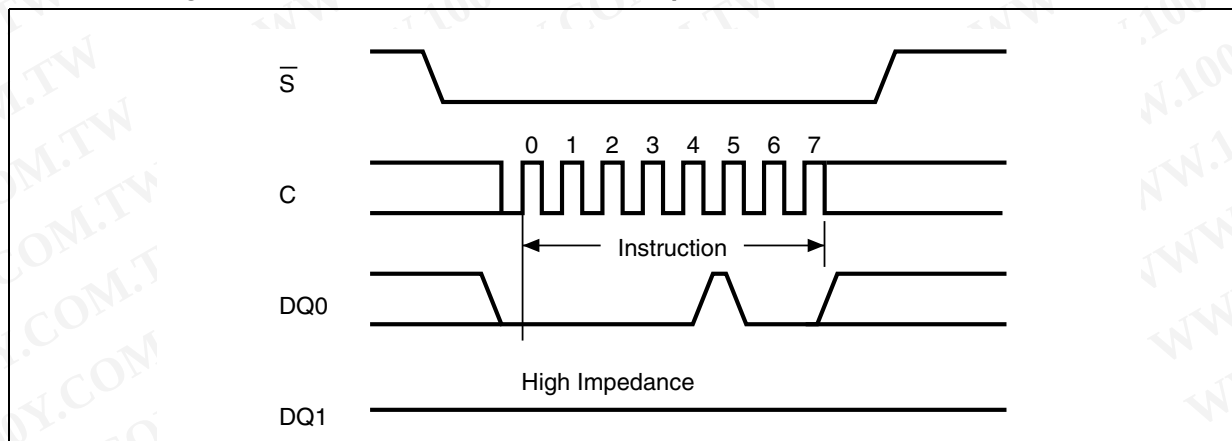
### 9.1.11 Write Disable (WRDI)

The Write Disable (WRDI) instruction resets the Write Enable Latch (WEL) bit. The Write Disable (WRDI) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, sending the instruction code, and then driving Chip Select ( $\overline{S}$ ) High.

The Write Enable Latch (WEL) bit is reset under the following conditions:

- Power-up
- Write Disable (WRDI) instruction completion
- Write Status Register (WRSR) instruction completion
- Write to Lock Register (WRLR) instruction completion
- Write Non Volatile Configuration Register (WRNVCR) instruction completion
- Write Volatile Configuration Register (WRVCR) instruction completion
- Write Volatile Enhanced Configuration Register (WRVECR) instruction completion
- Page Program (PP) instruction completion
- Dual Input Fast Program (DIFP) instruction completion
- Dual Input Extended Fast Program (DIEFP) instruction completion
- Quad Input Fast Program (QIFP) instruction completion
- Quad Input Extended Fast Program (QIEFP) instruction completion
- Program OTP (POTP) instruction completion
- Subsector Erase (SSE) instruction completion
- Sector Erase (SE) instruction completion
- Bulk Erase (BE) instruction completion

**Figure 20. Write Disable instruction sequence**



### 9.1.12 Page Program (PP)

The Page Program (PP) instruction allows bytes to be programmed in the memory (changing bits from 1 to 0). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded, the device sets the Write Enable Latch (WEL).

The Page Program (PP) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code, three address bytes, and at least one data byte on Serial Data input ( $DQ0$ ). If the 8 least significant address bits ( $A7-A0$ ) are not all zero, all transmitted data that go beyond the end of the current page are programmed from the start address of the same page (from the address whose 8 least significant bits ( $A7-A0$ ) are all zero). Chip Select ( $\overline{S}$ ) must be driven Low for the entire duration of the sequence.

If more than 256 bytes are sent to the device, previously latched data are discarded and the last 256 data bytes are guaranteed to be programmed correctly within the same page. If less

than 256 data bytes are sent to device, they are correctly programmed at the requested addresses without having any effects on the other bytes of the same page.

For optimized timings, it is recommended to use the Page Program (PP) instruction to program all consecutive targeted bytes in a single sequence versus using several Page Program (PP) sequences with each containing only a few bytes. See [Table 31.: AC Characteristics](#).

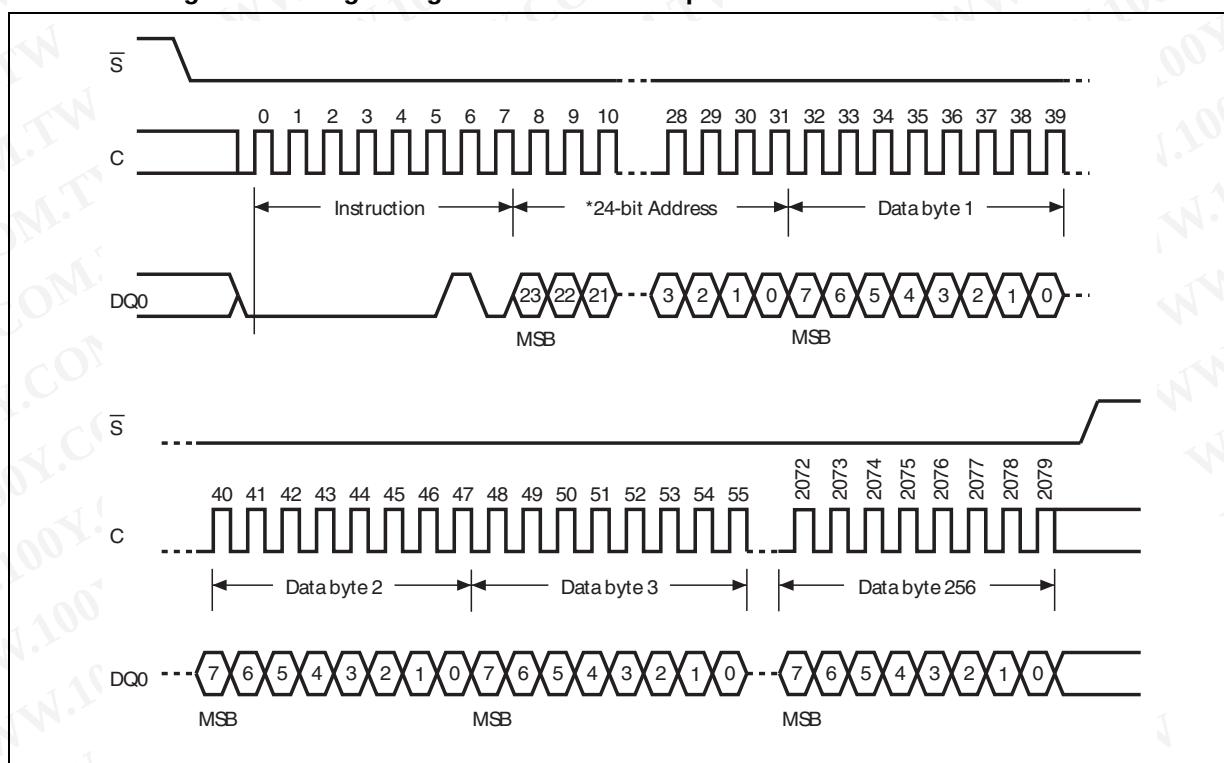
Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the last data byte has been latched in, otherwise the Page Program (PP) instruction is not executed.

As soon as Chip Select ( $\overline{S}$ ) is driven High, the self-timed Page Program cycle (whose duration is  $t_{PP}$ ) is initiated. While the Page Program cycle is in progress, the Status Register and the Flag Status Register may be read to check if the internal modify cycle is finished. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset.

A Page Program (PP) instruction applied to a page which is protected by the Block Protect (BP2, BP1, BP0 and TB) bits is not executed.

Page Program cycle can be paused by mean of Program/Erase Suspend (PES) instruction and resumed by mean of Program/Erase Resume (PER) instruction.

**Figure 21. Page Program Instruction Sequence**



\*Address bits A23 and A22 are "Don't Care."

### 9.1.13 Dual Input Fast Program (DIFP)

The Dual Input Fast Program (DIFP) instruction is very similar to the Page Program (PP) instruction, except that the data are entered on two pins (pin DQ0 and pin DQ1) instead of only one. Inputting the data on two pins instead of one doubles the data transfer bandwidth compared to the Page Program (PP) instruction.

The Dual Input Fast Program (DIFP) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code, three address bytes and at least one data byte on Serial Data input (DQ0).

If the 8 least significant address bits (A7-A0) are not all zero, all transmitted data that go beyond the end of the current page are programmed from the start address of the same page (from the address whose 8 least significant bits (A7-A0) are all zero). Chip Select ( $\overline{S}$ ) must be driven Low for the entire duration of the sequence.

If more than 256 bytes are sent to the device, previously latched data are discarded and the last 256 data bytes are guaranteed to be programmed correctly within the same page. If less than 256 data bytes are sent to device, they are correctly programmed at the requested addresses without having any effects on the other bytes in the same page.

For optimized timings, it is recommended to use the Dual Input Fast Program (DIFP) instruction to program all consecutive targeted bytes in a single sequence rather than using several Dual Input Fast Program (DIFP) sequences each containing only a few bytes. See [Table 31.: AC Characteristics](#).

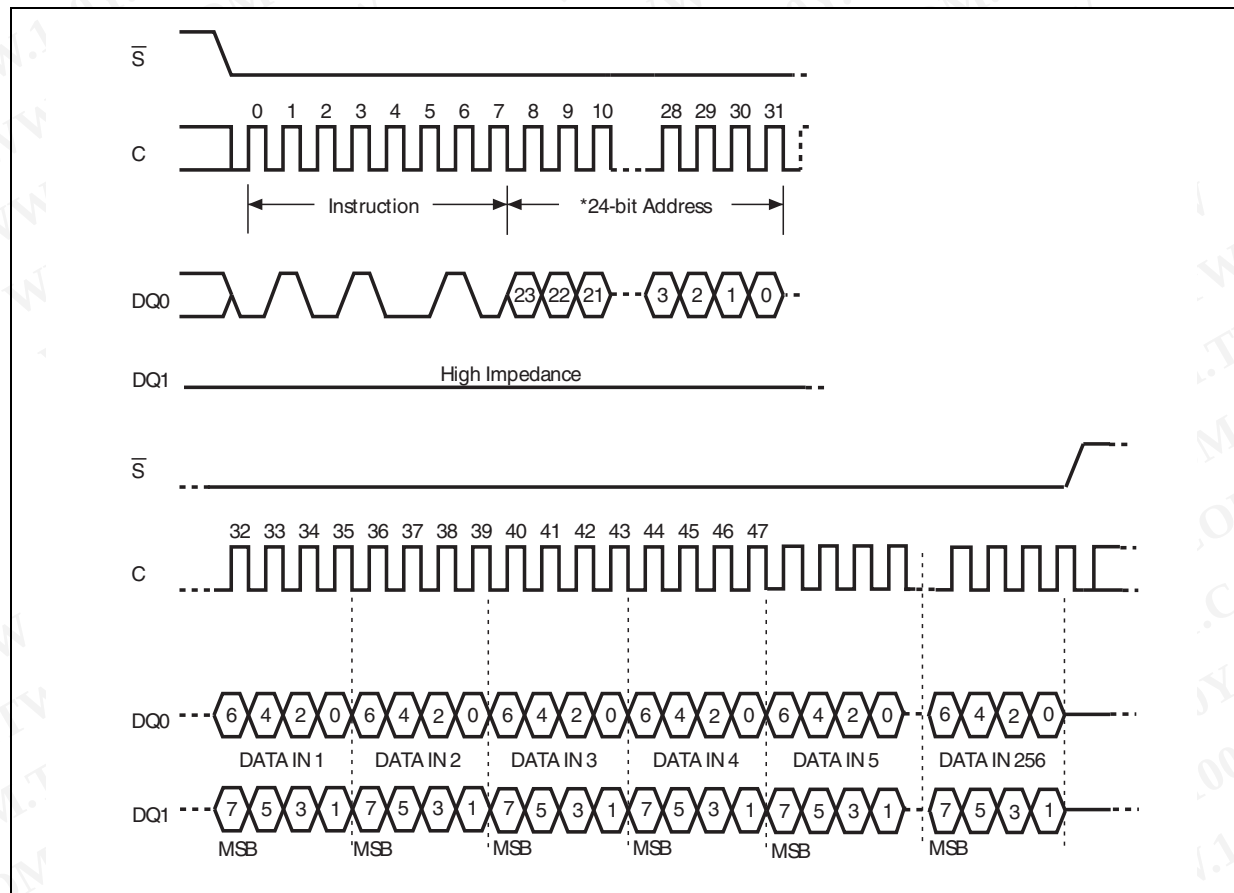
Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the last data byte has been latched in, otherwise the Dual Input Fast Program (DIFP) instruction is not executed.

As soon as Chip Select ( $\overline{S}$ ) is driven High, the self-timed Page Program cycle (whose duration is  $t_{PP}$ ) is initiated. While the Dual Input Fast Program (DIFP) cycle is in progress, the Status Register and the Flag Status Register may be read to check if the internal modify cycle is finished. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset.

A Dual Input Fast Program (DIFP) instruction applied to a page that belongs to a hardware or software protected sector is not executed.

Dual Input Fast Program cycle can be paused by mean of Program/Erase Suspend (PES) instruction and resumed by mean of Program/Erase Resume (PER) instruction.

Figure 22. Dual Input Fast Program Instruction Sequence

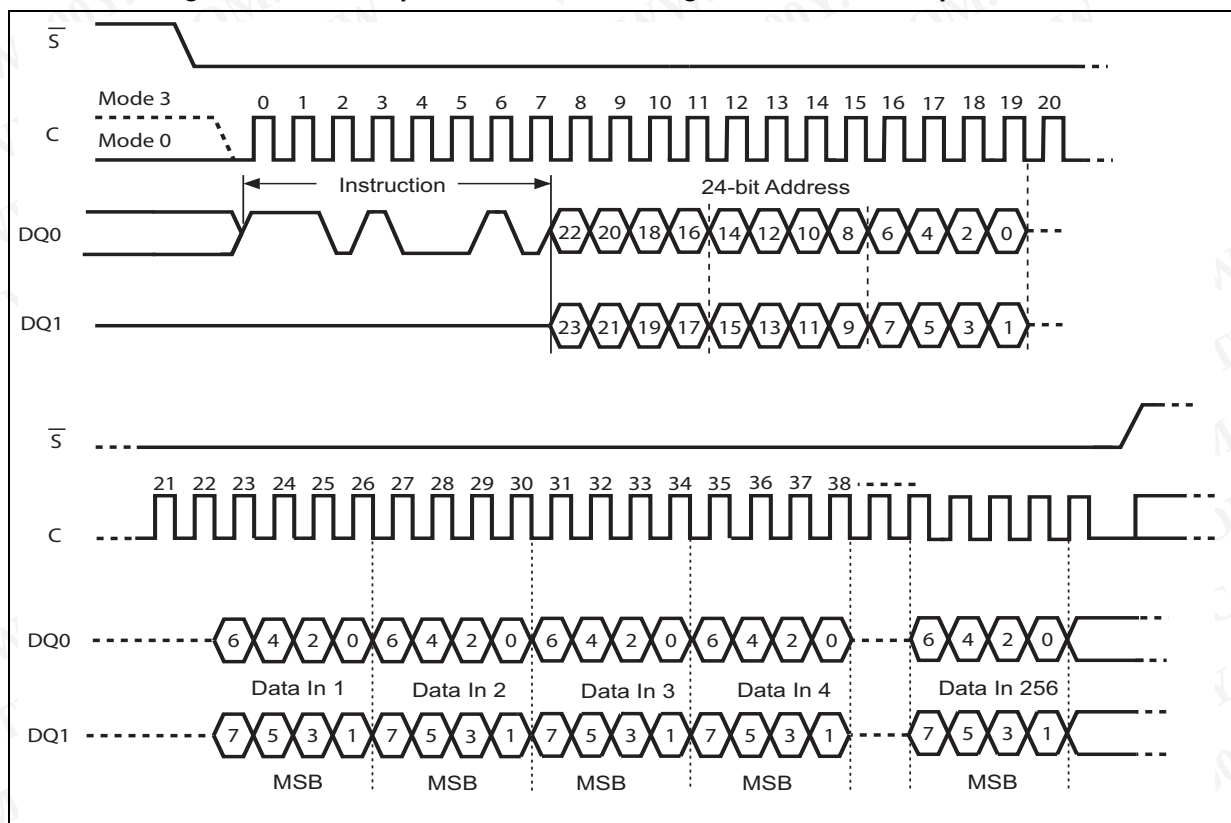


\*Address bits A23 and A22 are "Don't Care."

#### 9.1.14 Dual Input Extended Fast Program

The Dual Input Extended Fast Program (DIEFP) instruction is very similar to the Dual Input Fast Program (DIFP), except that the address bits are shifted in on two pins (pin DQ0 and pin DQ1) instead of only one.

Figure 23. Dual Input Extended Fast Program instruction sequence



\*Address bits A23 and A22 are "Don't Care."

### 9.1.15 Quad Input Fast Program

The Quad Input Fast Program (QIFP) instruction is very similar to the Dual Input Fast Program (DIFP) instruction, except that the data are entered on four pins (pin DQ0, pin DQ1, pin W/VPP/DQ2 and pin HOLD/ (DQ3) instead of only two. Inputting the data on four pins instead of two doubles the data transfer bandwidth compared to the Dual Input Fast Program (DIFP) instruction.

The Quad Input Fast Program (QIFP) instruction is entered by driving Chip Select ( $\bar{S}$ ) Low, followed by the instruction code, three address bytes on Serial Data input (DQ0), and at least one data byte on Serial Data I/Os (DQ0, DQ1, DQ2, DQ3).

If the 8 least significant address bits (A7-A0) are not all zero, all transmitted data that go beyond the end of the current page are programmed from the start address of the same page (from the address whose 8 least significant bits (A7-A0) are all zero). Chip Select ( $\bar{S}$ ) must be driven Low for the entire duration of the sequence.

If more than 256 bytes are sent to the device, previously latched data are discarded and the last 256 data bytes are guaranteed to be programmed correctly within the same page. If less than 256 data bytes are sent to device, they are correctly programmed at the requested addresses without having any effects on the other bytes in the same page.

For optimized timings, it is recommended to use the Quad Input Fast Program (QIFP) instruction to program all consecutive targeted bytes in a single sequence rather than using

several Quad Input Fast Program (QIFP) sequences each containing only a few bytes See [Table 31.: AC Characteristics](#).

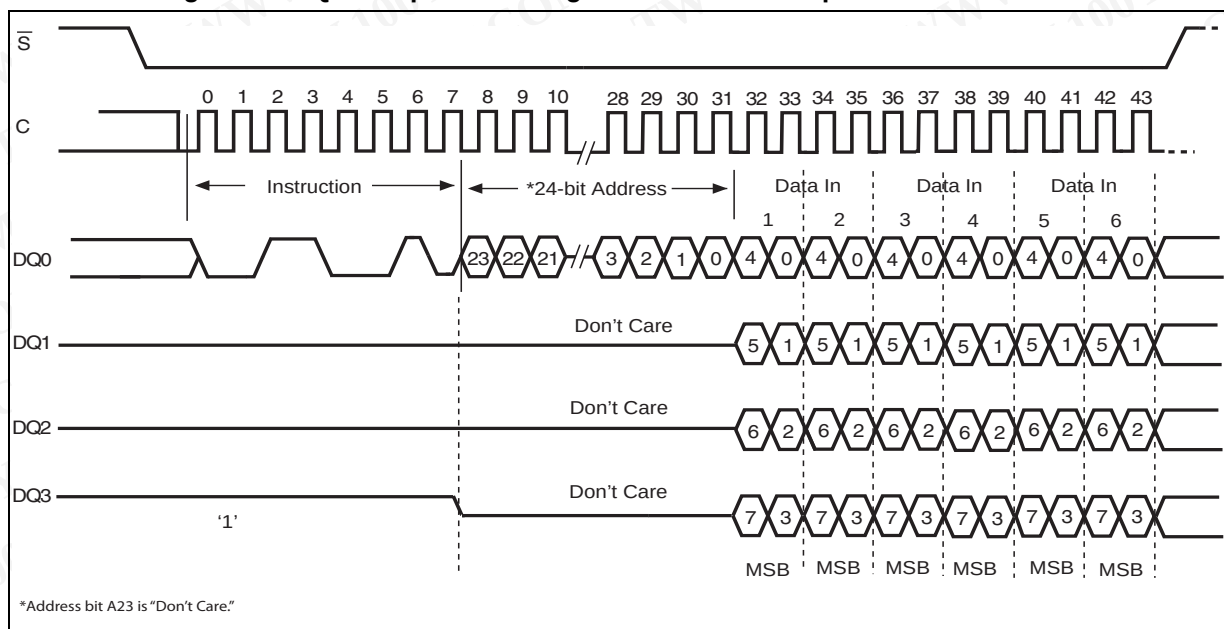
Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the last data byte has been latched in; otherwise, the Quad Input Fast Program (QIFP) instruction is not executed.

As soon as Chip Select ( $\overline{S}$ ) is driven High, the self-timed Page Program cycle (whose duration is tPP) is initiated. While the Quad Input Fast Program (QIFP) cycle is in progress, the Status Register may be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Page Program cycle, and 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. Alternately, it is possible to read the Flag Status Register to check if the internal modify cycle is finished.

A Quad Input Fast Program (QIFP) instruction applied to a page that belongs to a hardware or software protected sector is not executed.

A Quad Input Fast Program cycle can be paused by mean of Program/Erase Suspend (PES) instruction and resumed by mean of Program/Erase Resume (PER) instruction.

**Figure 24. Quad Input Fast Program instruction sequence**

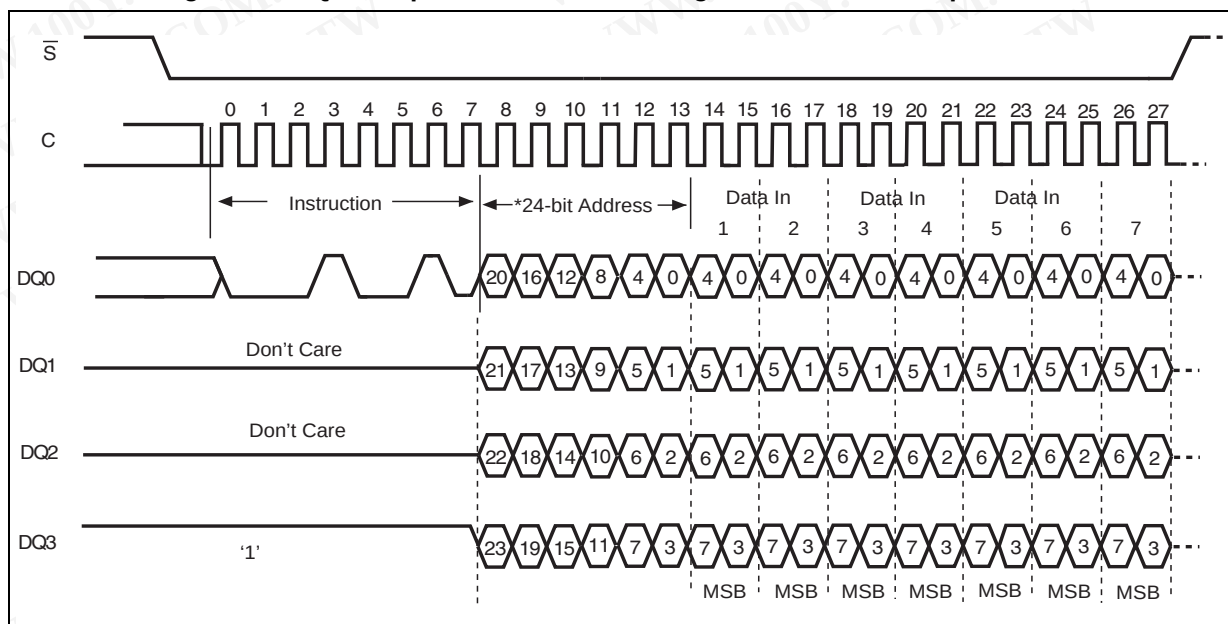


\*Address bits A23 and A22 are "Don't Care."

### 9.1.16 Quad Input Extended Fast Program

The Quad Input Extended Fast Program (QIEFP) instruction is very similar to the Quad Input Fast Program (QIFP), except that the address bits are shifted in on four pins (pin DQ0, pin DQ1, pin W/VPP/DQ2 and pin HOLD/DQ3) instead of only one.

Figure 25. Quad Input Extended Fast Program instruction sequence



\*Address bits A23 and A22 are "Don't Care."

### 9.1.17 Program OTP instruction (POTP)

The Program OTP instruction (POTP) is used to program at most 64 bytes to the OTP memory area (by changing bits from 1 to 0, only). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded, the device sets the Write Enable Latch (WEL) bit.

The Program OTP instruction is entered by driving Chip Select ( $\bar{S}$ ) Low, followed by the instruction opcode, three address bytes and at least one data byte on Serial Data input (DQ0). Chip Select ( $\bar{S}$ ) must be driven High after the eighth bit of the last data byte has been latched in, otherwise the Program OTP instruction is not executed.

There is no rollover mechanism with the Program OTP (POTP) instruction. This means that the Program OTP (POTP) instruction must be sent with a maximum of 65 bytes to program, once all 65 bytes have been latched in, any following byte will be discarded.

As soon as Chip Select ( $\bar{S}$ ) is driven High, the self-timed Page Program cycle (whose duration is  $t_{PP}$ ) is initiated. While the Program OTP cycle is in progress, the Status Register may be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Program OTP cycle, and it is 0 when it is completed. At some unspecified time before the cycle is complete, the Write Enable Latch (WEL) bit is reset. Alternately, it is possible to read the Flag Status Register to check if the internal modify cycle is finished.

Bit 0 of the OTP control byte, that is byte 64, is used to permanently lock the OTP memory array.

- When bit 0 of byte 64 = '1', the 64 bytes of the OTP memory array can be programmed.
- When bit 0 of byte 64 = '0', the 64 bytes of the OTP memory array are read-only and cannot be programmed anymore.

Once a bit of the OTP memory has been programmed to '0', it can no longer be set to '1'.

Therefore, as soon as bit 0 of byte 64 (control byte) is set to '0', the 64 bytes of the OTP memory array become read-only in a permanent way.

Any Program OTP (POTP) instruction issued while an Erase or Program is in progress is rejected without having any effect on the cycle that is in progress. A Program OTP cycle cannot be paused by a Program/Erase Suspend (PES) instruction.

**Figure 26. Program OTP instruction sequence**

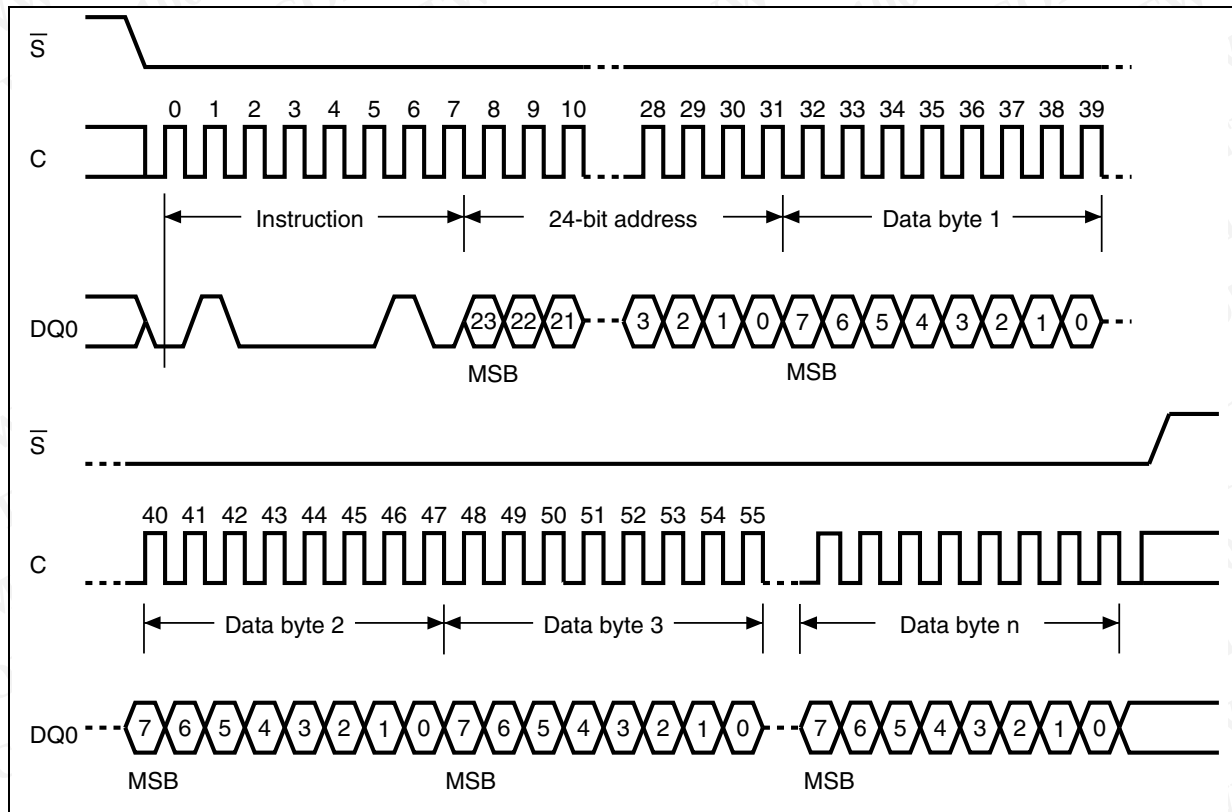
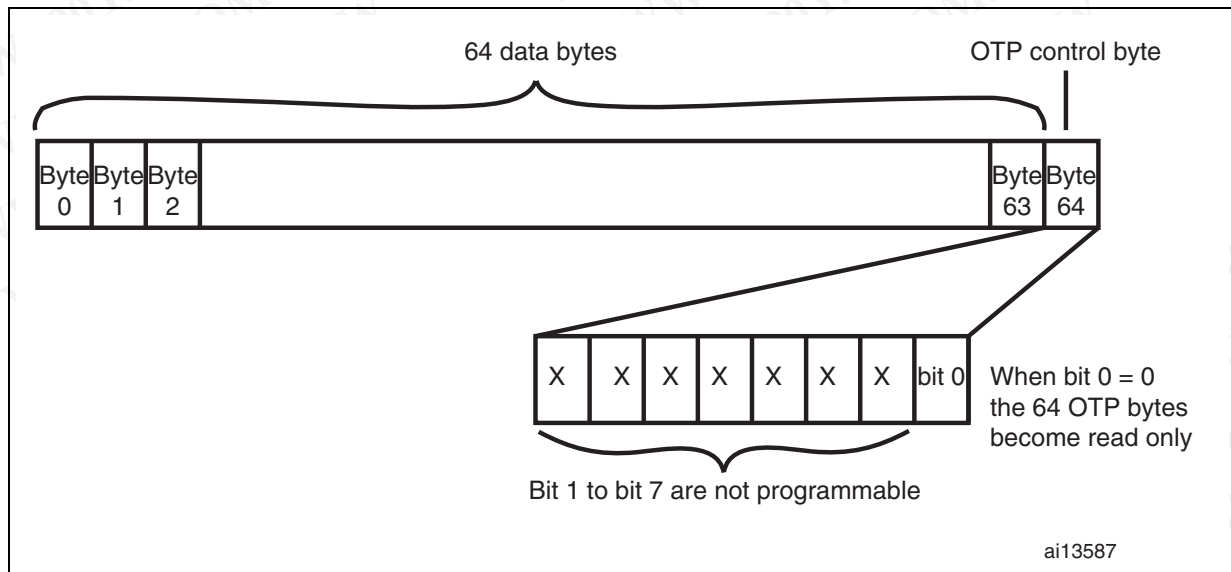


Figure 27. How to permanently lock the OTP bytes



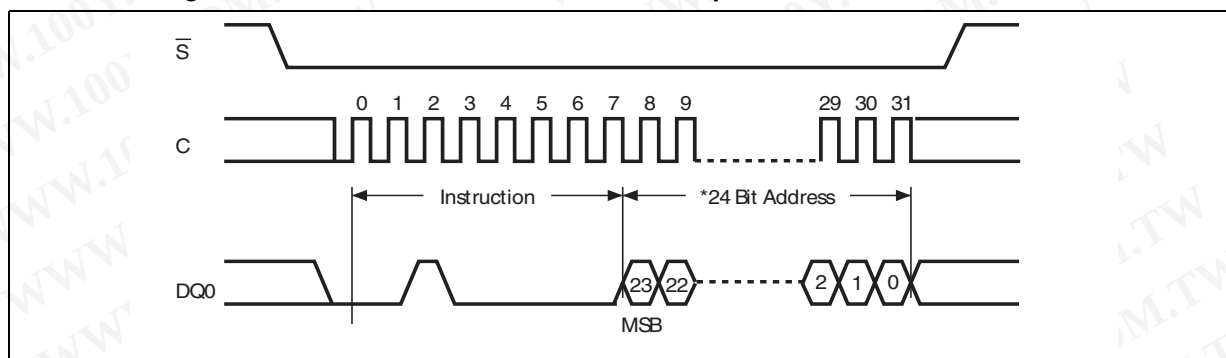
### 9.1.18 Subsector Erase (SSE)

The Subsector Erase (SSE) instruction sets to '1' (FFh) all bits inside the chosen subsector. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded, the device sets the Write Enable Latch (WEL).

The Subsector Erase (SSE) instruction is entered by driving Chip Select ( $\bar{S}$ ) Low, followed by the instruction code, and three address bytes on Serial Data input (DQ0). Any address inside the subsector is a valid address for the Subsector Erase (SSE) instruction. Chip Select ( $\bar{S}$ ) must be driven Low for the entire duration of the sequence.

Chip Select ( $\bar{S}$ ) must be driven High after the eighth bit of the last address byte has been latched in, otherwise the Subsector Erase (SSE) instruction is not executed. As soon as Chip Select ( $\bar{S}$ ) is driven High, the self-timed Subsector Erase cycle (whose duration is  $t_{SSE}$ ) is initiated. While the Subsector Erase cycle is in progress, the Status Register may be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Subsector Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is complete, the Write Enable Latch (WEL) bit is reset. Alternately, it is possible to read the Flag Status Register to check if the internal modify cycle is finished.

A Subsector Erase (SSE) instruction issued to a sector that is hardware or software protected, is not executed. Any Subsector Erase (SSE) instruction, while an Erase or Program cycle is in progress, is rejected without having any effects on the cycle that is in progress. A Subsector Erase cycle can be paused by a Program/Erase Suspend (PES) instruction and resumed by a Program/Erase Resume (PER) instruction.

**Figure 28. Subsector Erase instruction sequence**

\*Address bits A23 and A22 are "Don't Care."

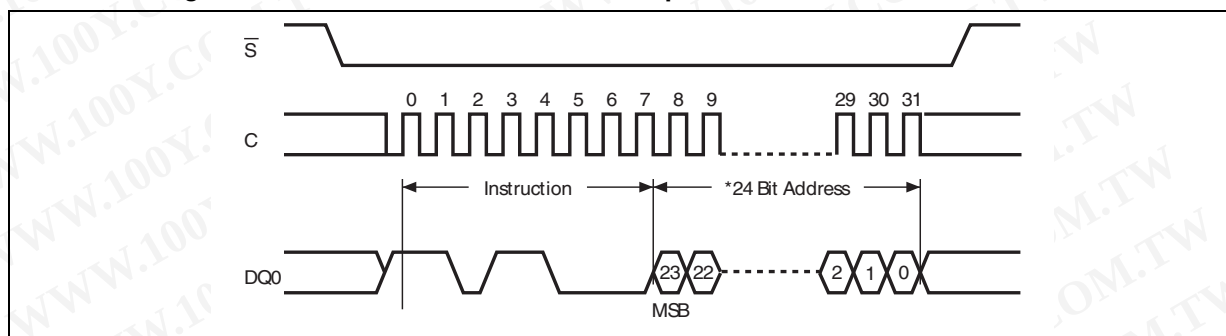
### 9.1.19 Sector Erase (SE)

The Sector Erase (SE) instruction sets to '1' (FFh) all bits inside the chosen sector. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded, the device sets the Write Enable Latch (WEL).

The Sector Erase (SE) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code, and three address bytes on Serial Data input (DQ0). Any address inside the sector is a valid address for the Sector Erase (SE) instruction. Chip Select ( $\overline{S}$ ) must be driven Low for the entire duration of the sequence.

Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the last address byte has been latched in; otherwise, the Sector Erase (SE) instruction is not executed. As soon as Chip Select ( $\overline{S}$ ) is driven High, the self-timed Sector Erase cycle (whose duration is  $t_{SE}$ ) is initiated. While the Sector Erase cycle is in progress, the Status Register may be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Sector Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. Alternately, it is possible to read the Flag Status Register to check if the internal modify cycle is finished.

A Sector Erase (SE) instruction applied to a page that is hardware or software protected is not executed. A Sector Erase cycle can be paused by mean of Program/Erase Suspend (PES) instruction and resumed by mean of Program/Erase Resume (PER) instruction.

**Figure 29. Sector Erase instruction sequence**

### 9.1.20 Bulk Erase (BE)

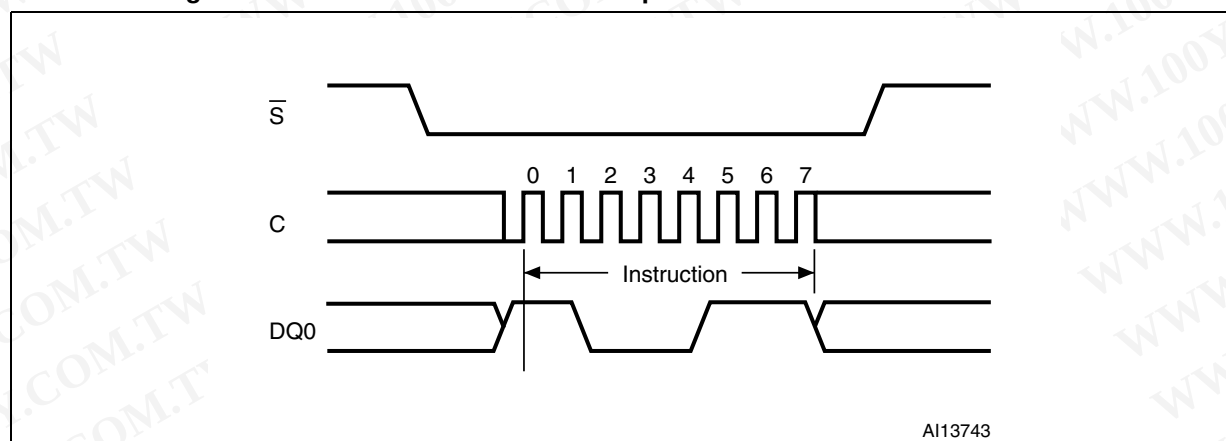
The Bulk Erase (BE) instruction sets all bits to '1' (FFh). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded, the device sets the Write Enable Latch (WEL).

The Bulk Erase (BE) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code on Serial Data input (DQ0). Chip Select ( $\overline{S}$ ) must be driven Low for the entire duration of the sequence.

Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the instruction code has been latched in, otherwise the Bulk Erase instruction is not executed. As soon as Chip Select ( $\overline{S}$ ) is driven High, the self-timed Bulk Erase cycle (whose duration is  $t_{BE}$ ) is initiated. While the Bulk Erase cycle is in progress, the Status Register may be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Bulk Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset.

The Bulk Erase (BE) instruction is ignored if one or more sectors are hardware or software protected. The Bulk Erase (BE) cycle cannot be paused by a Program Erase Suspend (PES) instruction.

**Figure 30. Bulk Erase instruction sequence**



### 9.1.21 Program/Erase Suspend

The Program/Erase Suspend instruction allows the controller to interrupt a Program or an Erase instruction, in particular: Sector Erase, Subsector Erase, Page Program, Dual Input Page Program, Dual Input Extended Page Program, Quad Input Page Program and Quad Input Extended Page Program instructions can be suspended and resumed.

**Note:** *Bulk Erase, Write Status Register, Write Non Volatile Configuration Register, and Program OTP cannot be suspended.*

After a Program/Erase Suspend instruction the bit 2 of the Flag Status register is immediately set to 1 and, after a latency time, both the WIP bit of the Status Register and the Program/Erase controller bit (Not WIP) of the Flag Status Register are cleared (to 0 and to 1 respectively).

The Suspended state is reset if a power-off is performed or after resume. After a sector erase instruction has been suspended, another erase instruction is not allowed; however, it is possible to perform program and reading instructions on all the sectors except the one

whose erase cycle is suspended. Any read instruction issued on this sector outputs Don't Care data.

After a subsector erase instruction has been suspended, neither an erase instruction or a program instruction is allowed; only a read instruction is allowed on all sectors except the one containing the subsector whose erase cycle is suspended. Any read instruction issued on this sector outputs Don't Care data.

After a program instruction has been suspended, neither a program instruction or an erase instructions is allowed; however, it is possible to perform a read instruction on all pages except the one whose program cycle is suspended. Any read instruction issued on this page outputs Don't Care data.

It's possible to nest a suspend instruction inside another suspended one just once, meaning that it's possible for example to send to the device an erase instruction, then suspend it, then send a program instruction and in the end suspend it as well. In this case, the next Program/Erase Resume Instruction resumes the more recent suspended modify cycle, and another Program/Erase Resume Instruction is need to resume also the former modify cycle.

**Table 16. Suspend Parameters**

| Parameter          | Condition                                                    | Typ | Max | Unit | Note                                                         |
|--------------------|--------------------------------------------------------------|-----|-----|------|--------------------------------------------------------------|
| Erase to Suspend   | Sector Erase or Erase Resume to Erase Suspend                | 700 |     | μs   | Timing not internally controlled                             |
| Program to Suspend | Program Resume to Program Suspend                            | 5   |     | μs   | Timing not internally controlled                             |
| SSErase to Suspend | Sub Sector Erase or Sub Sector Erase Resume to Erase Suspend | 50  |     | μs   | Timing not internally controlled                             |
| Suspend Latency    | Program                                                      | 7   |     | μs   | Any Read instruction accepted                                |
|                    | Sub Sector Erase                                             | 15  |     | μs   | Any Read instruction accepted                                |
|                    | Erase                                                        | 15  |     | μs   | Any instruction accepted but SE, SSE, BE, WRSR, WRNVCR, POTP |

Note: As shown here, the device can be in only one state at a time, such as Standby or Program.

**Table 17. Operations Allowed / Disallowed During Device States**

| Operation                                       | Device States and Sector (Same/Other) in Which Operation is Allowed/Disallowed (Yes/No) |       |               |       |                      |       |                                 |       |                         |       |                       |       |
|-------------------------------------------------|-----------------------------------------------------------------------------------------|-------|---------------|-------|----------------------|-------|---------------------------------|-------|-------------------------|-------|-----------------------|-------|
|                                                 | Standby State                                                                           |       | Program State |       | Erase State (SE/SSE) |       | Subsector Erase Suspended State |       | Program Suspended State |       | Erase Suspended State |       |
|                                                 | Sector                                                                                  |       | Sector        |       | Sector               |       | Sector                          |       | Sector                  |       | Sector                |       |
|                                                 | Same                                                                                    | Other | Same          | Other | Same                 | Other | Same                            | Other | Same                    | Other | Same                  | Other |
| All Reads except RDSR / RFSR                    | Yes                                                                                     | Yes   | No            | No    | No                   | No    | Yes <sup>(1)</sup>              | Yes   | Yes                     | Yes   | Yes <sup>(1)</sup>    | Yes   |
| Array Program: PP / DIFP / QIFP / DIEFP / QIEFP | Yes                                                                                     | Yes   | No            | No    | No                   | No    | No                              | No    | No                      | No    | No                    | Yes   |
| Sector Erase                                    | Yes                                                                                     | Yes   | No            | No    | No                   | No    | No                              | No    | No                      | No    | No                    | No    |
| Sub-Sector Erase                                | Yes                                                                                     | Yes   | No            | No    | No                   | No    | No                              | No    | No                      | No    | No                    | No    |
| WRLR / POTP / BE / WRSR / WRNVCR                | Yes                                                                                     |       | No            |       | No                   |       | No                              |       | No                      |       | No                    |       |
| WRVCR / WRVECR                                  | Yes                                                                                     |       | No            |       | No                   |       | Yes                             |       | Yes                     |       | Yes                   |       |
| RDSR / RFSR                                     | Yes                                                                                     |       | Yes           |       | Yes                  |       | Yes                             |       | Yes                     |       | Yes                   |       |
| Program / Erase Suspend                         | No                                                                                      |       | Yes           |       | Yes                  |       | No                              |       | No                      |       | No                    |       |

1. The Read operation is accepted but the data output is not guaranteed until the program or erase has completed.

### 9.1.22 Program/Erase Resume

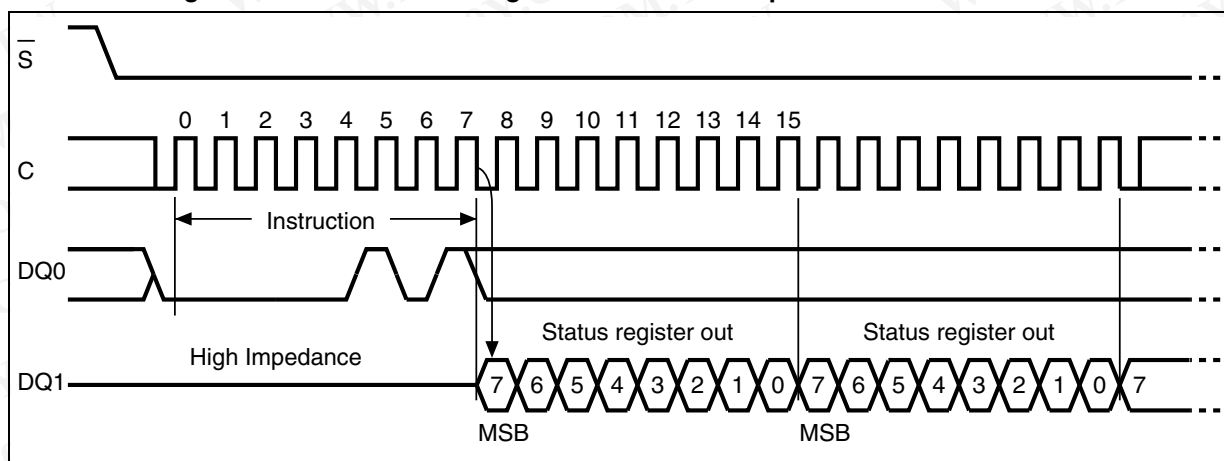
After a Program/Erase suspend instruction, a Program/Erase Resume instruction is required to continue performing the suspended Program or Erase sequence. Program/Erase Resume instruction is ignored if the device is not in a Program/Erase Suspended status. The WIP bit of the Status Register and Program/Erase controller bit (Not WIP) of the Flag Status Register both switch to the busy state (1 and 0 respectively) after Program/Erase Resume instruction until the Program or Erase sequence is completed.

In this case the next Program/Erase Resume Instruction resumes the more recent suspended modify cycle, and another Program/Erase Resume Instruction is needed to resume also the former modify cycle.

### 9.1.23 Read Status Register (RDSR)

The Read Status Register (RDSR) instruction allows the Status Register to be read. The Status Register may be read at any time, even while a Program, Erase or Write Status Register cycle is in progress. When one of these cycles is in progress, it is recommended to check the Write In Progress (WIP) bit (or the Program/Erase controller bit of the Flag Status Register) before sending a new instruction to the device. It is also possible to read the Status Register continuously, as shown here.

**Figure 31. Read Status Register instruction sequence**



### 9.1.24 Write status register (WRSR)

The write status register (WRSR) instruction allows new values to be written to the status register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed. After the write enable (WREN) instruction has been decoded and executed, the device sets the write enable latch (WEL).

The write status register (WRSR) instruction is entered by driving Chip Select ( $\bar{S}$ ) Low, followed by the instruction code and the data byte on serial data input (DQ0).

The write status register (WRSR) instruction has no effect on b1 and b0 of the status register.

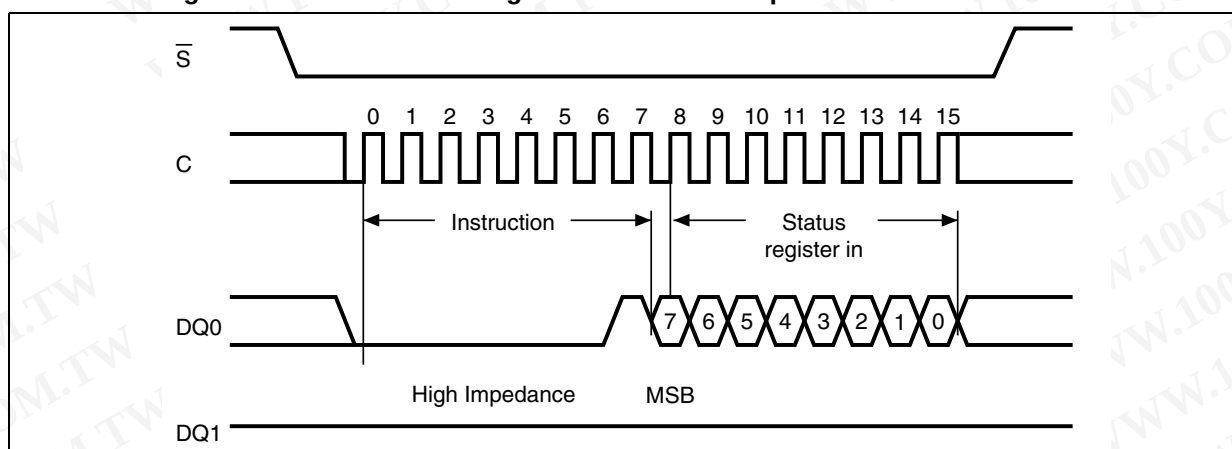
Chip Select ( $\bar{S}$ ) must be driven High after the eighth bit of the data byte has been latched in. If not, the write status register (WRSR) instruction is not executed. As soon as Chip Select ( $\bar{S}$ ) is driven High, the self-timed write status register cycle (whose duration is  $t_{W}$ ) is

initiated. While the write status register cycle is in progress, the status register may still be read to check the value of the write in progress (WIP) bit. The write in progress (WIP) bit is 1 during the self-timed write status register cycle, and is 0 when it is completed. When the cycle is completed, the write enable latch (WEL) is reset.

The write status register (WRSR) instruction allows the user to change the values of the block protect (BP2, BP1, BP0) bits, to define the size of the area that is to be treated as read-only, as defined in [Table 10.: Protected area sizes, Upper \(TB bit = 0\)](#) and [Table 11.: Protected area sizes, Lower \(TB bit = 1\)](#).

The write status register (WRSR) instruction also allows the user to set and reset the status register write disable (SRWD) bit in accordance with the Write Protect (W/VPP) signal. The status register write disable (SRWD) bit and Write Protect (W/VPP) signal allow the device to be put in the hardware protected mode (HPM). The write status register (WRSR) instruction is not executed once the hardware protected mode (HPM) is entered.

**Figure 32. Write Status Register instruction sequence**



When the Status Register Write Disable (SRWD) bit of the Status Register is 0 (its initial delivery state), it is possible to write to the Status Register provided that the Write Enable Latch (WEL) bit has previously been set by a Write Enable (WREN) instruction, regardless of the whether Write Protect (W/VPP) is driven High or Low.

When the Status Register Write Disable (SRWD) bit of the Status Register is set to '1', two cases need to be considered, depending on the state of Write Protect ( $\overline{W/VPP}$ ):

- If Write Protect ( $\overline{W/VPP}$ ) is driven High, it is possible to write to the Status Register provided that the Write Enable Latch (WEL) bit has previously been set by a Write Enable (WREN) instruction.
- If Write Protect ( $\overline{W/VPP}$ ) is driven Low, it is not possible to write to the Status Register even if the Write Enable Latch (WEL) bit has previously been set by a Write Enable (WREN) instruction (attempts to write to the Status Register are rejected, and are not accepted for execution). As a consequence, all the data bytes in the memory area that are software protected (SPM2) by the Block Protect (BP2, BP1, BP0) bits and the Top/Bottom (T/B) bit of the Status Register, are also hardware protected against data modification.

Regardless of the order of the two events, the Hardware Protected mode (HPM) can be entered in either of the following ways:

- setting the Status Register Write Disable (SRWD) bit after driving Write Protect ( $\overline{W/VPP}$ ) Low
- driving Write Protect ( $\overline{W/VPP}$ ) Low after setting the Status Register Write Disable (SRWD) bit.

The only way to exit the Hardware Protected mode (HPM) once entered is to pull Write Protect ( $\overline{W/VPP}$ ) High.

If Write Protect ( $\overline{W/VPP}$ ) is permanently tied High, the Hardware Protected mode (HPM) can never be activated, and only the Software Protected mode (SPM2), using the Block Protect (BP2, BP1, BP0) bits and the Top/Bottom (T/B) bits of the Status Register, can be used.

**Table 18. Protection modes**

| $\overline{W/VPP}$ Signal | SRWD bit | Mode                      | Write protection of the status register                                                                          | Memory content                                                               |                                                                         |
|---------------------------|----------|---------------------------|------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------|-------------------------------------------------------------------------|
|                           |          |                           |                                                                                                                  | Protected area <sup>(1)</sup>                                                | Unprotected area <sup>(1)</sup>                                         |
| 1                         | 0        | Software protected (SPM2) | Status register is writeable, if the WREN instruction has set the WEL bit.                                       | Protected against PP, DIFP, DIEFP, QIFP, QIEFP, SSE, SE and BE instructions. | Ready to accept PP, DIFP, DIEFP, QIFP, QIEFP, SSE, and SE instructions. |
| 0                         | 0        |                           | The values in the SRWD, TB, BP2, BP1, and BP0 bits can be changed.                                               |                                                                              |                                                                         |
| 1                         | 1        | Hardware protected (HPM)  | Status Register is hardware write protected. The values in the SRWD, TB, BP2, BP1 and BP0 bits cannot be changed | PP, DIFP, DIEFP, QIFP, QIEFP, SSE, SE and BE instructions.                   | PP, DIFP, DIEFP, QIFP, QIEFP, SSE, and SE instructions.                 |
| 0                         | 1        |                           |                                                                                                                  |                                                                              |                                                                         |

1. As defined by the values in the Block Protect (TB, BP2, BP1, BP0) bits of the Status Register, as shown in [Table 2: Status register format](#).

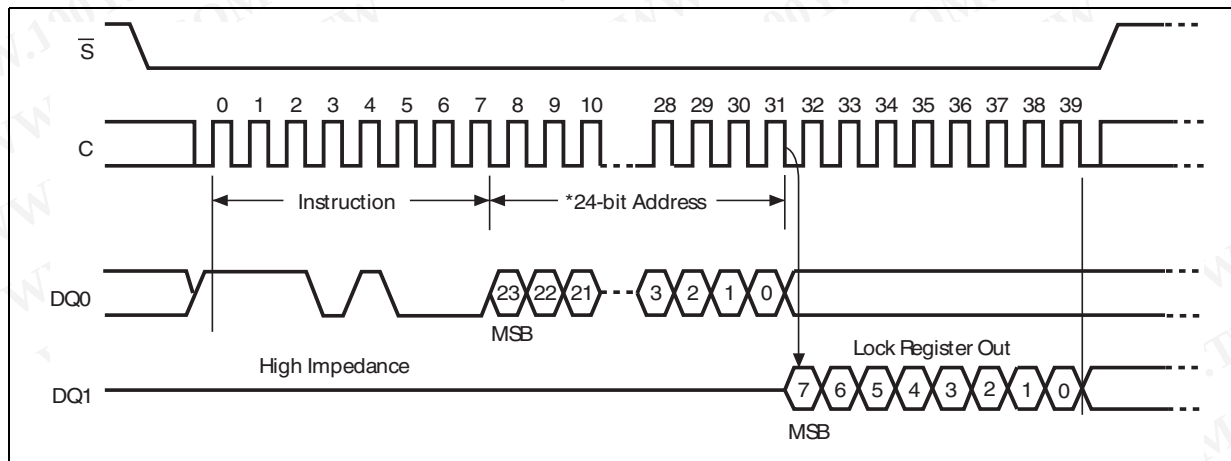
### 9.1.25 Read Lock Register (RDLR)

The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. The instruction code for the Read Lock Register (RDLR) instruction is followed by a 3-byte address (A23-A0) pointing to any location inside the concerned sector. Each address bit is latched-in during the rising edge of Serial Clock (C). Then the value of the Lock Register is shifted out on Serial Data output (DQ1), each bit being shifted out, at a maximum frequency  $f_C$ , during the falling edge of Serial Clock (C).

The Read Lock Register (RDLR) instruction is terminated by driving Chip Select ( $\overline{S}$ ) High at any time during data output.

Any Read Lock Register (RDLR) instruction, while an Erase, Program or Write cycle is in progress, is rejected without having any effects on the cycle that is in progress.

Figure 33. Read Lock Register instruction and data-out sequence



\*Address bits A23 and A22 are "Don't Care."

Table 19. Lock Register out<sup>(1)</sup>

| Bit   | Bit name          | Value | Function                                                                                                                                           |
|-------|-------------------|-------|----------------------------------------------------------------------------------------------------------------------------------------------------|
| b7-b2 |                   |       | Reserved                                                                                                                                           |
| b1    | Sector Lock Down  | '1'   | The Write Lock and Lock Down bits cannot be changed. Once a '1' is written to the Lock Down bit it cannot be cleared to '0', except by a power-up. |
|       |                   | '0'   | The Write Lock and Lock Down bits can be changed by writing new values to them.                                                                    |
| b0    | Sector Write Lock | '1'   | Program and Erase operations in this sector will not be executed. The memory contents will not be changed.                                         |
|       |                   | '0'   | Program and Erase operations in this sector are executed and will modify the sector contents.                                                      |

1. Values of (b1, b0) after power-up are defined in [Section 7: Protection modes](#).

### 9.1.26 Write to Lock Register (WRLR)

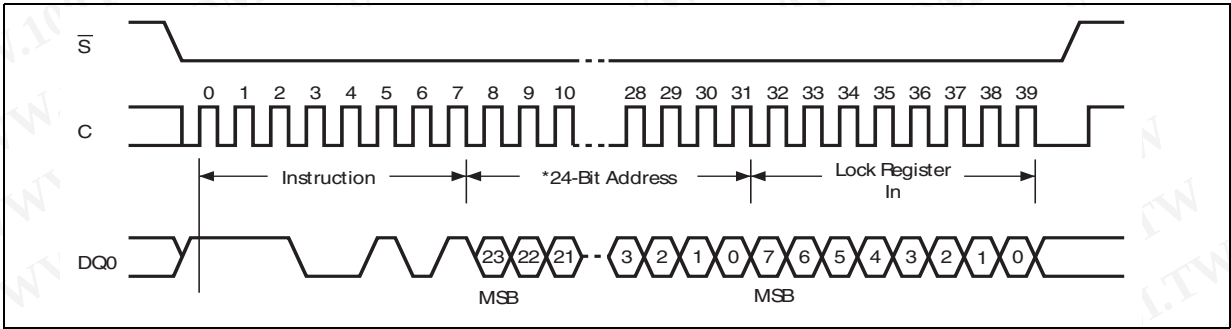
The Write to Lock Register (WRLR) instruction allows bits to be changed in the Lock Registers. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded, the device sets the Write Enable Latch (WEL).

The Write to Lock Register (WRLR) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code, three address bytes (pointing to any address in the targeted sector and one data byte on Serial Data input (DQ0). The instruction sequence is shown in Figure 22. Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the data byte has been latched in, otherwise the Write to Lock Register (WRLR) instruction is not executed.

Lock Register bits are volatile, and therefore do not require time to be written. When the Write to Lock Register (WRLR) instruction has been successfully executed, the Write Enable Latch (WEL) bit is reset after a delay time less than tSHSL minimum value.

Any Write to Lock Register (WRLR) instruction, while an Erase or Program cycle is in progress, is rejected without having any effects on the cycle that is in progress.

Figure 34. Write to Lock Register instruction sequence



\*Address bits A23 and A22 are "Don't Care."

Table 20. Lock Register in<sup>(1)</sup>

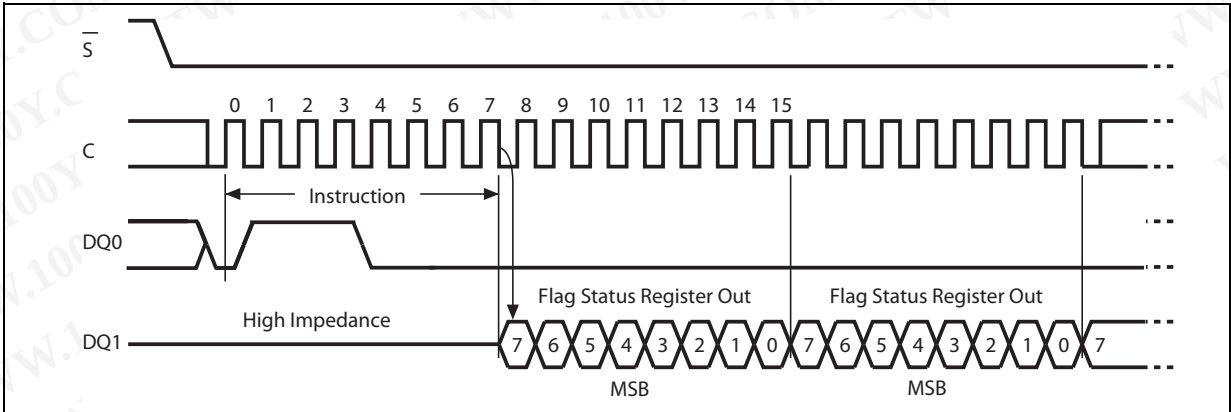
| Sector      | Bit   | Value                                                            |
|-------------|-------|------------------------------------------------------------------|
| All sectors | b7-b2 | '0'                                                              |
|             | b1    | Sector Lock Down bit value (refer to <a href="#">Table 19</a> )  |
|             | b0    | Sector Write Lock bit value (refer to <a href="#">Table 19</a> ) |

1. Values of (b1, b0) after power-up are defined in [Section 7: Protection modes](#).

### 9.1.27 Read Flag Status Register

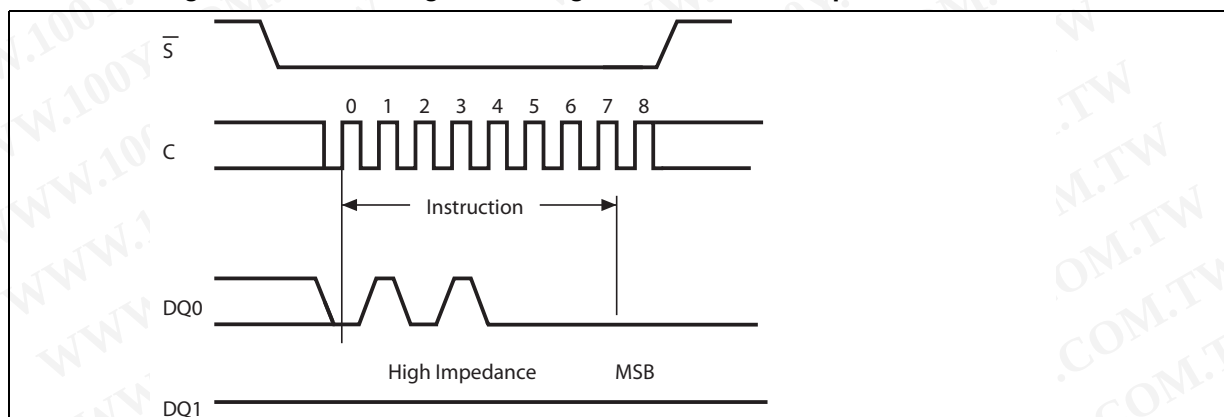
The Read Flag Status Register (RFSR) instruction allows the Flag Status Register to be read. The Status Register may be read at any time, even while a Program or Erase is in progress. When one of these cycles is in progress, it is recommended to check the P/E Controller bit (Not WIP) bit before sending a new instruction to the device. It is also possible to read the Flag Register continuously, as shown here.

Figure 35. Read Flag Status Register instruction sequence



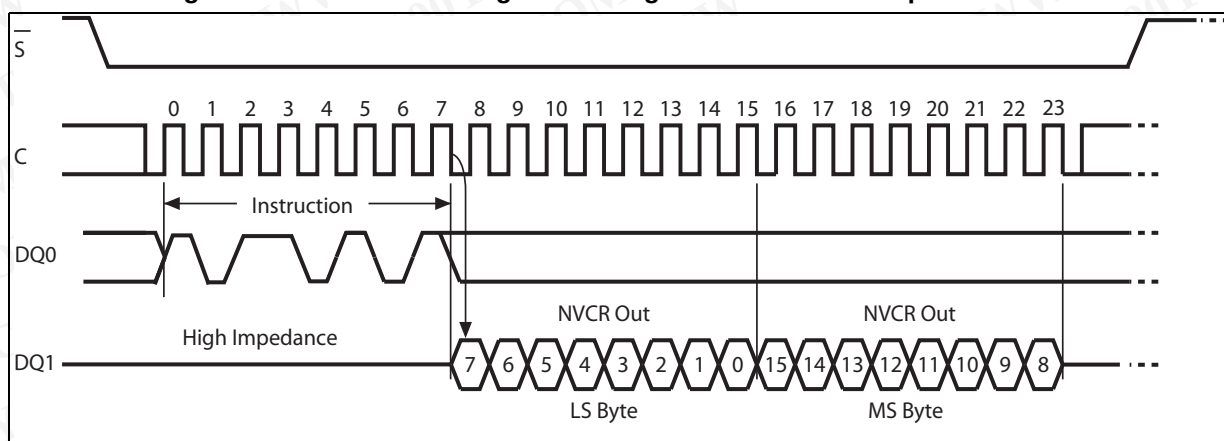
### 9.1.28 Clear Flag Status Register

The Clear Flag Status Register (CLFSR) instruction reset the error Flag Status Register bits (Erase Error bit, Program Error bit, VPP Error bit, Protection Error bit). It is not necessary to set the WEL bit before the Clear Flag Status Register instruction is executed. The WEL bit will be unchanged after this command is executed.

**Figure 36. Clear Flag Status Register instruction sequence**

### 9.1.29 Read NV Configuration Register

The Read Non Volatile Configuration Register (RDNVCR) instruction allows the Non Volatile Configuration Register to be read.

**Figure 37. Read NV Configuration Register instruction sequence**

### 9.1.30 Write NV Configuration Register

The Write Non Volatile Configuration register (WRNVCR) instruction allows new values to be written to the Non Volatile Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed. After the write enable (WREN) instruction has been decoded and executed, the device sets the write enable latch (WEL).

The Write Non Volatile Configuration register (WRNVCR) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code and the data bytes on serial data input (DQ0).

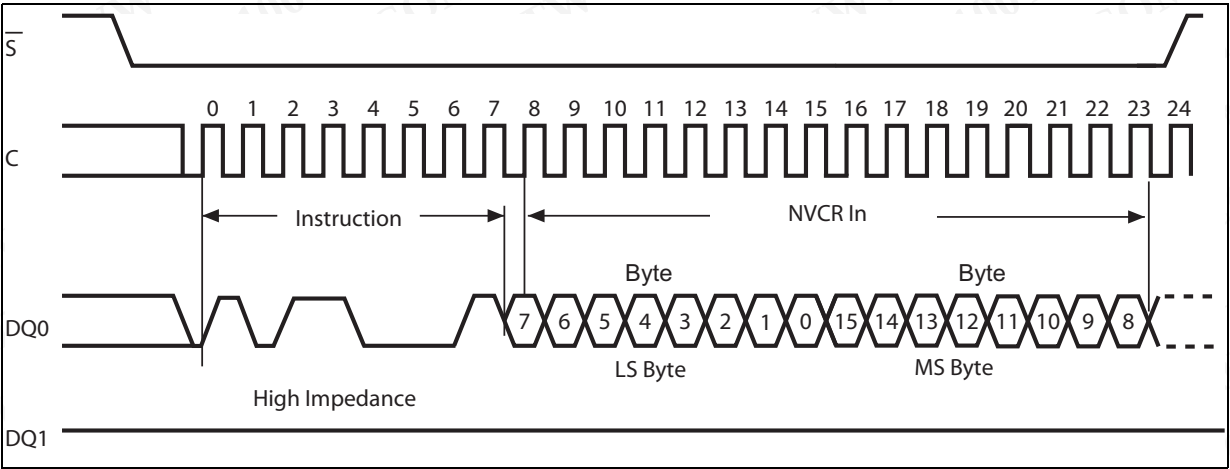
Chip Select ( $\overline{S}$ ) must be driven High after the 16th bit of the data bytes has been latched in. If not, the Write Non Volatile Configuration register (WRNVCR) instruction is not executed. As soon as Chip Select ( $\overline{S}$ ) is driven High, the self-timed write NV configuration register cycle (whose duration is  $t_{WRNVCR}$ ) is initiated.

While the Write Non Volatile Configuration register cycle is in progress, it is possible to monitor the end of the process by polling status Register write in progress (WIP) bit or the Flag Status Register Program/Erase Controller bit. The write in progress (WIP) bit is 1 during the self-timed Write Non Volatile Configuration register cycle, and is 0 when it is completed. When the cycle is completed, the write enable latch (WEL) is reset.

The Write Non Volatile Configuration register (WRNVCR) instruction allows the user to change the values of all the Non Volatile Configuration Register bits, described in [Table 3.: Non-Volatile Configuration Register](#).

The Write Non Volatile Configuration Register impacts the memory behavior only after the next power on sequence.

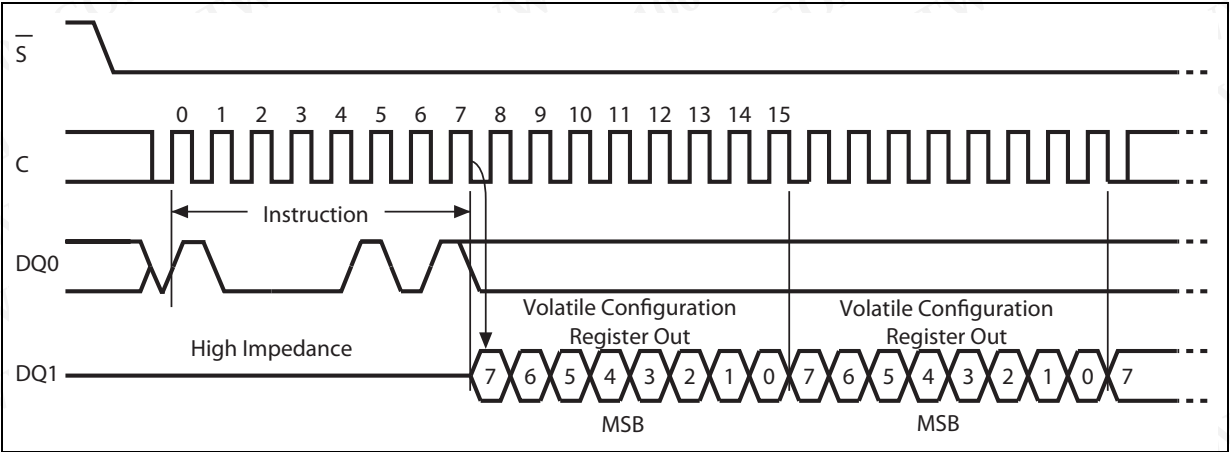
Figure 38. Write NV Configuration Register instruction sequence



### 9.1.31 Read Volatile Configuration Register

The Read Volatile Configuration Register (RDVCR) instruction allows the Volatile Configuration Register to be read. See [Table 5.: Volatile Configuration Register](#).

Figure 39. Read Volatile Configuration Register instruction sequence



9.1.32 Write Volatile Configuration Register

The Write Volatile Configuration register (WRVCR) instruction allows new values to be written to the Volatile Configuration register. Before it can be accepted, a write enable (WREN) instruction must have been executed. After the write enable (WREN) instruction has been decoded and executed, the device sets the write enable latch (WEL).

The Write Volatile Configuration register (WRVCR) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code and the data byte on serial data input (DQ0).

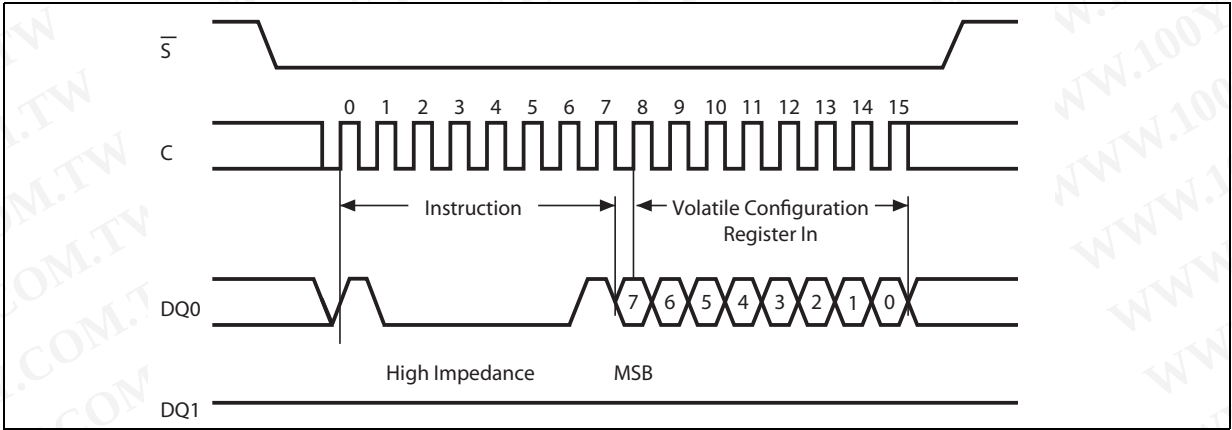
Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the data byte has been latched in. If not, the Write Volatile Configuration register (WRVCR) instruction is not executed.

When the new data are latched, the write enable latch (WEL) is reset.

The Write Volatile Configuration register (WRVCR) instruction allows the user to change the values of all the Volatile Configuration Register bits, described in [Table 5.: Volatile Configuration Register](#).

The Write Volatile Configuration Register impacts the memory behavior right after the instruction is received by the device.

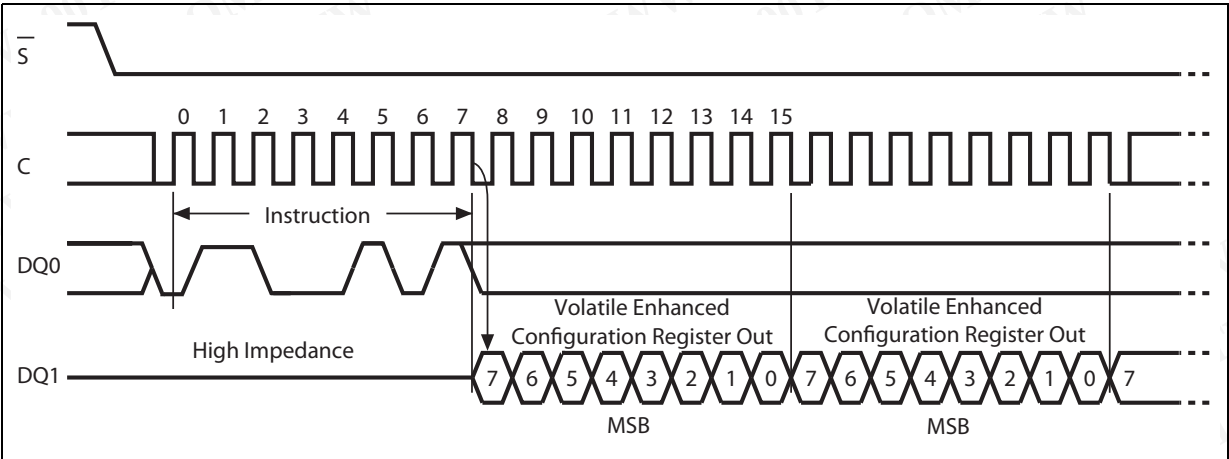
Figure 40. Write Volatile Configuration Register instruction sequence



9.1.33 Read Volatile Enhanced Configuration Register

The Read Volatile Enhanced Configuration Register (RDVECR) instruction allows the Volatile Configuration Register to be read.

Figure 41. Read Volatile Enhanced Configuration Register instruction sequence



9.1.34 Write Volatile Enhanced Configuration Register

The Write Volatile Enhanced Configuration register (WRVECR) instruction allows new values to be written to the Volatile Enhanced Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed. After the write enable (WREN) instruction has been decoded and executed, the device sets the write enable latch (WEL).

The Write Volatile Enhanced Configuration register (WRVECR) instruction is entered by driving Chip Select ( $\overline{S}$ ) Low, followed by the instruction code and the data byte on serial data input (DQ0).

Chip Select ( $\overline{S}$ ) must be driven High after the eighth bit of the data byte has been latched in.

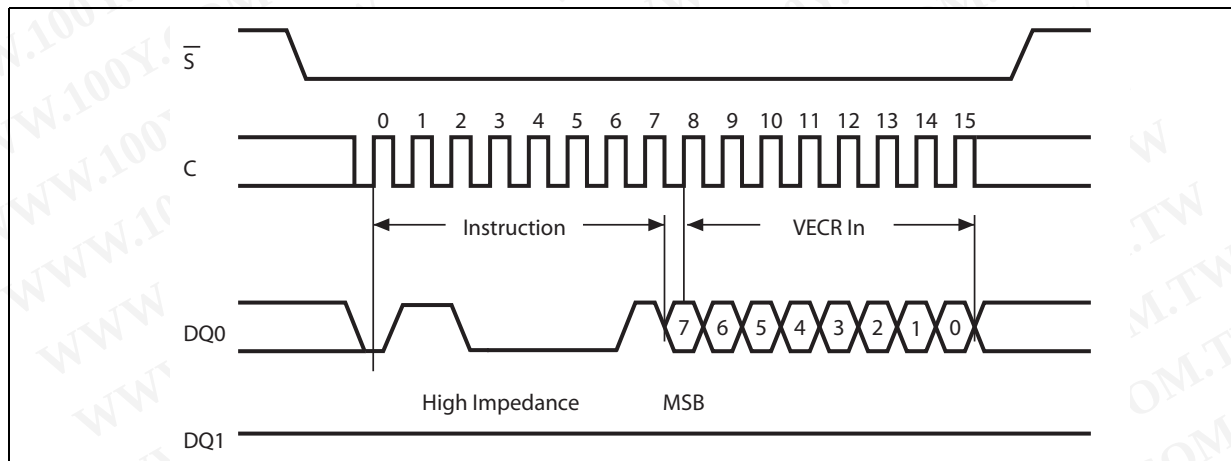
If not, the Write Volatile Enhanced Configuration register (WRVECR) instruction is not executed.

When the new data are latched, the write enable latch (WEL) is reset.

The Write Volatile Enhanced Configuration register (WRVECR) instruction allows the user to change the values of all the Volatile Enhanced Configuration Register bits, described in [Table 7.: Volatile Enhanced Configuration Register](#).

The Write Volatile Enhanced Configuration Register impacts the memory behavior right after the instruction is received by the device.

Figure 42. Write Volatile Enhanced Configuration Register instruction sequence



## 9.2 DIO-SPI Instructions

In DIO-SPI protocol, instructions, addresses and input/output data always run in parallel on two wires: DQ0 and DQ1.

In the case of a Dual Command Fast Read (DCFR), Read OTP (ROTP), Read Lock Registers (RDLR), Read Status Register (RDSR), Read Flag Status Register (RFSR), Read NV Configuration Register (RDNVCR), Read Volatile Configuration Register (RDVCR), Read Volatile Enhanced Configuration Register (RDVECR), Read Serial Flash Discovery Parameter (RDSFDP), and Multiple I/O Read Identification (MIORDID) instruction, the shifted-in instruction sequence is followed by a data-out sequence. Chip Select ( $\overline{S}$ ) can be driven High after any bit of the data-out sequence is being shifted out.

In the case of a Dual Command Page Program (DCPP), Program OTP (POTP), Subsector Erase (SSE), Sector Erase (SE), Bulk Erase (BE), Program/Erase Suspend (PES), Program/Erase Resume (PER), Write Status Register (WRSR), Clear Flag Status Register (CLFSR), Write to Lock Register (WRLR), Write Volatile Configuration Register (WRVCR), Write Volatile Enhanced Configuration Register (WRVECR), Write NV Configuration Register (WRNVCR), Write Enable (WREN) or Write Disable (WRDI) instruction, Chip Select ( $\overline{S}$ ) must be driven High exactly at a byte boundary, otherwise the instruction is rejected, and is not executed.

All attempts to access the memory array during a Write Status Register cycle, a Write Non Volatile Configuration Register, a Program cycle, or an Erase cycle are ignored. The internal Write Status Register cycle, Write Non Volatile Configuration Register, Program cycle, or Erase cycle continues unaffected. The exception is the Program/Erase Suspend instruction (PES), that can be used to pause all the Program and Erase cycles, except for the Program OTP (POTP), the Write Status Register, the Bulk Erase (BE), and the Write Non Volatile Configuration Register.

The suspended program or erase cycle can be resumed by mean of the Program/Erase Resume instruction (PER). During the program/erase cycles also the polling instructions (to check if the internal modify cycle is finished by mean of the WIP bit of the Status Register or of the Program/Erase controller bit of the Flag Status register) are also accepted to allow the application checking the end of the internal modify cycles, of course these polling instructions don't affect the internal cycles performing.

Table 21. Instruction set: DIO-SPI protocol

| Instruction | Description                                    | One-byte Instruction Code (BIN) | One-byte Instruction Code (HEX) | Address bytes | Dummy clock cycle | Data bytes |
|-------------|------------------------------------------------|---------------------------------|---------------------------------|---------------|-------------------|------------|
| MIORDID     | Multiple I/O read identification               | 1010 1111                       | AFh                             | 0             | 0                 | 1 to 3     |
| RDSFDP      | Read Serial Flash Discovery Parameter          | 01011010                        | 5Ah                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| DCFR        | Dual Command Fast Read                         | 0000 1011                       | 0Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
|             |                                                | 0011 1011                       | 3Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
|             |                                                | 1011 1011                       | BBh                             | 3             | 8 <sup>(1)</sup>  | 1 to ∞     |
| ROTP        | Read OTP                                       | 0100 1011                       | 4Bh                             | 3             | 8 <sup>(1)</sup>  | 1 to 65    |
| WREN        | Write Enable                                   | 0000 0110                       | 06h                             | 0             | 0                 | 0          |
| WRDI        | Write Disable                                  | 0000 0100                       | 04h                             | 0             | 0                 | 0          |
| DCPP        | Dual Command Page Program                      | 0000 0010                       | 02h                             | 3             | 0                 | 1 to 256   |
|             |                                                | 1010 0010                       | A2h                             | 3             | 0                 | 1 to 256   |
|             |                                                | 1101 0010                       | D2h                             | 3             | 0                 | 1 to 256   |
| POTP        | Program OTP                                    | 0100 0010                       | 42h                             | 3             | 0                 | 1 to 65    |
| SSE         | SubSector Erase                                | 0010 0000                       | 20h                             | 3             | 0                 | 0          |
| SE          | Sector Erase                                   | 1101 1000                       | D8h                             | 3             | 0                 | 0          |
| BE          | Bulk Erase                                     | 1100 0111                       | C7h                             | 0             | 0                 | 0          |
| PER         | Program/Erase Resume                           | 0111 1010                       | 7Ah                             | 0             | 0                 | 0          |
| PES         | Program/Erase Suspend                          | 0111 0101                       | 75h                             | 0             | 0                 | 0          |
| RDSR        | Read Status Register                           | 0000 0101                       | 05h                             | 0             | 0                 | 1 to ∞     |
| WRSR        | Write Status Register                          | 0000 0001                       | 01h                             | 0             | 0                 | 1          |
| RDLR        | Read Lock Register                             | 1110 1000                       | E8h                             | 3             | 0                 | 1 to ∞     |
| WRLR        | Write to Lock Register                         | 1110 0101                       | E5h                             | 3             | 0                 | 1          |
| RFSR        | Read Flag Status Register                      | 0111 0000                       | 70h                             | 0             | 0                 | 1 to ∞     |
| CLFSR       | Clear Flag Status Register                     | 0101 0000                       | 50h                             | 0             | 0                 | 0          |
| RDNVCR      | Read NV Configuration Register                 | 1011 0101                       | B5h                             | 0             | 0                 | 2          |
| WRNVCR      | Write NV Configuration Register                | 1011 0001                       | B1h                             | 0             | 0                 | 2          |
| RDVCR       | Read Volatile Configuration Register           | 1000 0101                       | 85h                             | 0             | 0                 | 1 to ∞     |
| WRVCR       | Write Volatile Configuration Register          | 1000 0001                       | 81h                             | 0             | 0                 | 1          |
| RDVECR      | Read Volatile Enhanced Configuration Register  | 0110 0101                       | 65h                             | 0             | 0                 | 1 to ∞     |
| WRVECR      | Write Volatile Enhanced Configuration Register | 0110 0001                       | 61h                             | 0             | 0                 | 1          |

1) The number of Dummy Clock cycles is configurable by the user

### 9.2.1 Multiple I/O Read Identification protocol

The Multiple Input/Output Read Identification (MIORDID) instruction allows to read the device identification data in the DIO-SPI protocol:

- Manufacturer identification (1 byte)
- Device identification (2 bytes)

Unlike the RDID instruction of the Extended SPI protocol, the Multiple Input/Output instruction can not read the Unique ID code (UID) (17 bytes).

For further details on the manufacturer and device identification codes please refer to [Section 9.1.1: Read Identification \(RDID\)](#).

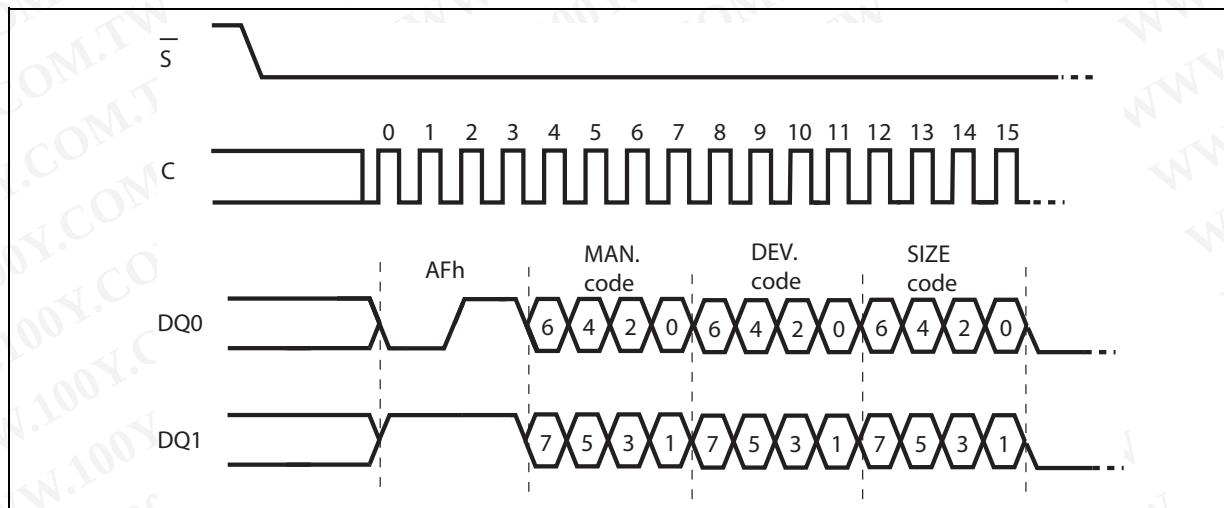
Any Multiple Input/Output Read Identification (MIORDID) instruction while an Erase or Program cycle is in progress, is not decoded, and has no effect on the cycle that is in progress.

The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. Then, the 8-bit instruction code for the instruction is shifted in parallel on the 2 pins DQ0 and DQ1. After this, the 24-bit device identification, stored in the memory, will be shifted out on again in parallel on DQ1 and DQ0. Each two bits are shifted out during the falling edge of Serial Clock (C).

The Read Identification (RDID) instruction is terminated by driving Chip Select ( $\overline{S}$ ) High at any time during data output.

When Chip Select ( $\overline{S}$ ) is driven High, the device is put in the Standby Power mode. Once in the Standby Power mode, the device waits to be selected, so that it can receive, decode and execute instructions.

**Figure 43. Multiple I/O Read Identification instruction and data-out sequence DIO-SPI**

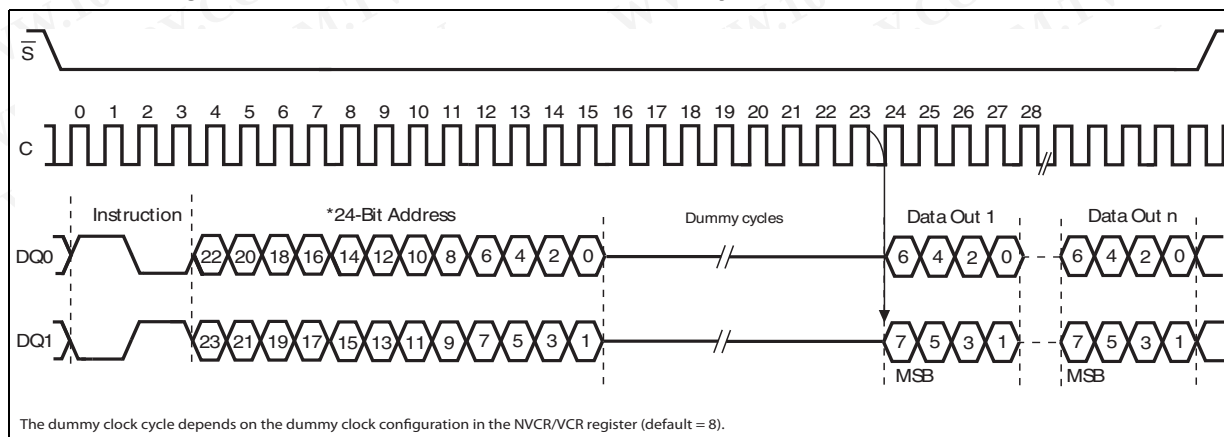


### 9.2.2 Read Serial Flash Discovery Parameter

The Read Serial Flash Discovery Parameter (RDSFDP) instruction allows reading the Serial Flash Discovery Parameter area (SFDP) in the DIO-SPI protocol. The instruction functionality is exactly the same as the Read Serial Flash Discovery Parameter instruction of the Extended SPI protocol; the only difference is that in the DIO-SPI protocol instruction code, address and output data are all parallelized on the two pins DQ0 and DQ1.

**Note:** The dummy bits can not be parallelized since these clock cycles are requested to perform the internal reading operation.

**Figure 44. Dual Read Serial Flash Discovery Parameter**



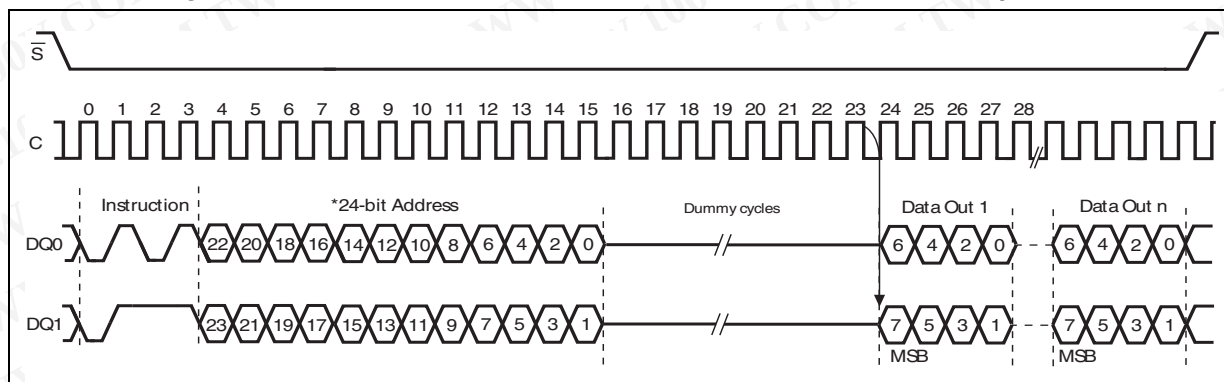
\*Address bits A[23:11] are "Don't Care."

### 9.2.3 Dual Command Fast Read (DCFR)

The Dual Command Fast Read (DCFR) instruction allows to read the memory in DIO-SPI protocol, parallelizing the instruction code, the address and the output data on two pins (DQ0 and DQ1). The Dual Command Fast Read (DCFR) instruction can be issued, when the device is set in DIO-SPI mode, by sending to the memory indifferently one of the 3 instructions codes: 0Bh, 3Bh or BBh, the effect is exactly the same. The 3 instruction codes are all accepted to help the application code porting from Extended SPI protocol to DIO-SPI protocol.

Apart for the parallelizing on two pins of the instruction code, the Dual Command Fast Read instruction functionality is exactly the same as the Dual I/O Fast Read of the Extended SPI protocol.

**Figure 45. Dual Command Fast Read instruction and data-out sequence DIO-SPI**



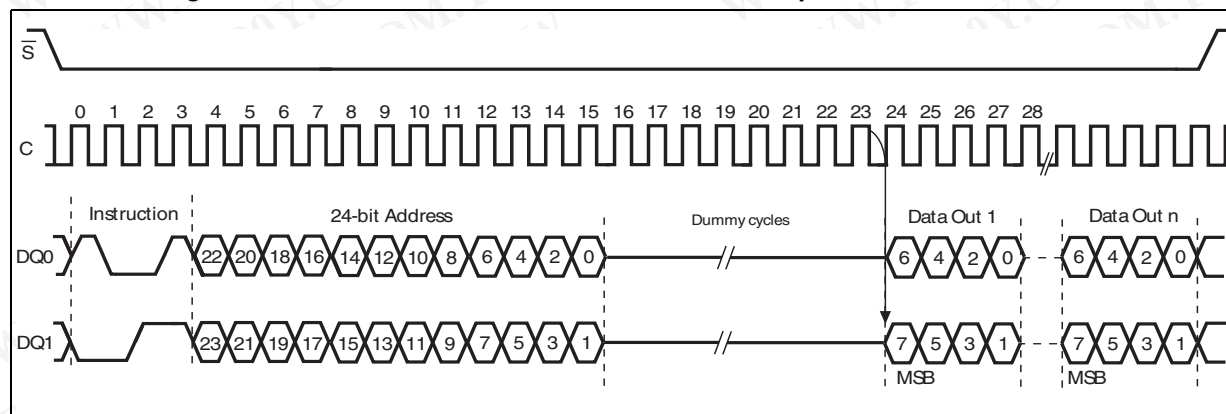
\*Address bits A23 and A22 are "Don't Care."

### 9.2.4 Read OTP (ROTP)

The Read OTP (ROTP) instruction is used to read the 64 bytes OTP area in the DIO-SPI protocol. The instruction functionality is exactly the same as the Read OTP instruction of the Extended SPI protocol; the only difference is that in the DIO-SPI protocol instruction code, address and output data are all parallelized on the two pins DQ0 and DQ1.

**Note:** The dummy bits can not be parallelized since these clock cycles are requested to perform the internal reading operation.

**Figure 46. Read OTP instruction and data-out sequence DIO-SPI**

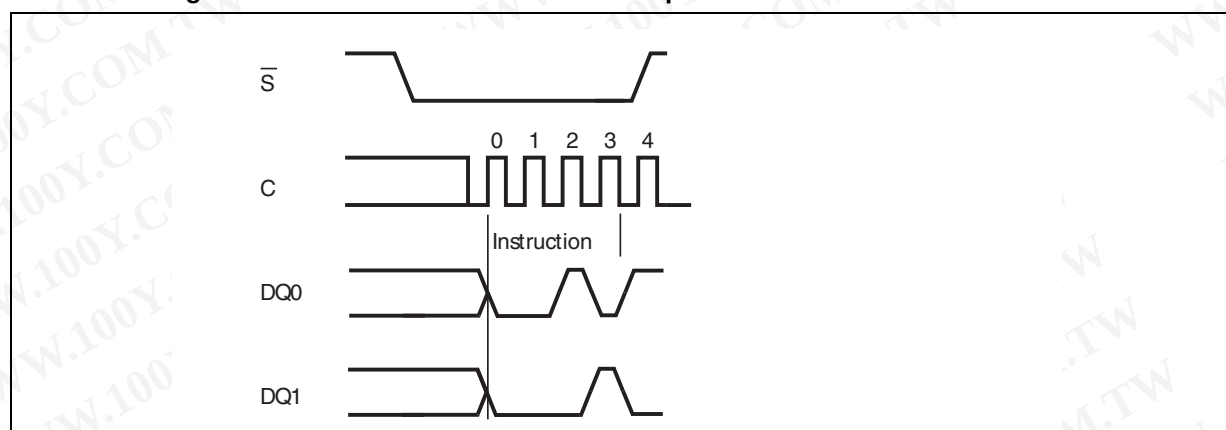


### 9.2.5 Write Enable (WREN)

The Write Enable (WREN) instruction sets the Write Enable Latch (WEL) bit.

Except for the parallelizing of the instruction code on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Write Enable (WREN) instruction of the Extended SPI protocol.

**Figure 47. Write Enable instruction sequence DIO-SPI**

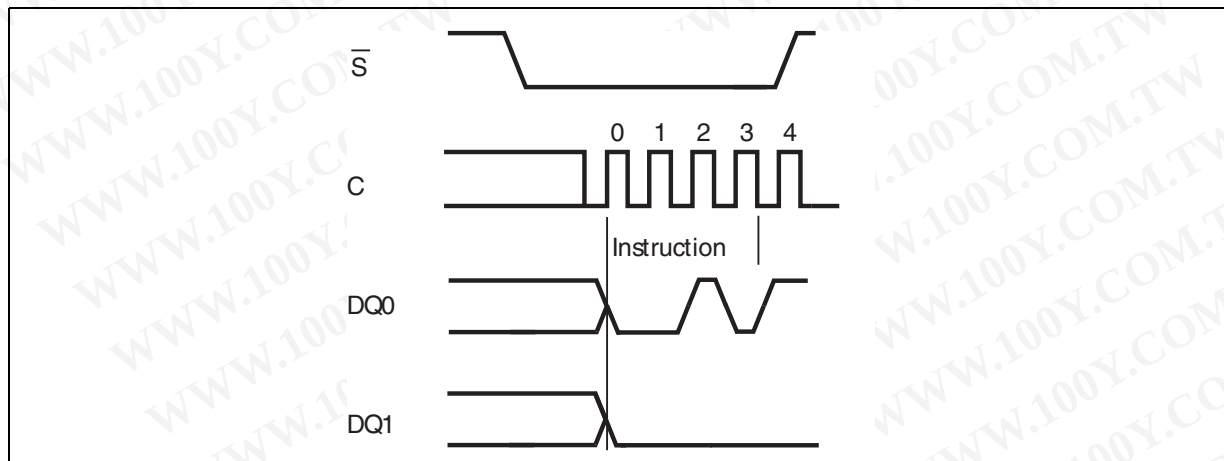


### 9.2.6 Write Disable (WRDI)

The Write Disable (WRDI) instruction resets the Write Enable Latch (WEL) bit.

Except for the parallelizing of the instruction code on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Write Disable (WRDI) instruction of the Extended SPI protocol.

**Figure 48. Write Disable instruction sequence DIO-SPI**

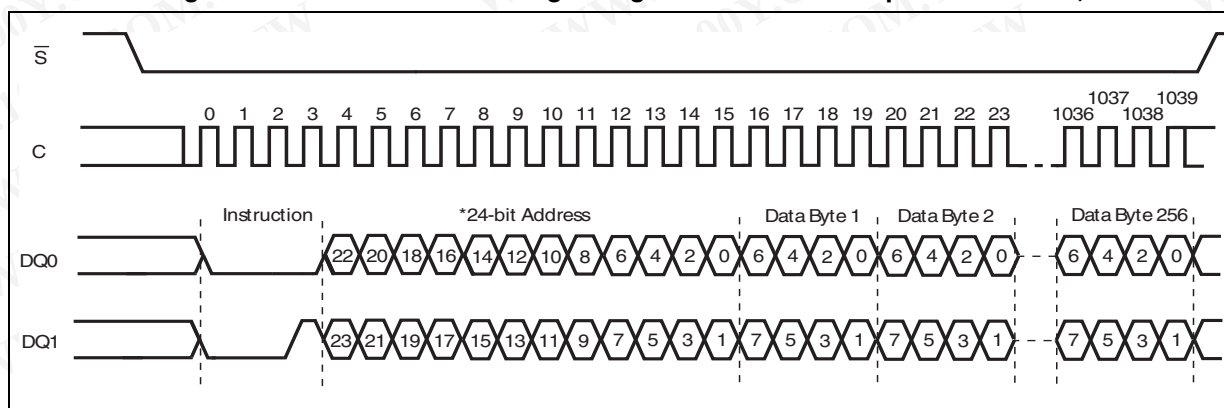


### 9.2.7 Dual Command Page Program (DCPP)

The Dual Command Page Program (DCPP) instruction allows to program the memory content in DIO-SPI protocol, parallelizing the instruction code, the address and the input data on two pins (DQ0 and DQ1). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. The Dual Command Page Program (DCPP) instruction can be issued, when the device is set in DIO-SPI mode, by sending to the memory indifferently one of the 3 instructions codes: 02h, A2h or D2h, the effect is exactly the same. The 3 instruction codes are all accepted to help the application code porting from Extended SPI protocol to DIO-SPI protocol.

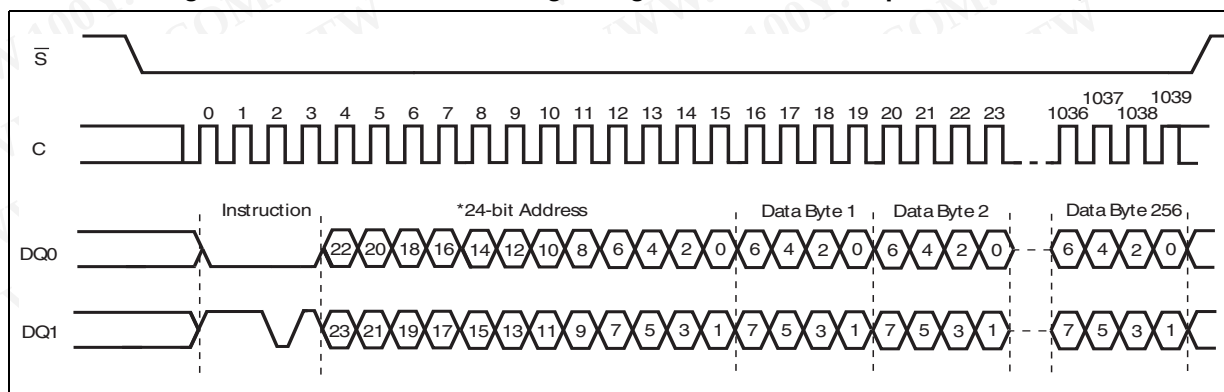
Apart for the parallelizing on two pins of the instruction code, the Dual Command Page Program instruction functionality is exactly the same as the Dual Input Extended Fast Program of the Extended SPI protocol.

**Figure 49. Dual Command Page Program instruction sequence DIO-SPI, 02h**



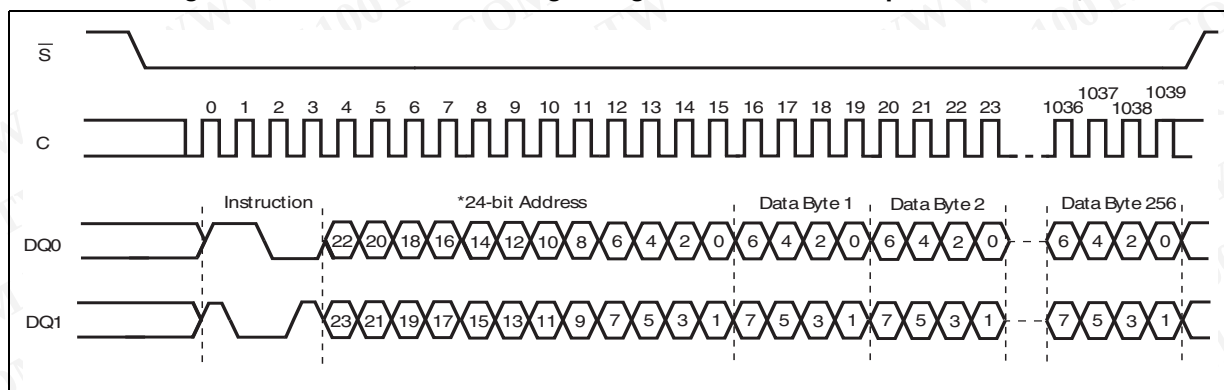
\*Address bits A[23:22] are "Don't Care."

Figure 50. Dual Command Page Program instruction sequence DIO-SPI, A2h



\*Address bits A[23:22] are "Don't Care."

Figure 51. Dual Command Page Program instruction sequence DIO-SPI, D2h



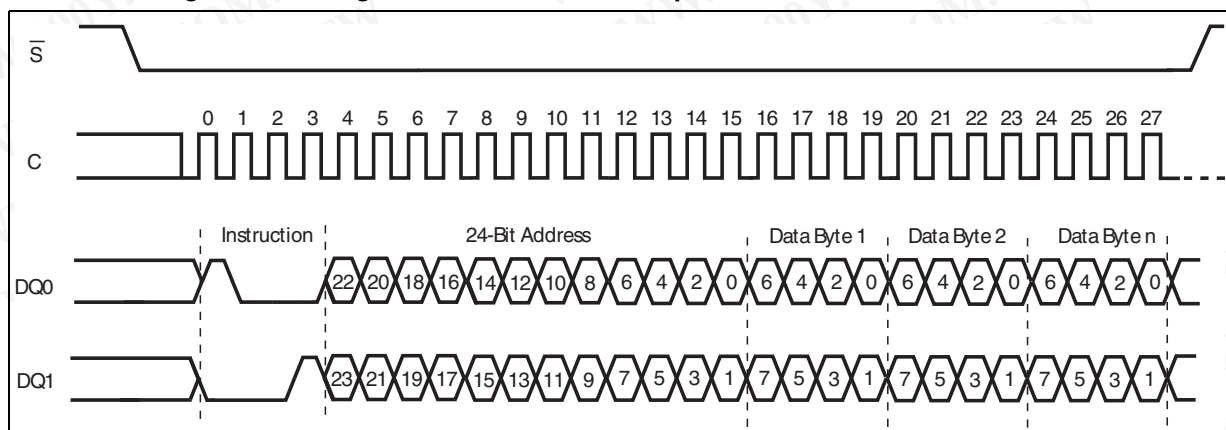
\*Address bits A[23:22] are "Don't Care."

### 9.2.8 Program OTP instruction (POTP)

The Program OTP instruction (POTP) is used to program at most 64 bytes to the OTP memory area (by changing bits from 1 to 0, only). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for parallelizing the instruction code, address, and input data on pins DQ0 and DQ1, the instruction functionality and the locking OTP method are the same as the Program OTP (POTP) instruction of the Extended SPI protocol.

Figure 52. Program OTP instruction sequence DIO-SPI

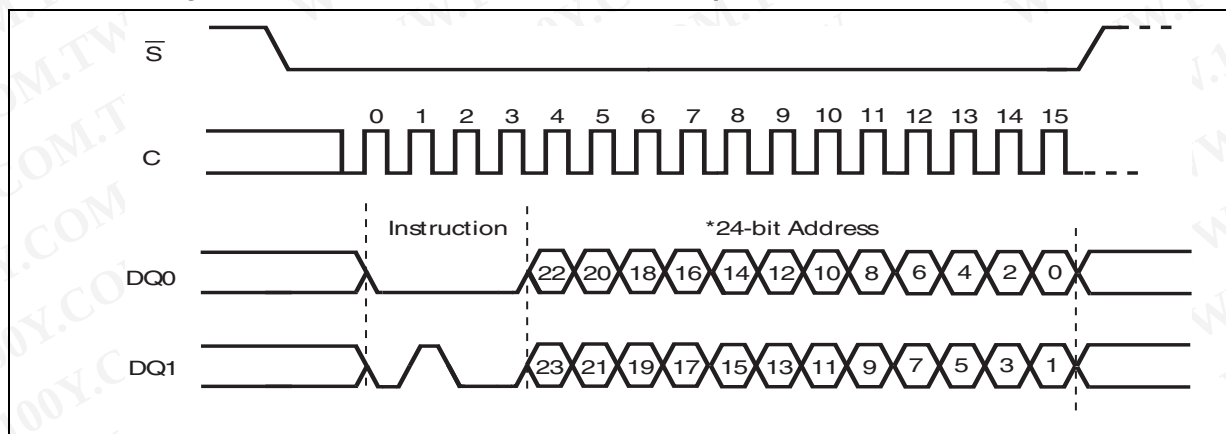


### 9.2.9 Subsector Erase (SSE)

The Subsector Erase (SSE) instruction sets to '1' (FFh) all bits inside the chosen subsector. Before it can be accepted, a Write Enable (WREN) instruction must have been executed previously.

Except for parallelizing the instruction code and the address on pins DQ0 and DQ1, the instruction functionality is the same as the Subsector Erase (SSE) instruction of the Extended SPI protocol.

Figure 53. Subsector Erase instruction sequence DIO-SPI

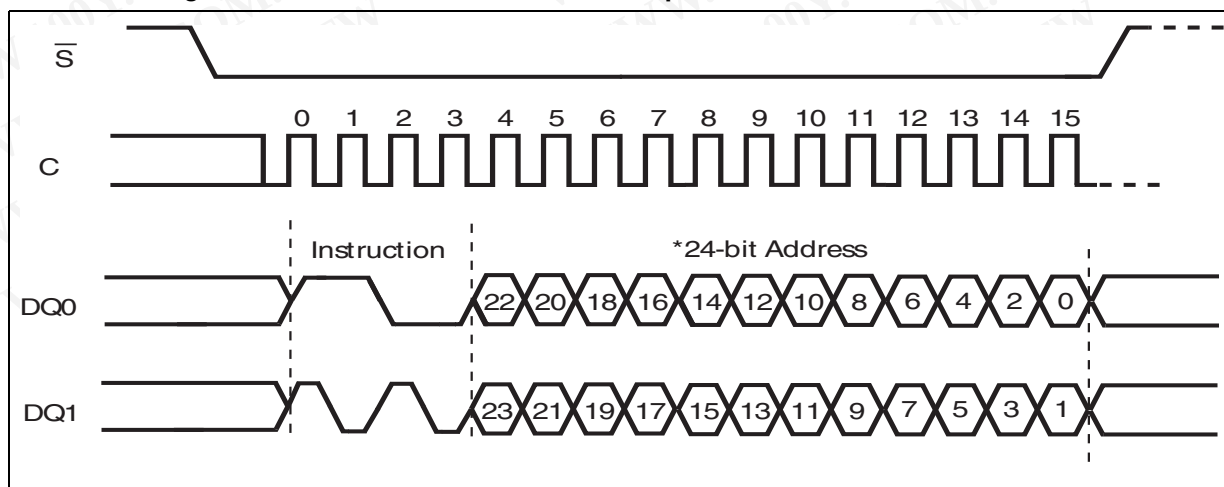


### 9.2.10 Sector Erase (SE)

The Sector Erase (SE) instruction sets to '1' (FFh) all bits inside the chosen sector. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for parallelizing the instruction code and the address on the two pins DQ0 and DQ1, the instruction functionality is the same as the Sector Erase (SE) instruction of the Extended SPI protocol.

Figure 54. Sector Erase instruction sequence DIO-SPI

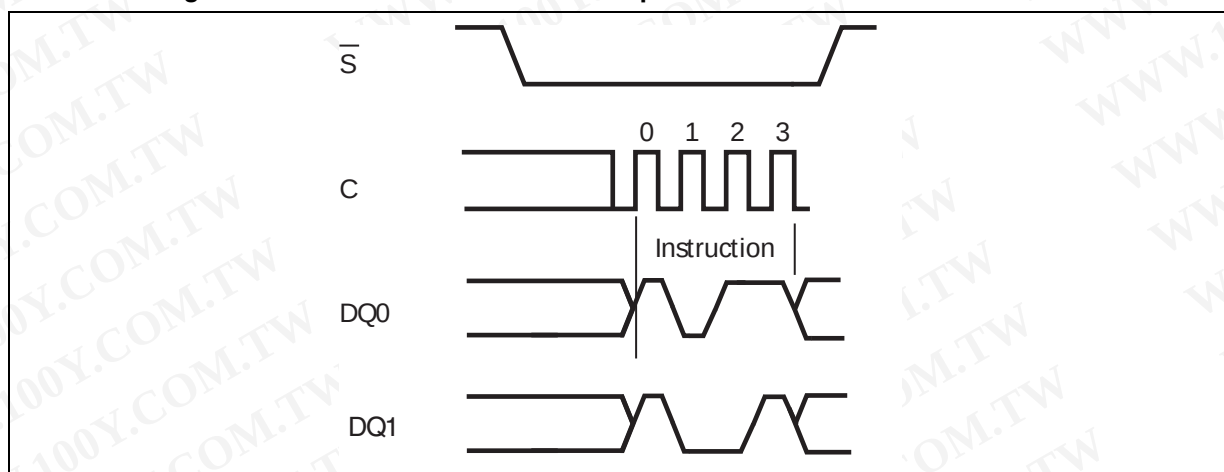


### 9.2.11 Bulk Erase (BE)

The Bulk Erase (BE) instruction sets all bits to '1' (FFh). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Bulk Erase (BE) instruction of the Extended SPI protocol.

Figure 55. Bulk Erase instruction sequence DIO-SPI

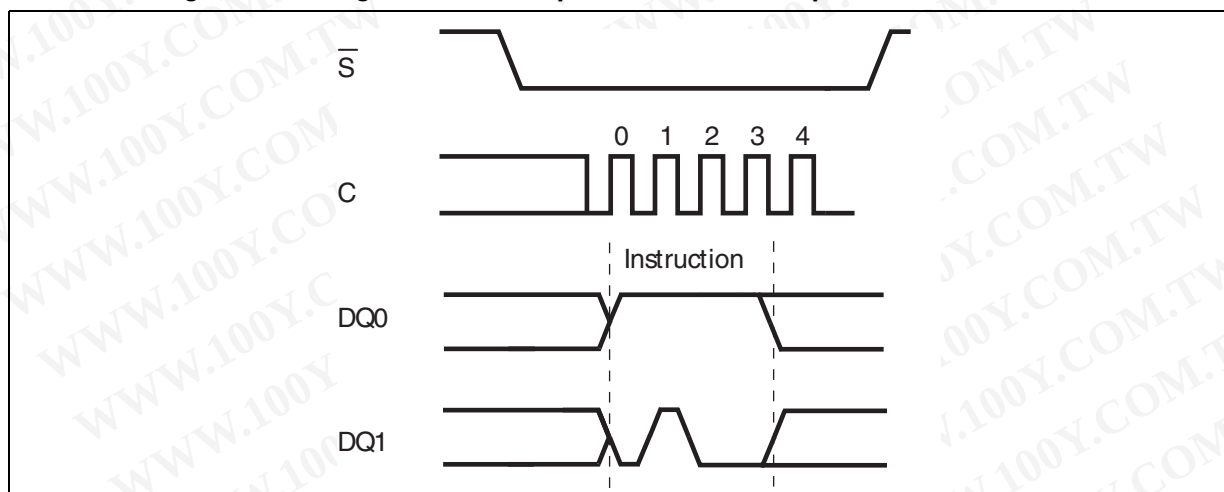


### 9.2.12 Program/Erase Suspend

The Program/Erase Suspend (PES) instruction allows the controller to interrupt a Program or an Erase instruction, in particular: Subsector Erase (SSE), Sector Erase (SE) and Dual Command Page Program (DCPP) can be suspended and resumed while Bulk Erase (BE), Write Status Register (WRSR), Write Non Volatile Configuration Register (WRNVCr), and Program OTP (POTP) cannot be suspended.

Apart for the parallelizing of the instruction code on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Program/Erase Suspend (PES) instruction of the Extended SPI protocol.

Figure 56. Program/Erase Suspend instruction sequence DIO-SPI

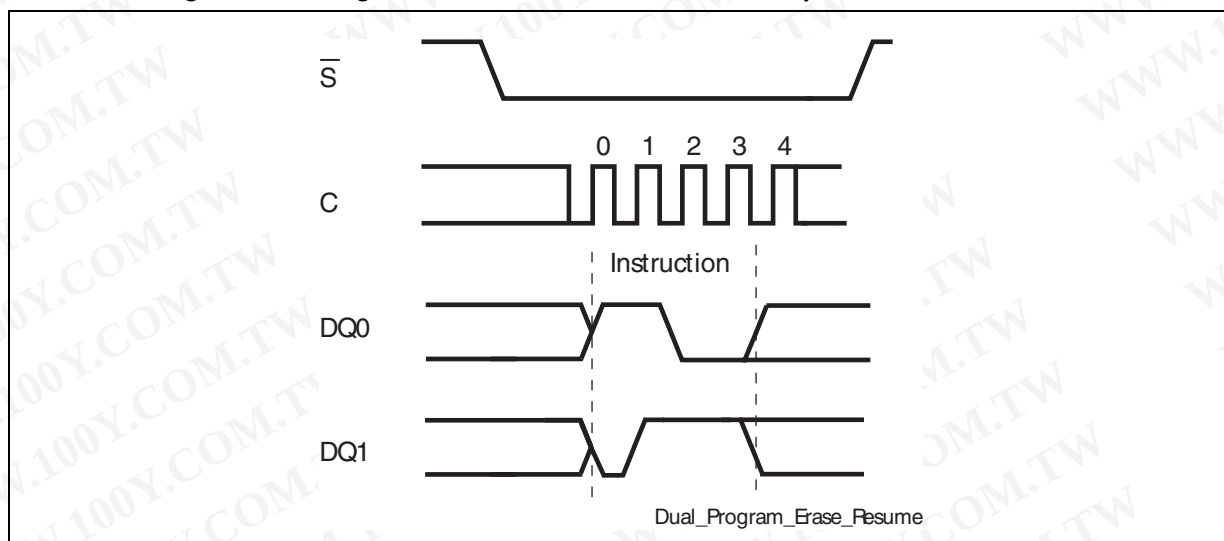


### 9.2.13 Program/Erase Resume

After a Program/Erase suspend instruction, a Program/Erase Resume instruction is required to continue performing the suspended Program or Erase sequence.

Except for the parallelizing of the instruction code on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Program/Erase Resume (PER) instruction of the Extended SPI protocol.

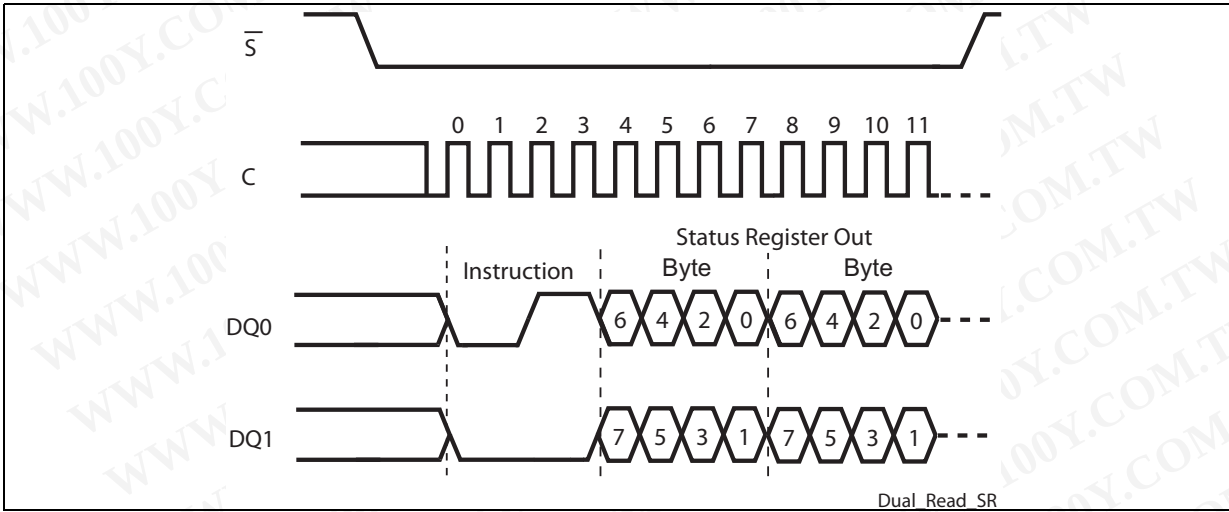
Figure 57. Program/Erase Resume instruction sequence DIO-SPI



### 9.2.14 Read Status Register (RDSR)

The Read Status Register (RDSR) instruction allows the Status Register to be read. Except for the parallelizing of the instruction code and the output data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Read Status Register (RDSR) instruction of the Extended SPI protocol.

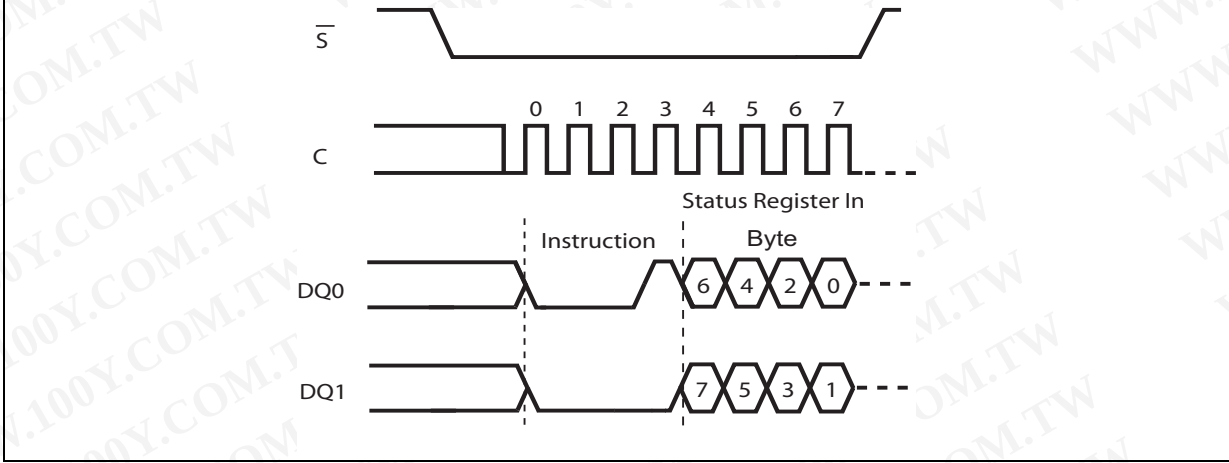
Figure 58. Read Status Register instruction sequence DIO-SPI



### 9.2.15 Write status register (WRSR)

The write status register (WRSR) instruction allows new values to be written to the status register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed. Except for the parallelizing of the instruction code and the input data on the two pins DQ0 and DQ1, the instruction functionality and the protection feature management is exactly the same as the Write Status Register (WRSR) instruction of the Extended SPI protocol.

Figure 59. Write Status Register instruction sequence DIO-SPI

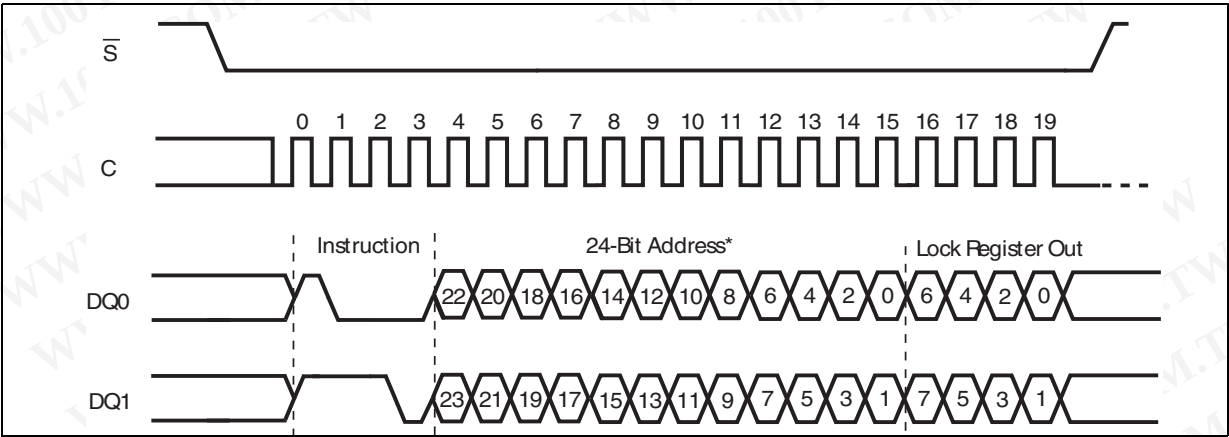


\*Address bits A[23:22] are "Don't Care."

### 9.2.16 Read Lock Register (RDLR)

The Read Lock Register instruction is used to read the lock register content. Except for the parallelizing of the instruction code, the address and the output data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Read Lock Register (RDLR) instruction of the Extended SPI protocol.

Figure 60. Read Lock Register instruction and data-out sequence DIO-SPI



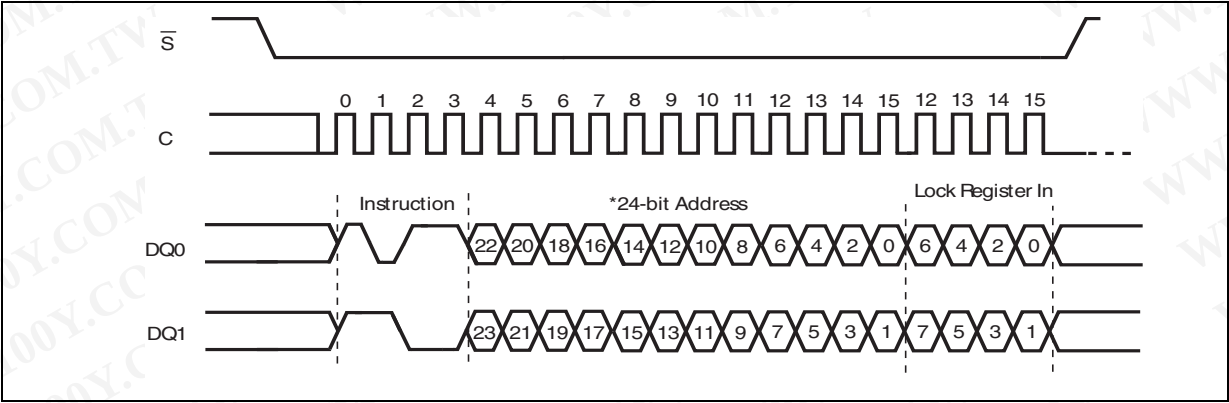
\*Address bits A23 and A22 are "Don't Care."

### 9.2.17 Write to Lock Register (WRLR)

The Write to Lock Register (WRLR) instruction allows bits to be changed in the Lock Registers. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code, the address and the input data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Write to Lock Register (WRLR) instruction of the Extended SPI protocol.

Figure 61. Write to Lock Register instruction sequence DIO-SPI



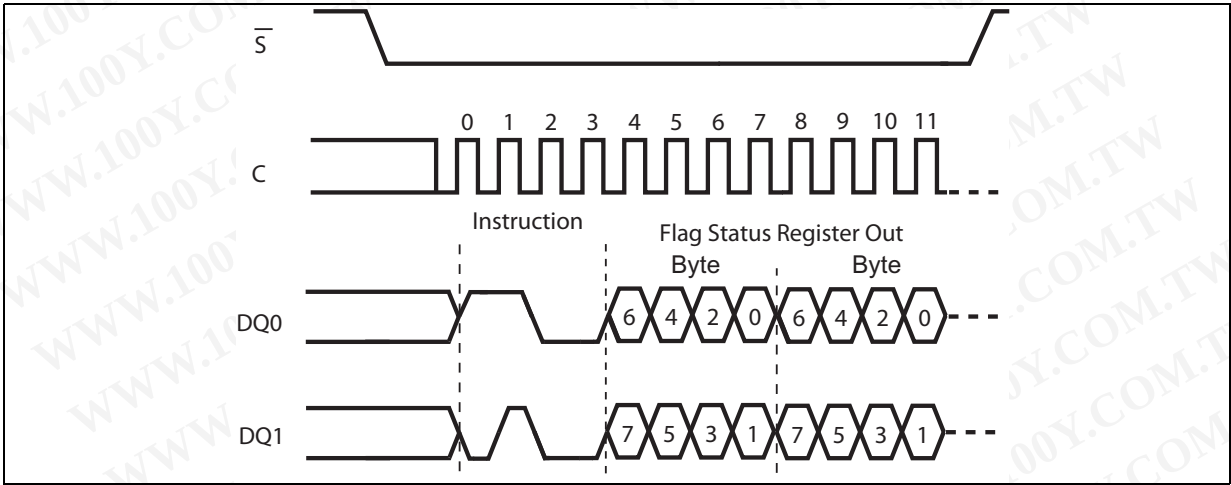
\*Address bits A23 and A22 are "Don't Care."

### 9.2.18 Read Flag Status Register

The Read Flag Status Register (RFSR) instruction allows the Flag Status Register to be read.

Except for the parallelizing of the instruction code and the output data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Read Flag Status Register (RFSR) instruction of the Extended SPI protocol.

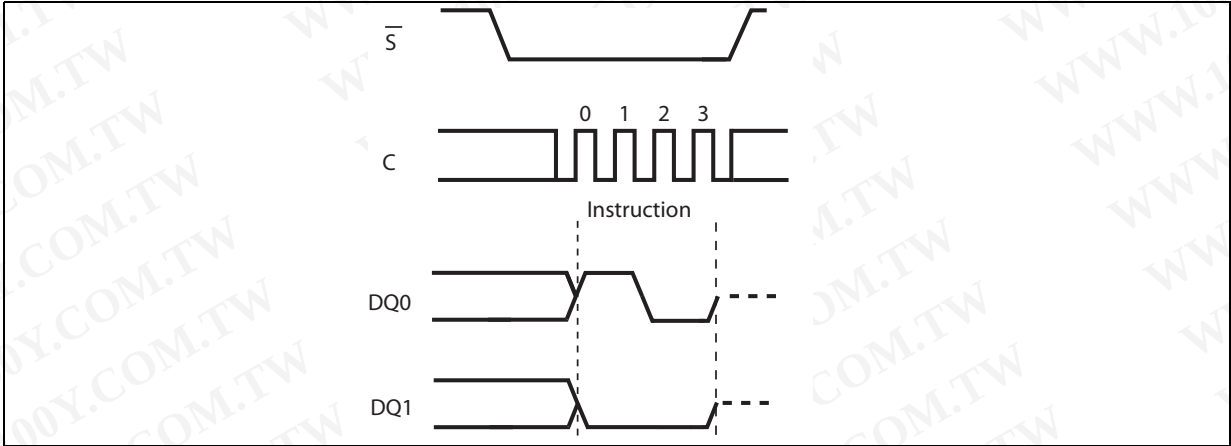
**Figure 62. Read Flag Status Register instruction sequence DIO-SPI**



### 9.2.19 Clear Flag Status Register

The Clear Flag Status Register (CLFSR) instruction reset the error Flag Status Register bits (Erase Error bit, Program Error bit, VPP Error bit, Protection Error bit). It is not necessary to set the WEL bit before the Clear Flag Status Register instruction is executed. The WEL bit will be unchanged after this command is executed.

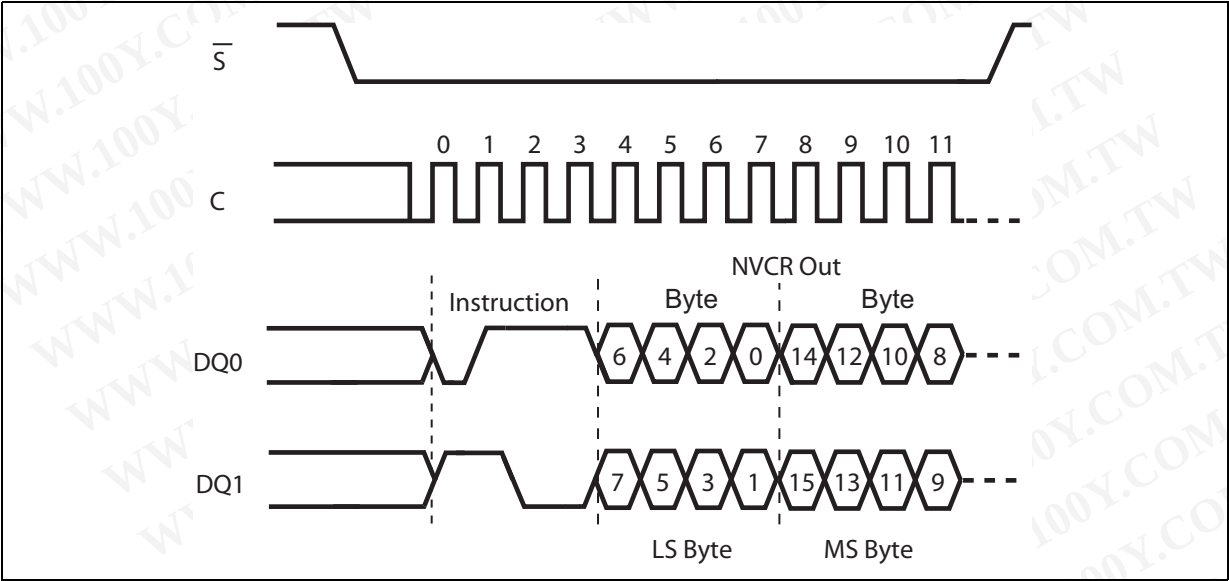
**Figure 63. Clear Flag Status Register instruction sequence DIO-SPI**



### 9.2.20 Read NV Configuration Register

The Read Non Volatile Configuration Register (RDNVCR) instruction allows the Non Volatile Configuration Register to be read.

Figure 64. Read NV Configuration Register instruction sequence DIO-SPI

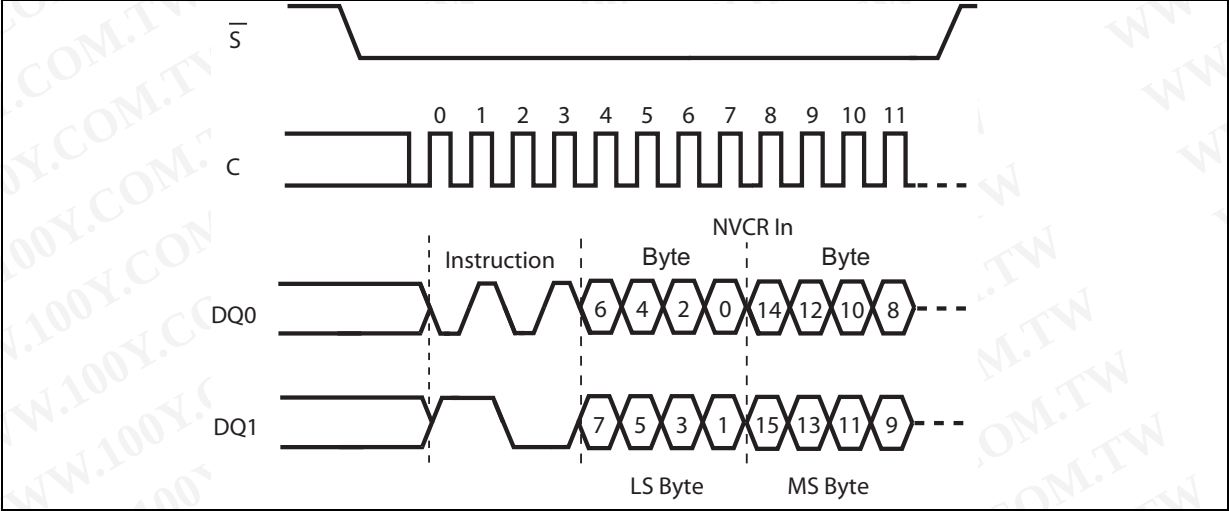


9.2.21 Write NV Configuration Register

The Write Non Volatile Configuration register (WRNVCR) instruction allows new values to be written to the Non Volatile Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed.

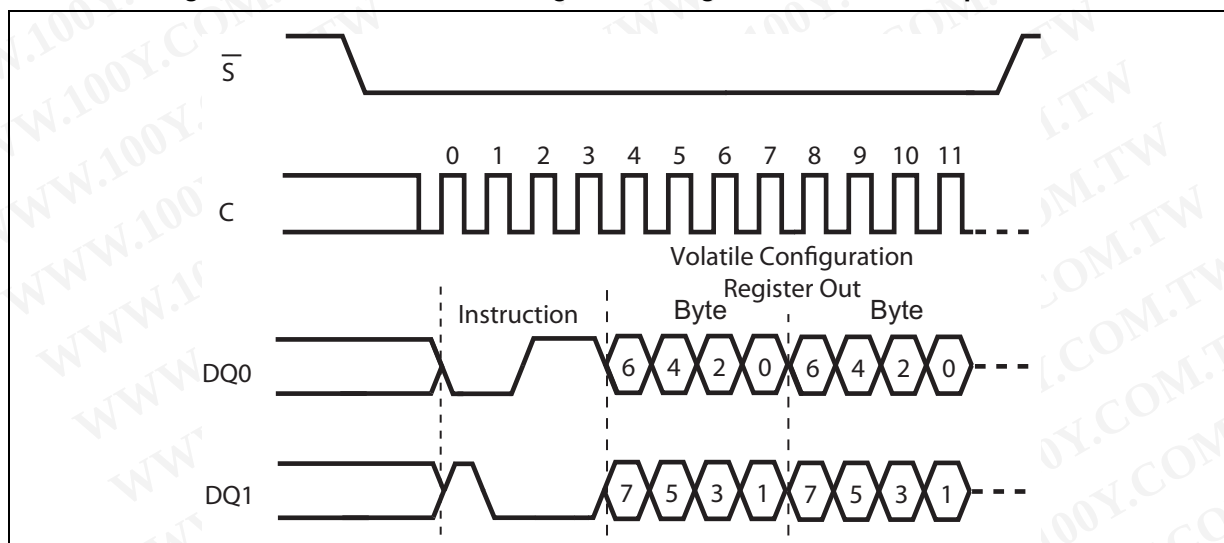
Except for the parallelizing of the instruction code and the input data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Write Non Volatile Configuration Register (WNVCR) instruction of the Extended SPI protocol.

Figure 65. Write NV Configuration Register instruction sequence DIO-SPI



9.2.22 Read Volatile Configuration Register

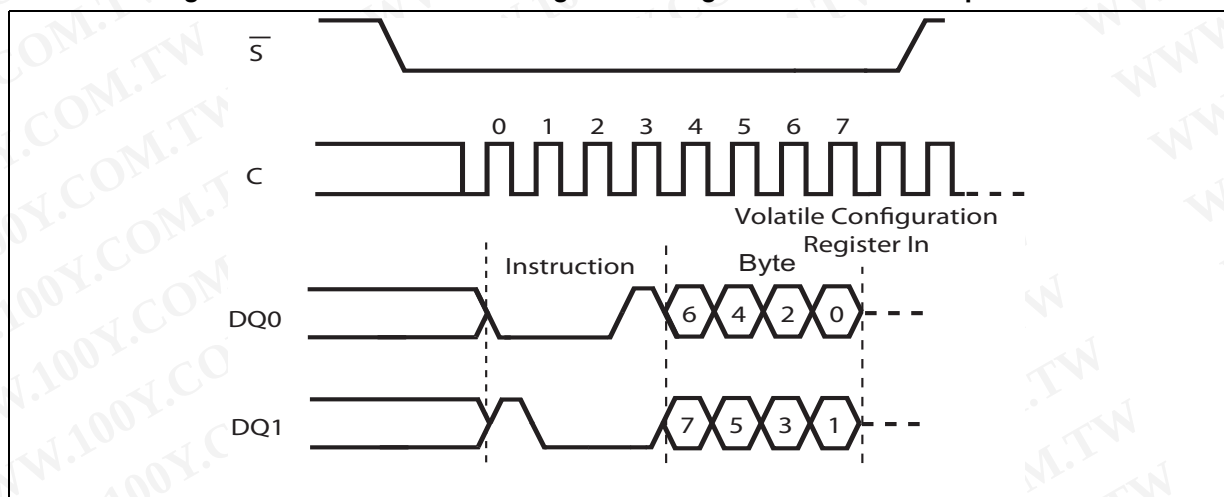
The Read Volatile Configuration Register (RDVCR) instruction allows the Volatile Configuration Register to be read. See [Table 5.: Volatile Configuration Register](#).

**Figure 66. Read Volatile Configuration Register instruction sequence DIO-SPI**

### 9.2.23 Write Volatile Configuration Register

The Write Volatile Configuration register (WRVCR) instruction allows new values to be written to the Volatile Configuration register. Before it can be accepted, a write enable (WREN) instruction must have been executed previously.

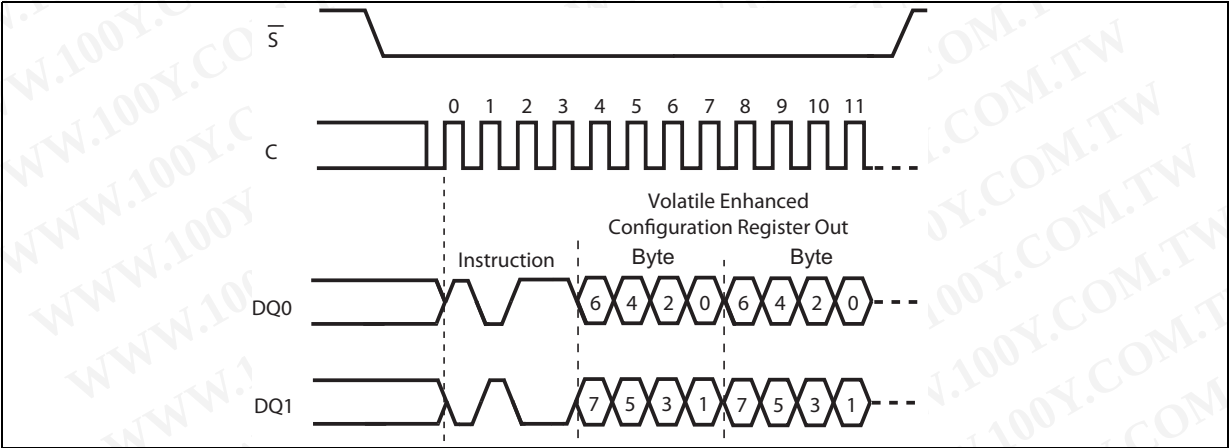
Except for the parallelizing of the instruction code and the input data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Write Volatile Configuration Register (WVCR) instruction of the Extended SPI protocol.

**Figure 67. Write Volatile Configuration Register instruction sequence DIO-SPI**

### 9.2.24 Read Volatile Enhanced Configuration Register

The Read Volatile Enhanced Configuration Register (RDVECR) instruction allows the Volatile Configuration Register to be read.

Figure 68. Read Volatile Enhanced Configuration Register instruction sequence DIO-SPI

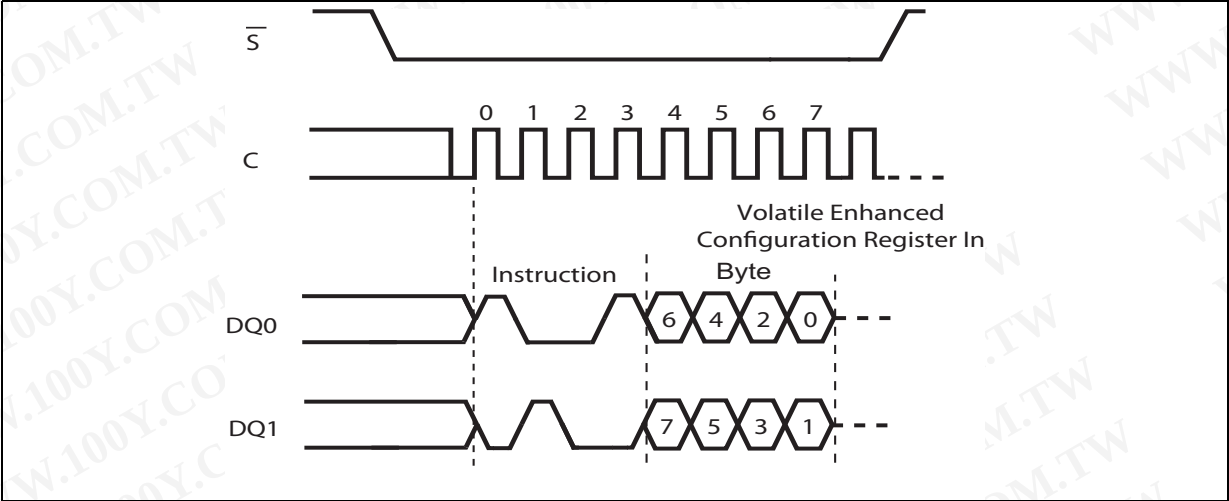


9.2.25 Write Volatile Enhanced Configuration Register

The Write Volatile Enhanced Configuration register (WRVECR) instruction allows new values to be written to the Volatile Enhanced Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code and the input data on the two pins DQ0 and DQ1, the instruction functionality is exactly the same as the Write Volatile Enhanced Configuration Register (WRVECR) instruction of the Extended SPI protocol.

Figure 69. Write Volatile Enhanced Configuration Register instruction sequence DIO-SPI



### 9.3 QIO-SPI Instructions

In QIO-SPI protocol, instructions, addresses and Input/Output data always run in parallel on four wires: DQ0, DQ1, DQ2 and DQ3 with the already mentioned exception of the modify instruction (erase and program) performed with the VPP=VPPH.

In the case of a Quad Command Fast Read (QCFR), Read OTP (ROTP), Read Lock Registers (RDLR), Read Status Register (RDSR), Read Flag Status Register (RFSR), Read NV Configuration Register (RDNVCR), Read Volatile Configuration Register (RDVCR), Read Volatile Enhanced Configuration Register (RDVECR), Read Serial Flash Discovery Parameter (RDSFDP), and Multiple I/O Read Identification (MIORDID) instruction, the shifted-in instruction sequence is followed by a data-out sequence. Chip Select ( $\bar{S}$ ) can be driven High after any bit of the data-out sequence is being shifted out.

In the case of a Quad Command Page Program (QCPP), Program OTP (POTP), Subsector Erase (SSE), Sector Erase (SE), Bulk Erase (BE), Program/Erase Suspend (PES), Program/Erase Resume (PER), Write Status Register (WRSR), Clear Flag Status Register (CLFSR), Write to Lock Register (WRLR), Write Volatile Configuration Register (WRVCR), Write Volatile Enhanced Configuration Register (WRVECR), Write NV Configuration Register (WRNVCR), Write Enable (WREN) or Write Disable (WRDI) instruction, Chip Select ( $\bar{S}$ ) must be driven High exactly at a byte boundary, otherwise the instruction is rejected, and is not executed.

All attempts to access the memory array during a Write Status Register cycle, a Write Non Volatile Configuration Register, a Program cycle or an Erase cycle are ignored, and the internal Write Status Register cycle, Write Non Volatile Configuration Register, Program cycle or Erase cycle continues unaffected, the only exception is the Program/Erase Suspend instruction (PES), that can be used to pause all the program and the erase cycles but the Program OTP (POTP), Write Status Register (WRSR), Bulk Erase (BE) and Write Non Volatile Configuration Register. The suspended program or erase cycle can be resumed by mean of the Program/Erase Resume instruction (PER). During the program/erase cycles also the polling instructions (to check if the internal modify cycle is finished by mean of the WIP bit of the Status Register or of the Program/Erase controller bit of the Flag Status register) are also accepted to allow the application checking the end of the internal modify cycles, of course these polling instructions don't affect the internal cycles performing.

Table 22. Instruction set: QIO-SPI protocol

| Instruction | Description                                    | One-byte Instruction Code (BIN) | One-byte Instruction Code (HEX) | Address bytes | Dummy clock cycle | Data bytes |
|-------------|------------------------------------------------|---------------------------------|---------------------------------|---------------|-------------------|------------|
| MIORDID     | Multiple I/O read identification               | 1010 1111                       | AFh                             | 0             | 0                 | 1 to 3     |
| RDSFDP      | Read Serial Flash Discovery Parameter          | 01011010                        | 5Ah                             | 3             | 10 <sup>(1)</sup> | 1 to ∞     |
| QCFR        | Quad Command Fast Read                         | 0000 1011                       | 0Bh                             | 3             | 10 <sup>(1)</sup> | 1 to ∞     |
|             |                                                | 0110 1011                       | 6Bh                             | 3             | 10 <sup>(1)</sup> | 1 to ∞     |
|             |                                                | 1110 1011                       | EBh                             | 3             | 10 <sup>(1)</sup> | 1 to ∞     |
| ROTP        | Read OTP (Read of OTP area)                    | 0100 1011                       | 4Bh                             | 3             | 10 <sup>(1)</sup> | 1 to 65    |
| WREN        | Write Enable                                   | 0000 0110                       | 06h                             | 0             | 0                 | 0          |
| WRDI        | Write Disable                                  | 0000 0100                       | 04h                             | 0             | 0                 | 0          |
| QCPP        | Quad Command Page Program                      | 0000 0010                       | 02h                             | 3             | 0                 | 1 to 256   |
|             |                                                | 0011 0010                       | 32h                             | 3             | 0                 | 1 to 256   |
|             |                                                | 0001 0010                       | 12h                             | 3             | 0                 | 1 to 256   |
| POTP        | Program OTP (Program of OTP area)              | 0100 0010                       | 42h                             | 3             | 0                 | 1 to 65    |
| SSE         | SubSector Erase                                | 0010 0000                       | 20h                             | 3             | 0                 | 0          |
| SE          | Sector Erase                                   | 1101 1000                       | D8h                             | 3             | 0                 | 0          |
| BE          | Bulk Erase                                     | 1100 0111                       | C7h                             | 0             | 0                 | 0          |
| PER         | Program/Erase Resume                           | 0111 1010                       | 7Ah                             | 0             | 0                 | 0          |
| PES         | Program/Erase Suspend                          | 0111 0101                       | 75h                             | 0             | 0                 | 0          |
| RDSR        | Read Status Register                           | 0000 0101                       | 05h                             | 0             | 0                 | 1 to ∞     |
| WRSR        | Write Status Register                          | 0000 0001                       | 01h                             | 0             | 0                 | 1          |
| RDLR        | Read Lock Register                             | 1110 1000                       | E8h                             | 3             | 0                 | 1 to ∞     |
| WRLR        | Write to Lock Register                         | 1110 0101                       | E5h                             | 3             | 0                 | 1          |
| RFSR        | Read Flag Status Register                      | 0111 0000                       | 70h                             | 0             | 0                 | 1 to ∞     |
| CLFSR       | Clear Flag Status Register                     | 0101 0000                       | 50h                             | 0             | 0                 | 0          |
| RDNVCR      | Read NV Configuration Register                 | 1011 0101                       | B5h                             | 0             | 0                 | 2          |
| WRNVCR      | Write NV Configuration Register                | 1011 0001                       | B1h                             | 0             | 0                 | 2          |
| RDVCR       | Read Volatile Configuration Register           | 1000 0101                       | 85h                             | 0             | 0                 | 1 to ∞     |
| WRVCR       | Write Volatile Configuration Register          | 1000 0001                       | 81h                             | 0             | 0                 | 1          |
| RDVECR      | Read Volatile Enhanced Configuration Register  | 0110 0101                       | 65h                             | 0             | 0                 | 1 to ∞     |
| WRVECR      | Write Volatile Enhanced Configuration Register | 0110 0001                       | 61h                             | 0             | 0                 | 1          |

1) The number of Dummy Clock cycles is configurable by the user.

### 9.3.1 Multiple I/O Read Identification (MIORDID)

The Multiple Input/Output Read Identification (MIORDID) instruction allows to read the device identification data in the QIO-SPI protocol:

- Manufacturer identification (1 byte)
- Device identification (2 bytes)

Unlike the RDID instruction of the Extended SPI protocol, the Multiple Input/Output instruction can not read the Unique ID code (UID) (17 bytes).

For further details on the manufacturer and device identification codes, see [9.1.1: Read Identification \(RDID\)](#).

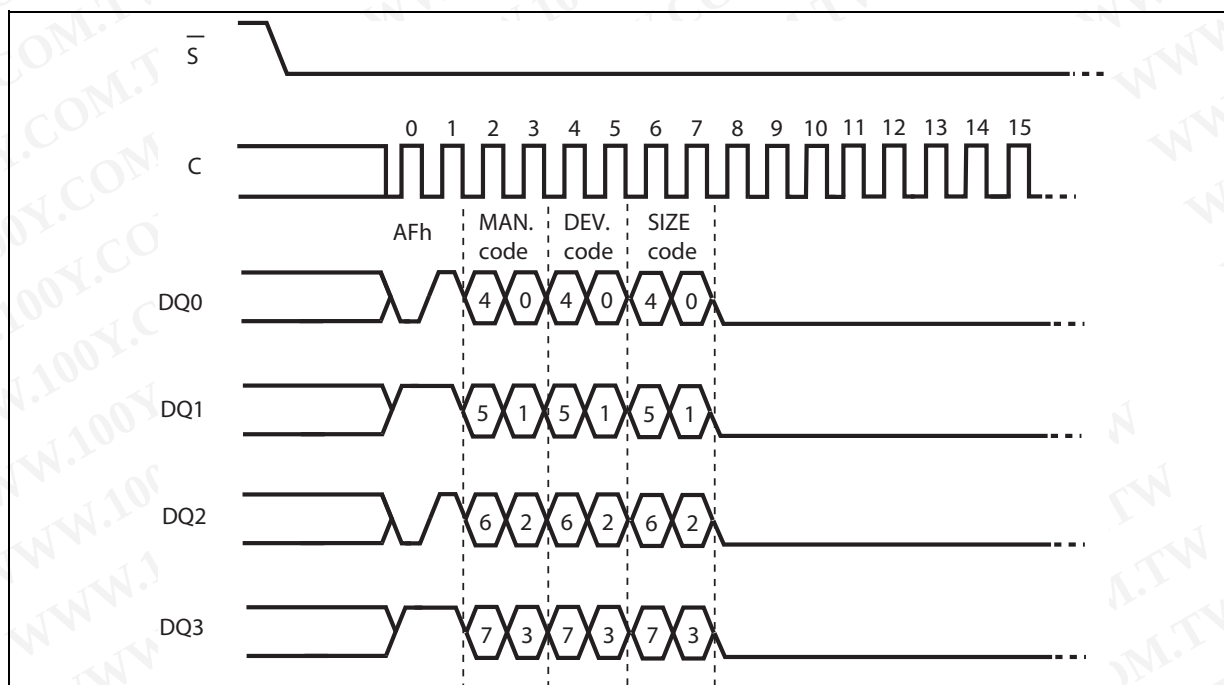
Any Multiple Input/Output Read Identification (MIORDID) instruction while an Erase or Program cycle is in progress, is not decoded, and has no effect on the cycle that is in progress.

The device is first selected by driving Chip Select ( $\overline{S}$ ) Low. Then, the 8-bit instruction code for the instruction is shifted in parallel on the 4 pins DQ0, DQ1, DQ2 and DQ3. After this, the 24-bit device identification, stored in the memory, will be shifted out on again in parallel on DQ0, DQ1, DQ2 and DQ3. The identification bits are shifted out 4 at a time during the falling edge of Serial Clock (C).

The Read Identification (RDID) instruction is terminated by driving Chip Select ( $\overline{S}$ ) High at any time during data output.

When Chip Select ( $\overline{S}$ ) is driven High, the device is put in the Standby Power mode. Once in the Standby Power mode, the device waits to be selected, so that it can receive, decode and execute instructions.

**Figure 70. Multiple I/O Read Identification instruction and data-out sequence QIO-SPI**

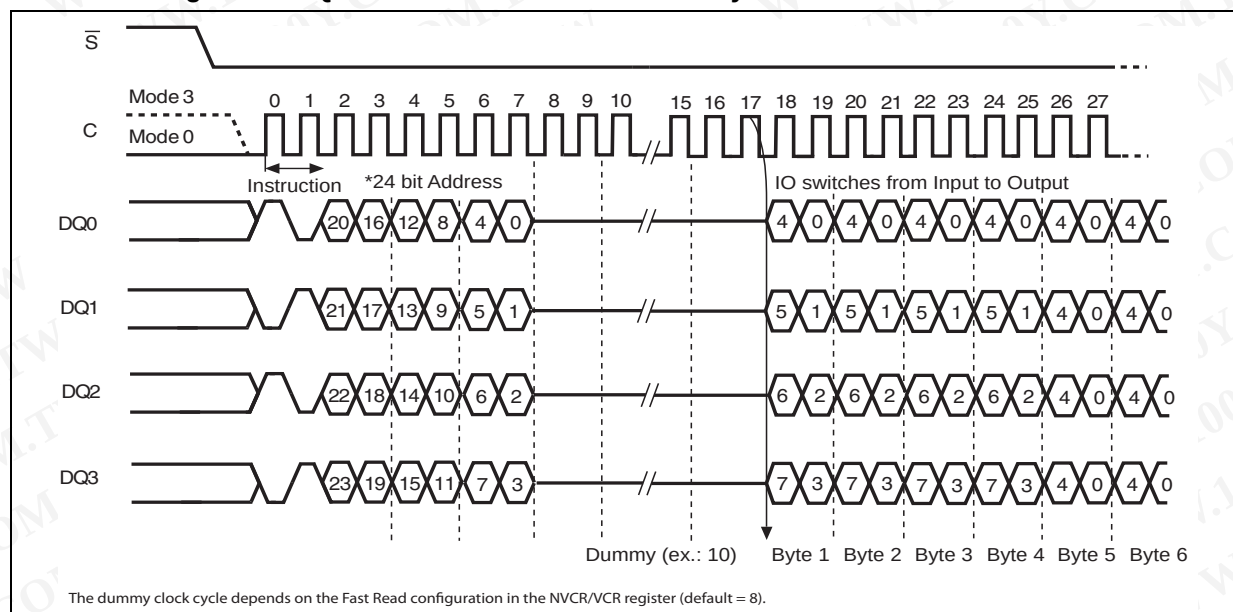


### 9.3.2 Read Serial Flash Discovery Parameter

The Read Serial Flash Discovery Parameter (RDSFDP) instruction allows reading the Serial Flash Discovery Parameter area (SFDP) in the QIO-SPI protocol. The instruction functionality is exactly the same as the Read Serial Flash Discovery Parameter instruction of the Extended SPI protocol. The only difference is that in the QIO-SPI protocol instruction code, address and output data are all parallelized on the four pins DQ0, DQ1, DQ2 and DQ3.

**Note:** The dummy byte bits can not be parallelized: 10 clock cycles are requested to perform the internal reading operation at highest frequency (108MHz).

**Figure 71. Quad Read Serial Flash Discovery Parameter**



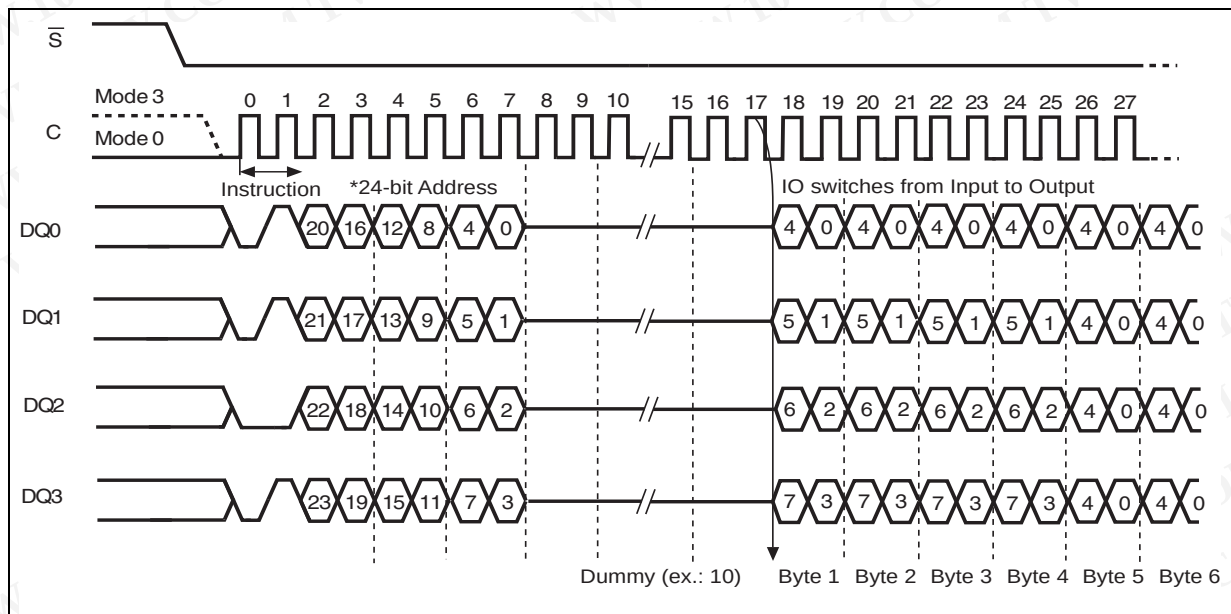
\*Address bits A[23:11] are "Don't Care."

### 9.3.3 Quad Command Fast Read (QCFR)

The Quad Command Fast Read (QCFR) instruction allows to read the memory in QIO-SPI protocol, parallelizing the instruction code, the address and the output data on four pins (DQ0, DQ1, DQ2 and DQ3). The Quad Command Fast Read (QCFR) instruction can be issued, after the device is set in QIO-SPI mode, by sending to the memory indifferently one of the 3 instructions codes: 0Bh, 6Bh or EBh, the effect is exactly the same. The 3 instruction codes are all accepted to help the application code porting from Extended SPI protocol to QIO-SPI protocol.

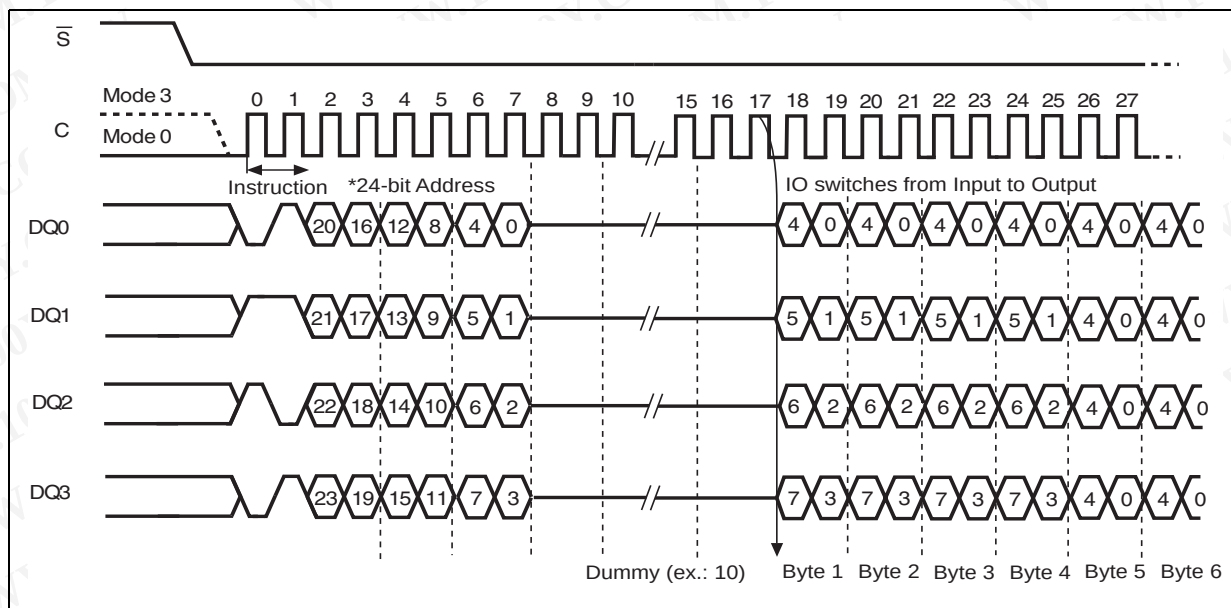
Apart for the parallelizing on four pins of the instruction code, the Quad Command Fast Read instruction functionality is exactly the same as the Quad I/O Fast Read of the Extended SPI protocol.

**Figure 72. Quad Command Fast Read instruction and data-out sequence QIO-SPI, 0Bh**



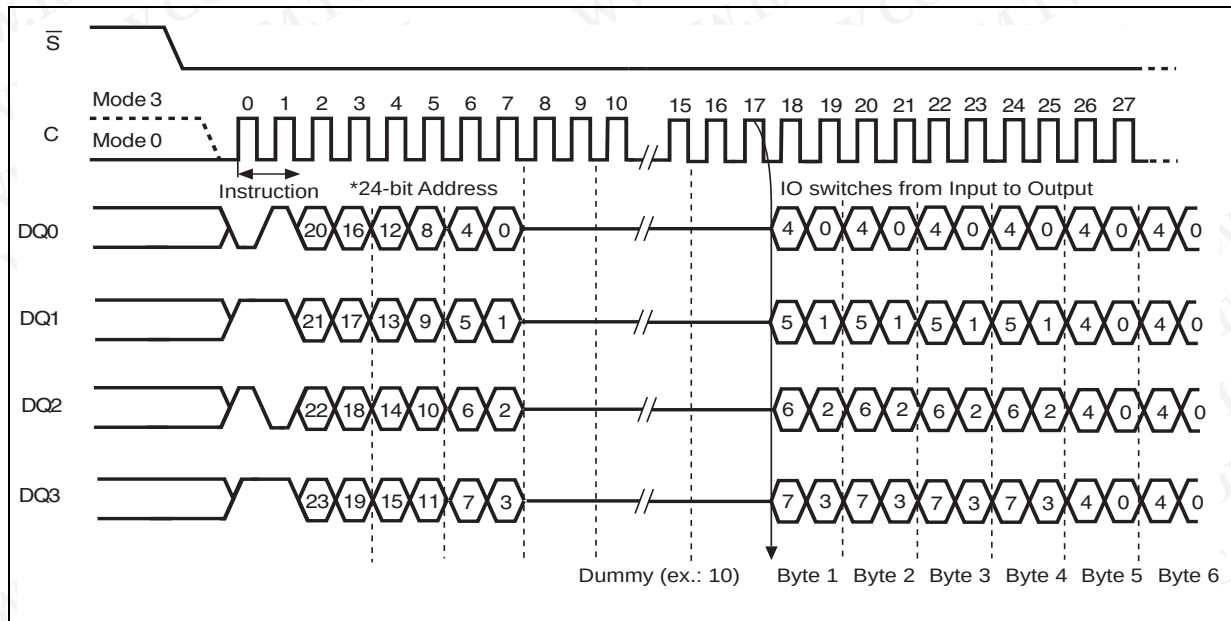
\*Address bits A23 and A22 are "Don't Care."

**Figure 73. Quad Command Fast Read instruction and data-out sequence QIO-SPI, 6Bh**



\*Address bits A23 and A22 are "Don't Care."

**Figure 74. Quad Command Fast Read instruction and data-out sequence QIO-SPI, EBh**



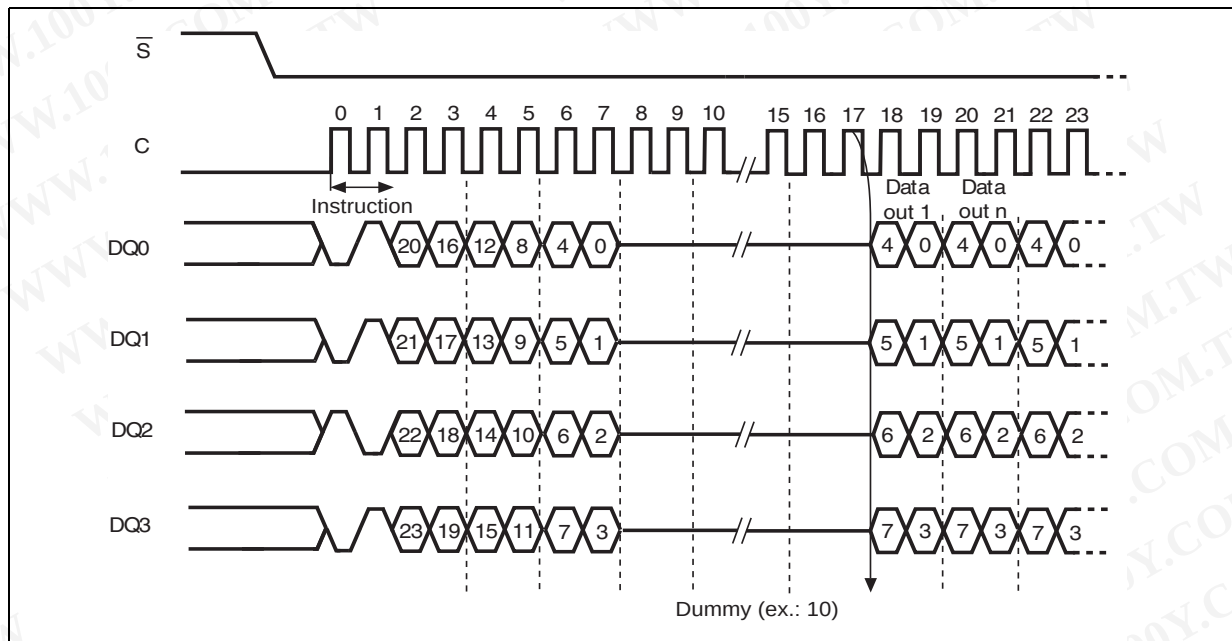
\*Address bits A23 and A22 are "Don't Care."

### 9.3.4 Read OTP (ROTP)

The Read OTP (ROTP) instruction is used to read the 64 bytes OTP area in the QIO-SPI protocol. The instruction functionality is exactly the same as the Read OTP instruction of the Extended SPI protocol. The only difference is that in the QIO-SPI protocol instruction code, address and output data are all parallelized on the four pins DQ0, DQ1, DQ2 and DQ3.

**Note:** The dummy byte bits can not be parallelized: 10 clock cycles are requested to perform the internal reading operation at highest frequency (108MHz).

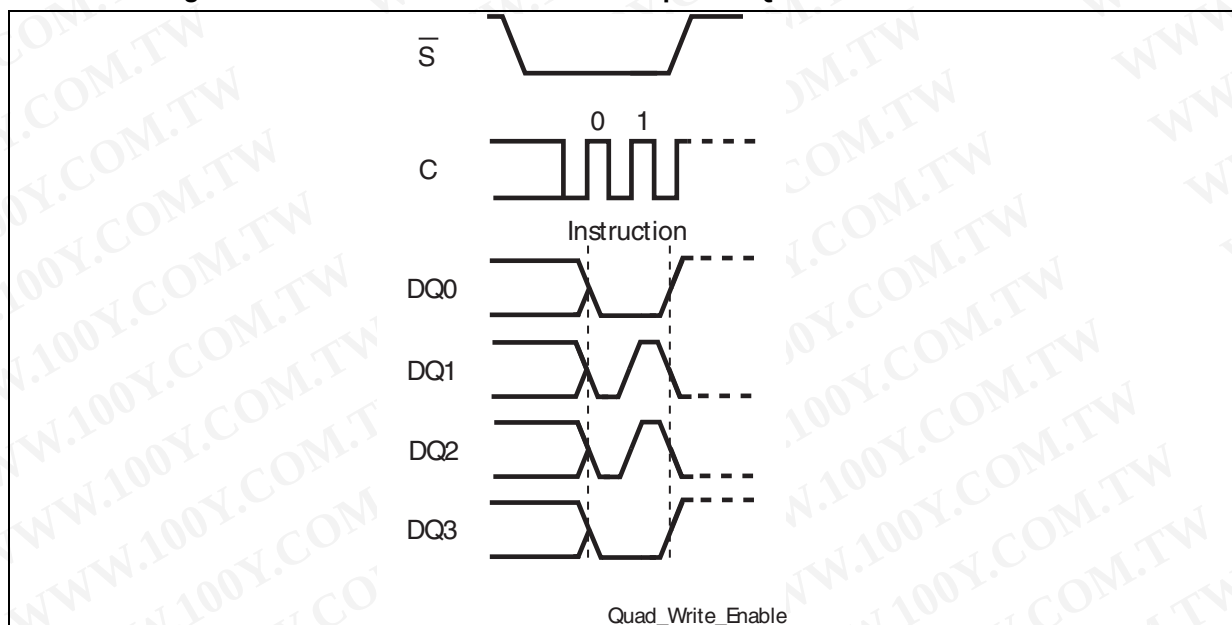
Figure 75. Read OTP instruction and data-out sequence QIO-SPI



### 9.3.5 Write Enable (WREN)

The Write Enable (WREN) instruction sets the Write Enable Latch (WEL) bit. Except for the parallelizing of the instruction code on the four pins  $DQ0$ ,  $DQ1$ ,  $DQ2$  and  $DQ3$ , the instruction functionality is exactly the same as the Write Enable instruction of the Extended SPI protocol.

Figure 76. Write Enable instruction sequence QIO-SPI

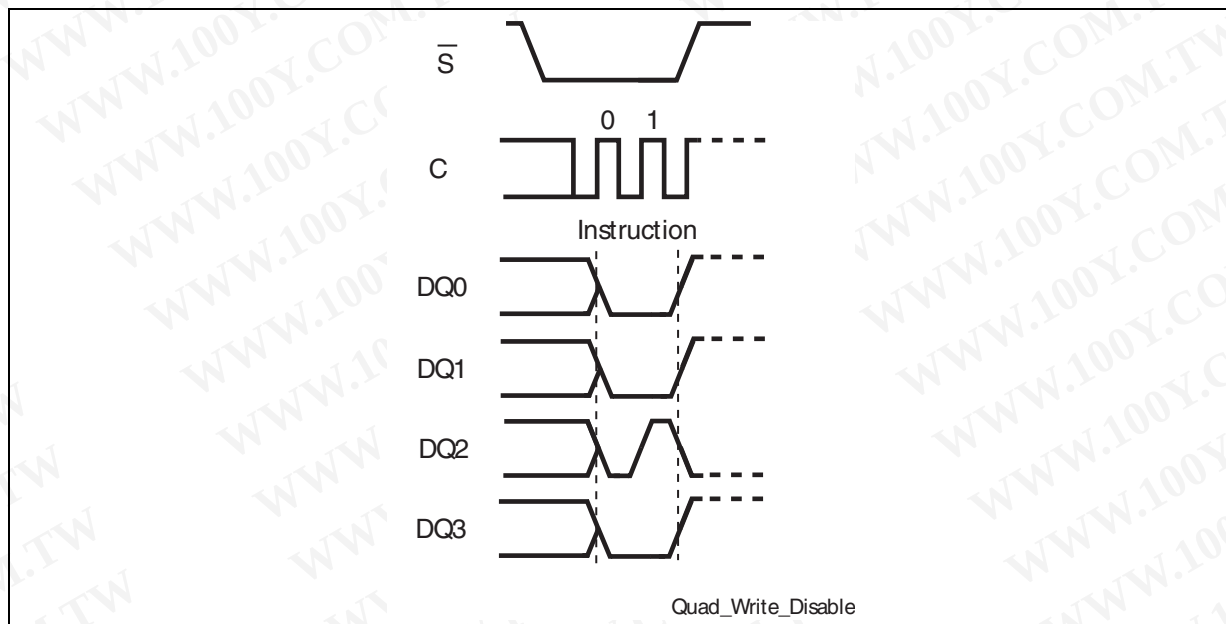


### 9.3.6 Write Disable (WRDI)

The Write Disable (WRDI) instruction resets the Write Enable Latch (WEL) bit.

Except for the parallelizing of the instruction code on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Write Disable (WRDI) instruction of the Extended SPI protocol.

**Figure 77. Write Disable instruction sequence QIO-SPI**



### 9.3.7 Quad Command Page Program (QCPP)

The Quad Command Page Program (QCPP) instruction allows to program the memory content in QIO-SPI protocol, parallelizing the instruction code, the address and the input data on four pins (DQ0, DQ1, DQ2 and DQ3). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. The Quad Command Page Program (QCPP) instruction can be issued, when the device is set in QIO-SPI mode, by sending to the memory indifferently one of the 3 instructions codes: 02h, 12h or 32h, the effect is exactly the same. The 3 instruction codes are all accepted to help the application code porting from Extended SPI protocol to QIO-SPI protocol.

Apart for the parallelizing on four pins of the instruction code, the Quad Command Page Program instruction functionality is exactly the same as the Quad Input Extended Fast Program of the Extended SPI protocol.

Figure 78. Quad Command Page Program instruction sequence QIO-SPI, 02h

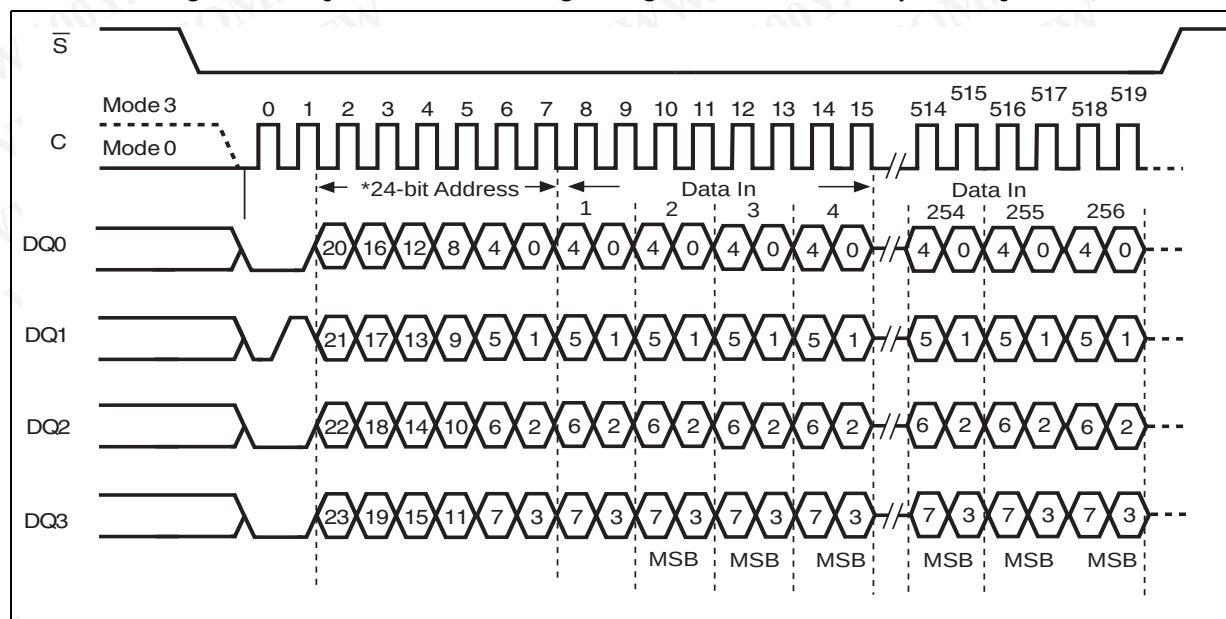
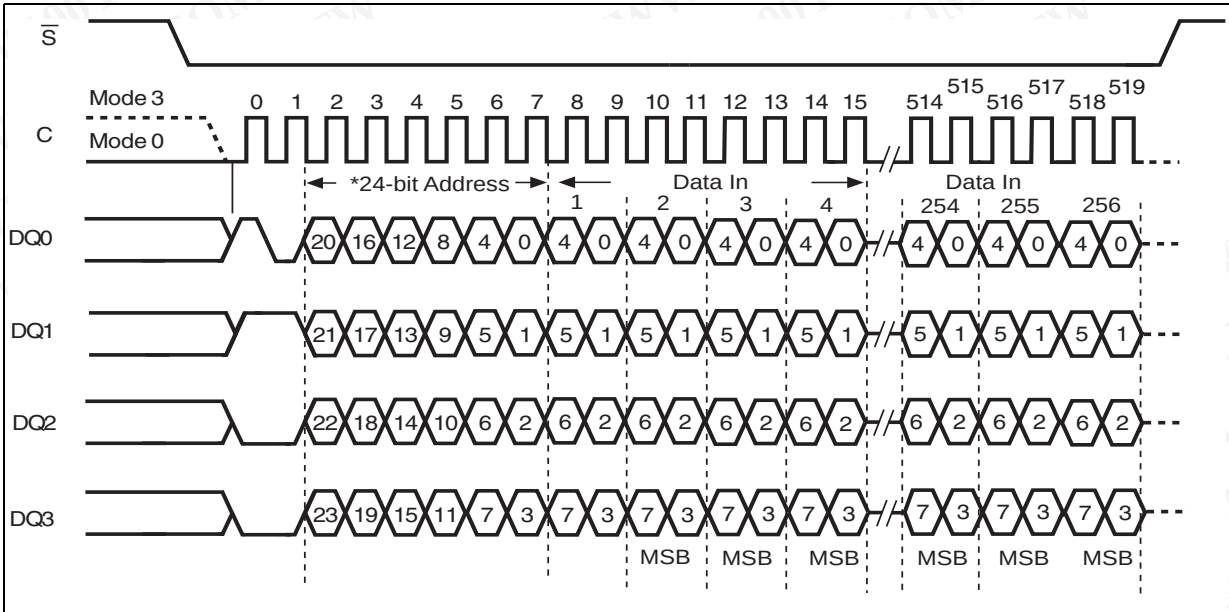


Figure 80. Quad Command Page Program instruction sequence QIO-SPI, 32h



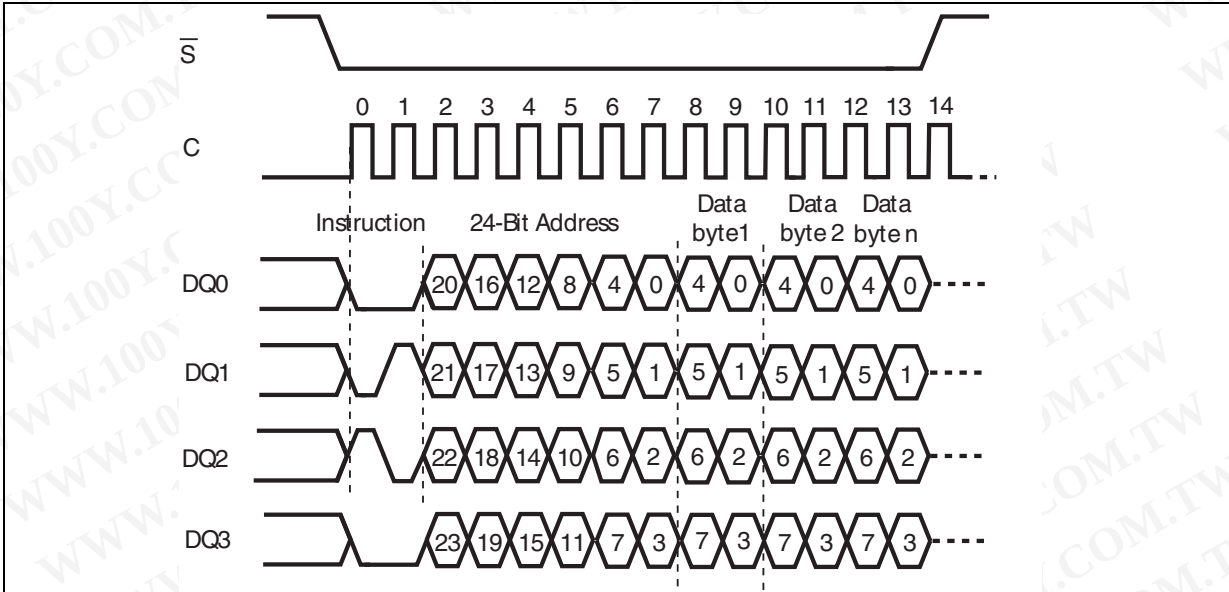
\*Address bits A[23:22] are "Don't Care."

### 9.3.8 Program OTP instruction (POTP)

The Program OTP instruction (POTP) is used to program at most 64 bytes to the OTP memory area (by changing bits from 1 to 0, only). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code, address and input data on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality (as well as the locking OTP method) is exactly the same as the Program OTP (POTP) instruction of the Extended SPI protocol.

Figure 81. Program OTP instruction sequence QIO-SPI

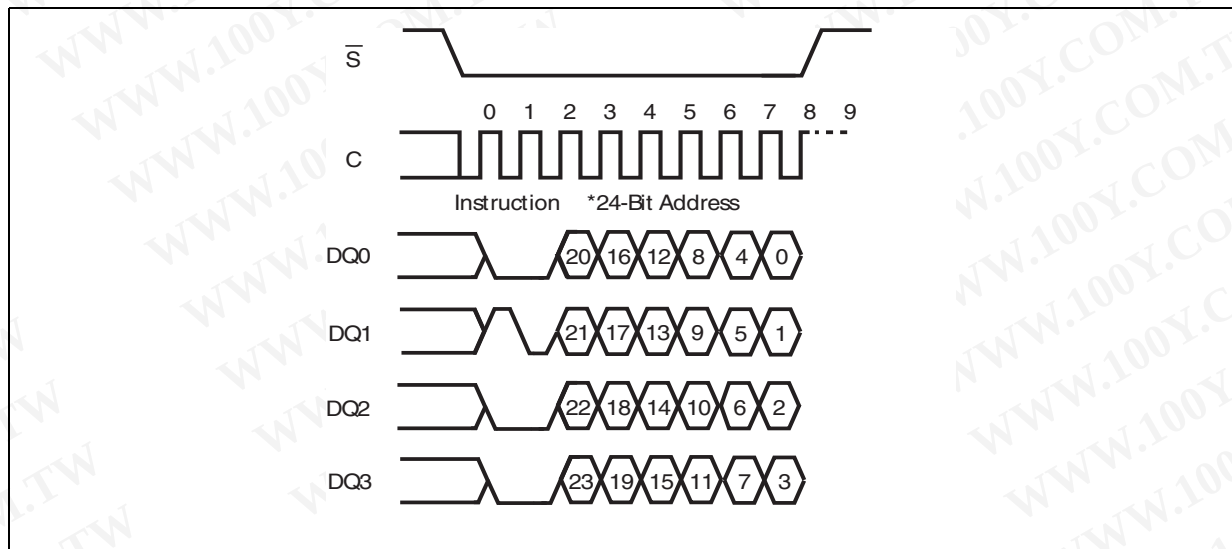


### 9.3.9 Subsector Erase (SSE)

The Subsector Erase (SSE) instruction sets to '1' (FFh) all bits inside the chosen subsector. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code and the address on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Subsector Erase (SSE) instruction of the Extended SPI protocol.

**Figure 82. Subsector Erase instruction sequence QIO-SPI**



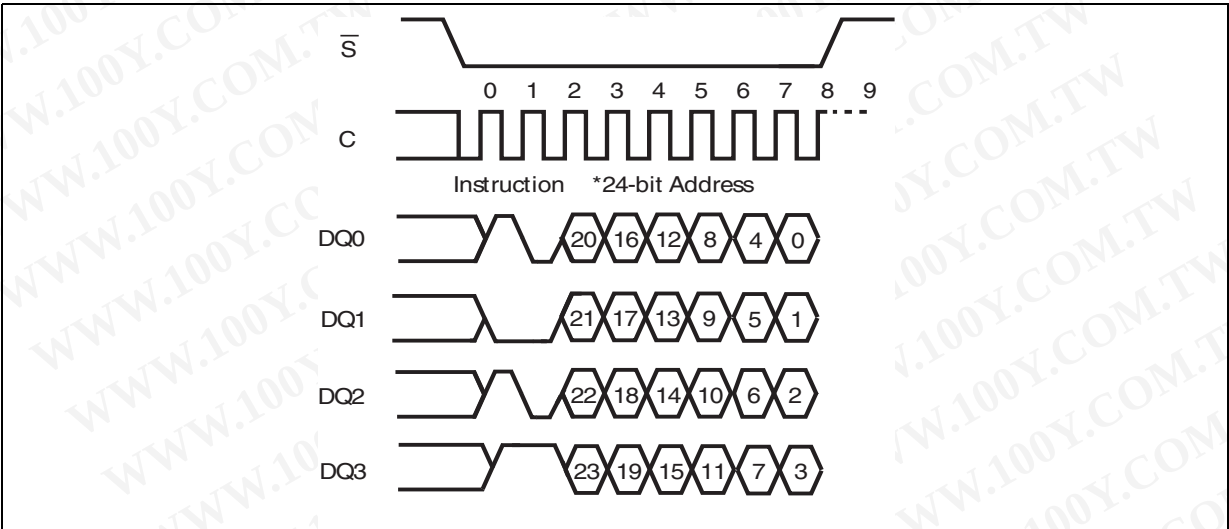
\*Address bits A[23:22] are "Don't Care."

### 9.3.10 Sector Erase (SE)

The Sector Erase (SE) instruction sets to '1' (FFh) all bits inside the chosen sector. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code and the address on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Sector Erase (SE) instruction of the Extended SPI protocol.

Figure 83. Sector Erase instruction sequence QIO-SPI



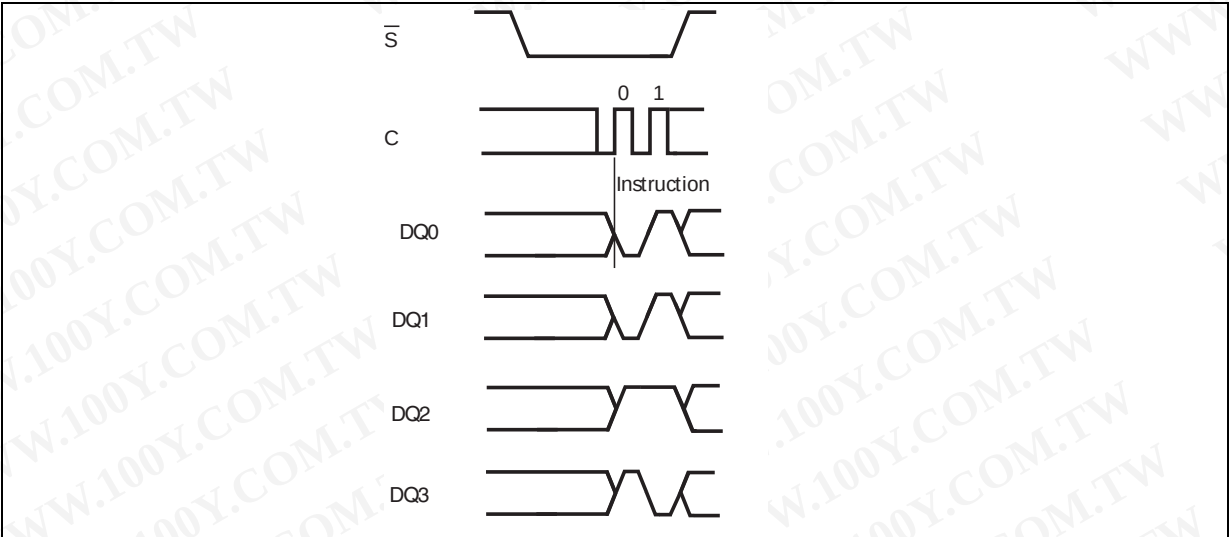
\*Address bits A[23:22] are "Don't Care."

### 9.3.11 Bulk Erase (BE)

The Bulk Erase (BE) instruction sets all bits to '1' (FFh). Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for parallelizing the instruction code on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Bulk Erase (BE) instruction of the Extended SPI protocol.

Figure 84. Bulk Erase instruction sequence QIO-SPI



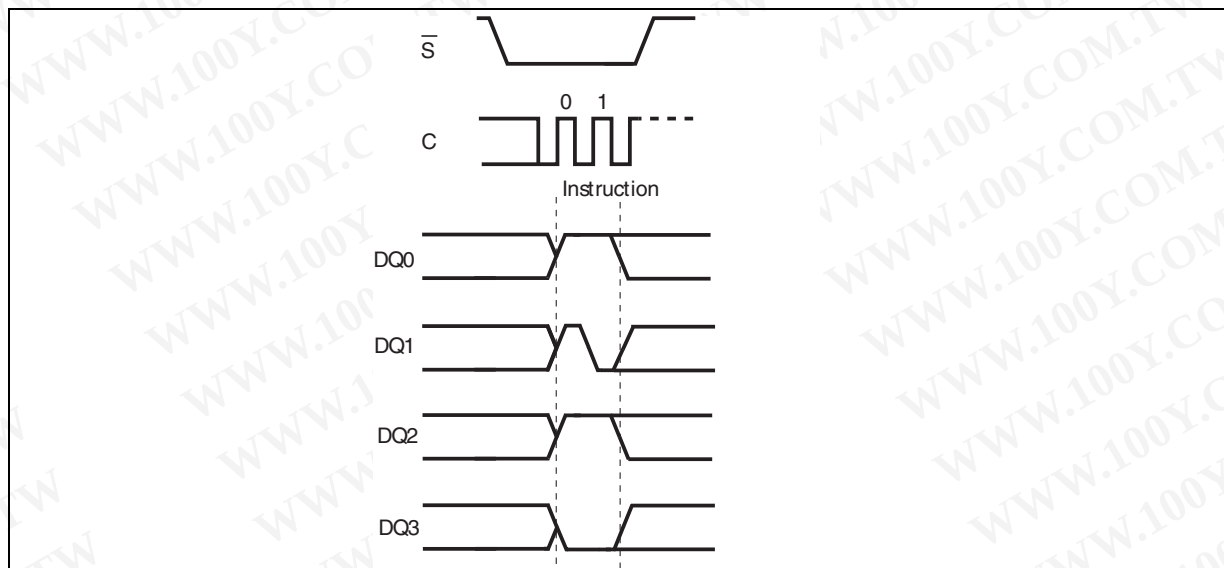
### 9.3.12 Program/Erase Suspend

The Program/Erase Suspend (PES) instruction allows the controller to interrupt a Program or an Erase instruction. In particular, Subsector Erase (SSE), Sector Erase (SE), and Dual Command Page Program (DCPP) can be suspended and resumed while Bulk Erase (BE),

Write Status Register (WRSR), Write Non Volatile Configuration Register (WRNVCR), and Program OTP (POTP) cannot be suspended.

Except for parallelizing the instruction code on four pins (DQ0, DQ1, DQ2, DQ3) the instruction functionality is the same as the Program/Erase Suspend (PES) instruction of the Extended SPI protocol.

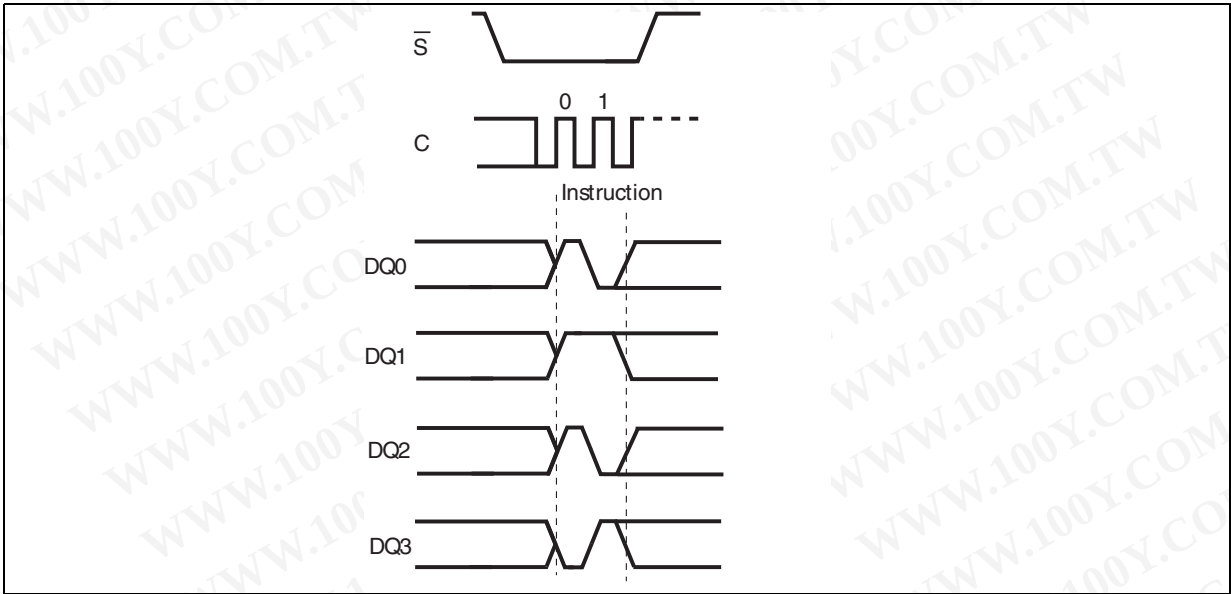
**Figure 85. Program/Erase Suspend instruction sequence QIO-SPI**



### 9.3.13 Program/Erase Resume

After a Program/Erase suspend instruction, a Program/Erase Resume instruction is required to continue performing the suspended Program or Erase sequence. Except for parallelizing the instruction code on four pins (DQ0, DQ1, DQ2, DQ3) the instruction functionality is the same as the Program/Erase Resume (PER) instruction of the Extended SPI protocol.

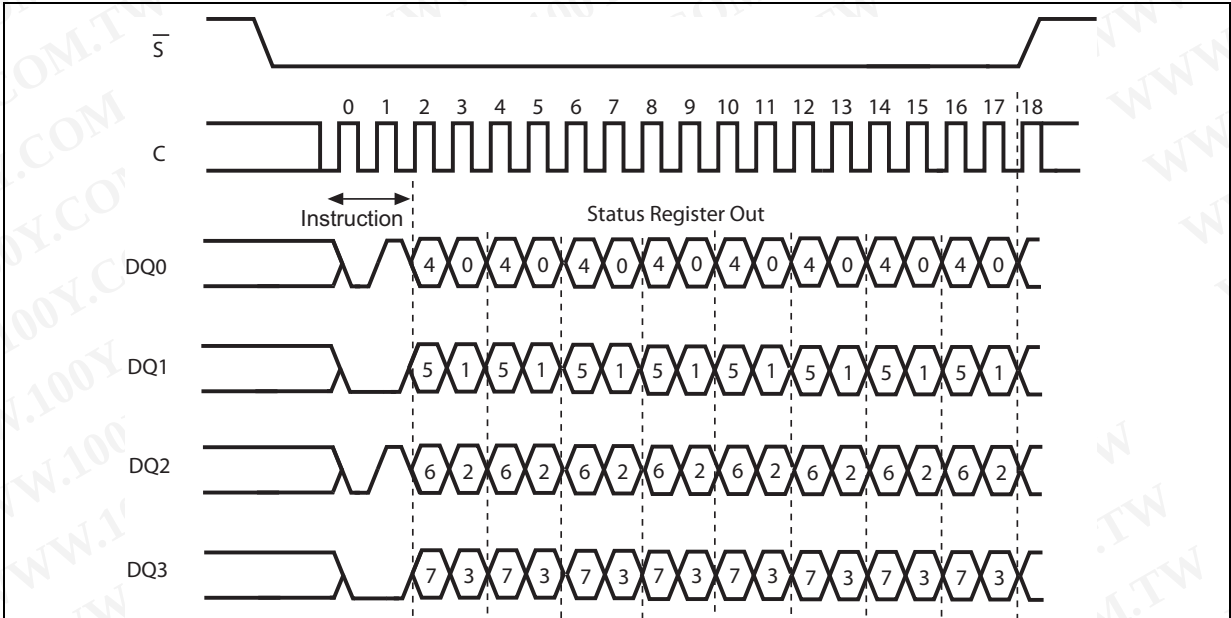
Figure 86. Program/Erase Resume instruction sequence QIO-SPI



### 9.3.14 Read Status Register (RDSR)

The Read Status Register (RDSR) instruction allows the Status Register to be read. Except for the parallelizing of the instruction code and the output data on the four pins  $DQ0$ ,  $DQ1$ ,  $DQ2$  and  $DQ3$ , the instruction functionality is exactly the same as the Read Status Register (RDSR) instruction of the Extended SPI protocol.

Figure 87. Read Status Register instruction sequence QIO-SPI

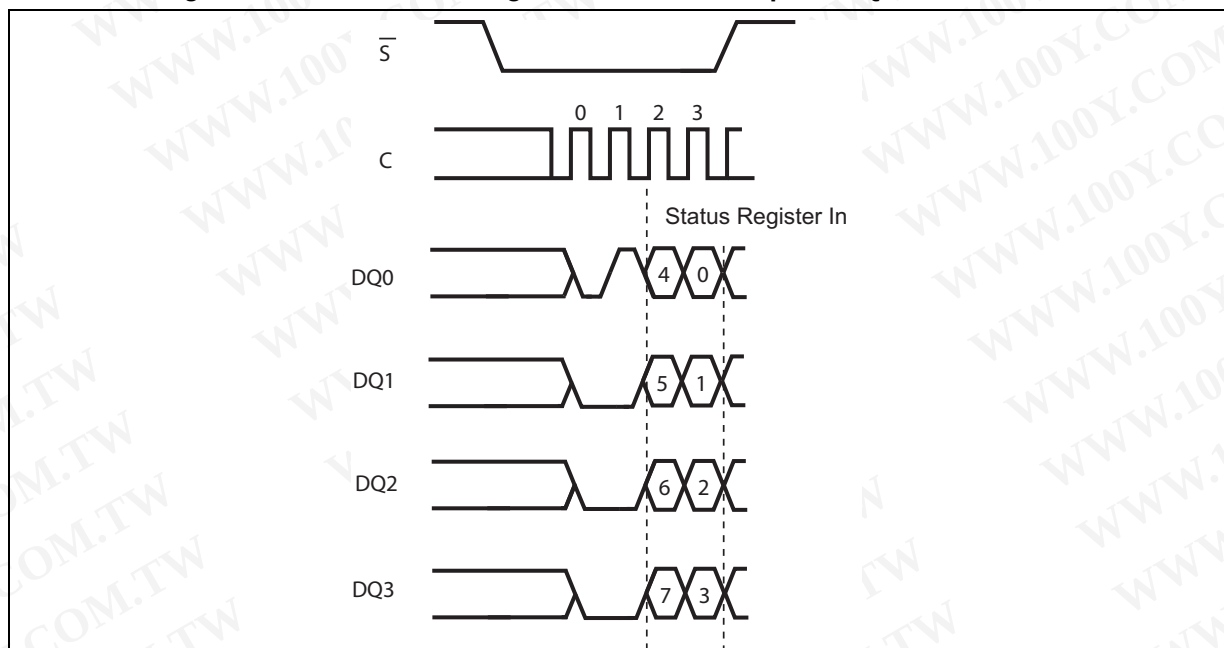


### 9.3.15 Write status register (WRSR)

The write status register (WRSR) instruction allows new values to be written to the status register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed.

The instruction code and the input data are sent on four pins DQ0, DQ1, DQ2 and DQ3. The instruction functionality is exactly the same as the Write Status Register (WRSR) instruction of the Extended SPI protocol. However, the protection feature management is different. In particular, once SRWD bit is set to '1' the device enters in the hardware protected mode (HPM) independently from Write Protect (W/VPP) signal value. To exit the HPM mode is needed to switch temporarily to the Extended SPI protocol.

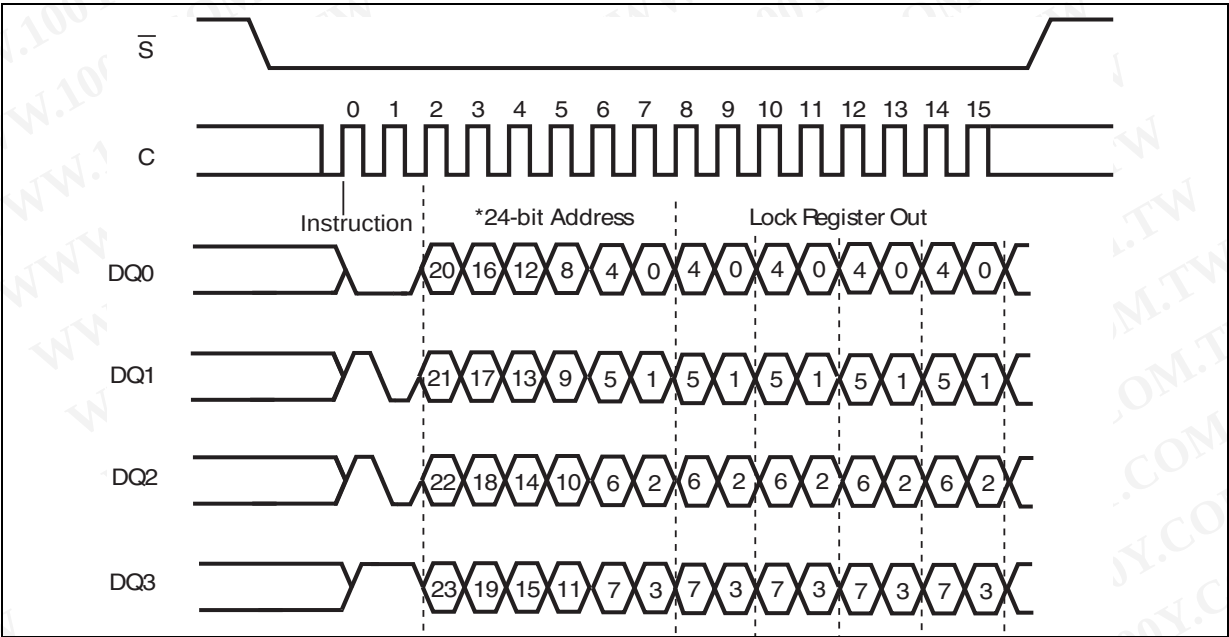
**Figure 88. Write Status Register instruction sequence QIO-SPI**



### 9.3.16 Read Lock Register (RDLR)

The Read Lock Register instruction is used to read the lock register content. Apart from parallelizing the instruction code, the address, and the output data on four pins (DQ0, DQ1, DQ2, DQ3) the instruction functionality is the same as the Read Lock Register (RDLR) instruction of the Extended SPI protocol.

Figure 89. Read Lock Register instruction and data-out sequence QIO-SPI



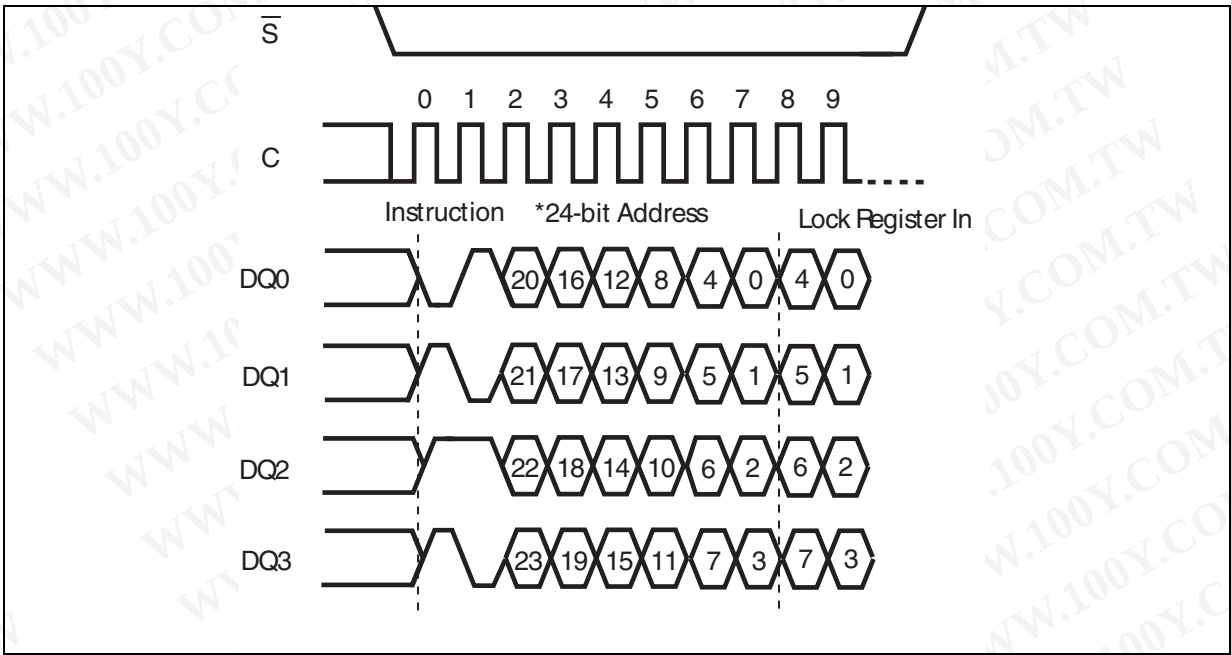
\*Address bits A23 and A22 are "Don't Care."

### 9.3.17 Write to Lock Register (WRLR)

The Write to Lock Register (WRLR) instruction allows bits to be changed in the Lock Registers. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code, the address and the input data on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Write to Lock Register (WRLR) instruction of the Extended SPI protocol.

Figure 90. Write to Lock Register instruction sequence QIO-SPI

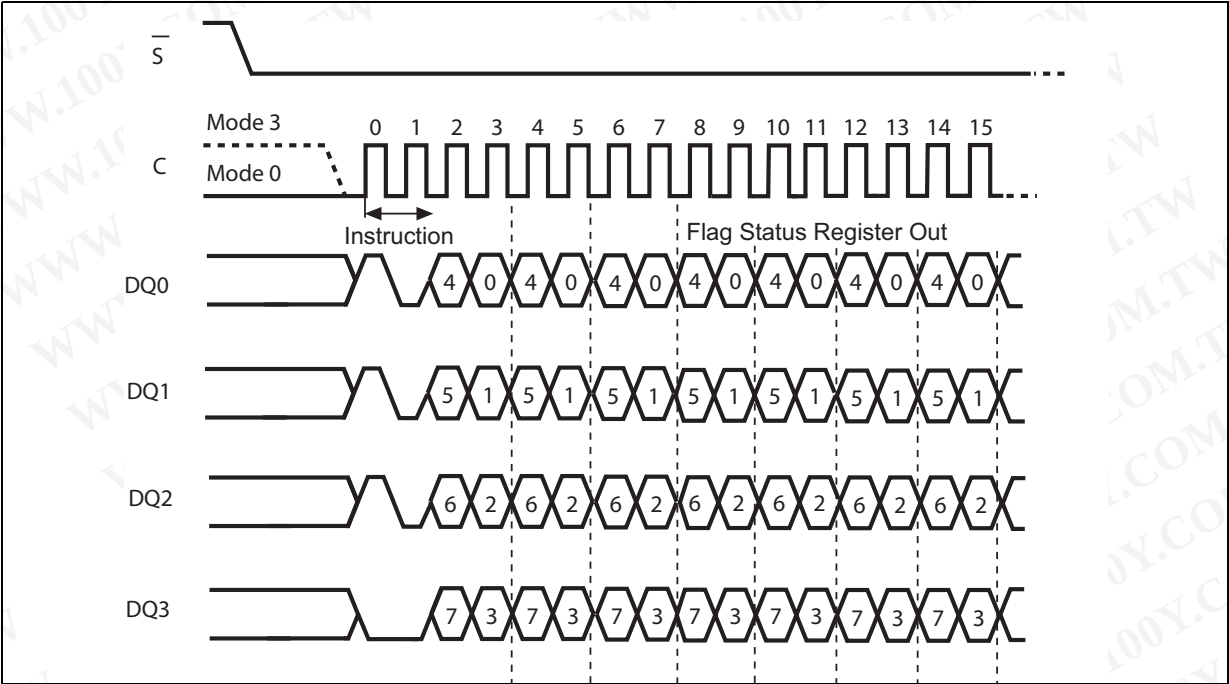


\*Address bits A23 and A22 are "Don't Care."

### 9.3.18 Read Flag Status Register

The Read Flag Status Register (RFSR) instruction allows the Flag Status Register to be read. Except for the parallelizing of the instruction code and the output data on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Read Flag Status Register (RFSR) instruction of the Extended SPI protocol.

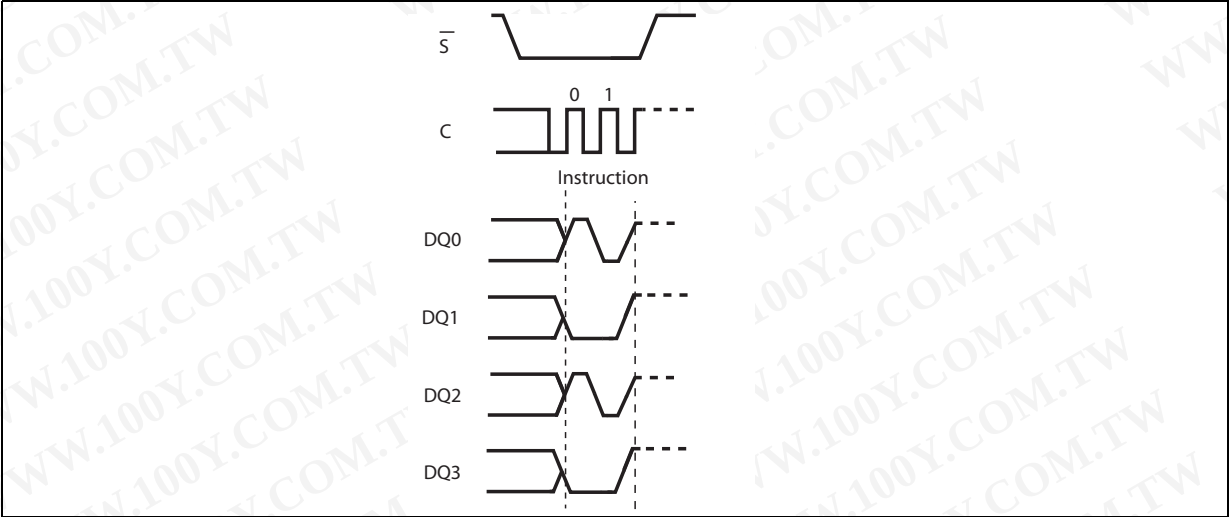
Figure 91. Read Flag Status Register instruction sequence QIO-SPI



9.3.19 Clear Flag Status Register

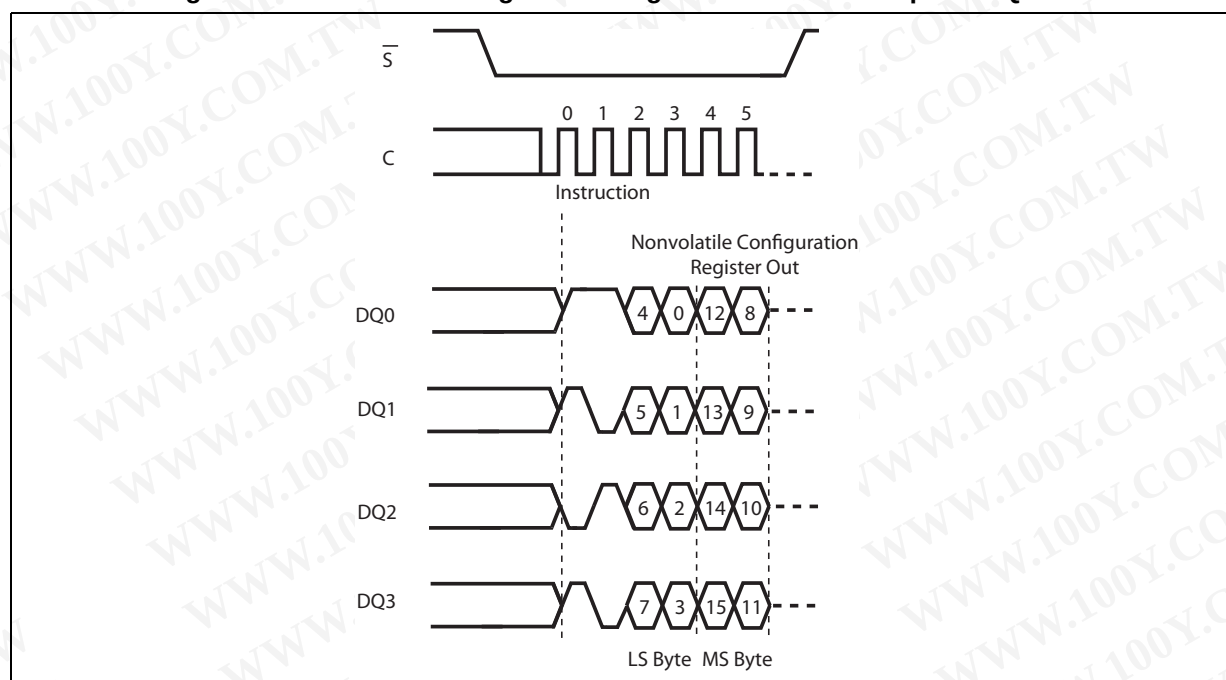
The Clear Flag Status Register (CLFSR) instruction reset the error Flag Status Register bits (Erase Error bit, Program Error bit, VPP Error bit, Protection Error bit). It is not necessary to set the WEL bit before the Clear Flag Status Register instruction is executed. The WEL bit will be unchanged after this command is executed.

Figure 92. Clear Flag Status Register instruction sequence QIO-SPI



9.3.20 Read NV Configuration Register

The Read Non Volatile Configuration Register (RDNVCR) instruction allows the Non Volatile Configuration Register to be read.

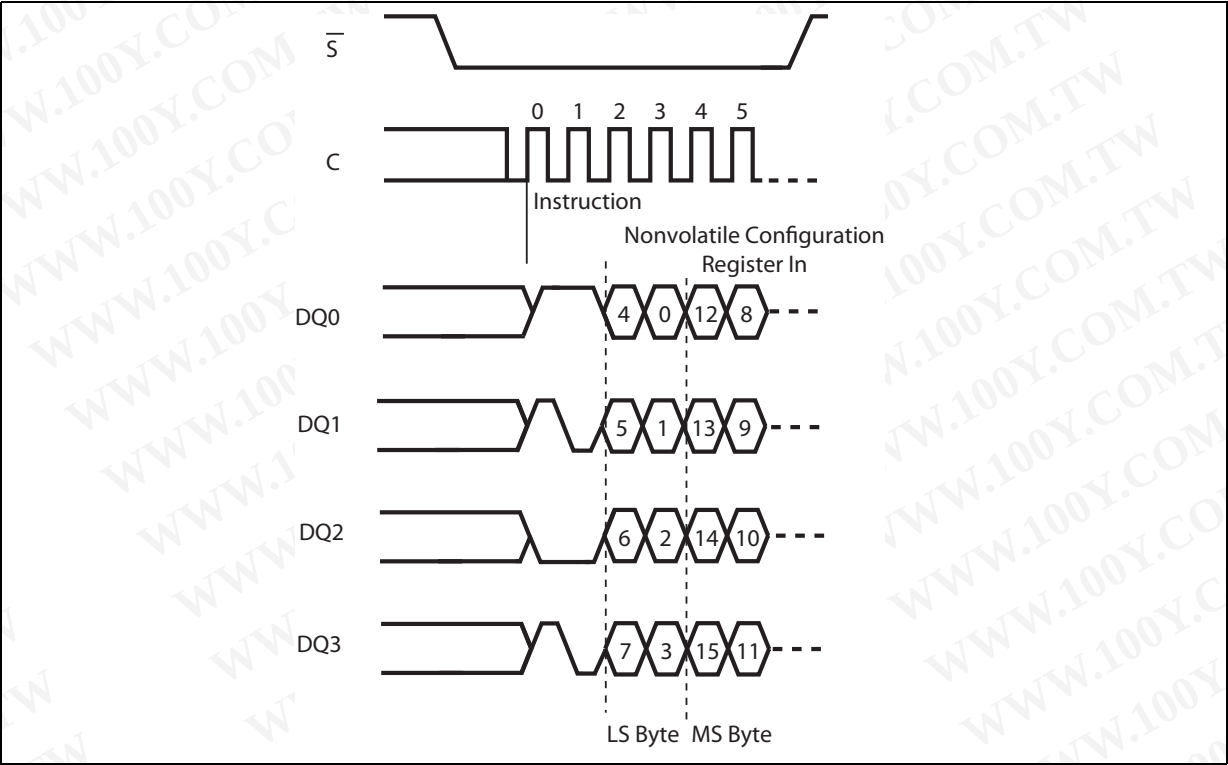
**Figure 93. Read NV Configuration Register instruction sequence QIO-SPI**

### 9.3.21 Write NV Configuration Register

The Write Non Volatile Configuration register (WRNVCR) instruction allows new values to be written to the Non Volatile Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed.

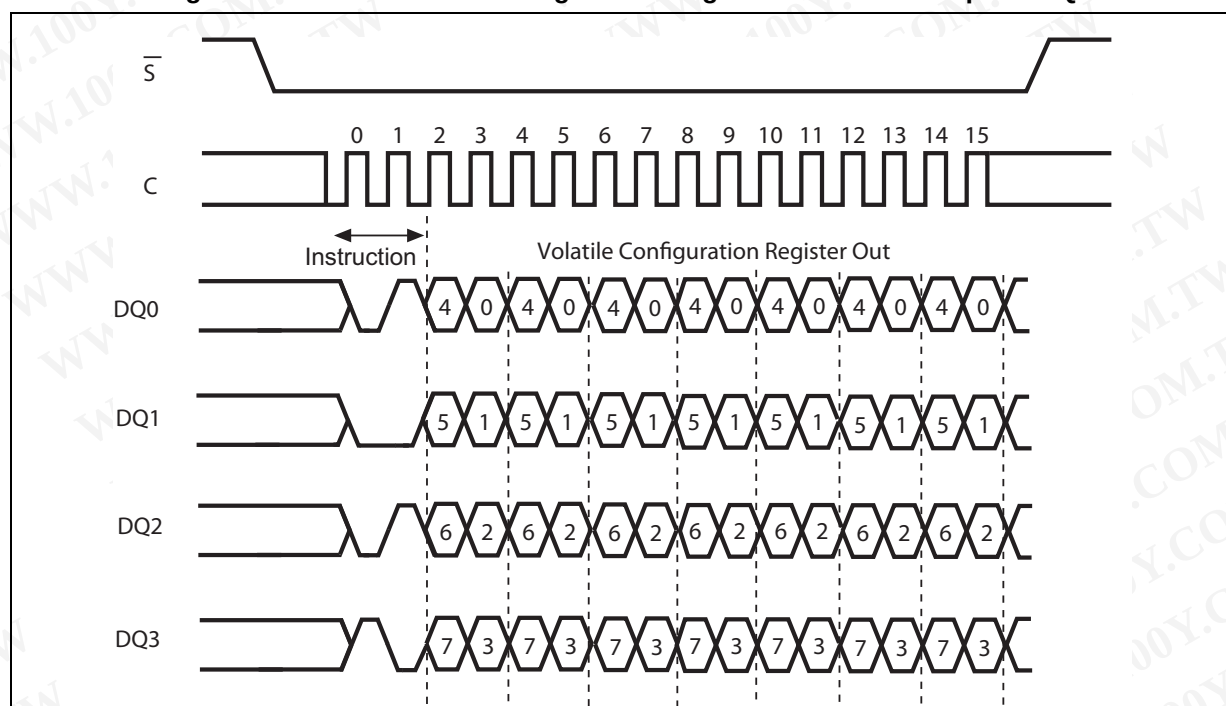
Except for the parallelizing of the instruction code and the input data on the four pins  $DQ0$ ,  $DQ1$ ,  $DQ2$  and  $DQ3$ , the instruction functionality is exactly the same as the Write Non Volatile Configuration Register (WRNVCR) instruction of the Extended SPI protocol.

Figure 94. Write NV Configuration Register instruction sequence QIO-SPI



9.3.22 Read Volatile Configuration Register

The Read Volatile Configuration Register (RDVCR) instruction allows the Volatile Configuration Register to be read.

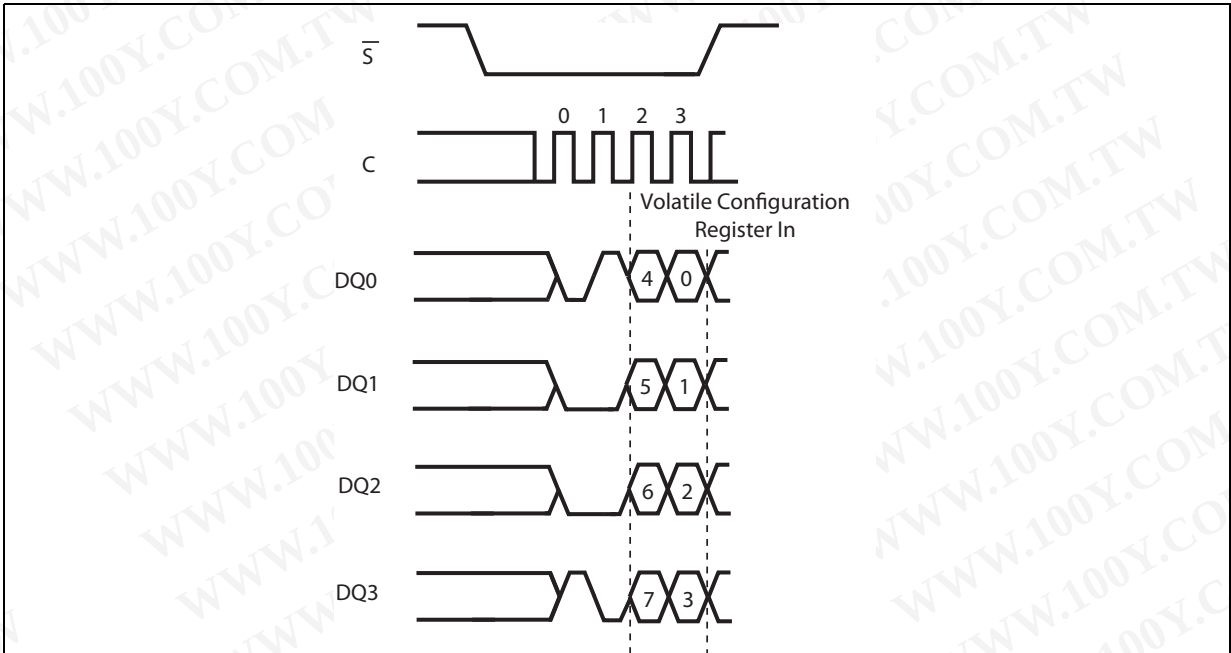
**Figure 95. Read Volatile Configuration Register instruction sequence QIO-SPI**

### 9.3.23 Write Volatile Configuration Register

The Write Volatile Configuration register (WRVCR) instruction allows new values to be written to the Volatile Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code and the input data on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Write Volatile Configuration Register (WRVCR) instruction of the Extended SPI protocol.

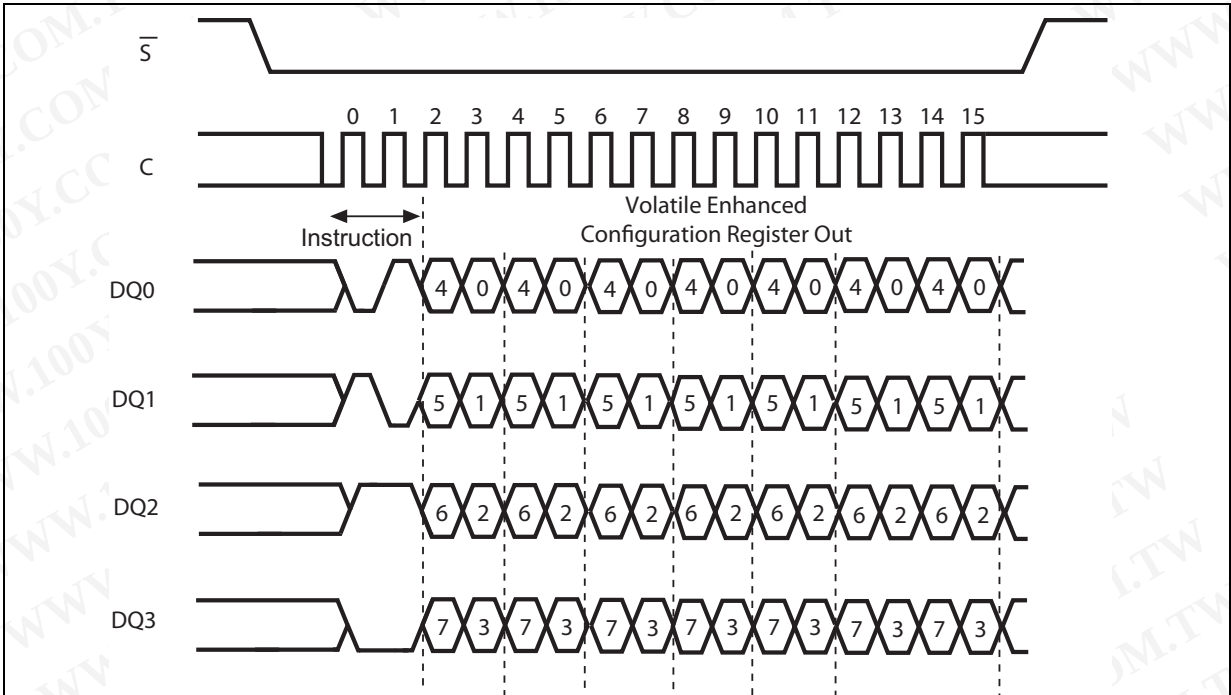
Figure 96. Write Volatile Configuration Register instruction sequence QIO-SPI



### 9.3.24 Read Volatile Enhanced Configuration Register

The Read Volatile Enhanced Configuration Register (RDVECR) instruction allows the Volatile Configuration Register to be read.

Figure 97. Read Volatile Enhanced Configuration Register instruction sequence QIO-SPI

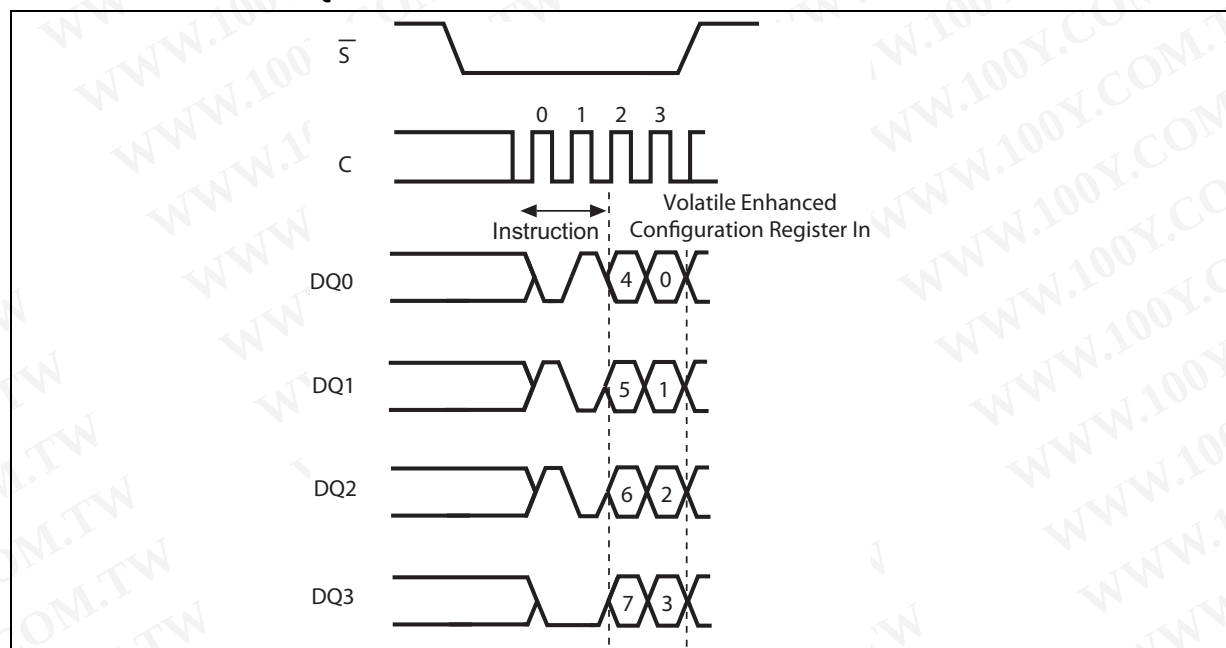


### 9.3.25 Write Volatile Enhanced Configuration Register

The Write Volatile Enhanced Configuration register (WRVECR) instruction allows new values to be written to the Volatile Enhanced Configuration register. Before it can be accepted, a write enable (WREN) instruction must previously have been executed.

Except for the parallelizing of the instruction code and the input data on the four pins DQ0, DQ1, DQ2 and DQ3, the instruction functionality is exactly the same as the Write Volatile Enhanced Configuration Register (WRVECR) instruction of the Extended SPI protocol.

**Figure 98. Write Volatile Enhanced Configuration Register instruction sequence QIO-SPI**



## 10 XIP Operations

XIP (eXecution in Place) mode is available in each protocol: Extended SPI, DIO-SPI, and QIO-SPI. XIP mode allows the memory to be read simply by sending an address to the device and then receiving the data on one, two, or four pins in parallel, depending on the customer requirements. It offers maximum flexibility to the application, saves instruction overhead, and allows a dramatic reduction to the Random Access time.

You can enable XIP mode in two ways:

- Using the Volatile Configuration Register: this is dedicated to applications that boot in SPI mode (Extended SPI, DIO-SPI or QIO-SPI) and then during the application life need to switch to XIP mode to directly execute some code in the flash.
- Using the Non Volatile Configuration Register: this is dedicated to applications that need to boot directly in XIP mode.

Setting to 0 the bit 3 of the Volatile Configuration Register the device is ready to enter in XIP mode right after the next fast read instruction (by 1, 2 or 4 pin).

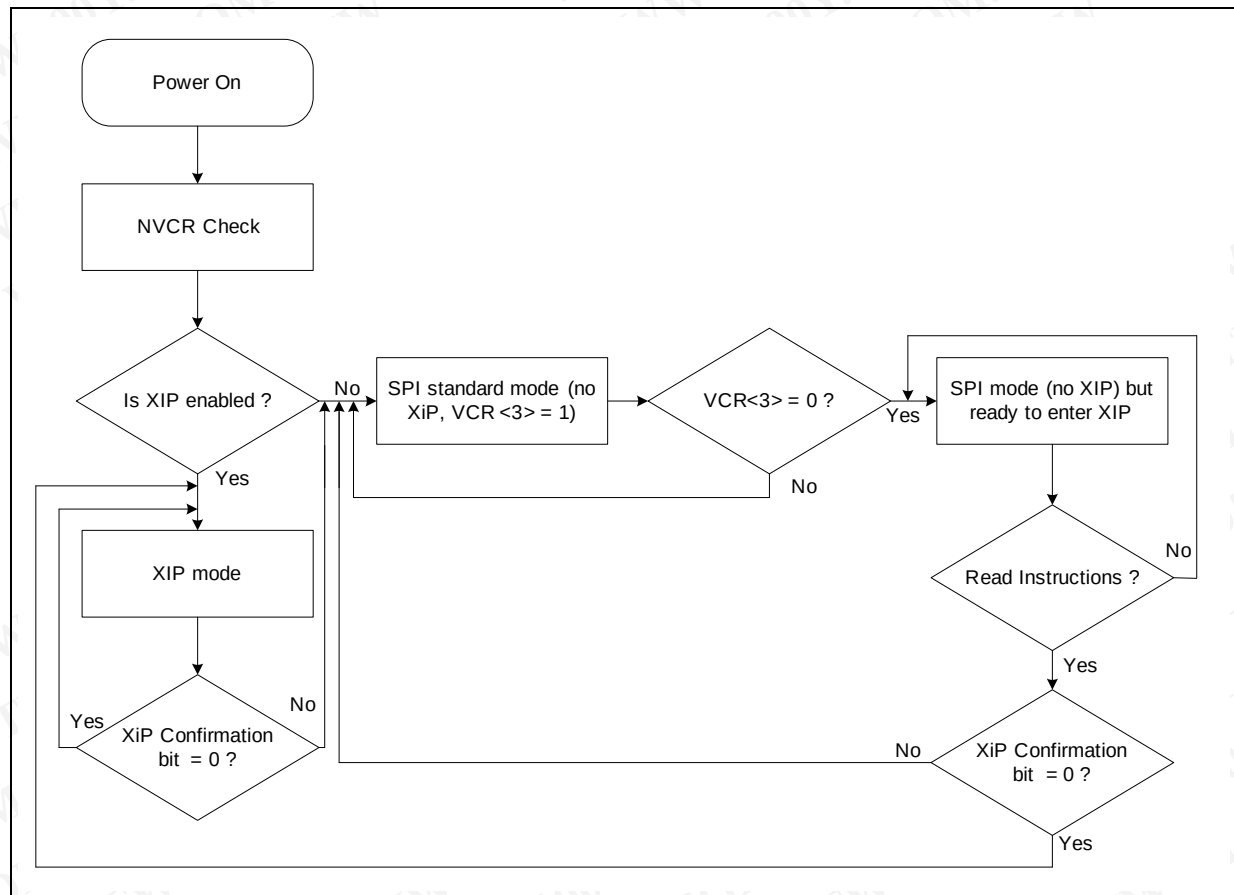
While acting on the Non Volatile Configuration Register (bit 11 to bit 9, depending on which XIP type is required, single, dual or quad I/O) the memory enters in the selected XIP mode only after the next power-on sequence. The Non Volatile Configuration Register XIP configuration bits allows the memory to start directly in the required XIP mode (Single, Dual or Quad) after the power on.

The XIP mode status must be confirmed forcing the XIP confirmation bit to "0", the XIP confirmation bit is the value on the DQ0 pin during the first dummy clock cycle after the address in XIP reading instruction. Forcing the bit "1" on DQ0 during the first dummy clock cycle after the address (XIP Confirmation bit) the memory returns in the previous standard read mode, that means it will codify as an instruction code the next byte received on the input pin(s) after the next chip select. Instead, if the XIP mode is confirmed (by forcing the XIP confirmation bit to 0), after the device next de-selection and selection cycle, the memory codify the first 3 bytes received on the inputs pin(s) as a new address.

Besides not confirming the XIP mode during the first dummy clock cycle, it is possible to exit the XIP mode by mean of a dedicated rescue sequence.

**Note:** *For devices with a feature set digit equal to 2 or 4 in the part number (Basic XiP), it is not necessary to set the Volatile Configuration Register bit 3 to enter XIP mode: it is possible to enter XIP mode directly by setting XIP Confirmation bit to 0 during the first dummy clock cycle after a fast read instruction. See [Section 16: Ordering information](#).*

Figure 99. N25Q032 Read functionality Flow Chart



## 10.1 Enter XIP mode by setting the Non Volatile Configuration Register

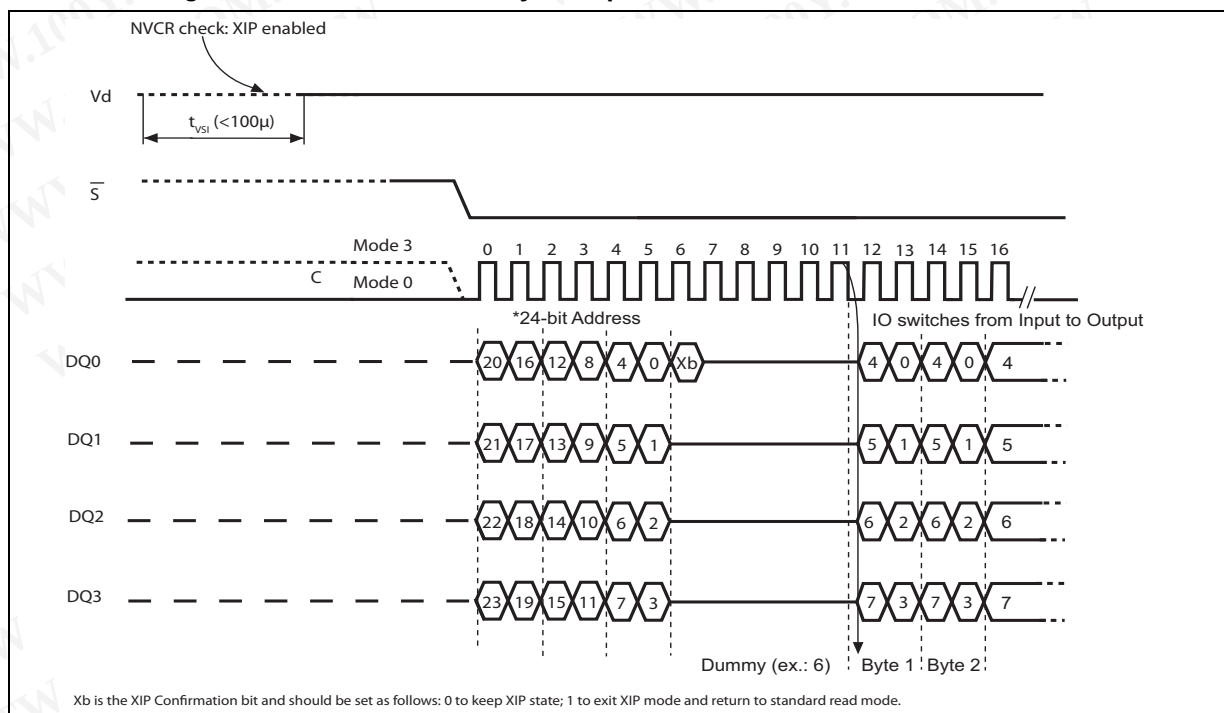
To use the Non Volatile Configuration Register method to enter in XIP mode it is necessary to set the Non Volatile Configuration Register bits from 11 to 9 with the pattern corresponding to the required XIP mode by mean of the Write Non Volatile Configuration Register (WRNVCR) instruction. (See [Table 23.: NVCR XIP bits setting example.](#))

This instruction doesn't affect the XIP state until the next Power on sequence. In this case, after the next power on sequence, the memory directly accept addresses and then, after the dummy clock cycles (configurable), outputs the data as described in [Table 23.: NVCR XIP bits setting example.](#) For example to enable XIP on QIOFR in normal SPI protocol with six dummy clock cycles the following pattern must be issued:

**Table 23. NVCR XIP bits setting example**

| B1h<br>(WRNVCR<br>opcode)                       | + 0110                                  | 100                                         | 111        | x                          | 1                        | 11            | xx |
|-------------------------------------------------|-----------------------------------------|---------------------------------------------|------------|----------------------------|--------------------------|---------------|----|
| 6 dummy cycles<br>for fast read<br>instructions | XIP set as<br>default; Quad<br>I/O mode | Output Buffer<br>driver strength<br>default | Don't Care | Hold/Reset<br>not disabled | Extended<br>SPI protocol | Don't<br>Care |    |

Figure 100. XIP mode directly after power on



## 10.2 Enter XIP mode by setting the Volatile Configuration Register

To use the Volatile Configuration Register method to enter XIP mode, it is necessary to write a 0 to bit 3 of the Volatile Configuration Register to make the device ready to enter XIP mode (2). This instruction doesn't permit to enter XIP state directly: a Fast Read instruction (either Single, Dual or Quad) is needed once to start the XIP Reading.

After the Fast Read instruction (Single, Dual or Quad) the XIP confirmation bit must be set to 0. (first bit on DQ0 during the first dummy cycle after the address has been received),

Then after the next de-select and select cycle ( $\bar{S}$  pin set to 1 and then to 0) the memory codify the first 3 bytes received on the input pin(s) directly as an address, without any instruction code, and after the dummy clock cycles (configurable) directly outputs the data.

For example to enable the XIP (without enter) with six dummy clock cycles, the pattern in [Table 24.: VCR XIP bits setting example](#) must be issued, and after that it is possible to enter, for example, in XIP mode from extended SPI read mode by mean of Quad Input Output Fast Read instruction, as described in [Table 24.: VCR XIP bits setting example](#).

**Note:** For devices with a feature set digit equal to 2 or 4 in the part number (Basic XiP), it is not necessary to set the Volatile Configuration Register bit 3 to enter in XIP mode: it is possible to enter directly in XIP mode by setting XIP Confirmation bit to 1 during the first dummy clock cycle after a fast read instruction. See [Section 16: Ordering information](#).

Table 24. VCR XIP bits setting example

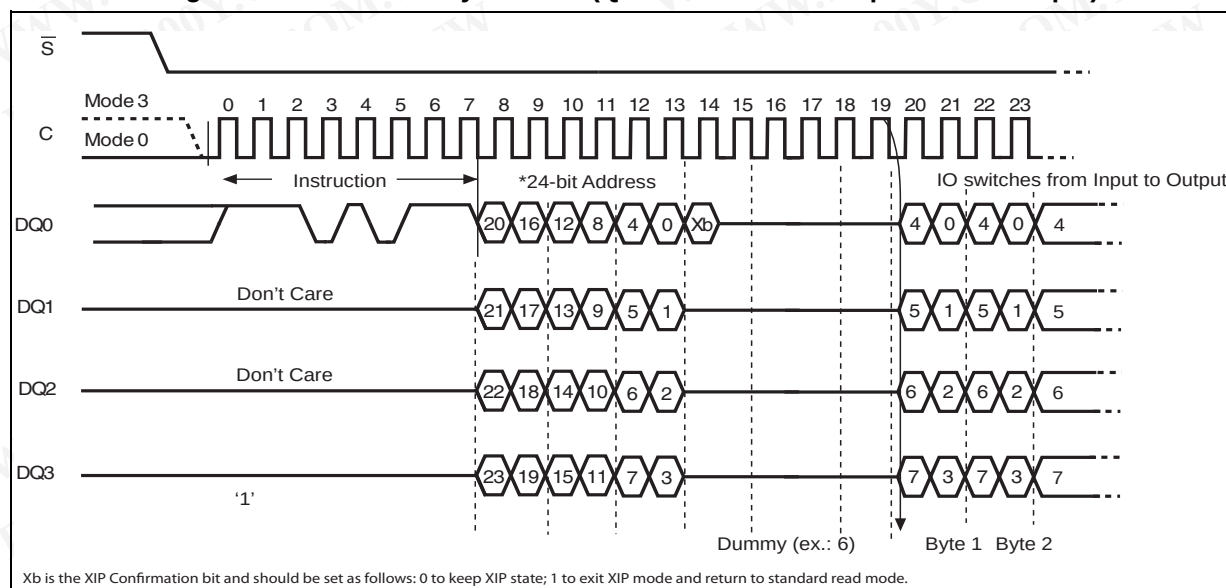
|                    |                |   |     |
|--------------------|----------------|---|-----|
| 81h (WRVCR opcode) | + 0110         | 0 | 011 |
|                    | 6 dummy cycles |   |     |

Table 24. VCR XIP bits setting example

Ready for  
XIP

Reserved

Figure 101. XiP: enter by VCR 2/2 (QIOFR in normal SPI protocol example)



### 10.3 XIP mode hold and exit

The XIP mode does require at least one additional clock cycle to allow the XIP Confirmation bit to be sent to the memory on DQ0 during the first dummy clock cycle.

The device decodes the XIP Confirmation bit with the scheme:

- XIP Confirmation bit=0 means to hold XIP Mode
- XIP Confirmation bit=1 means to exit XIP Mode and comes back to read mode, that means codifying the first byte after the next chip select as an instruction code.

In Dual I/O XIP mode, the values of DQ1 during the first dummy clock cycle after the addresses is always Don't Care.

In Quad I/O XIP mode, the values of DQ3, DQ2 and DQ1 during the first dummy clock cycle after the addresses are always Don't Care.

In Dual and Single I/O XIP mode, in presence of the  $\overline{\text{RESET}}$  pin enabled (in devices with a dedicated part number), a low pulse on that pin resets the XIP protocol as defined by the Volatile Configuration Register, reporting the memory at the state of last power up, as defined by the Non Volatile Configuration Register. In Quad I/O XiP modes, it is possible to reset the memory (for devices with a dedicated part number) only when the device is deselected. See [Section 16: Ordering information](#).

## 10.4 XIP Memory reset after a controller reset

If during the application life the system controller is reset during operation, and the device features the RESET functionality (in devices with a dedicated part number), and the feature has not been disabled, after the controller resets, the memory returns to POR state and there is no issue. See [Section 16: Ordering information](#).

In all the other cases, it is possible to exit the memory from the XIP mode by sending the following rescue sequence at the first chip selection after a system reset:

DQ0= '1' for:

- 7 clock cycles within  $\overline{S}$  low ( $\overline{S}$  becomes high before 8th clock cycle)
- + 13 clock cycles within  $\overline{S}$  low ( $\overline{S}$  becomes high before 14th clock cycle)
- + 25 clock cycles within  $\overline{S}$  low ( $\overline{S}$  becomes high before 26th clock cycle)

The global effect is only to exit from XIP without any other reset.

## 11 Power-up and power-down

At power-up and power-down, the device must not be selected (that is Chip Select ( $\overline{S}$ ) must follow the voltage applied on VCC) until VCC reaches the correct value:

- VCC(min) at power-up
- VSS at power-down

A safe configuration is provided in [Section 3: SPI Modes](#).

To avoid data corruption and inadvertent write operations during power-up, a Power On Reset (POR) circuit is included. The logic inside the device is held reset while VCC is less than the Power On Reset (POR) threshold voltage, VWI - all operations are disabled, and the device does not respond to any instruction.

During a standard power-up phase the device ignores all the instructions but RDSR and RFSR (they can be used to check the memory internal state according to [Figure 102.: Power-up timing](#)).

After power-up, the device is in the following state:

- The device is in the Standby Power mode
- The Write Enable Latch (WEL) bit is reset
- The Write In Progress (WIP) bit is reset
- The Lock Registers are configured as: (Write Lock bit, Lock Down bit) = (0,0).

Normal precautions must be taken for supply line decoupling, to stabilize the VCC supply.

Each device in a system should have the VCC line decoupled by a suitable capacitor close to the package pins (generally, this capacitor is of the order of 100 nF).

At power-down, when VCC drops from the operating voltage, to below the Power On Reset (POR) threshold voltage, VWI, all operations are disabled and the device does not respond to any instruction (the designer needs to be aware that if power-down occurs while a Program or Erase cycle is in progress, some data corruption may result).

VPPH must be applied only when VCC is stable and in the VCC(min) to VCC(max) voltage range.

**Figure 102. Power-up timing**

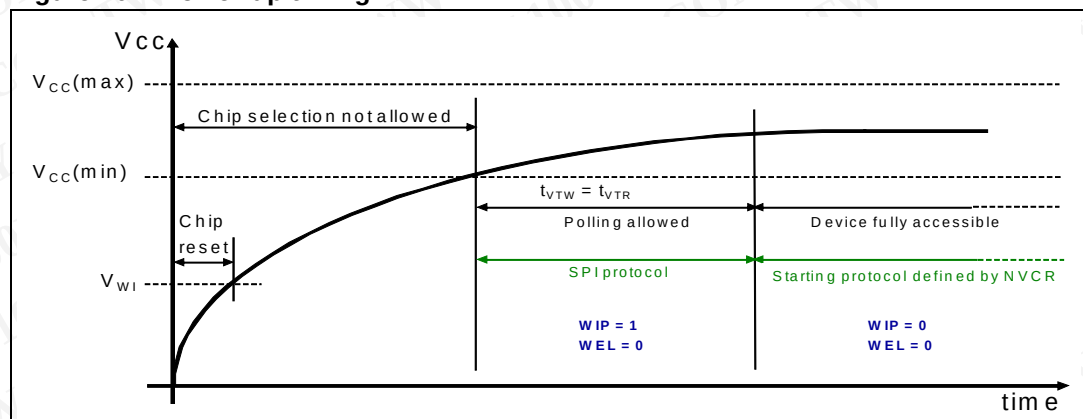


**Table 25. Power-up timing and  $V_{WI}$  threshold**

| Symbol          | Parameter                                       | Min | Max | Unit          |
|-----------------|-------------------------------------------------|-----|-----|---------------|
| $t_{VTR}^{(1)}$ | $V_{CC}(\text{min})$ to Read                    |     | 150 | $\mu\text{s}$ |
| $t_{VTW}^{(1)}$ | $V_{CC}(\text{min})$ to device fully accessible |     | 150 | $\mu\text{s}$ |
| $V_{WI}^{(1)}$  | Write inhibit voltage                           | 1.5 | 2.5 | V             |

1. These parameters are characterized only.

## 11.1 Rescue sequence in case of power loss during WRNVCR

If a power loss occurs during a Write Non Volatile Configuration Register instruction, after the next power on the device could eventually wake up in a not determined state, for example a not required protocol or XIP mode. In that case a particular rescue sequence must be used to recover the device at a fixed state (Extended SPI protocol without XIP) until the next power up. Then to fix the problem definitively is recommended to run the Write Non Volatile configuration Register again.

The rescue sequence is composed of two parts that have to be run in the correct order. During all the sequence the TSHSL must be 50ns at least. The sequence is:

DQ0 (PAD DATA) equal to '1' for:

7 clock cycles within  $\bar{S}$  low ( $\bar{S}$  becomes high before 8th clock cycle)

+ 13 clock cycles within  $\bar{S}$  low ( $\bar{S}$  becomes high before 14th clock cycle)

+ 25 clock cycles within  $\bar{S}$  low ( $\bar{S}$  becomes high before 26th clock cycle)

To exit from XIP.

DQ0 (PAD DATA) and DQ3 (PAD HOLD) equal to '1' for:

8 clock cycles within  $\bar{S}$  low ( $\bar{S}$  becomes high before 9th clock cycle) to force Normal SPI protocol.

## 12 Initial delivery state

The device is delivered with the memory array erased: all bits are set to 1 (each byte contains FFh). The Status Register contains 00h (all Status Register bits are 0).

## 13 Maximum rating

Stressing the device outside the ratings listed here may cause permanent damage to the device. These are stress ratings only, and operation of the device at these, or any other conditions outside those indicated in the operating sections of this specification, is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Table 26. Absolute maximum ratings**

| Symbol     | Parameter                                                         | Min   | Max                | Unit |
|------------|-------------------------------------------------------------------|-------|--------------------|------|
| $T_{STG}$  | Storage temperature                                               | -65   | 150                | °C   |
| $T_{LEAD}$ | Lead temperature during soldering                                 |       | see <sup>(1)</sup> | °C   |
| $V_{IO}$   | Input and output voltage (with respect to ground)                 | -0.6  | $V_{CC} + 0.6$     | V    |
| $V_{CC}$   | Supply voltage                                                    | -0.6  | 4.0                | V    |
| $V_{PP}$   | Fast program/erase voltage                                        | -0.2  | 10.0               | V    |
| $V_{ESD}$  | Electrostatic discharge voltage (human body model) <sup>(2)</sup> | -2000 | 2000               | V    |

1. Compliant with JEDEC Std. J-STD-020C (for small body, Sn-Pb or Pb assembly), the Numonyx ECOPACK® 7191395 specification, and the European directive on Restrictions on Hazardous Substances (RoHS) 2002/95/EU.

2. JEDEC Std JESD22-A114A ( $C1 = 100 \text{ pF}$ ,  $R1 = 1500 \text{ } \Omega$ ,  $R2 = 500 \text{ } \Omega$ ).

## 14 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC characteristics tables that follow are derived from tests performed under the measurement conditions summarized in the relevant tables. Designers should check that the operating conditions in their circuit match the measurement conditions when relying on the quoted parameters.

**Table 27. Operating conditions**

| Symbol    | Parameter                     | Min | Typ | Max | Unit |
|-----------|-------------------------------|-----|-----|-----|------|
| $V_{CC}$  | Supply voltage                | 2.7 |     | 3.6 | V    |
| $V_{PPH}$ | Supply voltage on VPP         | 8.5 |     | 9.5 | V    |
| $T_A$     | Ambient operating temperature | -40 |     | 85  | °C   |

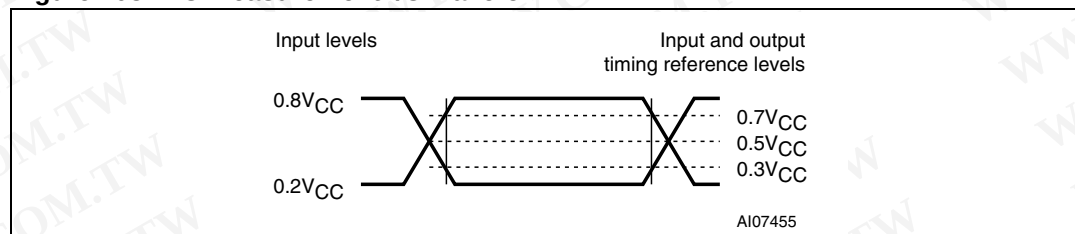
**Table 28. AC measurement conditions**

| Symbol | Parameter                        | Min                                         | Max | Unit |
|--------|----------------------------------|---------------------------------------------|-----|------|
| $C_L$  | Load capacitance                 | 30 <sup>(1)</sup>                           |     | pF   |
|        | Input rise and fall times        |                                             | 5   | ns   |
|        | Input pulse voltages             | 0.2 $V_{CC}$ to 0.8 $V_{CC}$ <sup>(2)</sup> |     | V    |
|        | Input timing reference voltages  | 0.3 $V_{CC}$ to 0.7 $V_{CC}$                |     | V    |
|        | Output timing reference voltages | $V_{CC} / 2$                                |     | V    |

1) Output Buffers are configurable by user.

2) For QUAD/DUAL operations: 0 to  $V_{CC}$ .

**Figure 103. AC measurement I/O waveform**



Note: For 0.8 $V_{CC}$ : for QUAD/DUAL operations, this is  $V_{CC}$ ; for 0.2 $V_{CC}$ : for QUAD/DUAL operations, this is 0V

**Table 29. Capacitance<sup>(1)</sup>**

| Symbol       | Parameter                                  | Test condition  | Min | Max | Unit |
|--------------|--------------------------------------------|-----------------|-----|-----|------|
| $C_{IN/OUT}$ | Input/output capacitance (DQ0/DQ1/DQ2/DQ3) | $V_{OUT} = 0$ V |     | 8   | pF   |
| $C_{IN}$     | Input capacitance (other pins)             | $V_{IN} = 0$ V  |     | 6   | pF   |

1. Sampled only, not 100% tested, at  $T_A = 25$  °C and a frequency of 54 MHz.

Table 30. DC Characteristics

| Symbol | Parameter                                                  | Test condition (in addition to those in Table 27.: Operating conditions) | Min     | Max     | Unit |
|--------|------------------------------------------------------------|--------------------------------------------------------------------------|---------|---------|------|
| ILI    | Input leakage current                                      |                                                                          |         | ± 2     | μA   |
| ILO    | Output leakage current                                     |                                                                          |         | ± 2     | μA   |
| ICC1   | Standby current                                            | S = VCC, VIN = VSS or VCC                                                |         | 100     | μA   |
| ICC3   | Operating current (Fast Read Single I/O)                   | C = 0.1VCC / 0.9VCC at 108 MHz, DQ1 = open                               |         | 15      | mA   |
|        |                                                            | C = 0.1VCC / 0.9VCC at 54 MHz, DQ1 = open                                |         | 6       | mA   |
|        | Operating current (Fast Read Dual I/O)                     | C = 0.1VCC / 0.9VCC at 108 MHz                                           |         | 18      | mA   |
|        | Operating current (Fast Read Quad I/O)                     | C = 0.1VCC / 0.9VCC at 108 MHz                                           |         | 20      | mA   |
| ICC4   | Operating current (Page Program Single, Dual and Quad I/O) | $\overline{S}$ = VCC                                                     |         | 20      | mA   |
| ICC5   | Operating current (WRSR)                                   | $\overline{S}$ = VCC                                                     |         | 20      | mA   |
| ICC6   | Operating current (SE)                                     | $\overline{S}$ = VCC                                                     |         | 20      | mA   |
| VIL    | Input low voltage                                          |                                                                          | − 0.5   | 0.3VCC  | V    |
| VIH    | Input high voltage                                         |                                                                          | 0.7VCC  | VCC+0.4 | V    |
| VOL    | Output low voltage                                         | IOL = 1.6 mA                                                             |         | 0.4     | V    |
| VOH    | Output high voltage                                        | IOH = −100 μA                                                            | VCC−0.2 |         | V    |

Note: The AC Characteristics data is preliminary.

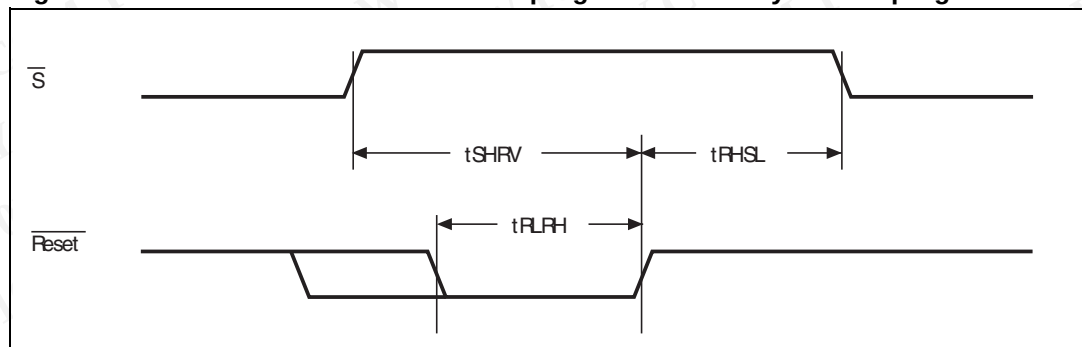
Table 31. AC Characteristics (page 1 of 2)

| Symbol                 | Alt. | Parameter                                                                                                          | Min  | Typ <sup>(2)</sup> | Max | Unit |
|------------------------|------|--------------------------------------------------------------------------------------------------------------------|------|--------------------|-----|------|
| fC                     | fC   | Clock frequency for the all the instructions (Extended SPI, DIO-SPI and QIO-SPI protocol) but the READ instruction | D.C. |                    | 108 | MHz  |
| fR                     |      | Clock frequency for read instructions                                                                              | D.C. |                    | 54  | MHz  |
| tCH <sup>(1)</sup>     | tCLH | Clock High time                                                                                                    | 4    |                    |     | ns   |
| tCL <sup>(2)</sup>     | tCLL | Clock Low time                                                                                                     | 4    |                    |     | ns   |
| tCLCH <sup>(3)</sup>   |      | Clock rise time <sup>(4)</sup> (peak to peak)                                                                      | 0.1  |                    |     | V/ns |
| tCHCL <sup>(3)</sup>   |      | Clock fall time <sup>(4)</sup> (peak to peak)                                                                      | 0.1  |                    |     | V/ns |
| tSLCH                  | tCSS | $\overline{S}$ active setup time (relative to C)                                                                   | 4    |                    |     | ns   |
| tCHSL                  |      |                                                                                                                    | 4    |                    |     | ns   |
| tDVCH                  | tDSU | Data in setup time                                                                                                 | 2    |                    |     | ns   |
| tCHDX                  | tDH  | Data in hold time                                                                                                  | 3    |                    |     | ns   |
| tCHSH                  |      | $\overline{S}$ active hold time (relative to C)                                                                    | 4    |                    |     | ns   |
| tSHCH                  |      | $\overline{S}$ not active setup time (relative to C)                                                               | 4    |                    |     | ns   |
| tSHSL                  | tCSH | $\overline{S}$ deselect time after a correct read instruction                                                      | 20   |                    |     | ns   |
|                        |      | $\overline{S}$ deselect time after a not correct read or after any different instruction                           | 50   |                    |     | ns   |
| tSHQZ <sup>(3)</sup>   | tDIS | Output disable time                                                                                                |      |                    | 8   | ns   |
| tCLQV                  | tV   | Clock Low to Output valid under 30 pF                                                                              |      |                    | 7   | ns   |
|                        |      | Clock Low to Output valid under 10 pF                                                                              |      |                    | 5   | ns   |
| tCLQX                  | tHO  | Output hold time                                                                                                   | 1    |                    |     | ns   |
| tHLCH                  |      | HOLD setup time (relative to C)                                                                                    | 4    |                    |     | ns   |
| tCHHH                  |      | HOLD hold time (relative to C)                                                                                     | 4    |                    |     | ns   |
| tHHCH                  |      | HOLD setup time (relative to C)                                                                                    | 4    |                    |     | ns   |
| tCHHL                  |      | HOLD hold time (relative to C)                                                                                     | 4    |                    |     | ns   |
| tHHQX <sup>(3)</sup>   | tLZ  | HOLD to Output Low-Z                                                                                               |      |                    | 8   | ns   |
| tHLQZ <sup>(3)</sup>   | tHZ  | HOLD to Output High-Z                                                                                              |      |                    | 8   | ns   |
| tWHSL <sup>(5)</sup>   |      | Write protect setup time                                                                                           | 20   |                    |     | ns   |
| tSHWL <sup>(5)</sup>   |      | Write protect hold time                                                                                            | 100  |                    |     | ns   |
| tVPPHSL <sup>(6)</sup> |      | Enhanced program supply voltage High (VPPH) to Chip Select Low for Single and Dual I/O Page Program                | 200  |                    |     | ns   |
| tW                     |      | Write status register cycle time                                                                                   |      | 1.3                | 8   | ms   |
| tCFSR                  |      | Clear flag status register cycle time                                                                              |      | 40                 |     | ns   |

**Table 31. AC Characteristics (page 2 of 2)**

| Symbol             | Alt. | Parameter                                                 | Min | Typ <sup>(2)</sup>                   | Max | Unit |
|--------------------|------|-----------------------------------------------------------|-----|--------------------------------------|-----|------|
| tWNVCR             |      | Write non volatile configuration register cycle time      |     | 0.2                                  | 3   | s    |
| tWVCR              |      | Write volatile configuration register cycle time          |     | 40                                   |     | ns   |
| tWRVECR            |      | Write volatile enhanced configuration register cycle time |     | 40                                   |     | ns   |
| tPP <sup>(7)</sup> |      | Page Program Cycle Time (256 Bytes)                       |     | 0.5                                  | 5   | ms   |
|                    |      | Page Program Cycle Time (n Bytes)                         |     | $\text{int}(n/8) \times 0.015^{(8)}$ | 5   |      |
|                    |      | Page Program Cycle Time Vpp=VPPH (256 Bytes)              |     | 0.4                                  | 5   |      |
|                    |      | Program OTP cycle time (64 bytes)                         |     | 0.2                                  |     | ms   |
| tSSE               |      | Subsector erase cycle time                                |     | 0.3                                  | 3   | s    |
| tSE                |      | Sector Erase Cycle Time                                   |     | 0.7                                  | 3   | s    |
|                    |      | Sector Erase Cycle Time Vpp=VPPH                          |     | 0.6                                  | 3   |      |
| tBE                |      | Bulk erase cycle time                                     |     | 30                                   | 60  | s    |
|                    |      | Bulk erase cycle time (with VPP=VPPH)                     |     | 25                                   | 60  | s    |

1. tCH + tCL must be greater than or equal to 1/ fC.
2. Typical values given for TA = 25 °C
3. Value guaranteed by characterization, not 100% tested in production.
4. Expressed as a slew-rate.
5. Only applicable as a constraint for a WRSR instruction when SRWD is set to '1'.
6. VPPH should be kept at a valid level until the program or erase operation has completed and its result (success or failure) is known.
7. When using the page program (PP) instruction to program consecutive bytes, optimized timings are obtained with one sequence including all the bytes versus several sequences of only a few bytes ( $1 \leq n \leq 256$ ).
8. int(A) corresponds to the upper integer part of A. For example  $\text{int}(12/8) = 2$ ,  $\text{int}(32/8) = 4$   $\text{int}(15.3) = 15$ .

**Figure 104. Reset AC waveforms while a program or erase cycle is in progress**

See [Table 32.: Reset Conditions](#).

Table 32. Reset Conditions

| Symbol                  | Alt. | Parameter              | Conditions                                                                                                                                        | Min | Typ                | Max | Unit    |
|-------------------------|------|------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------|-----|--------------------|-----|---------|
| tRLRH <sup>(1)(2)</sup> | tRST | Reset pulse width      |                                                                                                                                                   |     |                    | 50  | ns      |
| tRHSL <sup>(1)</sup>    | tREC | Reset Recovery Time    | Device selected ( $\overline{S}$ low), while decoding any modify instruction, during all read operations, CLFSR, WRDI, WREN, WRLR, WRVCR, WRVECR. |     |                    | 40  | ns      |
|                         |      |                        | Under completion of an internal erase or program cycle related to POTP, PP, DIEFP, DIFP, QIEFP, QIFP, SE, BE, PER, PES.                           |     |                    | 30  | $\mu$ s |
|                         |      |                        | Under completion of an SSE operation.                                                                                                             |     | t <sub>SSE</sub>   |     | ms      |
|                         |      |                        | Under completion of an WRSR operation.                                                                                                            |     | t <sub>W</sub>     |     | ms      |
|                         |      |                        | Under completion of an WRNVCR operation.                                                                                                          |     | t <sub>WNVCR</sub> |     | ms      |
|                         |      |                        | Device deselected ( $\overline{S}$ high) and in XiP mode.                                                                                         |     |                    | 40  | ns      |
|                         |      |                        | Device deselected ( $\overline{S}$ high) and in Standby mode.                                                                                     |     |                    | 40  | ns      |
| tSHRV <sup>(1)</sup>    |      | S# deselect to R valid | Deselect to R valid in Quad Output or in QIO-SPI.                                                                                                 |     |                    | 2   | ns      |

1. All values are guaranteed by characterization and not 100% tested in production.
2. The device reset is possible but not guaranteed if tRLRH < 50 ns.

Figure 105. Serial input timing

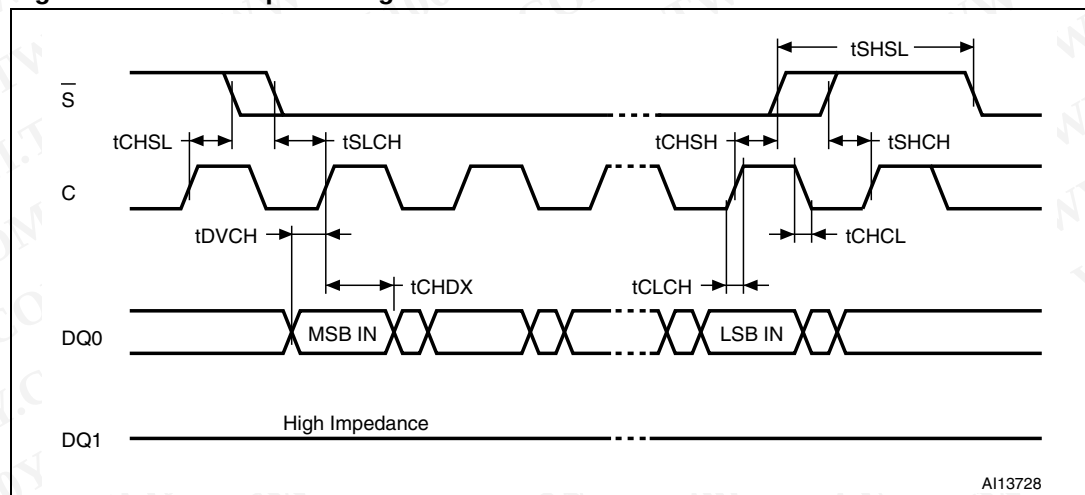


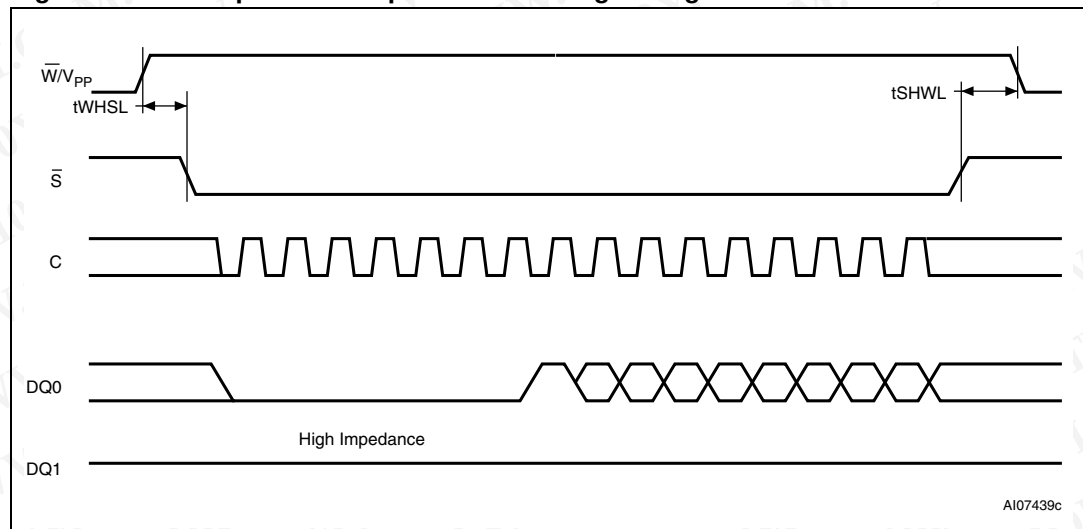
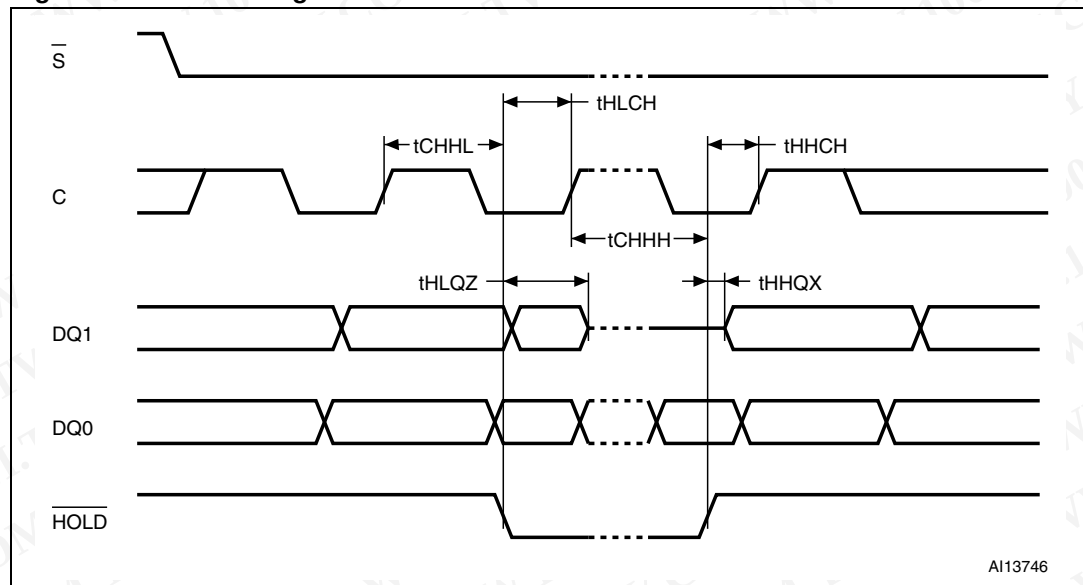
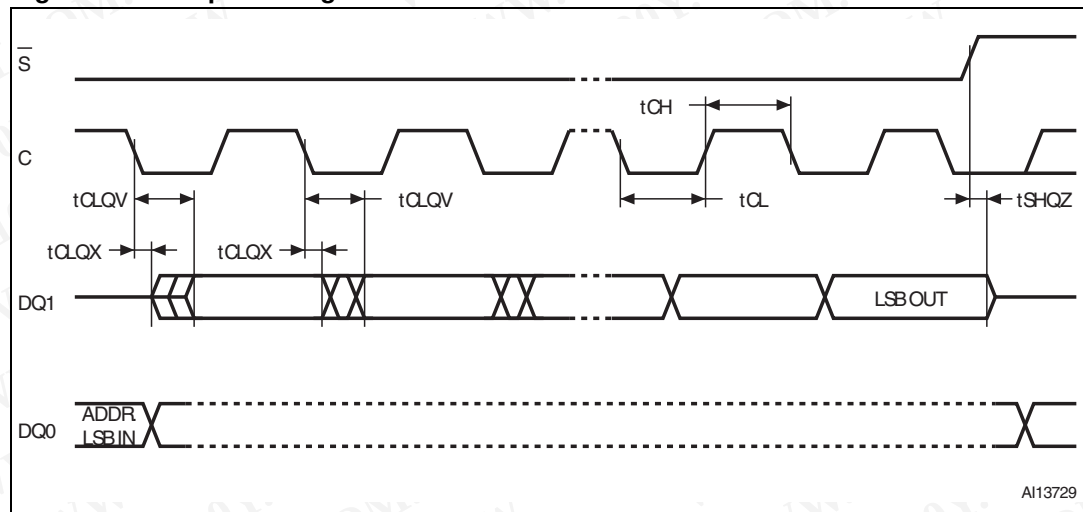
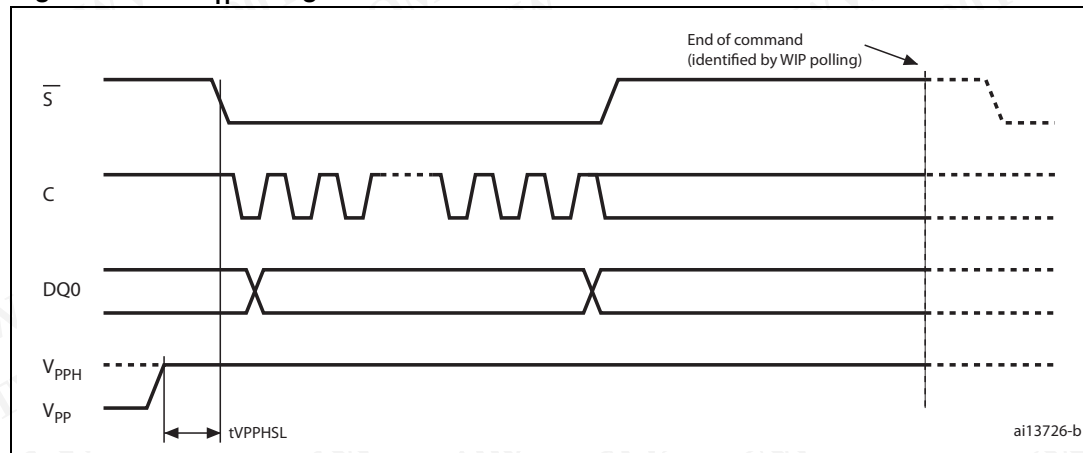
**Figure 106. Write protect setup and hold timing during WRSR when SRWD=1****Figure 107. Hold timing**

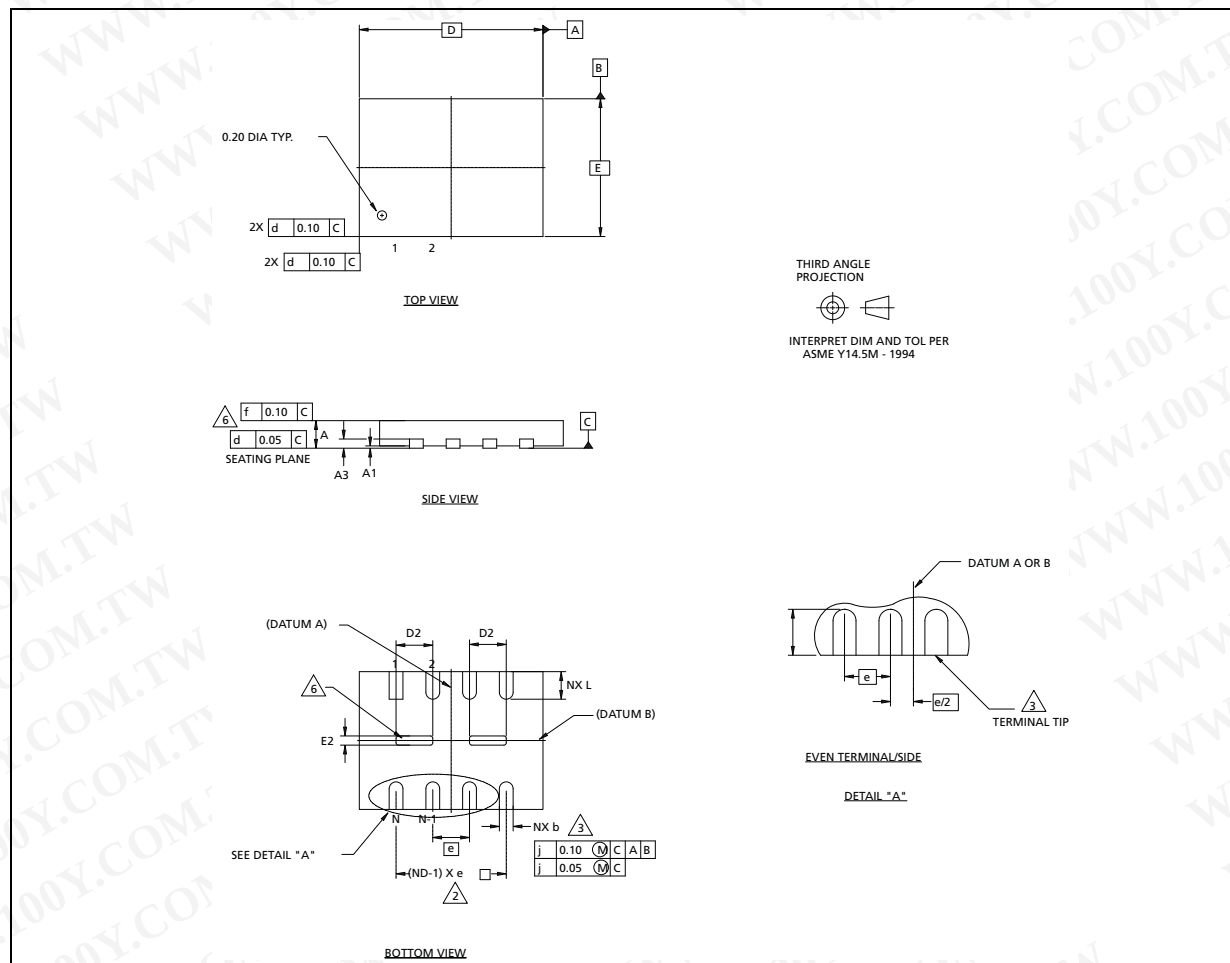
Figure 108. Output timing

Figure 109.  $V_{PPH}$  timing

## 15 Package mechanical

To meet environmental requirements, Numonyx offers these devices in RoHS compliant packages, which have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label in compliance with JEDEC Standard JESD97. Maximum ratings related to soldering conditions are also marked on the inner box label.

**Figure 110. UFDFPN8 (MLP8) Ultra Thin Dual Flat Package, No lead, 4×3 mm Drawing**

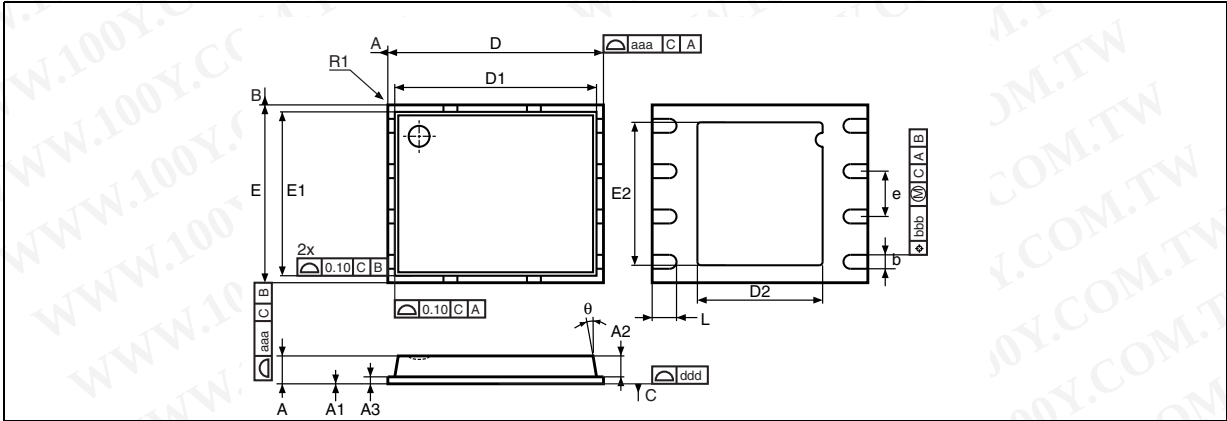


1. Drawing is not to scale.

**Table 33. UFDFPN8 (MLP8) Ultra Thin Dual Flat Package, No lead, 4×3 mm Dimensions**

| mm  | Symbol |      |       |     |      |      |      |   |    |      |      |      |      |
|-----|--------|------|-------|-----|------|------|------|---|----|------|------|------|------|
|     | A      | A1   | A3    | θ   | D2   | E2   | e    | N | ND | b    | L    | D    | E    |
| Typ | 0.55   | 0.02 | —     | —   | 0.80 | 0.20 | 0.80 | 8 | 4  | 0.30 | 0.60 | 4    | 3    |
| Min | 0.45   | 0    | 0.127 | 0°  | 0.70 | 0.10 | —    | — | —  | 0.25 | 0.55 | 3.90 | 2.90 |
| Max | 0.60   | 0.05 | 0.15  | 12° | 0.90 | 0.30 | —    | — | —  | 0.35 | 0.65 | 4.10 | 3.10 |

**Figure 111. VDFPN8 (MLP8) Very Thin Pitch Dual Flat Package, No lead, 6×5 mm Drawing**

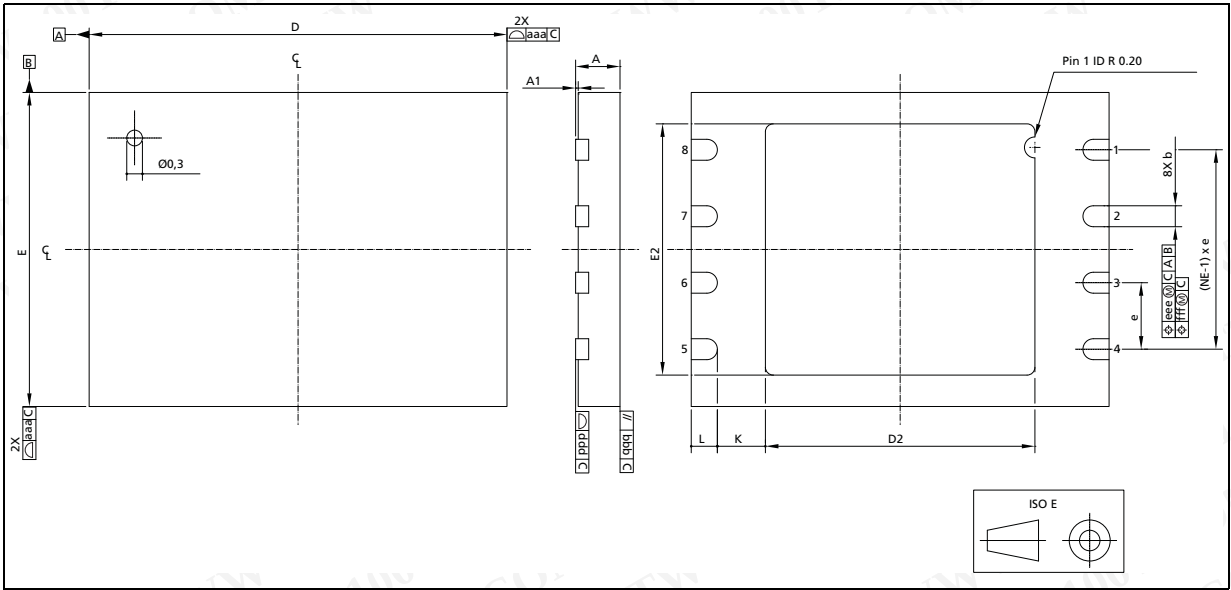


1. Drawing is not to scale.
2. The circle in the top view of the package indicates the position of pin 1.

**Table 34. VDFPN8 (MLP8) Very Thin Dual Flat Package No leads 6×5 mm Dimensions**

| mm  | Symbol |      |      |      |      |   |      |      |   |      |      |      |      |      |     |      |      |      |
|-----|--------|------|------|------|------|---|------|------|---|------|------|------|------|------|-----|------|------|------|
|     | A      | A1   | A2   | A3   | b    | D | D1   | D2   | E | E1   | E2   | e    | R1   | L    | Q   | aaa  | bbb  | ddd  |
| Typ | 0.85   | —    | 0.65 | 0.20 | 0.40 | 6 | 5.75 | 3.40 | 5 | 4.75 | 4    | 1.27 | 0.10 | 0.60 | —   | —    | —    | —    |
| Min | 0.80   | 0    | —    | —    | 0.35 | — | —    | 3.20 | — | —    | 3.80 | —    | 0    | 0.50 | —   | —    | —    | —    |
| Max | 1      | 0.05 | —    | —    | 0.48 | — | —    | 3.60 | — | —    | 4.30 | —    | —    | 0.75 | 12° | 0.15 | 0.10 | 0.05 |

Figure 112. VDFPN8 (MLP8) Very Thin Dual Flat Package 8 leads, 8×6x1 mm Drawing

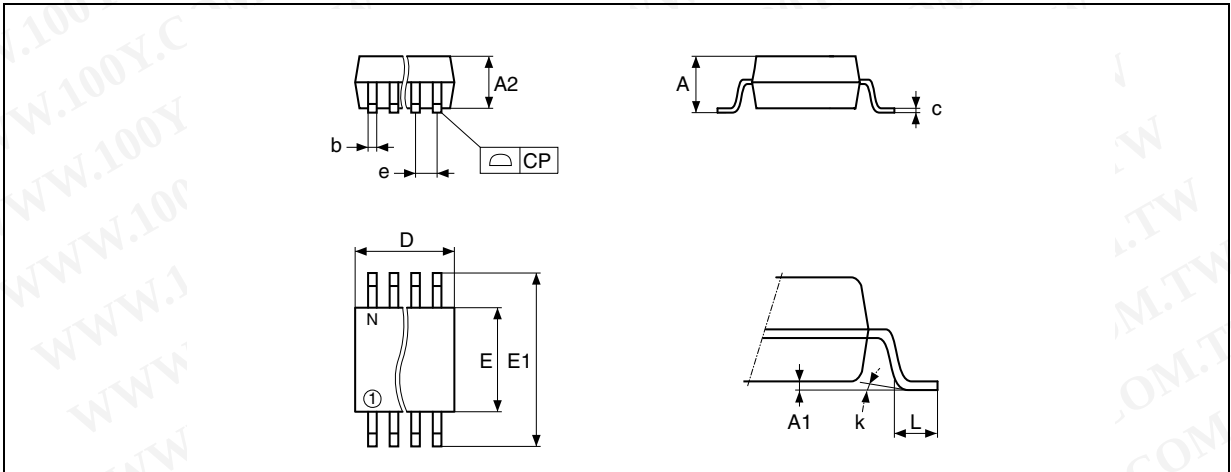


1. Drawing is not to scale.
2. The circle in the top view of the package indicates the position of pin 1.

Table 35. VDFPN8 (MLP8) Very Thin Dual Flat Package 8 leads 8×6x1 mm Dimensions

| mm  | Symbol |      |      |   |      |   |     |                 |     |      |
|-----|--------|------|------|---|------|---|-----|-----------------|-----|------|
|     | A      | A1   | b    | D | D2   | E | E2  | e               | K   | L    |
| Typ | 0.85   | —    | 0.4  | 8 | 5.16 | 6 | 4.8 | 1.27<br>(basic) | —   | 0.5  |
| Min | —      | 0    | 0.35 | — | —    | — | —   | 1.27<br>(basic) | 0.2 | 0.45 |
| Max | 1      | 0.05 | 0.48 | — | —    | — | —   | 1.27<br>(basic) | —   | 0.6  |

Figure 113. SO8W – 8 Lead Plastic Small Outline, 208 mils Body Width, Drawing

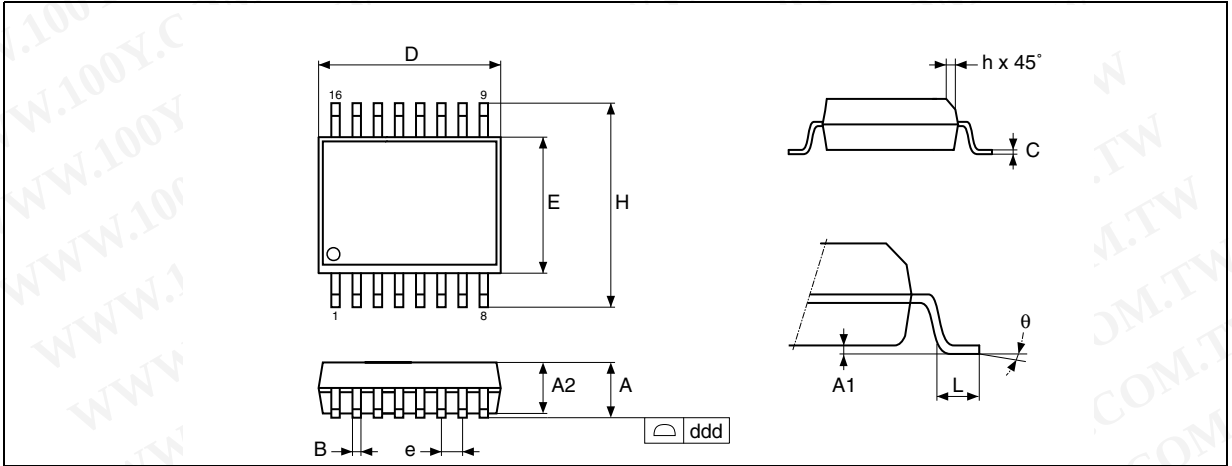


1. Drawing is not to scale.

Table 36. SO8 Wide – 8 Lead Plastic Small Outline, 208 mils Body Width, Dimensions

| mm  | Symbol |      |      |      |      |      |      |      |      |    |      |
|-----|--------|------|------|------|------|------|------|------|------|----|------|
|     | A      | A1   | A2   | b    | c    | D    | E    | E1   | e    | k  | L    |
| Typ | 1.91   | 0.10 | 1.80 | —    | 0.20 | 5.28 | 5.28 | 7.90 | 1.27 | 4° | 0.64 |
| Min | 1.78   | 0.05 | 1.70 | 0.36 | 0.15 | 5.08 | 5.08 | 7.70 | —    | 0° | 0.51 |
| Max | 2.16   | 0.25 | 1.91 | 0.48 | 0.25 | 5.49 | 5.49 | 8.10 | —    | 8° | 0.80 |

Figure 114. SO16 Wide – 16 Lead Plastic Small Outline, 300 mils Body Width, Drawing



1. Drawing is not to scale.

Table 37. SO16 Wide – 16 Lead Plastic Small Outline, 300 mils Body Width, Dimensions

| mm  | Symbol |      |      |      |       |      |      |       |      |      |          |      |
|-----|--------|------|------|------|-------|------|------|-------|------|------|----------|------|
|     | A      | A1   | B    | C    | D     | E    | e    | H     | h    | L    | $\theta$ | ddd  |
| Typ | —      | —    | —    | —    | —     | —    | 1.27 | —     | —    | —    | —        | —    |
| Min | 2.35   | 0.10 | 0.33 | 0.23 | 10.10 | 7.40 | —    | 10    | 0.25 | 0.40 | 0°       | —    |
| Max | 2.65   | 0.30 | 0.51 | 0.32 | 10.50 | 7.60 | —    | 10.65 | 0.75 | 1.27 | 8°       | 0.10 |

Figure 115. TBGA - 6 x 8 mm, 24-Ball, Drawing

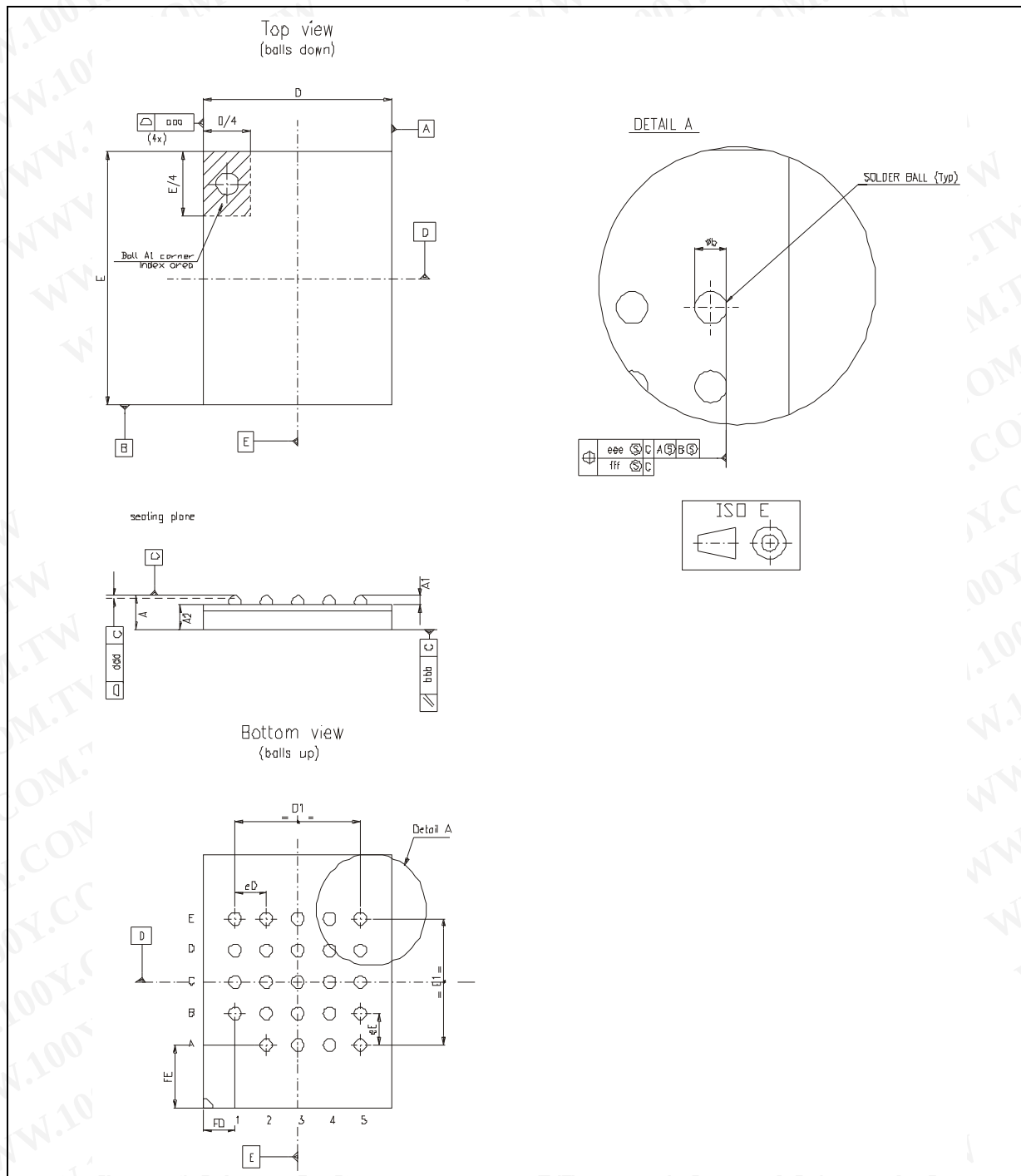


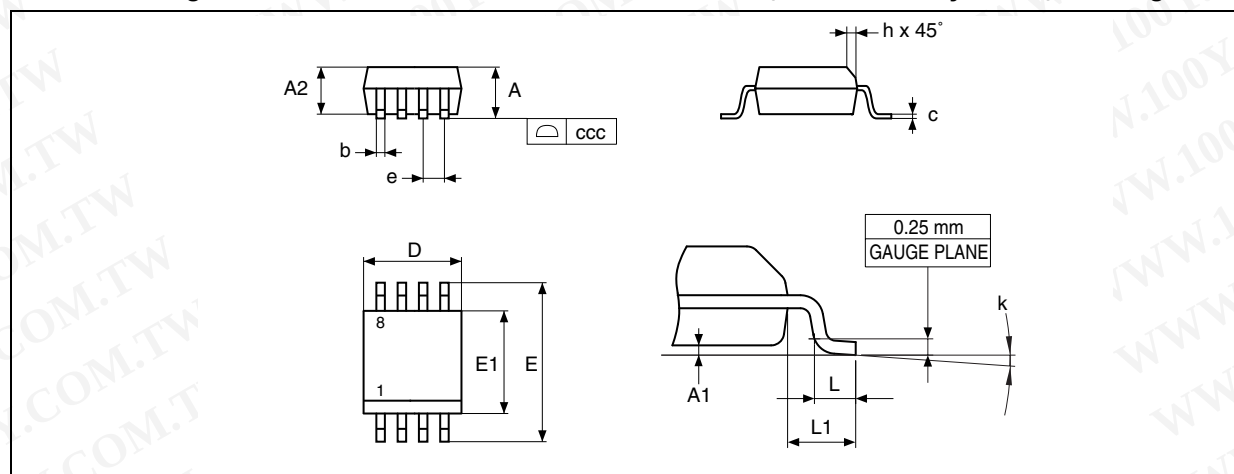
Table 38. TBGA 6x8 mm 24-Ball, Dimensions, Symbols A to eE

| mm  | Symbol |      |      |      |      |    |      |    |    |    |
|-----|--------|------|------|------|------|----|------|----|----|----|
|     | A      | A1   | A2   | θb   | D    | D1 | E    | E1 | eD | eE |
| Typ | —      | 0.20 | —    | 0.35 | 5.90 | —  | 7.90 | —  | —  | —  |
| Min | —      | —    | 0.79 | 0.40 | 6.00 | 4  | 8    | 4  | 1  | 1  |
| Max | 1.20   | —    | —    | 0.45 | 6.10 | —  | 8.10 | —  | —  | —  |

Table 39. TBGA 6x8 mm 24-Ball, Dimensions, Symbols FD to fff

| mm  | Symbol |    |    |    |          |      |      |      |      |      |
|-----|--------|----|----|----|----------|------|------|------|------|------|
|     | FD     | FE | MD | ME | n        | aaa  | bbb  | ddd  | eee  | fff  |
| Typ | —      | —  | 5  | 5  | 24 balls | —    | —    | —    | —    | —    |
| Min | 1      | 2  | 5  | 5  | 24 balls | —    | —    | —    | —    | —    |
| Max | —      | —  | 5  | 5  | 24 balls | 0.15 | 0.10 | 0.10 | 0.15 | 0.08 |

Figure 116. SO8N – 8 Lead Plastic Small Outline, 150 mils Body Width, Drawing



1. Drawing is not to scale.

Table 40. SO8N – 8 Lead Plastic Small Outline, 150 mils Body Width, Dimensions

| mm  | Symbol |      |      |      |      |      |      |      |      |      |      |    |      |      |
|-----|--------|------|------|------|------|------|------|------|------|------|------|----|------|------|
|     | A      | A1   | A2   | b    | c    | ccc  | D    | E    | E1   | e    | h    | k  | L    | L1   |
| Typ | —      | —    | —    | —    | —    | —    | 4.90 | 6    | 3.90 | 1.27 | —    | —  | —    | 1.04 |
| Min | —      | 0.10 | 1.25 | 0.28 | 0.17 | —    | 4.80 | 5.80 | 3.80 | —    | 0.25 | 0° | 0.40 | —    |
| Max | 1.75   | 0.25 | —    | 0.48 | 0.23 | 0.10 | 5    | 6.20 | 4    | —    | 0.50 | 8° | 1.27 | —    |

## 16 Ordering information

**Table 41. Ordering information scheme**

Example:

N25Q032 A 1 3 E F8 4 0 E

**Device type**

N25Q = serial Flash memory, Quad I/O, XiP

**Device density**

032 = 032 Mbit

**Technology**

A = 65 nm

**Feature set**

1 = Byte addressability, Hold pin, Numonyx XiP  
 2 = Byte addressability, Hold pin, Basic XiP  
 3 = Byte addressability, Reset pin, Numonyx XiP  
 4 = Byte addressability, Reset pin, Basic XiP

**Operating voltage**

3 = VCC = 2.7 V to 3.6 V

**Block Structure**

E = Uniform (no boot sectors)

**Package**

F4 = UDFPN8 4 x 3 mm (MLP8)  
 F6 = VDFPN8 6 x 5 mm (MLP8)  
 F8 = VDFPN8 8 x 6 mm (MLP8)  
 SC = SO8N (SO8 Narrow 150 mils body width)  
 SE = SO8W (SO8 Wide 208 mils body width)  
 SF = SO16W (SO16 Wide 300 mils body width)  
 12 = TBGA24 6 x 8 mm

**Temperature and test flow**

4 = Industrial temperature range, -40 to 85 °C; Device tested with standard test flow  
 A = Automotive temperature range, -40 to 125 °C; Device tested with high reliability certified test flow  
 H = Industrial temperature range, -40 to 85 °C; Device tested with high reliability certified test flow

**Security features <sup>(1)</sup>**

0 = No extra security

**Packing options**

E = Tray packing  
 F = Tape and reel packing  
 G = Tube packing

1. Additional secure options are available upon request. For security features options please refer to AN:309025

**Note:** All packages are RoHS compliant

**Note:** For further information on line items not listed here or on any aspect of this device, please contact your nearest Numonyx Sales Office.

**Table 42. Valid Order Information Line Items**

| Part Number                          | Features                                      | Block Structure | Package            | Temperature and Test Flow              | Security |
|--------------------------------------|-----------------------------------------------|-----------------|--------------------|----------------------------------------|----------|
| N25Q032A13E1240E<br>N25Q032A13E1240F | Byte addressability,<br>Hold pin, Numonyx XiP | Uniform         | TBGA24<br>6x8 mm   | Industrial temp;<br>Standard test flow | Default  |
| N25Q032A13EF640E<br>N25Q032A13EF640F | Byte addressability,<br>Hold pin, Numonyx XiP | Uniform         | VDFPN8<br>6 x 5 mm | Industrial temp;<br>Standard test flow | Default  |
| N25Q032A13ESC40F<br>N25Q032A13ESC40G | Byte addressability,<br>Hold pin, Numonyx XiP | Uniform         | SO8N               | Industrial temp;<br>Standard test flow | Default  |
| N25Q032A13ESE40F<br>N25Q032A13ESE40G | Byte addressability,<br>Hold pin, Numonyx XiP | Uniform         | SO8W               | Industrial temp;<br>Standard test flow | Default  |

**Note:** 1 Applies to all part numbers: Packing information details: E= tray, F= tape-n-reel, G= tube (16th digit of part number).

## 17 Revision history

**Table 43. Document revision history**

| Date        | Revision | Changes                      |
|-------------|----------|------------------------------|
| 10-May 2010 | 1        | Initial release.             |
| 14-Jan-2011 | 2        | Revised package information. |

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This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein.

Although considered final, these specifications are subject to change, as further product development and data characterization sometimes occur.